

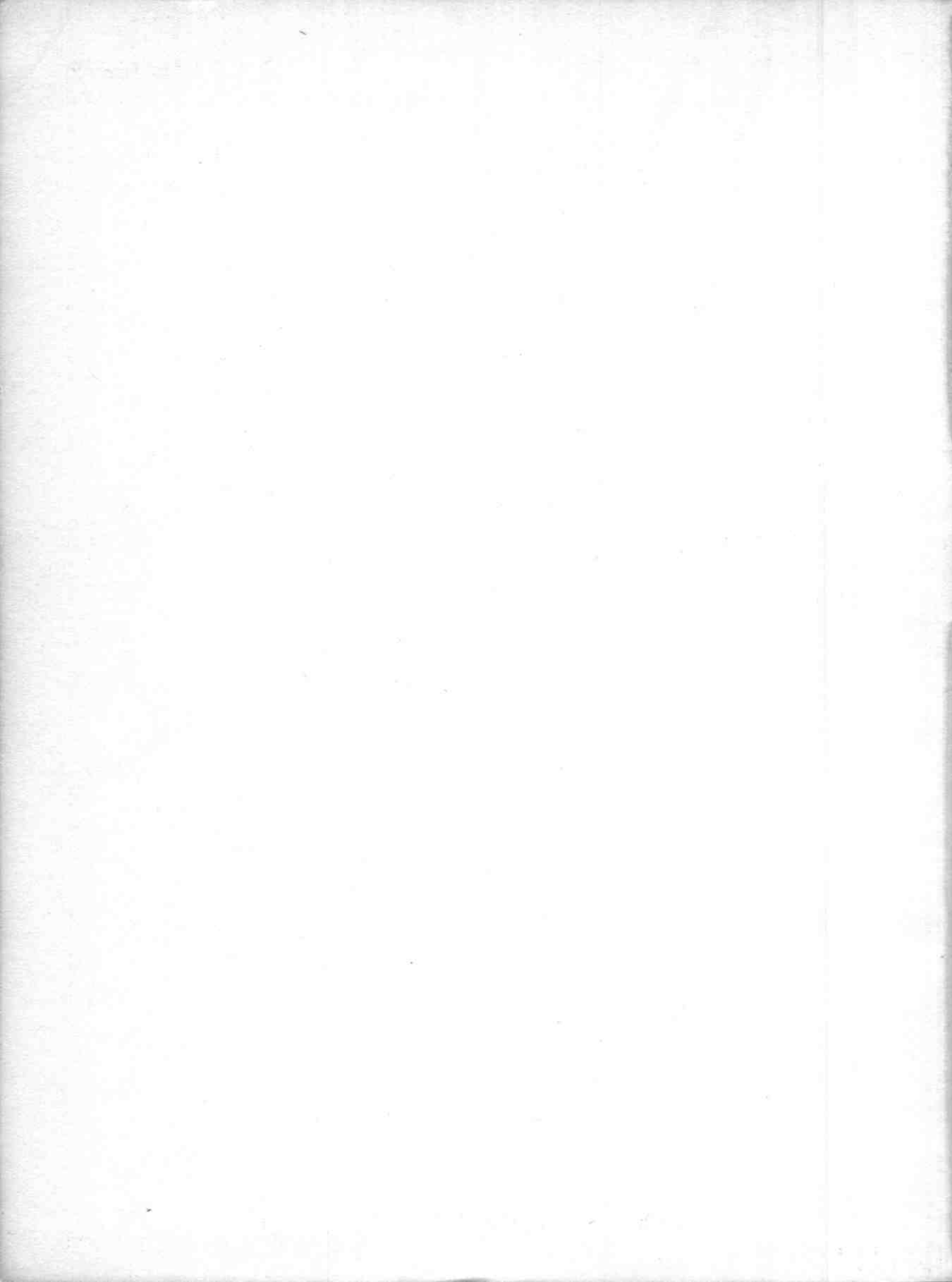


LINEAR IC's

RAYTHEON

RAYTHEON SEMICONDUCTOR
cramer

JANUARY 1976



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Fairchild	Raytheon Direct Replacement	Page	Motorola	Raytheon Direct Replacement	Page	National	Raytheon Direct Replacement	Page
μA555TC	RC555NB	6-2	MC1414L	RC1414DC	4-14	LM101AD	LM101AD	1-2
μA556DC	RC556D	6-6	MC1437L	RC1437DC	1-27	LM101AF	LM101AF	
μA556PC	RC556DB		LM101AH	LM101AH				
μA702FM	RM702Q	2-2	MC1456G	RC1556T	1-31	LM104H	LM104H	3-2
μA702HM	RM702T		MC1456CG	RC1556T		LM105H	LM105H	3-4
μA702HC	RC702T		MC1458G	RC1458T/ RC4558T*	1-29	LM106H	LM106H	4-2
μA702DM	RM702DC		MC1458P-1	RC1458NB/ RC4558NB*		LM107H	LM107H	1-4
μA702DC	RC702DC		MC1488L	RC1488DC	5-2	LM108H	LM108H	1-6
μA709AFM	RM709AQ	MC1489AL	RC1489ADC	5-4	LM108AH	LM108AH		
μA709FM	RM709Q	MC1489L	RC1489DC		LM109H	LM109H	3-7	
μA709AHM	RM709AT	MC1514L	RM1514DC	4-14	LM109K	LM109K	4-4	
μA709HM	RM709T	MC1537L	RM1537DC	1-27	LM111H	LM111H		
μA709HC	RC709T	MC1556G	RM1556T	1-31	LM118H	LM118H	1-10	
μA709ADM	RM709ADC	MC1558G	RM4558T	1-59	LM216H	LM216H	1-15	
μA709DM	RM709DC	MC1709CG	RC709T	1-17	LM216AH	LM216AH		
μA709DC	RC709DC	MC1709CL	RC709DC		LM301AH	LM301AH	1-2	
μA710FM	RM710Q	MC1709F	RM709Q	4-10	LM301AN	LM301AN	3-2	
μA710HM	RM710T	MC1709G	RM709T		LM304H	LM304H		
μA710HC	RC710T	MC1709L	RM709DC	LM305H	LM305H	3-4		
μA710DM	RM710DC	MC1710CG	RC710T	4-10	LM305AH	LM305AH	4-2	
μA710DC	RC710DC	MC1710CL	RC710DC		LM306H	LM306H		
μA711FM	RM711Q	MC1710F	RM710Q	4-12	LM307H	LM307H	1-4	
μA711HM	RM711T	MC1710G	RM710T		LM307N	LM307N		
μA711HC	RC711T	MC1710L	RM710DC	LM308H	LM308H	1-6		
μA711DM	RM711DC	MC1711CG	RC711T	4-12	LM308AH	LM308AH	3-7	
μA711DC	RC711DC	MC1711CL	RC711DC		LM309H	LM309H		
μA723H	RM723T	MC1711G	RM711T	4-4	LM309K	LM309K	4-4	
μA723HC	RC723T	MC1711L	RM711DC		LM311H	LM311H		
μA723DM	RM723DC	MC1712CG	RC702T	2-2	LM311N	LM311N	1-15	
μA723DC	RC723DC	MC1712F	RM702Q		LM316AH	LM316AH		
μA725HM	RM725T	MC1712G	RM702T	LM318H	LM318H	1-10		
μA725HC	RC725T	MC1303P	RC4739DB	1-63	LM709H	RM709T	1-17	
μA733HM	RM733T	MC1723CG	RC723T	3-9	LM709AH	RM709AT		
μA733HC	RC733T	MC1723G	RM723T		LM709CH	RC709T	4-10	
μA741FM	RM741Q	MC1723CL	RC723DC	2-5	LM710H	RM710T		4-10
μA741HM	RM741T	MC1723L	RM723DC		LM710AH	RM710AT		
μA741HC	RC741T	MC1733CG	RC733T	1-21	LM710H	RM710T	4-12	
μA741DM	RM741D	MC1733G	RM733T		LM710CH	RC710T		
μA741DC	RC741D	MC1741CF	RC741Q	1-25	LM711H	RM711T	3-9	
μA741TC	RC741NB	MC1741CG	RC741T		LM711AH	RM711AT		
μA747HM	RM747T	MC1741CL	RC741DC	1-21	LM711CH	RC711T	1-19	
μA747HC	RC747T	MC1741CP-1	RC741NB		LM723D	RM723DC		
μA747DM	RM747DC	MC1741CP-2	RC741DB	1-25	LM723CD	RC723DC	4-10	
μA747DC	RC747DC	MC1741G	RM741Q		LM723H	RM723T		
μA747PC	RC747DB	MC1741L	RM741DC	LM723CH	RC723T	1-19		
μA748HM	RM748T	MC1748G	RM748T	LM725H	RM725T			
μA748HC	RC748T	MC1748CG	RC748T	LM725CH	RC725T	1-21		
μA748TC	RC748NB	MC3403L	RC3403ADC	LM741F	RM741Q		1-21	
μA4136DC/DM	RC4136D	MC3403P	RC3403ADB	LM741H	RM741T	1-23		
μA4136PC	RC4136DB	MC3503L	RM3503ADC	LM741CH	RC741T			
μA558TC	RC4558NB	MC3416L	RC4444R	6-18	LM741CH	RC741NB	1-25	
μA4558HC	RC4558T	MCB7601L	RC4444R		LM747D	RM747DC		
μA9622DM	RM9622DC			LM747CD	RC747DC	1-23		
μA9622DC	RC9622DC			LM747F	RM747Q			
				LM747H	RM747T	1-25		
				LM747CH	RC747T			
				LM747CN	RC747DB	4-14		
				LM748H	RM748T			
				LM748CH	RC748T	1-25		
				LM748CH	RC748NB			
				LM1414J	RC1414DC	1-29		
				LM1514N	RM1514DC			
				LM1458H	RC1458T/ RC4558T*	1-29		
				LM1458N	RC1458NB/ RC4558NB*			
				LM1558H	RM1558T			

*Wideband, low-noise version

Manufacturers' Cross Reference

Signetics	Raytheon Direct Replacement	Page	Silicon General	Raytheon Direct Replacement	Page	Texas Instruments	Raytheon Direct Replacement	Page	
N8T13E	RC8T13DD	5-10	SG101AD	LM101AD	1-2	SN52101AL	LM101AH	1-2	
N8T14E	RC8T14DD	5-12	SG101AT	LM101AH		SN5107L	LM107H	1-4	
N8T23E	RC8T23DD	5-15	SG105T	LM105H	3-4	SN52108L	LM108H	1-6	
N8T24E	RC8T24DD	5-17	SG107F	LM107F	1-4	SN52108AL	LM108H		
NE531T	RC4531T	1-57	SG107T	LM107H			SN52558L	RM4558T	1-59
NE531V	RC4531NB			SG108T	LM108H		SN52702F	RM702Q	2-2
NE555T	RC555T	6-2	SG108AF	LM108AF	1-6	SN52702L	RM702T		
NE555V	RC555NB			SG108AT		LM108AH		SN52072S	RM702Q
NE556T	RC556T	6-6	SG109T	LM109H	3-7	SN52709J	RM709DC	1-17	
NE556V	RC556NB			SG109K		LM109K			SN52709L
NE5556T	RC1556T	1-31	SG111T	LM111H	4-4	SN52709S	RM709Q		
NE5556V	RC1556NB			SG301AT	LM301AH	1-2	SN52709AJ	RM709ADC	
N5558T	RC1458T	1-29	SG304T	LM304H	3-2	SN52709AL	RM709AT		
N5558V	RC4558T*			SG305T	LM305H	3-4	SN52709AS	RM709AT	
	RC1458NB/			SG305AT	LM305AH			SN52709AS	RM709AQ
	RC4558NB*		SG307M	LM307N	1-4	SN52710J	RM710DC	4-10	
S8T13E	RM8T13DD	5-10	SG307T	LM307H			SN52710L		RM710T
S8T14E	RM8T14DD	5-12	SG308T	LM308H	1-6	SN52710S	RM710Q		
SE531T	RM4531T	1-57	SG308AT	LM308AH			SN52711J	RM711DC	4-12
SE556T	RM1556T	1-31	SG309T	LM309H	3-7	SN52711L	RM711T		
SE5558T	RM1558T	1-29	SG309K	LM309K			SN52711S	RM711Q	
μA709CT	RC709T	1-17	SG311T	LM311H	4-4	SN52733L	RM733T	2-5	
μA709G	RM709Q			SG710T	RM710T	4-10	SN52741F	RM741Q	1-21
μA709AT	RM709AT			SG710AT	RM710AT			SN52741J	
μA709T	RM709T			SG710CT	RC710T		SN52741L	RM741T	
μA710CT	RC710T	4-10	SG711T	RM711T	4-12	SN52741P	RM741NB		
μA710T	RM710T			SG711AT		RM711T		SN52747J	RM747D
μA710G	RM710Q			SG711CT	RC711T		SN54747L	RM747T	
μA711CK	RC711T	4-12	SG723D	RM723DC	3-9	SN52748J	RM748D	1-25	
μA711G	RM711Q			SG723CD		RC723DC			SN52748L
μA711K	RM711T			SG723T		RM723T		SN72301AL	LM301AH
μA723CL	RC723T	3-9	SG723CT	RC723T		SN72301AP	LM301AN		
μA723L	RM723T			SG733T	RM733T	2-5	SN72307L	LM307H	1-4
μA733CK	RC733T	2-5	SG733CT	RC733T			SN72307P	LM307N	
μA733K	RM733T			SG741D	RM741DC	1-21	SN72308L	LM308H	1-6
μA741CA	RC741DB	1-21	SG741CD	RC741DC			SN72308L	LM308H	
μA741CV	RC741NB			SG741F	RM741Q		SN72558L	RC1458T/ RC4558T*	1-29
μA741CT	RC741T			SG741T	RM741T		RC1458NB/ RC4558NB*		
μA741G	RM741Q			SG741CT	RC741T		SN72702J	RC702DC	2-2
μA741T	RM741T			SG741CM	RC741NB		SN72702L	RC702T	
μA747CA	RC747DP	1-23	SG741CN	RC741NB		SN72709J	RC709DC	1-17	
μA747CK	RC747T			SG747D	RM747DC		SN72709L		RC709T
μA747K	RM747T			SG747CD	RC747DB	1-23	SN72709P	RC709NB	
μA748CT	RC748T	1-25	SG747CN	RC747DB			SN72709AJ	RC709AD	
μA748CV	RC748NB			SG747T	RM747T		SN72709L	RC709AT	
μA748T	RM748T			SG747CT	RC747T	1-25	SN72710J	RC710DC	4-10
			SG748T	RM748T			SN72710L	RC710T	
						SN72711J	RC710DC		
						SN72711L	RC710T		
						SN72733L	RC733T	2-5	
						SN72741L	RC741DC	1-21	
						SN72741L	RC741T		
						SN72741P	RC741NB		
						SN72741N	RC741NB		
						SN72747J	RC747DC	1-23	
						SN72747L	RC747T		
						SN72747N	RC747DB		
						SN72748L	RC748T	1-25	
						SN75325J	RC75325DD	5-19	

*Wideband, low-noise version

Dual Operational Amplifier Summary

	SYMBOL	RM/RC747			RM1537/RC1437			RM1558/RC1458			RC4558			RC4739			UNIT	
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		
Maximum Ratings																		
Supply Voltage	VCC	±22/±18*			±18			±22/±18**			±18			±18			V	
Differential Input Voltage	VID	±30			±5			±30			±30			±30			V	
Input Voltage		±15			±10			±15			±15			±15			V	
Power Dissipation	PD	500			500			500			500			500			mW	
Electrical Characteristics																		
Test Conditions	VCC	±15			±15			±15			±15			±15				
Input Offset Voltage	VID	1.0			5.0			1.0			5.0			1.0			mV	
		2.0*			6.0*			2.0***			6.0***			2.0				
Input Offset Current	IIO	30			200			30			200			30			nA	
Input Bias Current	IIB	200			500			200			500			40			nA	
Input Common Mode Voltage Range	VICR	±12			±13			±12			±13			±12			V	
Supply Current	ID	3.3			5.6			3.3			5.6			3.3			mA	
Open Loop Voltage Gain	AVOL	50			200			25/10**			45			70			V/mV	
Output Voltage Swing	VOR	±12			±14			±12			±14			±12			V	
Common Mode Rejection Ratio	CMRR	70			90			70/65**			90			70			dB	
Power Supply Rejection Ratio	PSSR	30			150			150			200**			30			150	μV/V
Unity Gain Bandwidth	BW	0.8						0.8			3.0			3.0			MHz	
Slew Rate	SR	0.5						0.5			1.0			1.0			V/μs	
Channel Separation		70						70			105			125			dB	
Noise Voltage	VN	-55			125			-55			0			10			nV/(Hz) ^{1/2}	
Operating Temperature Range	TA	0*			70*			0***			70***			0			70	°C
Package:	Hermetic TO-5	TF			DC			TE			T							
	Hermetic Dip	DC			DB			NB			NB			NB				
	Plastic Dip	DB			DB			NB			NB			NB				

* RC747

** RC1437

*** RC1458

† Broad Band noise voltage (μV RMS)

Quad Operational Amplifier Summary

SYMBOL	RMA136/RC4136		LM124/LM224/LM324		LM2902		RM3503A/ RV3403A/RC3403A		LM2900/LM3900		RV3301/RC3401		UNIT	
	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		
Maximum Ratings														
Supply Voltage	±22/±18*		+32 or ±16		+32 or ±16		+36 or ±18		+36 or ±18		+28/+18 ‡		V	
Differential Input Voltage	±30		32		26		36		36				V	
Input Voltage	±15		32		26		36		36				V	
Power Dissipation	800		Hermetic Package 900 Plastic Package 570		Plastic Package 570		Hermetic Package 650 Plastic Package 500		Plastic Package 570		Plastic Package 625		mW	
Electrical Characteristics	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		
Test Condition V _{CC} :														
Input Offset Voltage	±15	0.5	5.0		2	5		±15					mV	
		0.5	6.0*		7**	7**		2						
Input Offset Current	5	5	200	±3	±3	±35		±30					nA	
				±3	±3	±50**		±50						
Input Bias Current	40	40	500			300		150		30	200	300	nA	
						500**		400						
Input Common Mode Voltage Range	±12	±14		0 to +35									V	
Supply Current	7	7	11.3	0.8	2	2		3	4/5‡	6.2	10	6.9	mA	
Open Loop Voltage Gain	50	300		100	100			100		1.2	2.8	2	V/rmV	
	20*							20‡						
Output Voltage Swing	±12	±14		0	V ⁺ -1.5	0		V ⁺ -1.5	±13	13.5	14.2	14.2	V	
Common Mode Rejection Ratio	70	100		85	85			70	90				dB	
Power Supply Rejection Ratio		10	150		100									
		μV/V	μV/V											
Unity Gain Bandwidth	3	3								2.5	0.5	4.0	MHz	
Slew Rate	1.5	1.0*			0.3			1.2		0.5		0.6	V/μs	
Output Sink Current					20			10	20	0.5	1.3	1.0	mA	
Output Source Current				20	40			20	40	3	18	10	mA	
Channel Separation	105				120			120				65	dB	
Operating Temperature Range	-55	0	+125	-55	LM124	+125	+85	-55	RM	+2900	+85	3301	°C	
			+70	-25	LM224	+85	+70	-40	RV	3900	+70	3401		
				0	LM324	+70		0	RC					
Package: 14 pin Dip	DC		DB		N		DC		DB		N		DB	
Hermetic	DC		DB		N		DC		DB		N		DB	
Plastic	DC		DB		N		DC		DB		N		DB	

*RC4136
 **LM324
 †RC/RV3403A
 ‡RC3401

Quad Comparators Summary

	SYMBOL	LM139			LM239/LM339			LM2901			RV3302			UNIT
Maximum Ratings														
Supply Voltage	VCC	+36			+36			+36			+28 or ±14			V
Differential Input Voltage	V _{ID}	+36			+36			+36			+28			V
Input Voltage		+36			+36			+36			+28			V
Power Dissipation	P _D	800			800			570			625			mW
Electrical Characteristics														
Test Condition	VCC	+5			+5			+5			+5/+15**			V
Input Offset Voltage	V _{IO}	2/1	5/2*		2/1	5/2*		2	7		3	20		mV
Input Offset Current	I _{IO}	3	25		5	50		5	50		±3	±100		nA
Input Bias Current	I _{IB}	25	100		25	250		25	250		25/30**	500		nA
Input Common Mode Voltage Range	V _{ICR}	0	+3.5	0		+3.5	0		+3.5	0		+3.5		V
Supply Current	I _{OC}		2			2			2			1.5		nA
Open Loop Voltage Gain	AVOL	200			200			200		2	30			V/mV
Common Mode Rejection Ratio	CMRR										60			dB
Slew Rate	SR										-200			V/μs
Response Time	T _r	1.3			1.3						2.0			μs
Output Sink Current	I _{sink}	6	16	6	6	16	6	6	16	2	16			mA
Saturation Voltage	V _{sat}	0.2	0.4		0.2	0.4		0.2	0.4		0.25	0.5		V
Output Leak Current	I _{OL}	0.1			0.1			0.1				1.0		nA
Operating Temperature Range	T _A	-55	129	-25	239	85	-40	85	70	-40		85		°C
Package: 14 Pin Dip	Hermetic Plastic	DC	DB	DC	DC	DB	DC	DB	DB	DC	DB	DC	DB	

* A version
**3302

Quality and Reliability

RAYACT-883A PROGRAM

The Raytheon Acceptance Testing Program called Rayact-883A involves in-process inspections which assure compliance with MIL-STD-883A test methods and MIL-M-38510 Program Plan Requirements.

Table 1 defines the Standard Process Flow for Raytheon Semiconductor's Military Level Integrated Circuits. After completion of the in-process inspections and 100% production screens, each lot is subjected to a quality conformance inspection as defined in Table 2. The screening and acceptance

testing outlined in Tables 1 and 2 are provided at no extra cost.

In addition to the Standard Process Flow and acceptance testing, Qualification Tests in accordance with MIL-STD-883A, Method 5005 are conducted every three months on each product line. Generic Summary Data of Groups A, B, and C testing (Table 3) is available upon request.

The level of reliability you desire can be selected from Table 4. These tests are conducted in accordance with Method 5004 of MIL-STD-883A.

APPLICABLE DOCUMENTS:

Military: MIL-STD-883A
MIL-M-38510

Raytheon Semiconductor:
Quality/Reliability Assurance Manual

Table 1—Standard Process Flow Summary for Integrated Circuits

MANUFACTURING OPERATION	MANUFACTURING INSPECTION	QUALITY/RELIABILITY INSPECTION
Manufacturing Stores	Purchased Item Verification	Receiving Inspection To Applicable M&SS and Blueprint Number
Mask Making	Mask Inspection	Mask Inspection
Materials Preparation	Wafer Preparation and Epitaxial Growing	Q.C. Monitor
Photoengraving and Diffusion	Electrical Probe Check and 100% Visual Inspection	Q.C. Monitor
Final Wafer Lot Acceptance	100% Visual Inspection	Q.C. Wafer Lot Acceptance
Electrical Test of Wafer	100% Electrical Test	Q.C. Monitor
Scribing and Dicing	100% Visual Inspection	Q.C. Monitor
Visual Die Sort MIL-STD-883A, Method 2010.2, Condition B	100% Die Sort Inspection	Dice Lot Acceptance
Die Attach	100% Visual Inspection	Q.C. Monitor
Lead Bond	100% Visual Inspection	Q.C. Monitor
Pre-Seal Inspection at 100X Magnification MIL-STD-883A, Method 2010, Condition B	100% Visual Inspection at High-Power Magnification	Q.C. Lot Acceptance
Pre-Seal Inspection at 30X Magnification MIL-STD-883A, Method 2010, Condition B	100% Visual Inspection at Low-Power Magnification	Q.C. Lot Acceptance

Table 1—Standard Process Flow Summary for Integrated Circuits (Cont.)

MANUFACTURING OPERATIONS	MANUFACTURING INSPECTION	QUALITY/RELIABILITY INSPECTION
Final Seal	Visual and Hermeticity	Q.C. Monitor
High-Temperature Bake 150°C — 24 Hours Minimum (MIL-STD-883A, Method 1008, Condition C)	100% Processing	Q.C. Monitor
Temperature Cycling -65°C to +150°C, 10 Cycles (MIL-STD-883A, Method 1010, Condition C)	100% Processing	Q.C. Monitor
Centrifuge 30 KG Minimum Y ₁ Axis (MIL-STD-883A, Method 2001, Condition E)	100% Processing	Q.C. Monitor
Lead Form	100% Visual Inspection	Q.C. Monitor
Carrier Load	100% Visual Inspection	Q.C. Monitor
Hermeticity MIL-STD-883A, Method 1014		Q.C. Monitor
External Visual	100% Inspection	Q.C. Monitor
Electrical Test and Sort	100% Inspection	Q.C. Monitor

Table 2—Quality Conformance Inspection (Each Lot)

INSPECTION		LTPD/MAX. ACC. NO.	COMMENTS
External		7/2	MIL-STD-883A, Method 2009
Hermeticity Fine Leak Gross Leak		7/2	MIL-STD-883A, Method 1014, Condition A or B MIL-STD-883A, Method 1014, Condition C ₂
Electrical Static Parameters	+25°C	5/1	Per Applicable Electrical Test Specification
	+125°C	7/1	
	-55°C	7/1	
Dynamic Parameters	+25°C	5/1	
	+125°C	7/1	
	-55°C	7/1	
Package and Ship		Quality Assurance Monitor	

NOTE:

Generic Qualification Data in accordance with MIL-STD-883A, Method 5005, can be supplied if negotiated prior to procurement.

Quality and Reliability

Table 3A—Group A Electrical Tests—MIL-STD-883A

SUBGROUPS	CLASS A LTPD	CLASS B LTPD	CLASS C LTPD
Subgroup 1 Static tests at 25°C	5	5	5
Subgroup 2 Static tests at maximum rated operating temperature	5	7	10
Subgroup 3 Static tests at minimum rated operating temperature	5	7	10
Subgroup 4 Dynamic tests at 25°C	5	5	5
Subgroup 5 Dynamic tests at maximum rated operating temperature	5	7	10
Subgroup 6 Dynamic tests at minimum rated operating temperature	5	7	10
Subgroup 7 Functional tests at 25°C	3	5	5
Subgroup 8 Functional tests at maximum and minimum rated operating temperatures	5	10	15
Subgroup 9 Switching tests at 25°C	5	7	10
Subgroup 10 Switching tests at maximum rated operating temperature	5	10	15
Subgroup 11 Switching tests at minimum rated operating temperature	5	10	15

NOTE:

The specific parameters to be included for tests in each subgroup shall be as specified in the applicable reliability specification. Where no parameters have been identified in a particular subgroup or test within a subgroup, no group A testing shall be performed for that subgroup or test to satisfy group A requirements.

Table 3B—Group B Tests, MIL-STD-883A, Method 5005

	TEST	MIL-STD-883		CLASS A LTPD	CLASS B LTPD	CLASS C LTPD
		METHOD	CONDITION			
Subgroup 1	Physical dimensions	2016		10	15	20
Subgroup 2	Resistance to solvents	2015		3 devices (no failures)	3 devices (no failures)	3 devices (no failures)
	Visual and mechanical	2014	Criteria from design and construction requirements of applicable procurement document	1 device (no failures)	1 device (no failures)	1 device (no failures)
	Bond strength	2011		5	15	20
	Thermocompression		Test condition C or D			
	Ultrasonic or wedge		Test condition C or D			
Subgroup 3	Solderability	2003	Soldering temperature of 260°C ±10°	10	15	15
Subgroup 4	Lead fatigue	2004	Test condition B2	10	15	15
	Seal: Fine, Gross	1014	As applicable			

Table 3C—Group C Tests, MIL-STD-883A, Method 5005

TEST	MIL-STD-883A		CLASS A LTPD	CLASS B LTPD	CLASS C LTPD
	METHOD	CONDITION			
Subgroup 1 (Note 1) Thermal shock Temperature cycling Moisture resistance Seal a. Fine b. Gross (Note 7) Visual examination (Note 2) End point electrical parameters	1011 1010 1004 1014	Test condition B as a minimum. Test condition C As applicable As specified in the applicable procurement document.	10	15	15
Subgroup 2 (Note 1) Mechanical shock Vibration, variable frequency Constant acceleration Seal a. Fine b. Gross (Note 7) Visual examination (Note 3) End point electrical parameters	2002 2007 2001 1014	Test condition B Test condition A Test condition E As applicable As specified in the applicable procurement document.	10	15	15
Subgroup 3 Salt atmosphere (Note 4) Visual examination (Note 5)	1009	Test condition A	10	15	15
Subgroup 4 High temperature storage (Note 6) End point electrical parameters	1008	Test condition C 1000 hours. As specified in the applicable procurement document.	7	7	7
Subgroup 5 Operating life test (Note 6) End point electrical parameters	1005	Test condition to be specified in the applicable procurement document (1000 hours). As specified in the applicable procurement document.	5	5	5
Subgroup 6 Steady state reverse bias End point electrical parameters	1005	Test condition A, 72 hours at 150°C. As specified in the applicable procurement document.	7	—	—

NOTES:

1. Devices used for environmental tests in subgroup 1 may be used for mechanical tests in subgroup 2.
2. Visual examination shall be in accordance with method 1010 or 1011 at a magnification of 5X to 10X.
3. Visual examination shall be performed at a magnification of 5X to 10X for evidence of defects of damage to case, leads, or seals resulting from testing (not fixturing) such damage shall constitute a failure.
4. Electrical reject devices from the same inspection lot may be used for samples.
5. Visual examination shall be performed in accordance with 3.3.1 of method 1009.
6. See 40.4 of appendix B of MIL-M-38510.
7. When fluorocarbon gross leak testing is utilized, test condition C₂ shall apply as minimum.

Quality and Reliability

Table 4—Optional Screening—MIL-STD-883A, Method 5004

SCREEN	CLASS A		CLASS B		CLASS C	
	METHOD	REQUIREMENT	METHOD	REQUIREMENT	METHOD	REQUIREMENT
Internal visual (Precap)	2010 test condition A	100%	2010 test condition B	100%	2010 test condition B	100%
Stabilization bake	1008, 24 hrs. test condition C, 150°C	100%	1008, 24 hrs. test condition C, 150°C	100%	1008, 24 hrs. test condition C, 150°C	100%
Thermal shock	1011, test condition A, 0°C-100°C 15 cycles	100%	Not required		Not required	
Temperature cycling	1010 test condition C, -65°C to +150°C 10 cycles	100%	1010, test condition C, -65°C to +150°C 10 cycles	100%	1010, test condition C, -65°C to +150°C 10 cycles	100%
Mechanical shock	2002**	100%	Not required		Not required	
Constant Acceleration	2001, test condition E Y ₂ plane, then Y ₁ plane, 30,000 G's	100%	2001, test condition E Y ₁ plane, 30,000 G's	100%	2001, test condition E Y ₁ plane, 30,000 G's	100%
Seal Fine, Gross	1014, Condition A Condition C Hermetic devices only	100%	1014, Condition A Condition C* Hermetic devices only	100%	1014, Condition A Condition C Hermetic devices only	100%
Critical electrical parameters	*	100%	Go-No-Go		Not required	
Burn-in test	1015, 240 hrs. @ T _A = 125°C*	100%	1015, 168 hrs. @ T _A = 125°C*	100%	Not required	
Critical electrical parameters	*	100%	Not required		Not required	
Reverse bias burn-in	1015, test condition A or C, 72 hrs. @ 150°C	100%	Not required		Not required	
Final electrical test	*		*		*	
Static tests 25°C		100%		100%		100%
Maximum and minimum rated operating temp.		100%		100%		
Dynamic tests and switching tests 25°C		100%		100%		
Functional test 25°C (subgroup 7, table 1, 5005)		100%		100%		100%
Group A Testing	Per Table 3A		Per Table 3A		Per Table 3A	
Radiographic	2012	100%	Not required		Not required	
Qualification or quality conformance inspection Groups B and C optional, at extra cost	5005	*	5005	*	5005	*
External visual	2009	100%	2009	100%	2009	100%

* Per applicable procurement document

** Test Condition F one shock pulse in Y₁ plane only or five shock pulses at Condition B in Y₁ plane only.

SECTION 1

Operational Amplifiers

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GENERAL DESCRIPTION

The LM101A/LM201A and LM301A are general purpose, high performance operational amplifiers fabricated monolithically on a silicon chip by the planar epitaxial process. The units may be fully compensated with the addition of a 30pF capacitor stabilizing the circuit for all feedback configurations including capacitive loads.

The device may be operated as a comparator with a differential input as high as $\pm 30V$. Used as a comparator the output can be clamped at any desired level to make it compatible with logic circuits.

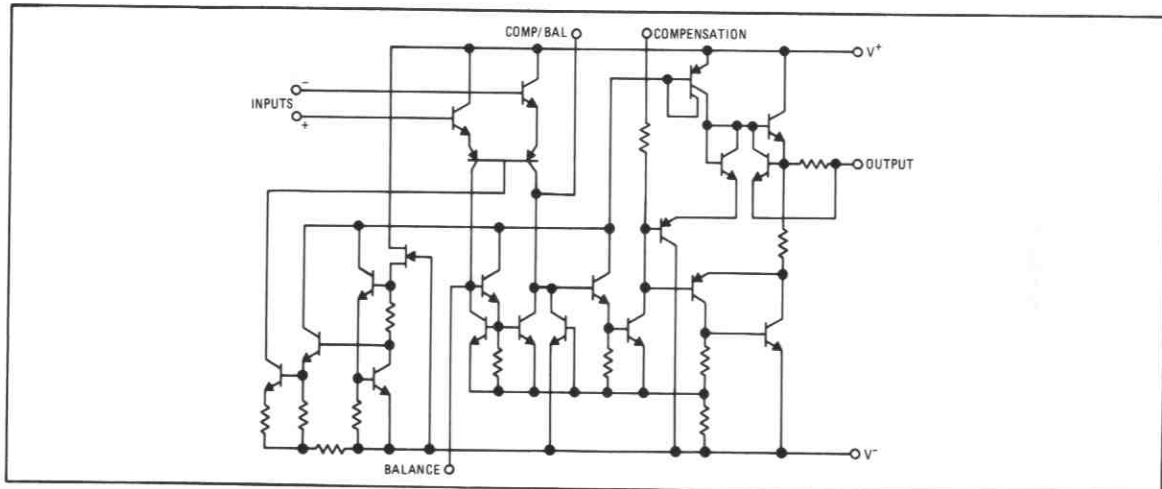
The LM101A operational amplifier will operate over the full military temperature range from $-55^{\circ}C$ to $+125^{\circ}C$. The commercial version, the LM301A operates over a temperature range from $0^{\circ}C$ to $+70^{\circ}C$.

The LM201A is the same as the LM101A except its performance is guaranteed from $-25^{\circ}C$ to $+85^{\circ}C$.

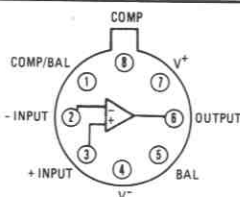
DESIGN FEATURES

- Offset Voltage 3mV Maximum Over Temperature
- Input Current 100nA Maximum Over Temperature
- Offset Current 20nA Maximum Over Temperature
- Offsets Guaranteed Over Entire Common-Mode Range
- Frequency Compensation 30pF
- Supply Voltage $\pm 5V$ to $\pm 20V$
- Continuous Short Circuit Protection

SCHEMATIC DIAGRAM

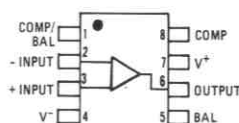


CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
LM101AH, LM201AH,
LM301AH



NB Dual In-line
Package
(Top View)

Order Part No.:
LM301AN

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	101A, 201A: $\pm 22V$ 301A: $\pm 18V$	Operating Temperature Range	
Power Dissipation (Note 1)	500mW	LM101A	$-55^{\circ}C$ to $+125^{\circ}C$
Differential Input Voltage	$\pm 30V$	LM201A	$-25^{\circ}C$ to $+85^{\circ}C$
Input Voltage (Note 2)	$\pm 15V$	LM301A	$0^{\circ}C$ to $+70^{\circ}C$
Output Short-Circuit Duration (Note 3)	Indefinite	Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$
		Lead Temperature (Soldering, 60s)	$300^{\circ}C$

ELECTRICAL CHARACTERISTICS LM101A, LM201A: $\pm 5V \leq V_S \leq \pm 20V$; LM301A: $\pm 5 \leq V_S \leq \pm 15V$ (Note 4)

PARAMETER	CONDITIONS	LM101A, LM201A			LM301A			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$T_A = 25^{\circ}C, R_S \leq 50 k\Omega$		0.7	2.0		1.5	7.5	mV
Input Offset Current	$T_A = 25^{\circ}C$		1.5	10		3	50	nA
Input Bias Current	$T_A = 25^{\circ}C$		30	75		70	250	nA
Input Resistance	$T_A = 25^{\circ}C$	1.5	4		0.5	2		M Ω
Supply Current	$T_A = 25^{\circ}C, V_S = \pm 20V$		1.8	3.0		1.8	3.0	mA
Large Signal Voltage Gain	$T_A = 25^{\circ}C, V_S = \pm 15V$ $V_{OUT} = \pm 10V, R_L \geq 2 k\Omega$	50	160		25	160		V/mV
Input Offset Voltage	$R_S \leq 50 k\Omega$			3.0			10	mV
Average Temperature Coefficient of Input Offset Voltage			3.0	15		5.0	30	$\mu V/^{\circ}C$
Input Offset Current				20			70	nA
Average Temperature Coefficient of Input Offset Current	$25^{\circ}C \leq T_A \leq 125^{\circ}C$ $25^{\circ}C \leq T_A \leq 70^{\circ}C$ $-55^{\circ}C \leq T_A \leq 25^{\circ}C$ $0^{\circ}C \leq T_A \leq 25^{\circ}C$		0.01	0.1		0.01	0.3	nA/ $^{\circ}C$ nA/ $^{\circ}C$ nA/ $^{\circ}C$ nA/ $^{\circ}C$
Input Bias Current				100			300	nA
Supply Current	$T_A = +125^{\circ}C, V_S = \pm 20V$		1.2	2.5				mA
Large Signal Voltage Gain	$V_S = \pm 15V, V_{OUT} = \pm 10V$ $R_L \geq 2 k\Omega$	25			15			V/mV
Output Voltage Swing	$V_S = \pm 15V, R_L = 10 k\Omega$ $R_L = 2 k\Omega$	± 12 ± 10	± 14 ± 13		± 12 ± 10	± 14 ± 13		V V
Input Voltage Range	LM101A: $V_S = \pm 20V$; LM301A: $V_S = \pm 15V$	± 15			± 12			V
Common Mode Rejection Ratio	$R_S \leq 10 k\Omega$	80	96		70	96		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 k\Omega$	80	96		70	96		dB

NOTES:

- For operating at elevated temperatures, the device must be derated based on $+150^{\circ}C$ for LM101A, $+100^{\circ}C$ for LM301A, maximum junction temperature and a thermal resistance of $150^{\circ}C/W$ junction to ambient or $45^{\circ}C/W$ junction to case.
- For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.
- Continuous short-circuit is allowed for case temperatures to $+125^{\circ}C$ and ambient temperatures to $+70^{\circ}C$ for LM101A, case temperatures to $+70^{\circ}C$ and ambient temperatures to $+55^{\circ}C$ for LM301A.
- Specifications apply for temperature ranges: LM101A: $-55^{\circ}C$ to $+125^{\circ}C$; LM201A: $-25^{\circ}C$ to $+85^{\circ}C$; LM301A: $0^{\circ}C$ to $+70^{\circ}C$.

GENERAL DESCRIPTION

The LM107, LM207, and LM307 high-gain, general purpose operational amplifiers are monolithically constructed and internally compensated. The addition of a 30pF MOS capacitor guarantees unconditional stability eliminating the need for external frequency compensation. Input currents are a factor of ten lower than an industry standard device such as the 709, LM101, and 741.

This series offers all the best features of the LM101. In addition, the devices provide better accuracy and lower noise in high impedance circuitry.

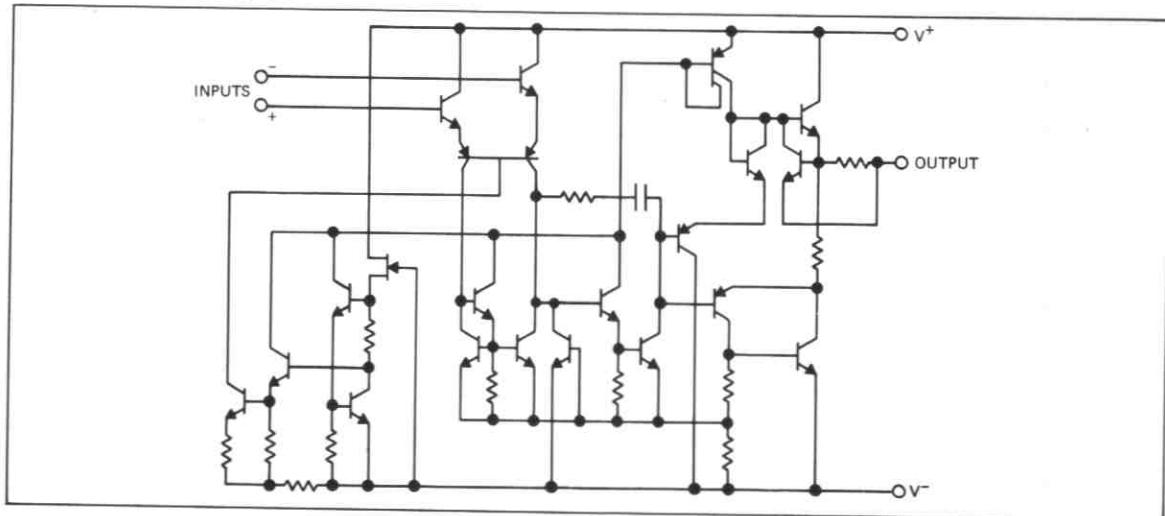
The LM107 operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The LM307 operates from 0°C to $+70^{\circ}\text{C}$.

The LM207 is the same as the LM107 except its performance is guaranteed from -20°C to $+85^{\circ}\text{C}$.

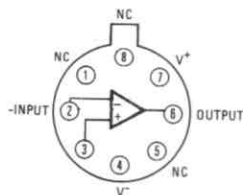
DESIGN FEATURES

- Offset Voltage 3mV Maximum Over Temperature
- Input Current 100nA Maximum Over Temperature
- Offset Current 20nA Maximum Over Temperature
- Offsets Guaranteed Over Entire Common-Mode Range
- Internal Frequency Compensation
- Supply Voltage $\pm 5\text{V}$ to $\pm 20\text{V}$
- Continuous Short Circuit Protection

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part No.:
LM107H, LM207H, LM307H



ABSOLUTE MAXIMUM RATINGS

Supply Voltage	101A, 201A: $\pm 22V$ 301A: $\pm 18V$	Operating Temperature Range	LM107: $-55^{\circ}C$ to $+125^{\circ}C$ LM207: $-25^{\circ}C$ to $+85^{\circ}C$ LM307: $0^{\circ}C$ to $+70^{\circ}C$
Power Dissipation (Note 1)	500mW	Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$
Differential Input Voltage	$\pm 30V$	Lead Temperature (Soldering, 60s)	$300^{\circ}C$
Input Voltage (Note 2)	$\pm 15V$		
Output Short-Circuit Duration (Note 3)	Indefinite		

ELECTRICAL CHARACTERISTICS LM101A, LM201A: $\pm 5V \leq V_S \leq \pm 20V$; LM301A: $\pm 5 \leq V_S \leq \pm 15V$ (Note 4)

PARAMETER	CONDITIONS	LM107			LM307 (Note 5)			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$T_A = 25^{\circ}C, R_S \leq 50 k\Omega$		0.7	2.0		1.5	7.5	mV
Input Offset Current	$T_A = 25^{\circ}C$		1.5	10		3	50	nA
Input Bias Current	$T_A = 25^{\circ}C$		30	75		70	250	nA
Input Resistance	$T_A = 25^{\circ}C$	1.5	4		0.5	2		M Ω
Supply Current	$T_A = 25^{\circ}C, V_S = \pm 20V$		1.8	3.0		1.8	3.0	mA
Large Signal Voltage Gain	$T_A = 25^{\circ}C, V_S = \pm 15V$ $V_{OUT} = \pm 10V, R_L \geq 2 k\Omega$	50	160		25	160		V/mV
Input Offset Voltage	$R_S \leq 50 k\Omega$			3.0			10	mV
Average Temperature Coefficient of Input Offset Voltage			3.0	15		5.0	30	$\mu V/^{\circ}C$
Input Offset Current				20			70	nA
Average Temperature Coefficient of Input Offset Current	$25^{\circ}C \leq T_A \leq 125^{\circ}C$		0.01	0.1				nA/ $^{\circ}C$
	$25^{\circ}C \leq T_A \leq 70^{\circ}C$ $-55^{\circ}C \leq T_A \leq 25^{\circ}C$ $0^{\circ}C \leq T_A \leq 25^{\circ}C$		0.02	0.2		0.01	0.3	nA/ $^{\circ}C$ nA/ $^{\circ}C$ nA/ $^{\circ}C$
Input Bias Current				100			300	nA
Supply Current	$T_A = +125^{\circ}C, V_S = \pm 20V$		1.2	2.5				mA
Large Signal Voltage Gain	$V_S = \pm 15V, V_{OUT} = \pm 10V$ $R_L \geq 2 k\Omega$	25			15			V/mV
Output Voltage Swing	$V_S = \pm 15V, R_L = 10 k\Omega$	± 12	± 14		± 12	± 14		V
	$R_L = 2 k\Omega$	± 10	± 13		± 10	± 13		V
Input Voltage Range	$V_S = \pm 20V$	± 15			± 12			V
Common Mode Rejection Ratio	$R_S \leq 10 k\Omega$	80	96		70	96		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 k\Omega$	80	96		70	96		dB

NOTES:

- For operating at elevated temperatures, the device must be derated based on $+150^{\circ}C$ for LM107 or $100^{\circ}C$ for LM307, maximum junction temperature and a thermal resistance of $150^{\circ}C/W$ junction to ambient or $45^{\circ}C/W$ junction to case.
- For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.
- Continuous short-circuit is allowed for case temperatures to $+125^{\circ}C$ and ambient temperatures to $+70^{\circ}C$ for LM107, case temperatures to $+70^{\circ}C$ and ambient temperatures to $+55^{\circ}C$ for LM307.
- These specifications apply for $-55^{\circ}C < T_A < +125^{\circ}C$ LM107, $-25^{\circ}C$ to $+85^{\circ}C$ LM207, and $5 < V_S < \pm 20V$ unless otherwise specified.
- These specifications apply for $0^{\circ}C < T_A < +70^{\circ}C$ and $\pm 5 < V_S < \pm 15V$ for LM307.

GENERAL DESCRIPTION

The LM108A/LM108, LM208A/LM208 and LM308A/LM308 are Super Beta operational amplifiers fabricated on single silicon chips using the planar epitaxial process.

The LM108A/LM108 offer specifications an order of magnitude better than FET amplifiers over a temperature range -55°C to $+125^{\circ}\text{C}$.

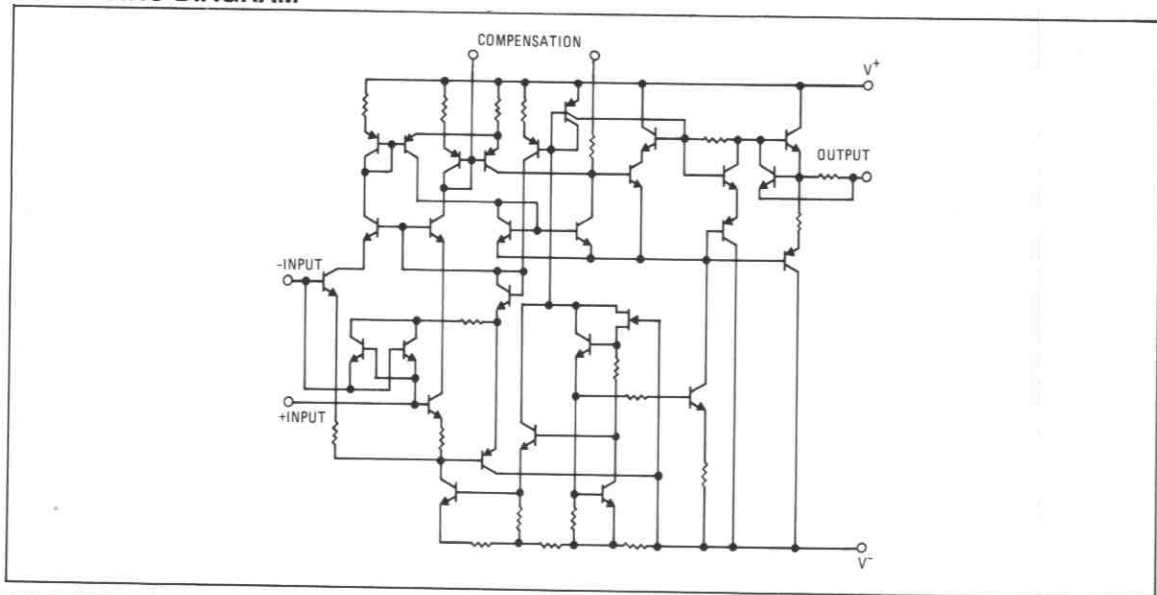
The LM208A/LM208 are identical to the LM108A/LM108 except their performance is guaranteed from -25°C to $+85^{\circ}\text{C}$.

The LM308A/LM308 provide lower input offset voltage of 0.5mV maximum, and drift characteristics of $5.0\mu\text{V}/^{\circ}\text{C}$ maximum. These devices can be compensated by the conventional technique used with the LM101/LM101A series.

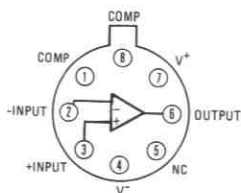
DESIGN FEATURES

- Offset Voltage Over Temperature Range 0.5mV Maximum
- Input Current Over Temperature Range 3.0nA Maximum
- Offset Current Over Temperature Range 400pA Maximum
- Supply Current Only 300 μA
- Guaranteed Drift Characteristics $5.0\mu\text{V}/^{\circ}\text{C}$ Maximum
- Supply Voltage $\pm 2\text{V}$ to $\pm 20\text{V}$

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
LM108AH, LM208AH,
LM308AH, LM108H,
LM208H, LM308H



Precision Operational Amplifiers

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	LM108A/LM108: $\pm 20V$ LM308A/LM308: $\pm 18V$	Operating Temperature Range	
Power Dissipation (Note 1)	500mW	LM108A/LM108	$-55^{\circ}C$ to $+125^{\circ}C$
Differential Input Current (Note 3)	$\pm 10mA$	LM208A/LM208	$-25^{\circ}C$ to $+85^{\circ}C$
Input Voltage (Note 2)	$\pm 15V$	LM308A/LM308	$0^{\circ}C$ to $+70^{\circ}C$
Output Short-Circuit Duration	Indefinite	Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$
		Lead Temperature (Soldering, 60s)	$300^{\circ}C$

ELECTRICAL CHARACTERISTICS (Notes 4 and 5)

PARAMETER	CONDITIONS	LM108A/LM208A			LM308A			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$T_A=25^{\circ}C$		0.3	0.5		0.3	0.5	mV
Large Signal Voltage Gain	$T_A=25^{\circ}C, V_S=\pm 15V, V_{out}=\pm 10V, R_L \geq 10k\Omega$	80	300		80	300		V/mV
Input Offset Voltage				1.0			0.73	mV
Average Temperature Coefficient of Input Offset Voltage			1.0	5.0		1.0	5.0	$\mu V/^{\circ}C$
Large Signal Voltage Gain	$V_S=\pm 15V, V_{out}=\pm 10V, R_L \geq 10k\Omega$	40			60			V/mV
Common Mode Rejection Ratio		96	110		96	110		dB
Supply Voltage Rejection Ratio		96	110		96	110		dB

PARAMETER	CONDITIONS	LM108/LM208			LM308			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$T_A=25^{\circ}C$		0.7	2.0		2.0	7.5	mV
Input Offset Current	$T_A=25^{\circ}C$		0.05	0.2		0.2	1.0	nA
Input Bias Current	$T_A=25^{\circ}C$		0.8	2.0		1.5	7.0	nA
Input Resistance	$T_A=25^{\circ}C$	30	70		10	40		$M\Omega$
Supply Current	$T_A=25^{\circ}C$		0.3	0.6		0.3	0.8	mA
Large Signal Voltage Gain	$T_A=25^{\circ}C, V_S=\pm 15V, V_{out}=\pm 10V, R_L \geq 10k\Omega$	50	300		25	300		V/mV
Input Offset Voltage				3.0			10	mV
Average Temperature Coefficient of Input Offset Voltage			3.0	15		6.0	30	$\mu V/^{\circ}C$
Input Offset Current				0.4			1.5	nA
Average Temperature Coefficient of Offset Current			0.5	2.5		2.0	10	$pA/^{\circ}C$
Input Bias Current				3.0			10	nA
Supply Current	$T_A=+125^{\circ}C$		0.15	0.4				mA
Large Signal Voltage Gain	$V_S=\pm 15V, V_{out}=\pm 10V, R_L \geq 10k\Omega$	25			15			V/mV
Output Voltage Swing	$V_S=\pm 15V, R_L=10k\Omega$	± 13	± 14		± 13	± 14		V
Input Voltage Range	$V_S=\pm 15V$	± 13.5			14			V
Common Mode Rejection Ratio		85	100		80	100		dB
Supply Voltage Rejection Ratio		80	96		80	96		dB

NOTES:

- For operating at elevated temperatures, the device must be derated based on $+150^{\circ}C$ for LM108, $+100^{\circ}C$ for LM308 maximum junction temperature and a thermal resistance of $150^{\circ}C/W$ junction to ambient or $45^{\circ}C/W$ junction to case.
- For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.
- The inputs are shunted with back-to-back diodes for overvoltage protection. Therefore, excessive current will flow if a differential input voltage in excess of 1V is applied between the inputs unless some limiting resistance is used.
- These specifications apply for $\pm 5V < V_S < \pm 20V$ and $-55^{\circ}C < T_A < +125^{\circ}C$, LM108A/LM108; $\pm 5V < V_S < \pm 20V$ and $-25^{\circ}C < T_A < +85^{\circ}C$, LM208A/LM208.
- These specifications apply for $\pm 5V < V_S < \pm 15V$ and $0^{\circ}C < T_A < +70^{\circ}C$, LM308A/LM308.



GENERAL DESCRIPTION

The LM112, LM212, and LM312 are Super Beta operational amplifiers, each fabricated on a silicon chip by the planar epitaxial process.

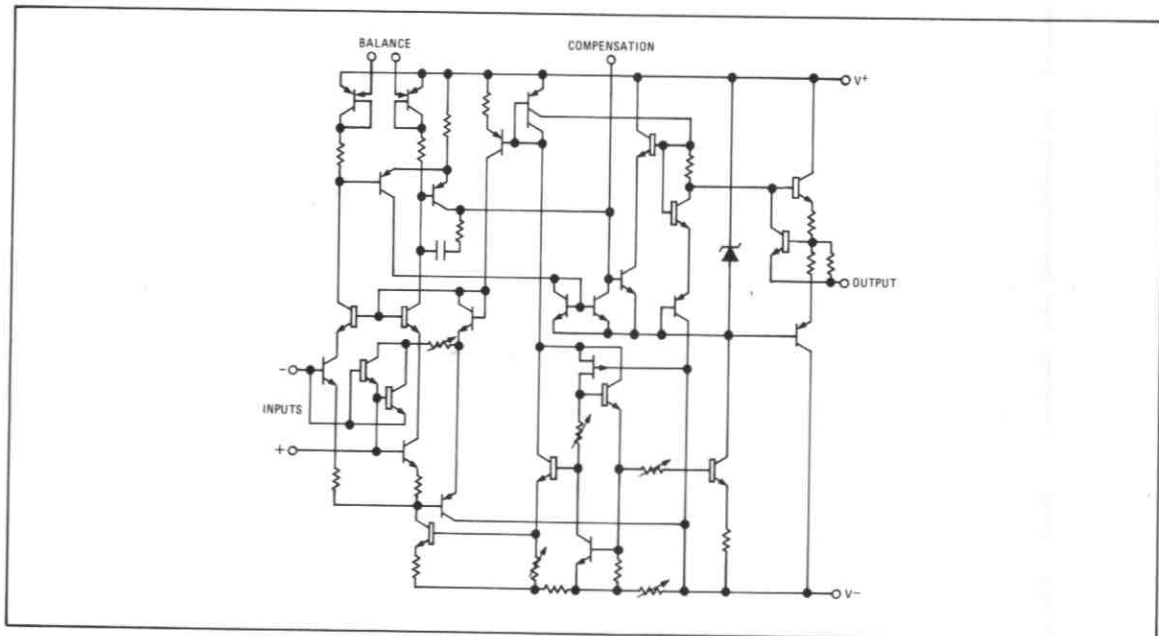
The LM112 offers specifications an order of magnitude better than FET amplifiers over a temperature range of -55°C to $+125^{\circ}\text{C}$. The LM212 is the same as the LM112 except its performance is guaranteed from -25°C to $+85^{\circ}\text{C}$. The LM312 is the commercial type which operates from 0°C to $+70^{\circ}\text{C}$.

In addition to internal compensation, external compensation may be added by means of a capacitor to increase stability. They also feature offset null adjustment by use of a single potentiometer.

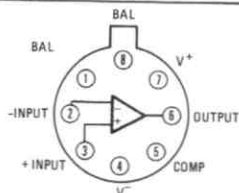
DESIGN FEATURES

- Input Bias Current 3.0nA Maximum Over Temperature Range
- Offset Current Less Than 400pA Over Temperature Range
- Low Noise
- Guaranteed Drift Specifications
- Supply Voltage Range $\pm 2\text{V}$ to $\pm 20\text{V}$ With Typical Quiescent Current of Only $300\mu\text{A}$

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
LM112H, LM212H
LM312H

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	LM112: $\pm 20V$ LM312: $\pm 18V$	Operating Temperature Range	
Power Dissipation (Note 1)	500mW	LM112	$-55^{\circ}C$ to $+125^{\circ}C$
Differential Input Current (Note 2)	$\pm 10mA$	LM212	$-25^{\circ}C$ to $+85^{\circ}C$
Input Voltage (Note 3)	$\pm 15V$	LM312	$0^{\circ}C$ to $+70^{\circ}C$
Output Short-Circuit Duration	Indefinite	Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$
		Lead Temperature (Soldering, 10s)	$+300^{\circ}C$

ELECTRICAL CHARACTERISTICS (Note 4)

PARAMETER	CONDITIONS	LM112, LM212			LM312			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$T_A = 25^{\circ}C$		0.7	2.0		2.0	7.5	mV
Input Offset Current	$T_A = 25^{\circ}C$		0.05	0.2		0.2	1.0	nA
Input Bias Current	$T_A = 25^{\circ}C$		0.8	2.0		1.5	7.0	nA
Input Resistance	$T_A = 25^{\circ}C$	30	70		10	40		M Ω
Supply Current	$T_A = 25^{\circ}C$		0.3	0.6		0.3	0.8	mA
Large Signal Voltage Gain	$T_A = 25^{\circ}C, V_S = \pm 15V,$ $V_{OUT} = \pm 10V, R_L = \geq 10k\Omega$	50	300		25	300		V/mV
Input Offset Voltage				3.0			10	mV
Average Temperature Coefficient of Input Offset Voltage			3.0	15		6.0	30	$\mu V/^{\circ}C$
Input Offset Current				0.4			1.5	nA
Average Temperature Coefficient of Input Offset Current			0.5	2.5		2.0	10	$pA/^{\circ}C$
Input Bias Current				3.0			10	nA
Supply Current	$T_A = +125^{\circ}C$		0.15	0.4				mA
Large Signal Voltage Gain	$V_S = \pm 15V, V_{OUT} = \pm 10V,$ $R_L \geq 10k\Omega$	25			15			V/mV
Output Voltage Swing	$V_S = \pm 15V, R_L = 10k\Omega$	± 13	± 14		± 13	± 14		V
Input Voltage Range	$V_S = \pm 15V$	± 13.5			± 14			V
Common-Mode Rejection Ratio		85	100		80	100		dB
Supply Voltage Rejection Ratio		80	96		80	96		dB

NOTES:

- The maximum junction temperature of the LM112 is $+150^{\circ}C$, and $+85^{\circ}C$ for the LM312. For operating at elevated temperatures, devices in the TO-5 package must be derated based on a thermal resistance of $+150^{\circ}C/W$, junction to ambient, or $+45^{\circ}C/W$, junction to case.
- The inputs are shunted with shunt diodes for overvoltage protection. Therefore, excessive current will flow if a differential input voltage in excess of 1V is applied between the inputs unless some limiting resistance is used.
- For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.
- These specifications apply for $\pm 5V < V_S < \pm 20V$ and $-55^{\circ}C < T_A < +125^{\circ}C$ for the LM112, unless otherwise specified, $\pm 5V < V_S < \pm 20V$ and $-25^{\circ}C < T_A < +85^{\circ}C$ for the LM212, $\pm 5V < V_S < \pm 15V$ and $0^{\circ}C < T_A < +70^{\circ}C$ for the LM312, unless otherwise specified.

GENERAL DESCRIPTION

The LM118, LM218, and LM318 are precision operational amplifiers which offer fast slewing and wide bandwidth. They feature internal frequency compensation and ten times the speed of general purpose amplifiers.

External feedforward compensation may be used for an additional increase in speed. For inverting applications this will increase the slew rate to more than $100\text{V}/\mu\text{s}$ and almost double the bandwidth. (Feedforward is not used for non-inverting or differential applications.)

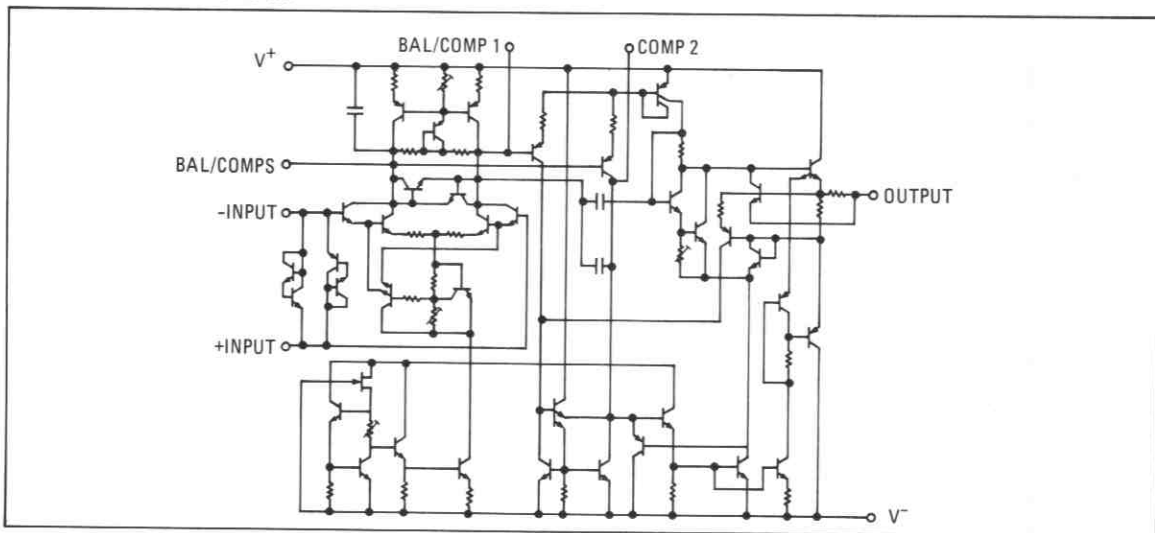
Their high speed and fast settling time make them ideal devices for A/D converters, oscillators, active filters, sample-and-hold circuits, as well as general purpose amplifiers.

The LM118 military version operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The LM218 is the same as the LM118 except its performance is guaranteed from -25°C to $+85^{\circ}\text{C}$. The LM318 operates from 0°C to $+70^{\circ}\text{C}$.

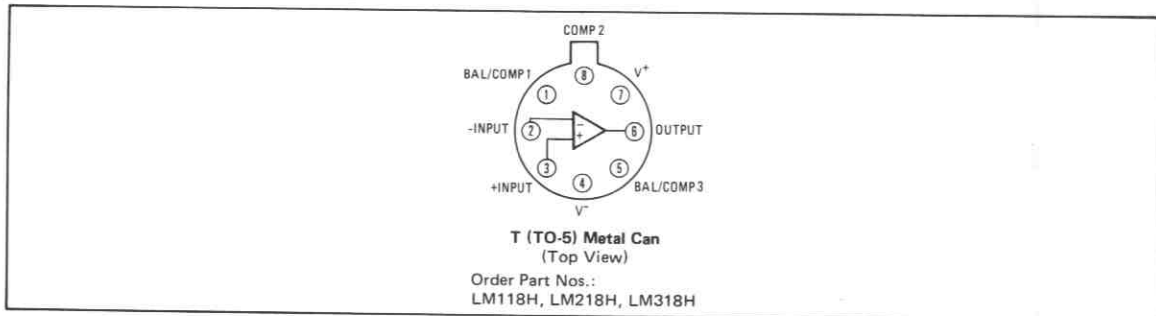
DESIGN FEATURES

- 15MHz Small Signal Bandwidth
- Guaranteed $50\text{V}/\mu\text{s}$ Slew Rate
- Operates from $\pm 5\text{V}$ to $\pm 18\text{V}$ Supply
- Internal Frequency Compensation
- Input and Output Overload Protected
- Pin Compatible With General Purpose Op Amps

SCHEMATIC DIAGRAM



CONNECTION INFORMATION


RAYTHEON

RAYTHEON COMPANY • SEMICONDUCTOR DIVISION • 350 ELLIS STREET • MOUNTAIN VIEW, CALIFORNIA

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±18V	Operating Temperature Range	
Power Dissipation (Note 1)	500mW	LM118	-55°C to +125°C
Differential Input Current (Note 2)	±10mA	LM218	-25°C to +85°C
Input Voltage (Note 3)	±15V	LM318	0°C to +70°C
Output Short-Circuit Duration	Indefinite	Storage Temperature Range	-65°C to +150°C
		Lead Temperature (Soldering, 10s)	+300°C

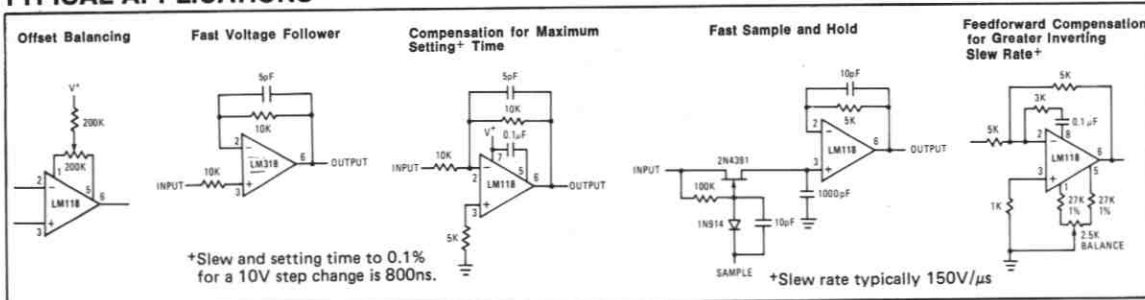
ELECTRICAL CHARACTERISTICS (Note 4)

PARAMETER	CONDITIONS	LM118/LM218	LM318	UNITS	
Input Offset Voltage	$T_A = 25^\circ\text{C}$	4	10	mV	Max.
Input Offset Current	$T_A = 25^\circ\text{C}$	50	200	nA	Max.
Input Bias Current	$T_A = 25^\circ\text{C}$	250	600	nA	Max.
Input Resistance	$T_A = 25^\circ\text{C}$	1	0.5	MΩ	Min.
Supply Current	$T_A = 25^\circ\text{C}$	8	10	mA	Max.
Large Signal Voltage Gain	$T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $V_{OUT} = \pm 10\text{V}$, $R_L \geq 2\text{k}$	50	25	V/mV	Min.
Input Offset Voltage		6	15	mV	Max.
Small Signal Bandwidth	$T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$	15	15	MHz	Typ.
Slew Rate	$T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $A_V = 1$, $R_S = 10\text{k}\Omega$	50	50	V/μs	Min.
Input Offset Current		100	300	nA	Max.
Input Bias Current		500	1000	nA	Max.
Supply Current	$T_A = T_{MAX}$	7	10	mA	Max.
Large Signal Voltage Gain	$V_S = \pm 15\text{V}$, $V_{OUT} = \pm 10\text{V}$, $R_L \geq 2\text{k}$	25	20	V/mV	Min.
Output Voltage Swing	$V_S = \pm 15\text{V}$, $R_L = 2\text{k}\Omega$	±12	±12	V	Min.
Input Voltage Range	$V_S = \pm 15\text{V}$	±11.5	±11.5	V	Min.
Common Mode Rejection Ratio		80	70	dB	Min.
Supply Voltage Rejection Ratio		70	65	dB	Min.

NOTES:

- The maximum junction temperature of the LM118 is +150°C, and +85°C for the LM318. For operating at elevated temperatures, devices in the TO-5 package must be derated based on a thermal resistance of 150°C/W, junction to ambient, or 45°C/W, junction to case.
- The inputs are shunted with shunt diodes for overvoltage protection. Therefore, excessive current will flow if a differential input voltage in excess of 1V is applied between the inputs unless some limiting resistance is used.
- For supply voltages less than ±15V, the absolute maximum input voltage is equal to the supply voltage.
- These specifications apply for $\pm 5\text{V} < V_S < \pm 18\text{V}$ and $-55^\circ\text{C} < T_A < +125^\circ\text{C}$ for the LM118; $\pm 15\text{V} < V_S < \pm 18\text{V}$ and $-20^\circ\text{C} < T_A < +85^\circ\text{C}$ for the LM218; $\pm 5\text{V} < V_S < \pm 15\text{V}$ and $0^\circ\text{C} < T_A < +70^\circ\text{C}$ for the LM318. Also, power supplies must be bypassed with 0.1μF ceramic disc capacitors.

TYPICAL APPLICATIONS



GENERAL DESCRIPTION

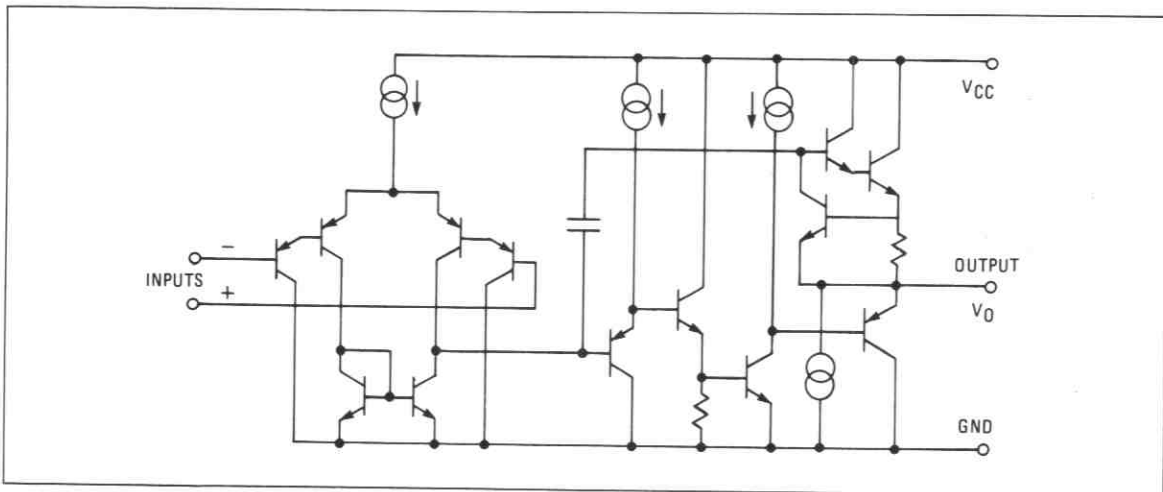
Each of the devices in this series consists of four independent, high-gain, operational amplifiers that are designed for single-supply operation. Operation from split power supplies is also possible and the low power supply drain is independent of the magnitude of the power supply voltage.

Used with a dual supply, the circuit will operate over a wide range of supply voltages. However, a large amount of crossover distortion may occur with loads to ground. An external current-sinking resistor to $-V_{CC}$ will reduce crossover distortion. There is no crossover distortion problem in single supply operation if the load is direct-coupled to ground.

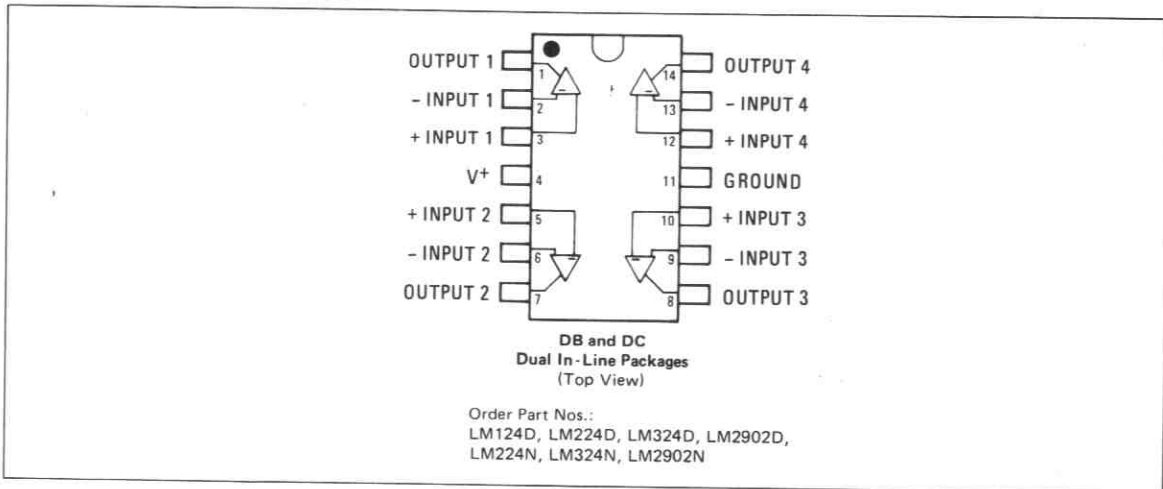
DESIGN FEATURES

- Large DC Voltage Gain 100 dB
- Compatible with All Forms of Logic
- Temperature Compensated
- Wide Bandwidth at Unity Gain Frequency 1 MHz
- Large Output Voltage Swing: 0 V_{DC} to V⁺ -1.5 V_{DC}
- Input Common Mode Voltage Range Includes Ground

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



Quad Single-Supply Operational Amplifier

1

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V^+	32 V or ± 16 V	Output Short-Circuit to GND (Note 2)	Continuous
Differential Input Voltage		Operating Temperature Range . LM324:	0°C to $+70^{\circ}\text{C}$
LM124	32 V	LM224:	-25°C to $+85^{\circ}\text{C}$
LM2902	-0.3 V to $+26$ V	LM124:	-55°C to $+125^{\circ}\text{C}$
Input Voltage	-0.3 V to $+32$ V	LM2902:	-40°C to $+85^{\circ}\text{C}$
Power Dissipation (Note 1)		Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
Molded DIP	LM324N, LM2902N: 570 mW	Lead Temperature (Soldering, 60s)	300°C
Cavity DIP	LM124D, LM224D & LM324D: 900 mW		

ELECTRICAL CHARACTERISTICS ($V^+ = +5$ V and $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	LM124			LM224, LM324			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S = 0\Omega$ (Note 5)		2	5		2	7	mV
Input Offset Current	$I_{IN(+)} - I_{IN(-)}$		± 3	± 30		± 5	± 50	nA
Input Bias Current (Note 3)	$I_{IN(+)}$ or $I_{IN(-)}$		45	150		45	250	nA
Common Mode Range	(Note 4)	0		$V^+ - 1.5$	0		$V^+ - 1.5$	V
Supply Current	$R_L = \infty$		0.8	2		0.8	2	mA
Large Signal Voltage Gain	$R_L \geq 2k\Omega$	50	100		25*	100		V/mV
Output Voltage Swing	$R_L = 2k\Omega$	0		$V^+ - 1.5$	0		$V^+ - 1.5$	V
Common Mode Rejection Ratio	DC	70	85	65*		85		dB
Power Supply Rejection Ratio	DC		100			100		dB
Channel Separation	$f = 1\text{kHz}$ to 20kHz (Input Referred) (Note 7)		-120			-120		dB
Output Source Current	$V_{IN^+} = +1\text{V}$ $V_{IN^-} = 0\text{V}$	20	40		20	40		mA
Output Sink Current	$V_O > 1\text{V}$		20			20		mA

NOTES

- For operating at high temperatures, the LM324 must be derated based on a $+125^{\circ}\text{C}$ maximum junction temperature and a thermal resistance of $175^{\circ}\text{C}/\text{W}$ which applies for the device soldered in a printed circuit board operating in a still air ambient. The LM224 and LM124 can be derated based upon a $+150^{\circ}\text{C}$ maximum junction temperature.
- Short circuits from the output to V^- can cause excessive heating and eventual destruction. The maximum output current is approximately 40mA independent of the magnitude of V^+ . At values of supply voltage in excess of $+15V_{DC}$, continuous short-circuits can exceed the power dissipation ratings and cause eventual destruction.
- The direction of the input current is out of the IC due to the PNP input stage. This current is essentially constant, independent of the state of the output so no loading change exists on the input lines.
- The input common-mode voltage on either input signal voltage should not be allowed to go negative by more than 0.3V. The upper end of the common-mode voltage range is $V^+ - 1.5\text{V}$, but either or both inputs can go to $+30V_{DC}$ without damage.
- $V_O \approx 1.4V_{DC}$, $R_S = 0\Omega$ with V^+ from $5V_{DC}$ to $30V_{DC}$; and over the full input common-mode range ($0V_{DC}$ to $V^+ - 1.5V_{DC}$).
- The direction of the input current is out of the IC due to the PNP input stage. This current is essentially constant, independent of the state of the output so no loading change exists on the input lines.
- Due to proximity of external components, insure that coupling is not originating via stray capacitance between these external parts. This typically can be detected as this type of capacitive coupling increases at higher frequencies.

ELECTRICAL CHARACTERISTICS

$V^+ = +5V_{DC}$ and $-55^{\circ}C \leq T_A \leq +125^{\circ}C$, unless otherwise stated. With the LM224, all temperature specifications are limited to $-25^{\circ}C \leq T_A \leq +85^{\circ}C$ and the LM324 temperature specifications are limited to $0^{\circ}C \leq T_A \leq +70^{\circ}C$.

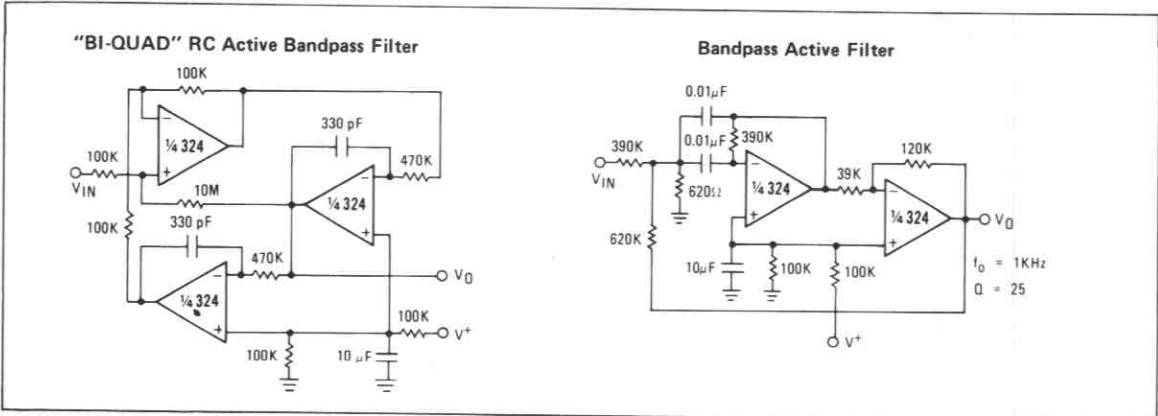
PARAMETER	CONDITIONS	LM124			LM224, LM324			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	(Note 5)			7			9	mV
Input Offset Current	$I_{IN(+)} - I_{IN(-)}$			± 100			± 150	nA
Input Bias Current				300			500	nA
Common Mode Range	$V^+ = 30V$ (Note 4)	0		$V^+ - 2$	0		$V^+ - 2$	V
Voltage Gain	$V^+ = 15V, R_L = 2k\Omega$	25			15			V/mV
Output Voltage Swing	$V^+ = 30V, R_L = 2k\Omega$	26			26			V
	$V^+ = 5V, R_L = 10k\Omega$		5	20		5	20	mV
Output Source Current	$V_{IN} = 1V, V^+ = 15V$	10	20		10	20		mA
Output Sink Current		5	8		5	8		mA

LM 2902

ELECTRICAL CHARACTERISTICS ($V^+ = +5V_{DC}$ and $T_A = 25^{\circ}C$ unless otherwise noted)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Input offset Voltage	$R_S = 0\Omega$		2	10	mV _{DC}
Input Bias Current (Note 3)	$I_{IN(+)} \text{ or } I_{IN(-)}$		45	500	nADC
Input Offset Current	$I_{IN(+)} - I_{IN(-)}$		± 5	± 50	nADC
Common-Mode Range	(Note 4)	0		$V^+ - 1.5$	V _{DC}
Supply Current	$R_L = \infty$		0.8	2	mADC
Large Signal Voltage Gain	$R_L \geq 2k\Omega$		100		V/mV
	$R_L = 2k\Omega$	0		$V^+ - 1.5$	V _{DC}
Common Mode Rejection Ratio	DC		85		dB
Power Supply Rejection Ratio	DC		100		dB
Amplifier-to-Amplifier Coupling	$f = 1kHz \text{ to } 20kHz$ (Input Referred)		-120		dB
Output Current Source	$V_{IN}^+ = +1V_{DC}, V_{IN}^- = 0V_{DC}$	20	40		mADC
Output Current Sink	$V_{IN}^- = +1V_{DC}, V_{IN}^+ = 0V_{DC}$	8	20		mADC

324 TYPICAL APPLICATIONS



Precision Operational Amplifiers

GENERAL DESCRIPTION

The LM216A/LM216 and LM316A/LM316 are precision, high input impedance operational amplifiers ideally suited for applications requiring extremely low input current errors. Super Beta transistors are used in a Darlington input stage to obtain input bias currents equal to high quality FET amplifiers.

They are frequency compensated internally, and allow offset balancing with an external potentiometer. The MOS compensation capacitor is protected to prevent catastrophic failure due to overvoltage spikes on the supplies.

The low current error of these amplifiers permits many designs previously impractical with monolithic devices. They can operate from 100M Ω source resistances, introducing less error than general purpose amplifiers with 10k Ω sources. Also inte-

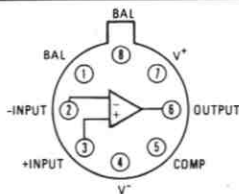
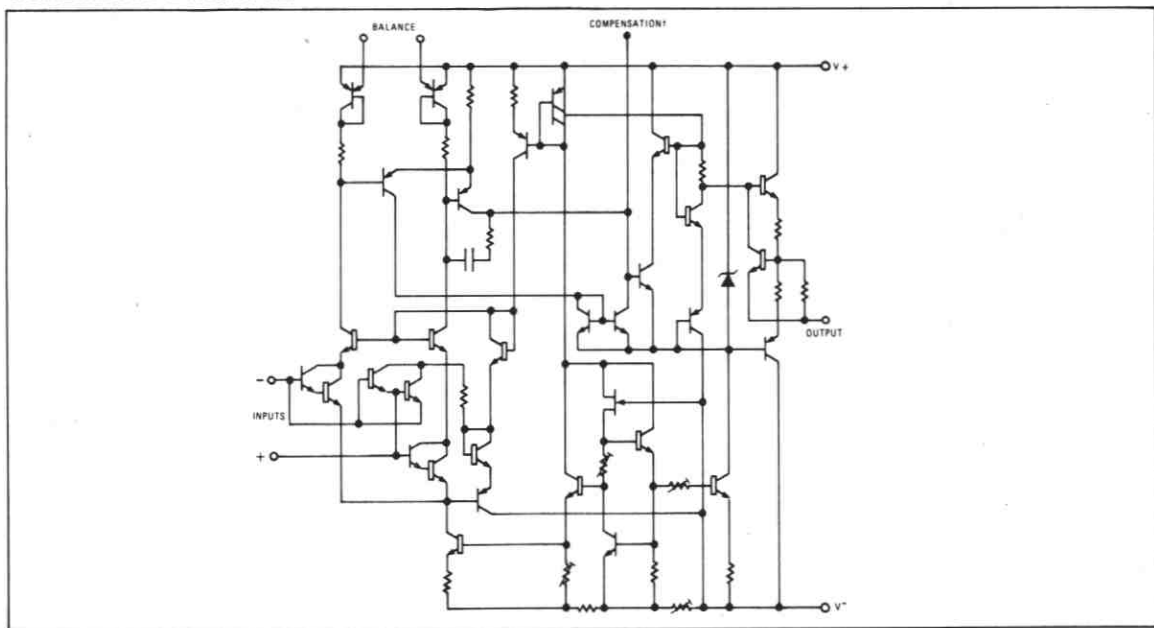
grators with worst-case drifts of less than 10 μ V/s and analog time delays in excess of one day can be made using capacitors no larger than 1 μ F.

The LM216A/LM216 are specified for operation from -25 $^{\circ}$ C to +85 $^{\circ}$ C. The LM316A/LM316 operates over a range of 0 $^{\circ}$ C to +55 $^{\circ}$ C.

DESIGN FEATURES

- Guaranteed Bias Currents as Low as 50pA
- Maximum Offset Currents as Low as 15pA
- Operates from \pm 3V to \pm 20V Supplies
- Supply Current Only 300 μ A

SCHEMATIC DIAGRAM



NOTE: Pin 4 connected to case.

TE (TO-5) Metal Can
(Top View)

Order Part Nos.:
LM216H, LM216AH,
LM316H, LM316AH

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±20V	Operating Temperature Range	
Power Dissipation (Note 1)	500mW	LM216A/216	-25°C to +85°C
Differential Input Current (Note 2)	±10mA	LM316A/316	0°C to +55°C
Input Voltage (Note 3)	±15V	Storage Temperature Range	-65°C to +150°C
Output Short-Circuit Duration	Indefinite	Lead Temperature (Soldering, 10s)	300°C

ELECTRICAL CHARACTERISTICS (Note 4)

PARAMETER	CONDITIONS	LM216	LM216A	LM316	LM316A	UNITS
Input Offset Voltage	T _A = 25°C	10	3	10	3	mV max
Input Offset Current	T _A = 25°C	50	15	50	15	pA max
Input Bias Current	T _A = 25°C	150	50	150	50	pA max
Input Resistance	T _A = 25°C	1	5	1	5	GΩ typ
Supply Current	T _A = 25°C	0.8	0.6	0.8	0.6	mA max
Large Signal Voltage Gain	T _A = 25°C, V _S = ±15V, V _{OUT} = ±10V, R _L ≥ 10kΩ	20	40	20	40	V/mV min
Input Offset Voltage		15	6	15	6	mV max
Input Offset Current		100	30	100	30	pA max
Input Bias Current		250	100	250	100	pA max
Supply Current	T _A = T _{MAX}		0.5		0.5	mA max
Large Signal Voltage Gain	V _S = ±15V, V _{OUT} = ±10V, R _L ≥ 10kΩ	10	20	15	30	V/mV min
Output Voltage Swing	V _S = ±15V, R _L = 10kΩ	±13	±13	±13	±13	V min
Input Voltage Range	V _S = ±15V	±13	±13	±13	±13	V min
Common Mode Rejection Ratio		80	80	80	80	dB min
Supply Voltage Rejection Ratio		80	80	80	80	dB min

NOTES:

1. The maximum junction temperature of the LM216 and LM216A is 100°C, while that of the LM316 and LM316A is 70°C. For operating at elevated temperatures, devices in the TO-5 package must be derated based on a thermal resistance of 150°C/W, junction to ambient, or 45°C/W, junction to case.
2. The inputs are shunted with back-to-back diodes for overvoltage protection. Therefore, excessive current will flow if a differential input voltage in excess of 1V is applied between the inputs unless some limiting resistance is used.
3. For supply voltages less than ±15V, the absolute maximum input voltage is equal to the supply voltage.
4. These specifications apply for ±5V ≤ V_S ≤ ±20V and -25°C ≤ T_A ≤ 85°C, unless otherwise specified. With the LM316 and LM316A, however, all temperature specifications are limited to 0°C ≤ T_A ≤ +70°C.



High-Gain Operational Amplifiers

GENERAL DESCRIPTION

The RM709A/RM709 and RC709 are monolithic, high gain DC operational amplifiers fabricated on a single silicon chip by the planar process.

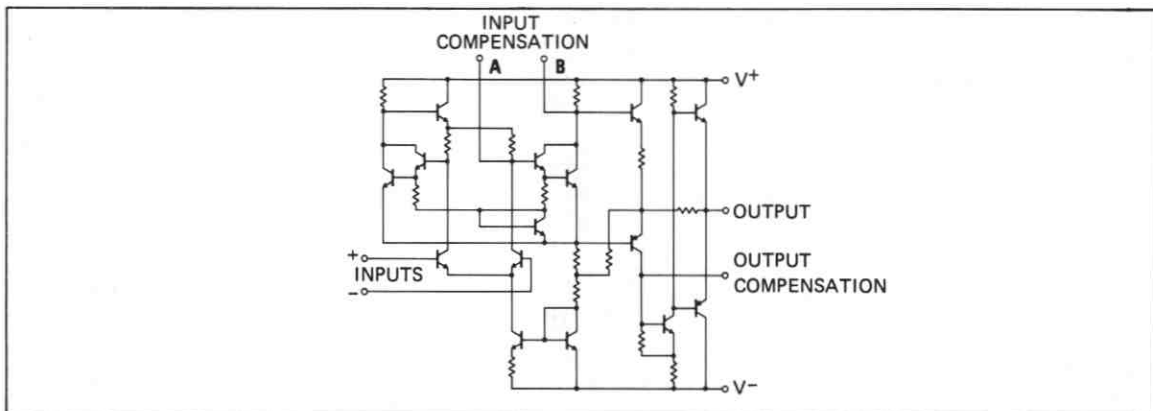
These devices are designed for use in operational amplifier signal processing, low level instrumentation, control systems and for the generation of special linear and non-linear transfer functions.

The RM709A/RM709 operate over the full military temperature range from -55°C to $+125^{\circ}\text{C}$. The RC709 is the commercial device intended to operate over a temperature range of 0°C to $+70^{\circ}\text{C}$.

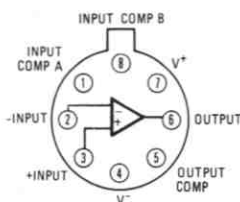
DESIGN FEATURES

- Low Input Offset Voltage $\pm 1.0\text{mV}$ Maximum
- Low Temperature Drift of Input Offset Voltage $\pm 6\mu\text{V}/^{\circ}\text{C}$ Maximum
- Low Temperature Drift of Input Offset Current ($+25^{\circ}\text{C}$ to $+125^{\circ}\text{C}$) $0.3\text{nA}/^{\circ}\text{C}$ Maximum (-55°C to $+25^{\circ}\text{C}$) $1.0\text{nA}/^{\circ}\text{C}$ Maximum
- Low Power Consumption 90mW Maximum
- High Performance Open Loop Gain Characteristics 45k Typical

SCHEMATIC DIAGRAM



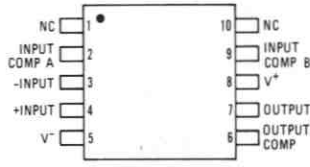
CONNECTION INFORMATION



NOTE: Pin 4 connected to case.

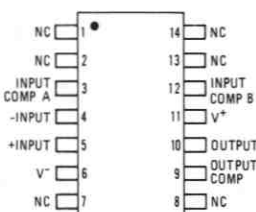
TE (TO-5) Metal Can
(Top View)

Order Part Nos.:
RM709AT, RM709T,
RC709T



Q Flat Package
(Top View)

Order Part Nos.:
RM709AQ, RM709Q



NOTE: Pin 7 connected to bottom of package.

DC Dual In-line
Package
(Top View)

Order Part Nos.:
RM709ADC, RM709DC,
RC709DC

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±18V	Output Short-Circuit Duration (T _A = 25°C)	5 sec
Differential Input Voltage	±5V	Storage Temperature Range	-65°C to +150°C
Input Voltage	±10V	Operating Temperature Range	
Power Dissipation (Note)		RM709/709A	-55°C to +125°C
Dual In-line Package	300mW	RC709	0°C to +70°C
TO-5 Package	300mW	Lead Temperature (Soldering, 60s)	300°C
Flat Package	250mW		

ELECTRICAL CHARACTERISTICS (±9 ≤ V_S ≤ ±15V, T_A = 25°C unless otherwise specified)

PARAMETER	CONDITIONS	RM709A			RM709			RC709			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	R _S ≤ 10kΩ	0.2	1.0		1.0	3.0		2.0	7.5	mV	
Input Offset Current		10	50		25	100		100	500	nA	
Input Bias Current		100	200		180	300		300	1500	nA	
Input Resistance		350	700		220	400		50	250	kΩ	
Output Resistance			150			150			150	Ω	
Supply Current	V _S = ±15V	2.3	3.0		2.6	4.0				mA	
Power Consumption	V _S = ±15V	70	90		80	120		80	200	mW	
Transient Response	R _L = 2kΩ, V _S = ±15V, V _{IN} = 20mV										
Rise Time	C ₁ = 5nF, R ₁ = 1.5k, C ₂ = 200pF, R ₂ = 50Ω	0.3	1.0		0.3	1.0		0.3	1.0	μs	
Overshoot	C _L ≤ 100pF	10	30		10	30		10	30	%	
Slew Rate	V _S = ±15V, R _L ≥ 10kΩ, A _V = 1	0.2	0.4		0.15	0.4		0.4		V/μs	
Large Signal Voltage Gain	V _S = ±15V, R _L = 2k, V _{OUT} = ±10V							15	45	kV/V	
The following specifications apply for -55°C ≤ T_A ≤ +125°C for RM; 0°C ≤ T_A ≤ 70°C for RC.											
Large Signal Voltage Gain	V _S = ±15V, R _L ≥ 2k, V _{OUT} = ±10V	25	45	70	25	45	70	12		kV/V	
Input Offset Voltage	R _S ≤ 10kΩ			2.0			4.0		10	mV	
Input Offset Current	T _A = max		3.0	50		10	100			nA	
	T _A = min		30	250		50	300		750	nA	
Input Bias Current	T _A = min		300	600		400	1000		2000	nA	
Average Temperature of Coefficient of Input Offset Voltage	R _S = 50Ω, T _A = 25°C to T _A = max		1.0	6.0		1.8	10			μV/°C	
	R _S = 50Ω, T _A = 25°C to T _A = min		1.0	6.0		1.8	10				
	R _S = 10k, T _A = 25°C to T _A = max		1.6	9.0		2.0	15				
	R _S = 10k, T _A = 25°C to T _A = min		3.0	16		6.0	15				
Average Temperature Coefficient of Input Offset Current	T _A = +25°C to max		0.06	0.3						nA/°C	
	T _A = +25°C to min		0.2	1.0							
Input Voltage Range	V _S = ±15V	±8.0	±10		±8.0	±10		±8.0	±10	V	
Output Voltage Swing	V _S = ±15V, R _L ≥ 10kΩ	±12	±14		±12	±14		±12	±14	V	
	V _S = ±15V, R _L ≥ 2kΩ	±10	±13		±10	±13		±10	±13		
Input Resistance	T _A = min	85	170		50	125		35	125	kΩ	
Common Mode Rejection Ratio	R _S ≤ 10kΩ	80	90		70	90		65	90	dB	
Supply Voltage Rejection Ratio	R _S ≤ 10kΩ		40	75		25	150		25	200	μV/V
Supply Current	V _S = ±15V, T _A = max		2.0	2.7						mA	
	V _S = ±15V, T _A = min		2.6	3.9							
Power Consumption	V _S = ±15V, T _A = max		60	81						mW	
	V _S = ±15V, T _A = min		78	117							

NOTE:

Derate linearly the maximum power dissipation of the dual in-line package at 8.6mW/°C for ambient temperature above +115°C, of the TO-5 package at 5.6mW/°C for ambient temperature above +95°C and of the flat package at 5.4mW/°C for ambient temperature above +103°C. For RC709, rating applies for case temperatures to +70°C.



GENERAL DESCRIPTION

The RM725 and RC725 are high performance, high gain operational amplifiers on a silicon planar epitaxial processed chip.

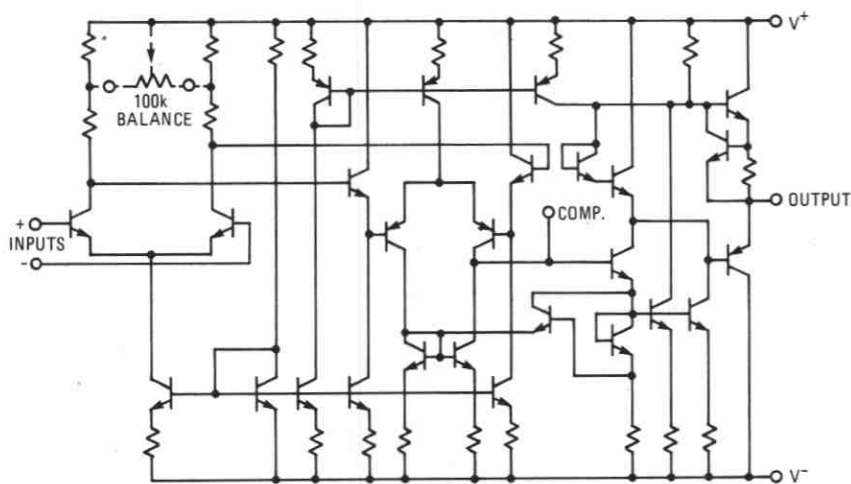
The RM725 military version operates over full temperature range from -55°C to $+125^{\circ}\text{C}$. The commercial RC725 operates from 0°C to $+70^{\circ}\text{C}$.

The RM725 and RC725 offer offset null capability, very high voltage gain and low power consumption over a wide power supply voltage range. They are used for all instrumentation applications requiring precise, low level signal amplification, low noise, low drift and accurate closed loop gain.

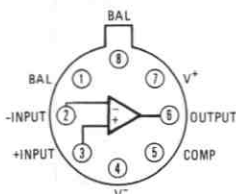
DESIGN FEATURES

- Low Input Noise Current $0.15\text{pA}/\sqrt{\text{Hz}}$
- High Open Loop Gain 3,000,000
- Low Input Offset Current 2nA
- Low Input Voltage Drift $0.6\mu\text{V}/^{\circ}\text{C}$
- High Common-Mode Rejection 120dB
- High Input Voltage Range $\pm 14\text{V}$
- Wide Power Supply Range $\pm 3\text{V}$ to $\pm 22\text{V}$
- Offset Null Capability

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



Note: Pin 4 connected to case

TE Metal Can Package
(Top View)

Order Part Nos.:
RM725T, RC725T

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±22V	Storage Temperature Range	-65°C to +150°C
Internal Power Dissipation (Note 1)	500mW	Operating Temperature Range	
Differential Input Voltage (Note 2)	±22V	RM725	-55°C to +125°C
Input Voltage (Note 3)	±22V	RC725	0°C to +70°C
Voltage Between Offset Null and V ⁺	±0.5V	Lead Temperature (Soldering, 60s)	300°C

ELECTRICAL CHARACTERISTICS (V_S = ±15V, T_A = 25°C unless otherwise specified)

PARAMETER	CONDITIONS	RM725			RC725			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage (without external trim)	R _S ≤ 10kΩ		0.5	1.0		0.5	2.5	mV
Input Offset Current			2.0	20		2.0	35	nA
Input Bias Current			42	100		42	125	nA
Input Noise Voltage	f _o = 10Hz		15			15		nV/√Hz
	f _o = 100Hz		9.0			9.0		
	f _o = 1kHz		8.0			8.0		
Input Noise Current	f _o = 10Hz		1.0			1.0		pA/√Hz
	f _o = 100Hz		0.3			0.3		
	f _o = 1kHz		0.15			0.15		
Input Resistance			1.5			1.5		MΩ
Input Voltage Range		±13.5	±14		±13.5	±14		V
Large Signal Voltage Gain	R _L ≥ 2kΩ V _{out} = ±10V	1,000,000	3,000,000		250,000	3,000,000		
Common Mode Rejection Ratio	R _S ≤ 10kΩ	110	120		94	120		dB
Power Supply Rejection Ratio	R _S ≤ 10kΩ		2.0	10		2.0	35	μV/V
Output Voltage Swing	R _L ≥ 10kΩ	±12	±13.5		±12	±13.5		V
	R _L ≥ 2kΩ	±10	±13.5		±10	±13.5		
Output Resistance			150			150		Ω
Power Consumption			80	105		80	150	mW

The following specifications apply for -55°C ≤ T_A ≤ +125°C for RM725; 0°C ≤ T_A ≤ +70°C for RC725.

Input Offset Voltage (without external trim)	R _S ≤ 10kΩ			1.5			3.5	mV
Average Input Offset Voltage Drift (without external trim)	R _S = 50Ω		2.0	5.0		2.0		μV/°C
Average Input Offset Voltage Drift (with external trim)	R _S = 50Ω		0.6		0.6			μV/°C
Input Offset Current	T _A = 125°C; 70°C		1.2	20		1.2	3.5	nA
	T _A = -55°C; 0°C		7.5	40		4.0	50	
Average Input Offset Current Drift			35	150		10		pA/°C
Input Bias Current	T _A = 125°C; 70°C		20	100			125	nA
	T _A = -55°C; 0°C		80	200			250	
Large Signal Voltage Gain	T _A = 125°C; 70°C	1,000,000				125,000		
	T _A = -55°C; 0°C	250,000				125,000		
Common Mode Rejection Ratio	R _S ≤ 10kΩ	100				115		dB
Power Supply Rejection Ratio	R _S ≤ 10kΩ			20		20		μV/V
Output Voltage Swing	R _L ≥ 2kΩ	±10				±10		V

NOTES:

- Rating applies for case temperature to +125°C; derate linearly at 6.5 mW/°C for ambient temperature above +75°C.
- Rating applies for 5 ms pulses with 10% duty cycle, derate to ±5V for continuous operation.
- For supply voltages less than ±22V, the absolute maximum input voltage is equal to the supply voltage.



GENERAL DESCRIPTION

The RM741 and RC741 integrated circuits are high performance, high gain internally compensated monolithic operational amplifiers fabricated on a single silicon chip using the planar epitaxial process.

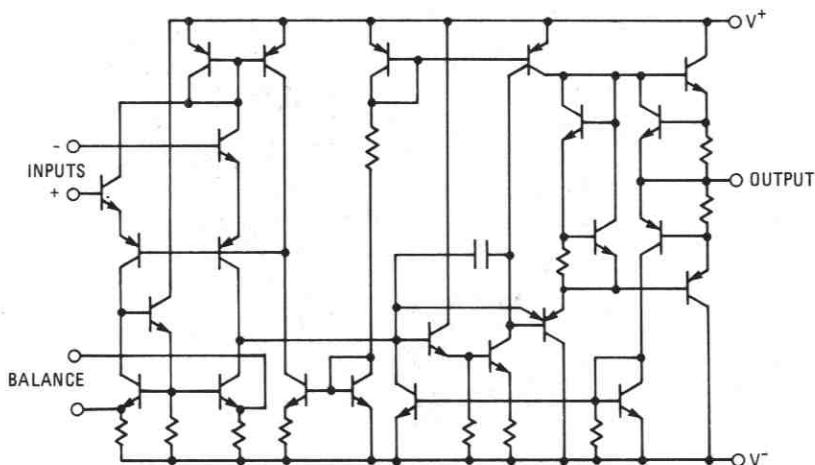
High common-mode voltage range and absence of latch-up tendencies make the RM741 and RC741 ideal for use as a voltage follower. High gain and wide ranges of operating voltages provide superior performance in integrator; summary amplifier and general feedback applications.

Both RM741 and RC741 are pin compatible with the RM709, RM101 and the LH101. The military version, RM741 operates over a temperature range from -55°C to $+125^{\circ}\text{C}$. The commercial version RC741 operates from 0°C to $+70^{\circ}\text{C}$.

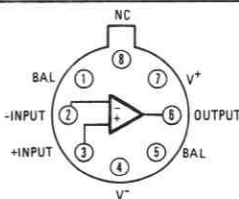
DESIGN FEATURES

- Supply Voltage $\pm 22\text{V}$ RM741, $\pm 18\text{V}$ RC741
- Offset Voltage Null Capability
- Continuous Short-Circuit Protection
- No Frequency Compensation Required
- No Latch-up
- Large Common-Mode and Differential Voltage Ranges
- Low Power Consumption

SCHEMATIC DIAGRAM

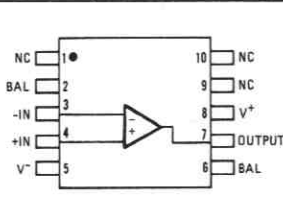


CONNECTION INFORMATION



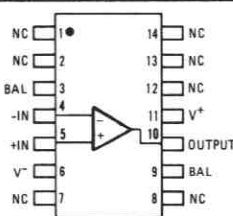
TE Metal Can Package
(Top View)

Order Part Nos.:
RM741T, RC741T



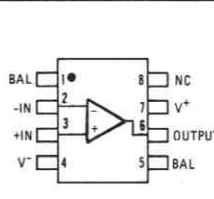
Q Flat Package
(Top View)

Order Part No.:
RM741Q



D and DB Dual In-line Packages
(Top View)

Order Part Nos.:
RM741D, RC741D,
RC741DB



DN Dual In-line Package
(Top View)

Order Part No.:
RC741DN

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM741: $\pm 22V$ RC741: $\pm 18V$	Operating Temperature Range	RM741: $-55^{\circ}C$ to $+125^{\circ}C$ RC741: $0^{\circ}C$ to $+70^{\circ}C$
Internal Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 60s)	300 $^{\circ}C$
Differential Input Voltage	$\pm 30V$	Output Short-Circuit Duration (Note 3)	Indefinite
Input Voltage (Note 2)	$\pm 15V$		
Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$		

ELECTRICAL CHARACTERISTICS ($V_S = \pm 15V$, $T_A = 25^{\circ}C$ unless otherwise specified)

PARAMETER	CONDITIONS	RM741			RC741			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10k\Omega$		1.0	5.0		2.0	6.0	mV
Input Offset Current			30	200		30	200	nA
Input Bias Current			200	500		200	500	nA
Input Resistance		0.3	1.0		0.3	1.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2k\Omega$, $V_{out} = \pm 10V$	50,000	200,000		20,000	100,000		
Output Voltage Swing	$R_L \geq 10k\Omega$	± 12	± 14		± 12	± 14		V
	$R_L \geq 2k\Omega$	± 10	± 13		± 10	± 13		V
Input Voltage Range		± 12	± 13		± 12	± 13		V
Common Mode Rejection Ratio	$R_S \leq 10k\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10k\Omega$		30	150		30	150	$\mu V/V$
Power Consumption			50	85		50	85	mW
Transient Response (unity gain)	$V_{in} = 20mV$, $R_L = 2k\Omega$, $C_L \leq 100pF$							
		Risetime	0.3			0.3		μs
Overshoot		5.0			5.0		%	
Slew Rate (unity gain)	$R_L \geq 2k\Omega$		0.5			0.5		V/ μs

The following specifications apply for $-55^{\circ}C \leq T_A \leq +125^{\circ}C$ for RM741; $0^{\circ}C \leq T_A \leq +70^{\circ}C$ for RC741.

Input Offset Voltage	$R_S \leq 10k\Omega$			6.0			7.5	mV
Input Offset Current				500			300	nA
Input Bias Current				1500			800	nA
Large-Signal Voltage Gain	$R_L \geq 2k\Omega$, $V_{out} = \pm 10V$	25,000			15,000			
Output Voltage Swing	$R_L \geq 2k\Omega$	± 10			± 10			V
Common Mode Rejection Ratio	$R_S \leq 10k\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10k\Omega$		30	150		30	150	$\mu V/V$

NOTES:

- Rating applies for case temperatures to $+125^{\circ}C$; derate linearly at 6.5 mW/ $^{\circ}C$ for ambient temperatures above $+75^{\circ}C$ for RM741.
- For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.
- Short-circuit may be to ground or either supply. Rating applies to $+125^{\circ}C$ case temperature or $+75^{\circ}C$ ambient temperature for RM741.



GENERAL DESCRIPTION

The RM747 and RC747 integrated circuits are high gain operational amplifiers internally compensated and constructed on a single silicon chip using the planar epitaxial process.

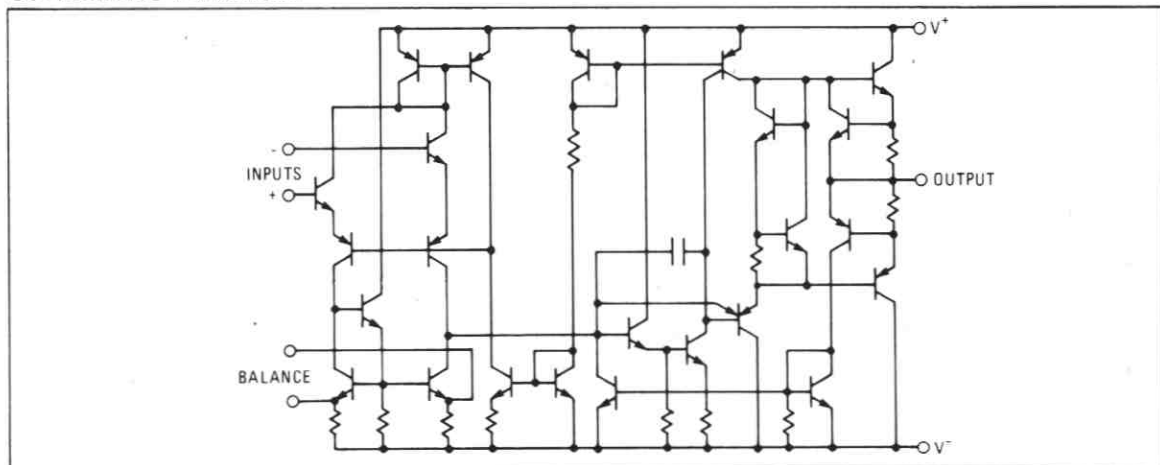
The military version, RM747, operates over a temperature range from -55°C to $+125^{\circ}\text{C}$. The commercial version, RC747, operates from 0°C to $+70^{\circ}\text{C}$.

Combining all of the outstanding features of the 741 with the close parameter matching and tracking of a dual device on a monolithic chip results in unique performance characteristics. Excellent channel separation allows the use of the dual device in all single 741 operational amplifier applications providing the highest possible packaging density. It is especially well suited for applications in differential-in, differential-out as well as in potentiometric amplifiers and where gain and phase matched channels are mandatory.

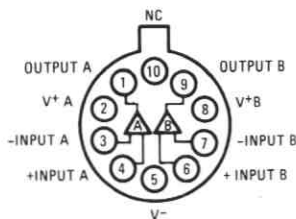
DESIGN FEATURES

- Supply Voltage $\pm 22\text{ V}$ for RM747
 $\pm 18\text{ V}$ for RC747
- Continuous Short-Circuit Protection
- No Frequency Compensation Required
- No Latch-Up
- Large Common-Mode and Differential Voltage Ranges
- Low Power Consumption
- Parameter Tracking Over Temperature Range
- Gain and Phase Match Between Amplifiers

SCHEMATIC DIAGRAM

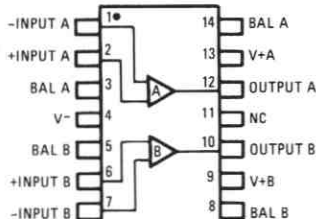


CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
RM747T, RC747T



DB and DC
Dual In-line Packages
(Top View)

Order Part Nos.:
RM747DC, RC747DC
RC747DB

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM747: ± 22 V RC747: ± 18 V	Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
Internal Power Dissipation (Note 1)	500 mW	Operating Temperature Range . RM747: -55°C to $+125^{\circ}\text{C}$ RC747: 0°C to $+70^{\circ}\text{C}$	
Differential Input Voltage	± 30 V	Lead Temperature (Soldering, 60s)	300°C
Input Voltage (Note 2)	± 15 V	Output Short-Circuit Duration (Note 3)	Indefinite

ELECTRICAL CHARACTERISTICS ($V_{CC} = \pm 15\text{V}$, $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	RM747			RC747			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		1.0	5.0		2.0	6.0	mV
Input Offset Current			30	200		30	200	nA
Input Bias Current			200	500		200	500	nA
Input Resistance		0.3	1.0		0.3	1.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2 \text{ k}\Omega$ $V_{out} = \pm 10\text{V}$	50,000	200,000		50,000	200,000		V/V
Output Voltage Swing	$R_L \geq 10 \text{ k}\Omega$	± 12	± 14		± 12	± 14		V
	$R_L \geq 2 \text{ k}\Omega$	± 10	± 13		± 10	± 13		V
Input Voltage Range		± 12	± 13		± 12	± 13		V
Common Mode Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		30	150		30	150	$\mu\text{V/V}$
Power Consumption			100	170		100	170	mW
Transient Response (unity gain)	$V_{in} = 20 \text{ mV}$ $R_L = 2 \text{ k}\Omega$ $C_L \leq 100 \text{ pF}$							
Risetime			0.3			0.3		μs
Overshoot			5.0			5.0		%
Slew Rate (unity gain)	$R_L \geq 2 \text{ k}\Omega$		0.5			0.5		V/ μs
Channel Separation (open loop) (Gain = 100)	$f = 10 \text{ kHz}$ $R_S = 1 \text{ k}\Omega$		70			70		dB
	$f = 10 \text{ kHz}$ $R_S = 1 \text{ k}\Omega$		83			83		dB

The following specifications apply for $-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$ for RM747; $0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$ for RC747.

Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$			6.0			7.5	mV
Input Offset Current				500			300	nA
Input Bias Current				1.5			800	nA
Large-Signal Voltage Gain	$R_L \geq 2 \text{ k}\Omega$ $V_{out} = \pm 10\text{V}$	25,000				25,000		V/V
Output Voltage Swing	$R_L \geq 2 \text{ k}\Omega$	± 10	± 13		± 10	± 13		V
Common Mode Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		30	150		30	150	$\mu\text{V/V}$
Power Consumption	$V_S = \pm 15\text{V}$ $T_A = +125^{\circ}\text{C}$		90	150		90	150	mW
	$T_A = -55^{\circ}\text{C}$		120	200		120	200	

NOTES:

- Rating applies for case temperatures to $+125^{\circ}\text{C}$; derate linearly at 6.5 mW/ $^{\circ}\text{C}$ for ambient temperatures above $+75^{\circ}\text{C}$ for RM747.
- For supply voltages less than $\pm 15\text{V}$ the absolute maximum input voltage is equal to the supply voltage.
- Short-circuit may be to ground or either supply. Rating applies to $+125^{\circ}\text{C}$ case temperature or $+75^{\circ}\text{C}$ ambient temperature for RC747.



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GENERAL DESCRIPTION

The RM748 and RC748 integrated circuits are high performance, high gain internally compensated monolithic operational amplifiers fabricated on a single silicon chip using the planar epitaxial process.

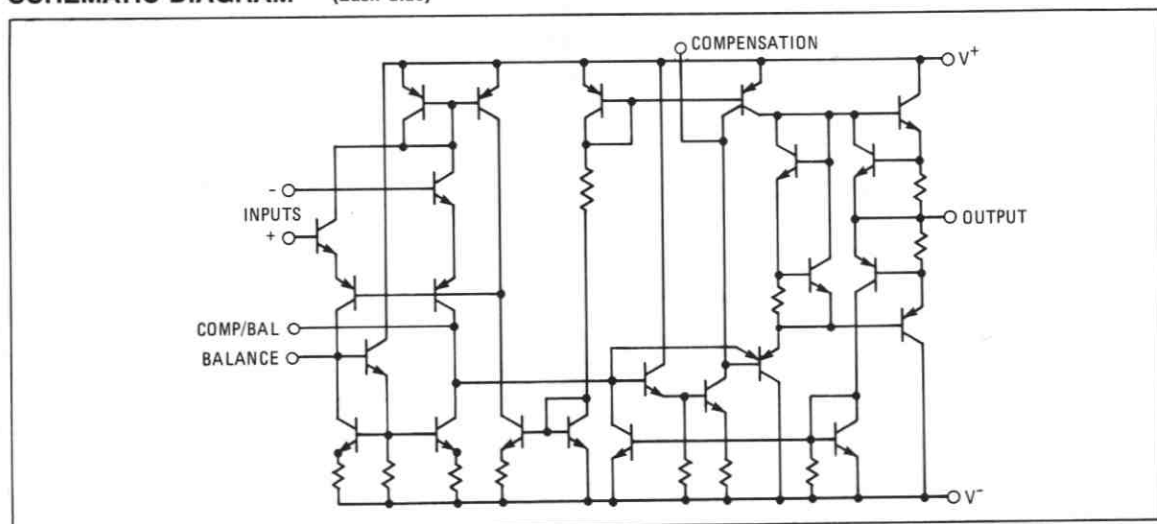
High common-mode voltage range and absence of latch-up tendencies make the RM748 and RC748 ideal for use as a voltage follower. High gain and wide ranges of operating voltages provide superior performance in integrator, summary amplifier and general feedback applications. Unity gain compensation is achieved by means of a single 30pF capacitor.

Both RM748 and RC748 are pin compatible with the RM709, LM101 and RM4101. The military version, RM748 operates over a temperature range from -55°C to $+125^{\circ}\text{C}$ while the commercial version RC748 operates from 0° to $+70^{\circ}\text{C}$.

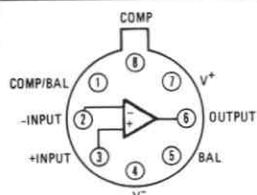
DESIGN FEATURES

- Supply Voltage $\pm 22\text{V}$ RM748, $\pm 18\text{V}$ RC748
- Offset Voltage Null Capability
- Continuous Short-Circuit Protection
- No Latch-up
- Large Common-Mode and Differential Voltage Ranges
- Low Power Consumption

SCHEMATIC DIAGRAM (Each Side)



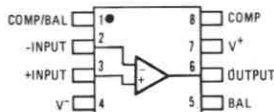
CONNECTION INFORMATION



Note: Pin 4 connected to case

TE Metal Can Package
(Top View)

Order Part Nos.:
RM748T, RC748T



NB
Dual In-line
Packages
(Top View)

Order Part No.:
RC748NB

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM748: $\pm 22\text{V}$ RC748: $\pm 18\text{V}$	Operating Temperature Range	RM748: -55°C to $+125^{\circ}\text{C}$ RC748: 0°C to $+70^{\circ}\text{C}$
Internal Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 60s)	300°C
Differential Input Voltage	$\pm 30\text{V}$	Output Short-Circuit Duration (Note 3)	Indefinite
Input Voltage (Note 2)	$\pm 15\text{V}$		
Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$		

ELECTRICAL CHARACTERISTICS ($V_S = \pm 15\text{V}$, $T_A = 25^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	CONDITIONS	RM748			RC748			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10\text{k}\Omega$		1.0	5.0		2.0	6.0	mV
Input Offset Current			30	200		30	200	nA
Input Bias Current			200	500		200	500	nA
Input Resistance		0.3	1.0		0.3	1.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2\text{k}\Omega$, $V_{out} = \pm 10\text{V}$	50,000	200,000		20,000	100,000		
Output Voltage Swing	$R_L \geq 10\text{k}\Omega$	± 12	± 14		± 12	± 14		V
	$R_L \geq 2\text{k}\Omega$	± 10	± 13		± 10	± 13		V
Input Voltage Range		± 12	± 13		± 12	± 13		V
Common Mode Rejection Ratio	$R_S \leq 10\text{k}\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10\text{k}\Omega$		30	150		30	150	$\mu\text{V}/\text{V}$
Power Consumption			50	85		50	85	mW
Transient Response (unity gain)	$V_{in} = 20\text{mV}$, $R_L = 2\text{k}\Omega$, $C_L \leq 100\text{pF}$							
		Risetime		0.3			0.3	
Overshoot			5.0			5.0		%
Slew Rate (unity gain)	$R_L \geq 2\text{k}\Omega$		0.5			0.5		V/ μs

The following specifications apply for $-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$ for RM748; $0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$ for RC748.

Input Offset Voltage	$R_S \leq 10\text{k}\Omega$			6.0			7.5	mV
Input Offset Current				500			300	nA
Input Bias Current				1500			800	nA
Large-Signal Voltage Gain	$R_L \geq 2\text{k}\Omega$, $V_{out} = \pm 10\text{V}$	25,000			15,000			
Output Voltage Swing	$R_L \geq 2\text{k}\Omega$	± 10			± 10			V
Common Mode Rejection Ratio	$R_S \leq 10\text{k}\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10\text{k}\Omega$		30	150		30	150	$\mu\text{V}/\text{V}$

NOTES:

- Rating applies for case temperatures to $+125^{\circ}\text{C}$; derate linearly at $6.5\text{ mW}/^{\circ}\text{C}$ for ambient temperatures above $+75^{\circ}\text{C}$ for RM748.
- For supply voltages less than $\pm 15\text{V}$, the absolute maximum input voltage is equal to the supply voltage.
- Short-circuit may be to ground or either supply. Rating applies to $+125^{\circ}\text{C}$ case temperature or $+75^{\circ}\text{C}$ ambient temperature for RM748.



Dual High-Gain Operational Amplifier

GENERAL DESCRIPTION

The RC1437 and RM1537, previously referred to as the 4709, integrated circuits are monolithic dual high gain operational amplifiers. The device is composed of two 709 operational amplifiers fabricated on a single silicon chip. It has all the outstanding features of the 709.

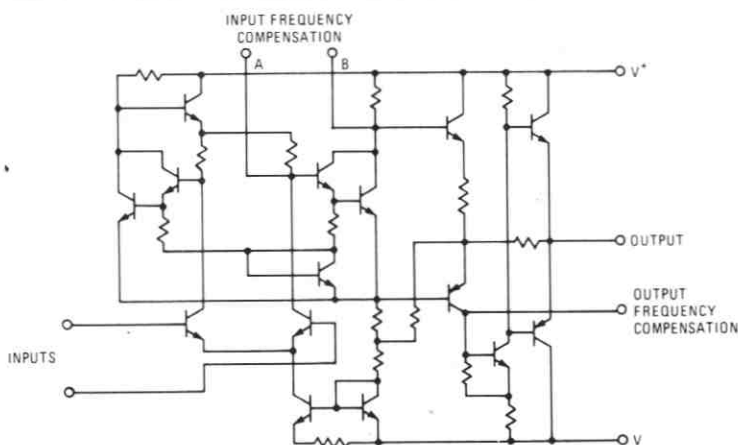
Due to the inherent matching and tracking of parameters, the 1537/1437 has several unique applications: differential in/out amplifiers, non-inverting amplifiers, gain and phase matched channels.

The RM1537 operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. RC 1437 is the commercial temperature range device for operation from 0°C to $+75^{\circ}\text{C}$.

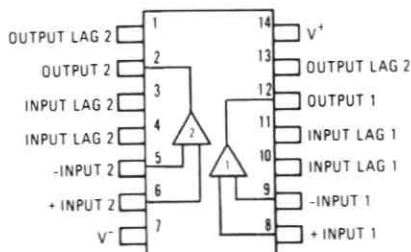
DESIGN FEATURES

- Gain and Phase Matching Between Amplifiers
- Low Temperature Drift $\pm 3 \mu\text{V}/^{\circ}\text{C}$
- Large Output Voltage Swing $\pm 14 \text{ V}$ Typical

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



DC and DB

Dual In-line Packages
(Top View)

Order Part Nos.:
RM1537DC, RC1437DC,
RC1437DB

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±18 V	Operating Temperature Range	RM1537: -55°C to +125°C RC1437: 0°C to +75°C
Differential Mode Input Voltage	±5 V	Storage Temperature Range	-65°C to +150°C
Common Mode Input Voltage	±10 V	Lead Temperature (Soldering, 60s)	300°C
Power Dissipation	500 mW		
Derate above 75°C	5.0 mW/°C		

ELECTRICAL CHARACTERISTICS (RM1537: -55°C to +125°C; RC1437: 0°C to +75°C, unless otherwise noted)

PARAMETER	CONDITIONS	RM1537			RC1437			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$50\Omega \leq R_S \leq 10k\Omega$ $\pm 9V < V^+ < 15V$ $T_A = 25^\circ C$		1.0	5.0		1.0	7.5	mV
Input Offset Current	$\pm 9V < V^+ < \pm 15V$ RM1537: +25°C to +125°C RC1437: +25°C to +75°C		50	200		50	750	nA
		RM1537: -55°C RC1437: 0°C	100	500			750	
Input Bias Current	$\pm 9V < V^+ < \pm 15V$ RM1537: +25°C to +125°C RC1437: +25°C to +75°C		0.2	0.5		0.4	1.5	µA
		RM1537: -55°C RC1437: 0°C	0.5	1.5			2.0	
Input Resistance	$+9V < V^+ < \pm 15V$	150	400		50	150		kΩ
Output Resistance	$+9V < V^+ < \pm 15V$		150			150		Ω
Power Consumption	$V^+ = \pm 15V, R_L = \infty$		160	225		160	225	mW
Large Signal Voltage Gain	$V^+ = \pm 15V, V_0 = \pm 10V, R_L \geq 2k\Omega$	25	45	70	15	45		KV/V
Output Voltage Swing	$V^+ = \pm 15V$ $R_L \geq 10k\Omega$ $R_L \geq 2k\Omega$	±12 ±10	±14 ±13		±12 ±10	±14 ±13		V
Input Common Mode Voltage	$V^+ = \pm 15V$	±8	±10		±8	±10		V
Common Mode Rejection Ratio	$R_S \leq 10k\Omega, +9V < V^+ < \pm 15V$	70	90		65	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10k\Omega, +9V < V^+ < \pm 15V$			150			200	µV/V
Transient Response	$V^+ = \pm 15V, V_{in} = 20mV, R_L = 2k\Omega, C_L = 5nF,$ $R_1 = 1.5k\Omega, C_2 = 200pF, R_2 = 50\Omega$		0.3	1.0		0.3	1.0	µs %
Average Temperature Coefficient of Input Offset Voltage	$+9V < V^+ < \pm 15V$ $R_S = 50\Omega$ $R_S = 10k\Omega$		1.5 3.0			1.5 3.0		µV/°C
Average Temperature Coefficient of Input Offset Current	$+9 < V^+ < \pm 15V$		0.6			0.7		nA/°C
Separation, f = 10kHz Open Loop	$+9V < V^+ < \pm 15V$		73			73		dB

MATCHING CHARACTERISTICS ($T_A = 25^\circ C, \pm 9V < V^+ < \pm 15V$ unless otherwise noted)

PARAMETER	RM1537			RC1437			UNITS
	MIN	TYP	MAX	MIN	TYP	MAX	
Voltage Gain		±0.5			±1.0		dB
Input Bias Current		±100			±150		nA
Input Offset Current		±15			±20		nA
Input Offset Voltage		±0.15			±0.2		mV
Average Temperature Coefficient of Input Offset Voltage		±0.5			±0.5		µV/°C
Average Temperature Coefficient of Input Offset Current		±0.2			±0.2		nA/°C



GENERAL DESCRIPTION

The RM1558 and RC1458 integrated circuits are high gain operational amplifiers internally compensated and constructed on a single silicon chip using the planar epitaxial process.

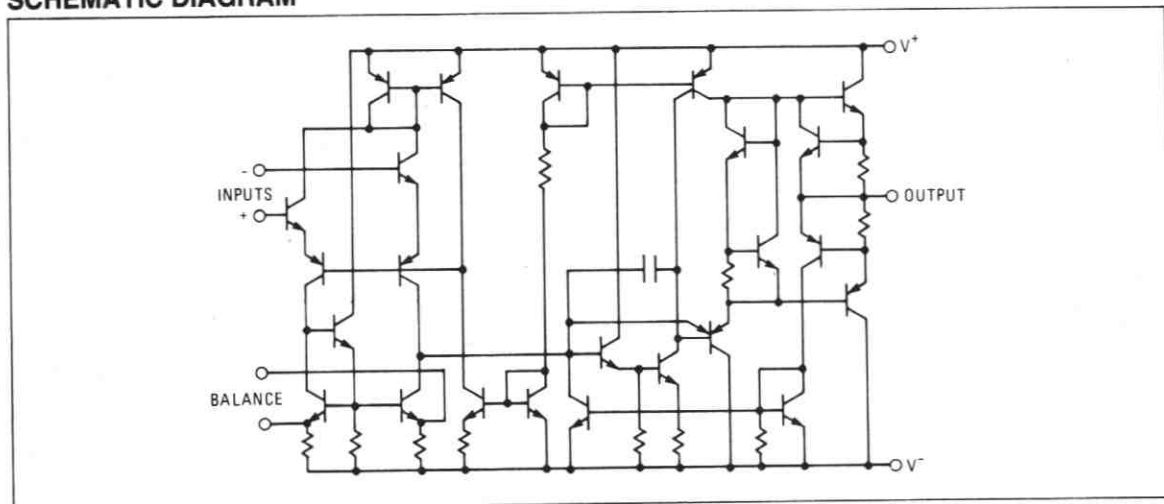
The military version, RM1558, operates over a temperature range from -55°C to $+125^{\circ}\text{C}$. The commercial version, RC1458, operates from 0°C to $+70^{\circ}\text{C}$.

Combining all of the outstanding features of the 741 with the close parameter matching and tracking of a dual device on a monolithic chip results in unique performance characteristics. Excellent channel separation allows the use of the dual device in all single 741 operational amplifier applications providing the highest possible packaging density. It is especially well suited for applications where gain and phase matched channels are mandatory.

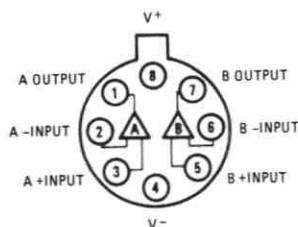
DESIGN FEATURES

- Continuous Short-Circuit Protection
- No Frequency Compensation Required
- No Latch-Up
- Large Common-Mode and Differential Voltage Ranges
- Low Power Consumption
- Parameter Tracking Over Temperature Range
- Gain and Phase Match Between Amplifiers

SCHEMATIC DIAGRAM

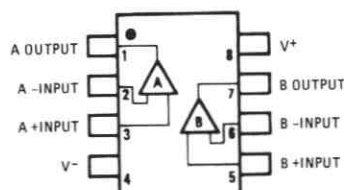


CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
RM1558T, RC1458T



NB Dual
In-line Package
(Top View)

Order Part No.:
RC1458NB

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM1558: ± 22 V RC1458: ± 18 V	Storage Temperature Range	-65°C to +150°C
Internal Power Dissipation (Note 1)	500 mW	Operating Temperature Range	RM1558: -55°C to +125°C RC1458: 0°C to +70°C
Differential Input Voltage	± 30 V	Lead Temperature (Soldering, 60s)	300°C
Input Voltage (Note 2)	± 15 V	Output Short-Circuit Duration (Note 3)	Indefinite

ELECTRICAL CHARACTERISTICS ($V_{CC} = \pm 15$ V, $T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	RM1558			RC1458			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		1.0	5.0		2.0	6.0	mV
Input Offset Current			30	200		30	200	nA
Input Bias Current			200	500		200	500	nA
Input Resistance		0.3	1.0		0.3	1.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2 \text{ k}\Omega$ $V_{out} = \pm 10$ V	50,000	200,000		50,000	200,000		V/V
Output Voltage Swing	$R_L \geq 10 \text{ k}\Omega$	± 12	± 14		± 12	± 14		V
	$R_L \geq 2 \text{ k}\Omega$	± 10	± 13		± 10	± 13		V
Input Voltage Range		± 12	± 13		± 12	± 13		V
Common Mode Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		30	150		30	150	$\mu\text{V/V}$
Power Consumption			100	170		100	170	mW
Transient Response (unity gain)	$V_{in} = 20$ mV $R_L = 2 \text{ k}\Omega$ $C_L \leq 100$ pF							
		Risetime		0.3		0.3		μs
		Overshoot		5.0		5.0		%
Slew Rate (unity gain)	$R_L \geq 2 \text{ k}\Omega$		0.5			0.5		V/ μs
Channel Separation (open loop) (Gain = 100)	$f = 10 \text{ kHz}$ $R_S = 1 \text{ k}\Omega$		70			70		dB
	$f = 10 \text{ kHz}$ $R_S = 1 \text{ k}\Omega$		83			83		dB
The following specifications apply for $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$ for RM1558; $0^\circ\text{C} \leq T_A \leq +70^\circ\text{C}$ for RC1458.								
Input Offset Voltage	$R_L \leq 10 \text{ k}\Omega$			6.0			7.5	mV
Input Offset Current				500			300	nA
Input Bias Current				1500			800	nA
Large-Signal Voltage Gain	$R_L \geq 2 \text{ k}\Omega$ $V_{out} = \pm 10$ V	25,000			25,000			
Output Voltage Swing	$R_L \geq 2 \text{ k}\Omega$	± 10			± 10			V
Power Consumption	$V_S = \pm 15$ V							
	$T_A = +125^\circ\text{C}$		90	150		90	150	mW
	$T_A = -55^\circ\text{C}$		120	200		120	200	

NOTES:

- Rating applies for case temperatures to +125°C; derate linearly at 6.5 mW/°C for ambient temperatures above +75°C for RM1558.
- For supply voltages less than ± 15 V, the absolute maximum input voltage is equal to the supply voltage.
- Short-circuit may be to ground or either supply. Rating applies to +125°C case temperature or +75°C ambient temperature for RC1458.



GENERAL DESCRIPTION

The RM1556A/RC1556A and RM1556/RC1556 are high performance, high gain operational amplifiers. Each amplifier is internally compensated and fabricated on a single silicon chip by the planar epitaxial process.

These amplifiers feature high common-mode and differential voltage range, very low input bias current, optimum performance over a wide range of supply voltage, and freedom from "latch-up." They are ideal for use as voltage followers, comparators, integrators, summing and general purpose amplifiers.

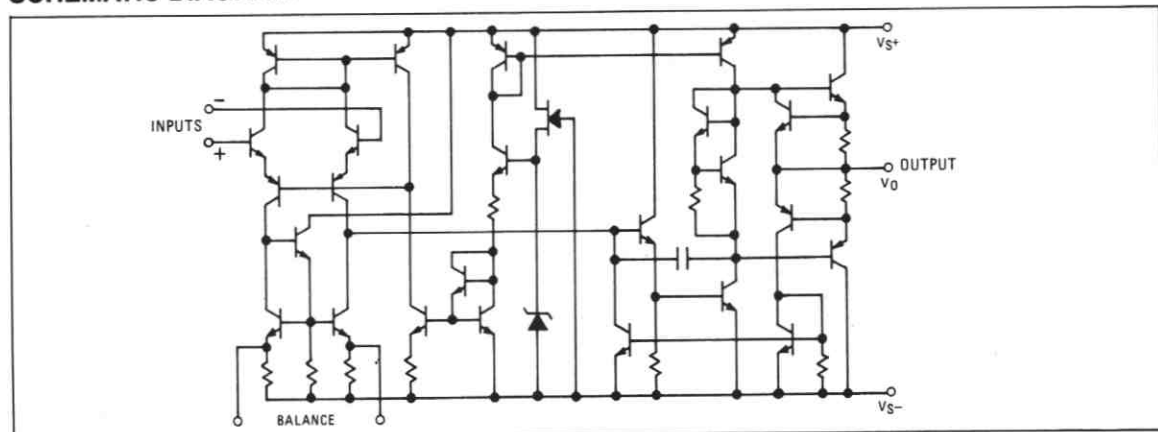
The RM1556A/RC1556A offers features beyond that of super Beta amplifiers. These include exceptional improvements in the input offset voltage, bandwidth, slew rate, and noise characteristics.

The RM types operate over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC types operate from 0°C to $+70^{\circ}\text{C}$. Each device is available in the 8-pin TO-5, 8 or 14-pin dual in-line packages.

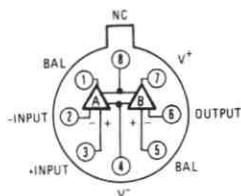
DESIGN FEATURES

- Input Bias Current 15nA Maximum
- Input Offset Current 2nA Maximum
- Input Offset Voltage 2mV Maximum
- At $\pm 15\text{V}$ Current Drain 1.0mA
- Offset Voltage Nulling (10k pot)
- Slew Rate $2.0\text{V}/\mu\text{s}$
- Unity Gain Bandwidth 4MHz
- Gain Variation 3dB from $\pm 3\text{V}$ to $\pm 20\text{V}$
- Open Loop Voltage Gain 106dB

SCHEMATIC DIAGRAM

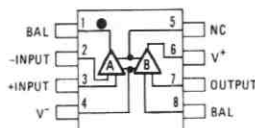


CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
RM1556AT, RM1556T,
RC1556AT, RC1556T



**NB Dual In-line
Plastic Package**
(Top View)

Order Part Nos.:
RC1556NB, RC1556NB



ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM1556A, RM1556: $\pm 22V$ RC1556: $\pm 18V$	Operating Temperature Range RM1556A, RM1556	$-55^{\circ}C$ to $+125^{\circ}C$
Internal Power Dissipation (Note 1)	500mW	RC1556A, RC1556	$0^{\circ}C$ to $+70^{\circ}C$
Differential Input Voltage	$\pm 30V$	Lead Temperature (Soldering, 60s)	$300^{\circ}C$
Input Voltage (Note 2)	$\pm 15V$	Output Short-Circuit Duration (Note 3)	Indefinite
Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$		

RM1556 AND RC1556 ELECTRICAL CHARACTERISTICS

(RM1556: $-55^{\circ}C \leq T_A \leq 125^{\circ}C$; RC1556: $0^{\circ}C \leq T_A \leq 70^{\circ}C$; $V_S = \pm 15V$)

PARAMETER	CONDITIONS	RM1556			RC1556			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$T_A = 25^{\circ}C$, $R_S \leq 50k\Omega$		2.0	4.0		5.0	10	mV
Input Offset Current	$T_A = 25^{\circ}C$		1.0	2.0		5.0	10	nA
Input Bias Current	$T_A = 25^{\circ}C$		8.0	15		15	30	nA
Input Resistance	$T_A = 25^{\circ}C$		5.0			3.0		M Ω
Supply Current	$T_A = 25^{\circ}C$		1.0	1.5		1.3	3.0	mA
Large Signal Voltage Gain	$T_A = 25^{\circ}C$ $V_{OUT} = \pm 10V$, $R_L > 2k\Omega$	100	200		70	100		V/mV
Input Offset Voltage	$R_S \leq 50k\Omega$			6.0			14	mV
Input Offset Current	$+25^{\circ}C$ to T_H			3.0			14	nA
	T_L to $+25^{\circ}C$			5.0			14	
Input Bias Current				30			40	nA
Supply Current				1.9			2.5	mA
Slew Rate (Unity Gain)	$T_A = 25^{\circ}C$, $R_L \geq 2k\Omega$		2.0			2.0		V/ μs
Bandwidth (Unity Gain)	$T_A = 25^{\circ}C$, $R_L \geq 2k\Omega$		4			4		MHz
Large Signal Voltage Gain	$R_L \geq 2k\Omega$, $V_{OUT} = \pm 10V$	40			40			V/mV
Output Voltage Swing	$T_A = 25^{\circ}C$, $R_L \geq 2k\Omega$, $V_S = \pm 15V$	± 12	± 13		± 11	± 12		V
Input Voltage Range		± 12	± 13		± 11	± 12		V
Input Noise Voltage	$R_S = 10k\Omega$, $f = 1.0kHz$, $AV = 100$, $BW = 1.0Hz$		25			25		nV/ \sqrt{Hz}
Common-Mode Rejection Ratio	$R_S \leq 50k\Omega$	80	110		70	110		dB
Supply Voltage Rejection Ratio	$R_L \leq 50k\Omega$	80	86		74	83		dB

NOTES:

- For operating at elevated temperatures, the device must be derated based on $150^{\circ}C$ for RM1556A and RM1556; $100^{\circ}C$ for RC1556 maximum junction temperature and a thermal resistance of $150^{\circ}C/W$ junction to ambient or $45^{\circ}C/W$ junction to case.
- For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.
- Short-circuit to ground rating applies to $+125^{\circ}C$ case temperature or $+75^{\circ}C$ ambient temperature for RM1556A and RM1556.

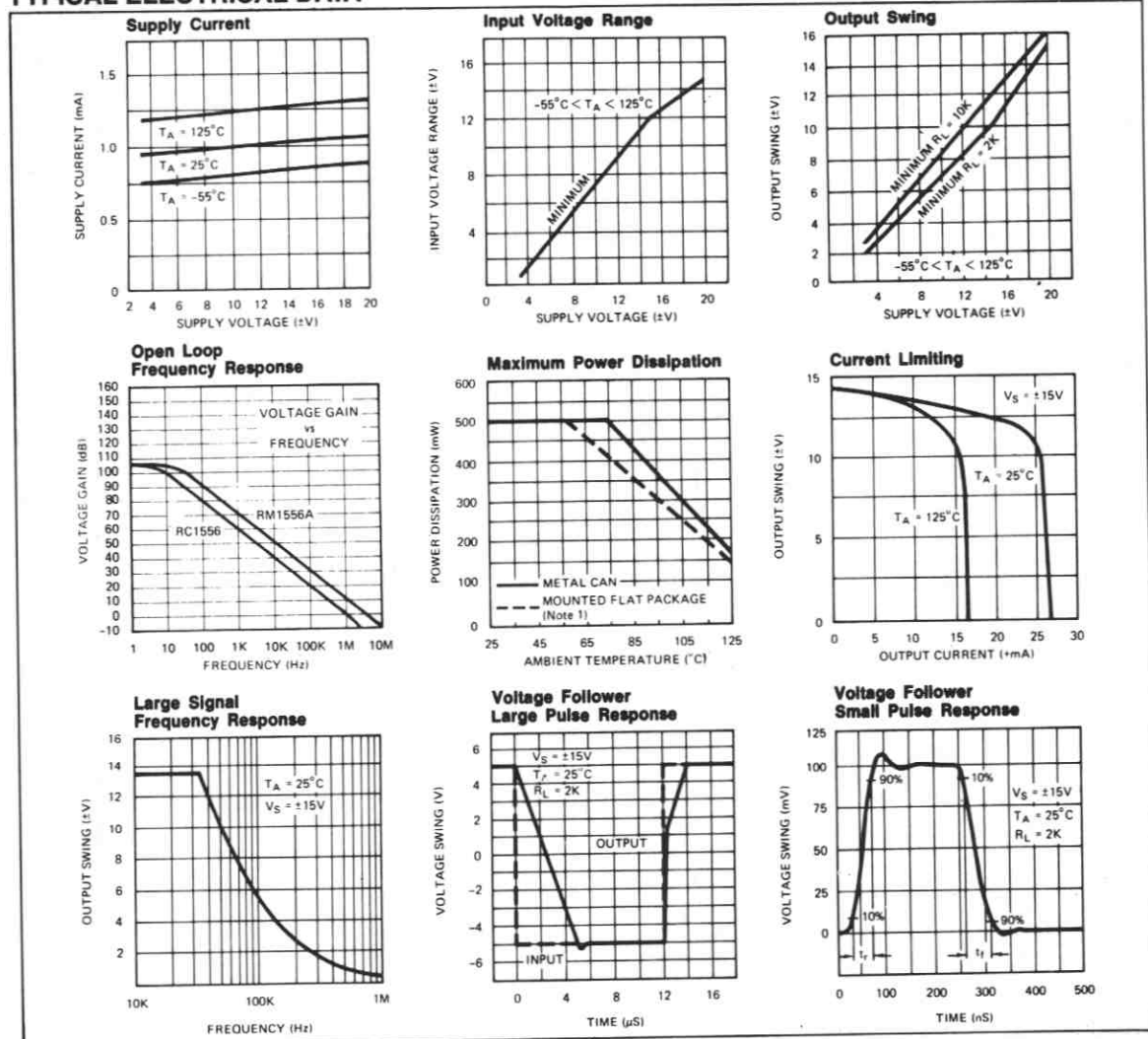
High-Performance Operational Amplifiers

RM1556A AND RC1556A ELECTRICAL CHARACTERISTICS

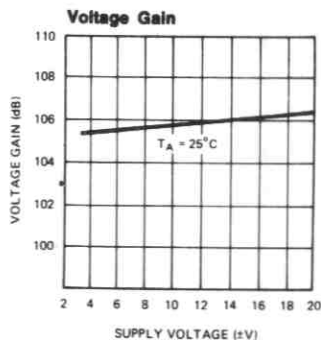
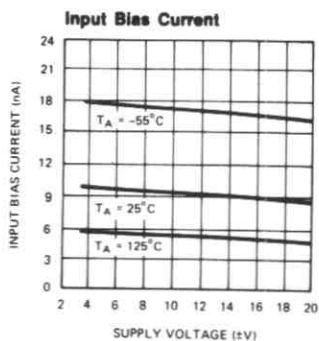
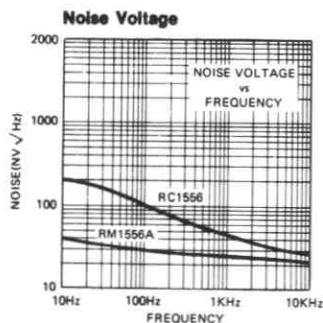
(All other electrical characteristics are listed with RM1556 and RC1556)

PARAMETER	CONDITIONS	RM1556A			RC1556A			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$T_A = 25^\circ\text{C}, R_S \leq 50\text{k}\Omega$		0.7	2.0		1.5	5.0	mV
	$R_S \leq 50\text{k}\Omega,$ $-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$		1.0	3.0				
	$R_S \leq 50\text{k}\Omega, 0^\circ\text{C to } +70^\circ\text{C}$					1.0	6.0	
Slew Rate (Unity Gain)	$T_A = 25^\circ\text{C}, R_L = 2\text{k}\Omega,$ $V_S = \pm 15\text{V}$		2.0			2.0		V/ μs
Bandwidth (Unity Gain)	$T_A = 25^\circ\text{C}, R_L = 2\text{k}\Omega$		4.0			4.0		MHz

TYPICAL ELECTRICAL DATA



TYPICAL ELECTRICAL DATA (Cont.)



Quad Current Mode Single-Supply Operational Amplifier

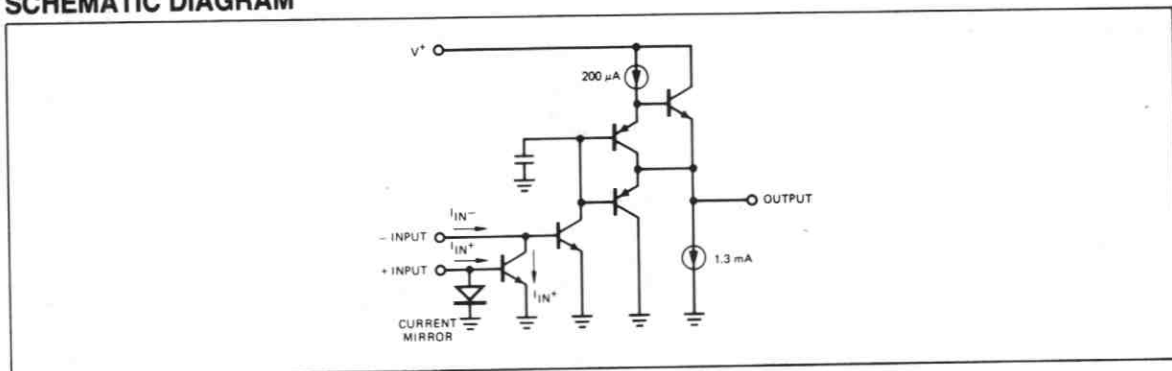
GENERAL DESCRIPTION

The LM2900 and LM3900 consist of four independent, dual input, internally compensated amplifiers which were designed specifically to operate off a single power supply voltage and to provide a large output voltage swing. These amplifiers make use of a current mirror to achieve the non-inverting input function. Application areas include: AC amplifiers, RC active filters; low frequency triangle, squarewave and pulse waveform generation circuits, tachometers and low speed, high voltage digital logic gates.

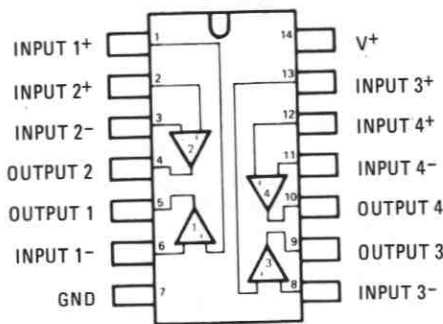
DESIGN FEATURES

- Wide Single Supply Voltage Range 4V to 36V
- Supply Current Drain Independent of Supply Voltage
- Low Input Biasing Current 30 nA
- High Open-loop Gain 70 dB
- Wide Bandwidth 2.5MHz (Unity Gain)
- Larger Gain-Bandwidth Product in Non-Inverting Mode ($A_V = 100$ @ $f = 1$ MHz)
- Large Output Voltage Swing, $(V^+ - 1)V_{p.p}$
- Internally Frequency Compensated for Unity Gain
- Output Short-Circuit Protection

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



DB

Dual In-line Package

Order Part Nos.:
LM2900N, LM3900N

ABSOLUTE MAXIMUM RATINGS

Supply Voltage (LM 2900)	+36V	Output Short Circuit Duration —	Continuous
(LM 3900)	+32V	One Amplifier, $T_A = 25^\circ\text{C}$	
Supply Voltage	$\pm 18\text{V}$	Operating Temperature Range (LM 2900)	-40°C to $+85^\circ\text{C}$
Power Dissipation ($T_A = 25^\circ\text{C}$)(Note 1)	570mW	Operating Temperature Range (LM 3900)	0°C to $+70^\circ\text{C}$
Input Currents, I_{IN+} or I_{IN-}	20mA	Storage Temperature Range	-65°C to $+150^\circ\text{C}$
		Lead Temperature (Soldering, 10 sec)	300°C

ELECTRICAL CHARACTERISTICS ($V_{CC} = +15\text{V}$, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

PARAMETER	CONDITIONS	LM 2900/LM 3900			
		MIN	TYP	MAX	UNITS
Open Loop Voltage Gain	$f = 100\text{ Hz}$	1200	2800		V/V
Input Resistance	Inverting Input		1		$\text{M}\Omega$
Output Resistance			8		$\text{k}\Omega$
Unity Gain Bandwidth	Inverting Input (Note 2)		2.5		MHz
Input Bias Current	Inverting Input		30	200	nA
Slew Rate	Positive Output Swing		0.5		V/ μs
	Negative Output Swing		20		V/ μs
Supply Current	$R_L = \infty$ On All Amplifiers		6.2	10	mA
Output Voltage Swing $R_L = 5.1\text{ k}$	V_{OUT} High	$I_{IN-} = 0, I_{IN+} = 0$	13.5	14.2	V
	V_{OUT} Low	$I_{IN-} = 10\ \mu\text{A}, I_{IN+} = 0$		0.09	0.2
Output Current Capability	Source		3	18	mA
	Sink (Note 3)		0.5	1.3	mA
Power Supply Rejection	$f = 100\text{ Hz}$		70		dB
Mirror Gain	$I_{IN+} = 200\ \mu\text{A}$ (Note 4)	0.90	1	1.1	$\mu\text{A}/\mu\text{A}$
Mirror Current	(Note 5)		10	500	μA
Negative Input Current	(Note 6)		1.0		mA

NOTES:

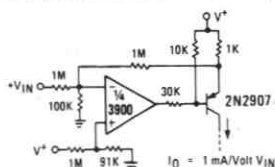
- For operating at high temperatures, the device must be derated based on a 125°C maximum junction temperature and a thermal resistance of $175^\circ\text{C}/\text{W}$ which applies for the device soldered in a printed circuit board, operating in a still air ambient.
- When used as a "non-inverting amplifier" (see bottom of page), the gain-bandwidth product is not limited to 2.5 MHz. The isolation provided by the "current mirror" allows a constant unity voltage gain feedback for the main inverting amplifier. This means that large values of gain can be achieved at high frequencies and the dominate limit is due to the slew rate of the amplifier. For example: a voltage gain of 100 is easily obtained at 1 MHz and an output voltage swing of 160 mVp-p can be achieved prior to slew rate limiting. This operational mode is useful for signal frequencies in the 50 kHz to 1 MHz range as would be encountered in IF or carrier frequency applications.
- The output current sink capability can be increased for large signal conditions by overdriving the inverting input.
- This spec indicates the current gain of the current mirror which is used as the non-inverting input.
- Input V_{BE} match between the non-inverting and the inverting inputs occurs for a mirror-current (non-inverting input current) of approximately $10\ \mu\text{A}$. This is therefore a typical design center for many of the application circuits.
- Clamp transistors are included on the IC to prevent the input voltages from swinging below ground more than approximately -0.3 V_{DC} . The negative input currents which may result from large signal overdrive with capacitance input coupling need to be externally limited to values of approximately 1 mA. Negative input currents in excess of 4 mA will cause the output voltage to drop to a low voltage. This maximum current applies to any one of the input terminals. If more than one of the input terminals are simultaneously driven, negative smaller maximum currents are allowed. Common-mode current biasing can be used to prevent negative input voltages; for example, see the "Differentiator Circuit" in the applications section.



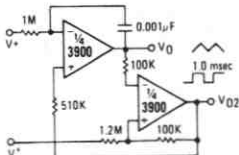
Quad Current Mode Single-Supply Operational Amplifier

3900 TYPICAL APPLICATIONS ($V^+ = 15V$)

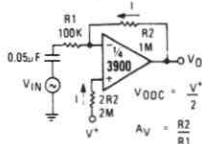
Voltage-Controlled Current Source
(Transconductance Amplifier)



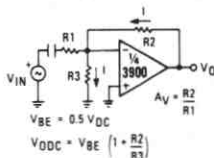
Triangle/Square Generator



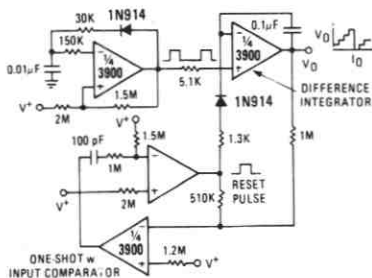
Inverting Amplifier



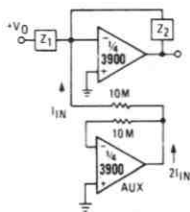
VBE Biasing



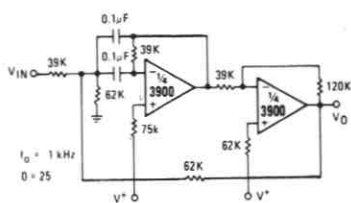
Free-Running Staircase
Generator/Pulse Counter



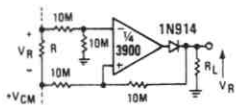
Supplying I_{IN} with Aux. Amp
(to Allow High Z Feedback Networks)



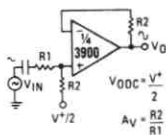
Bandpass Active Filter



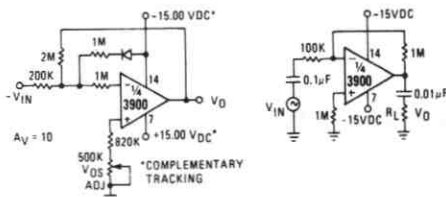
Ground Referencing a
Differential Input Signal



Non-Inverting Amplifier



Split Supply ($V^+ = +15V_{DC}$ & $V^- = -15V_{DC}$)
Non-Inverting DC Gain
AC Amplifier



GENERAL DESCRIPTION

The RV3301 and RC3401 consist of four independent amplifiers, with internal frequency compensation, designed to operate from a single power supply.

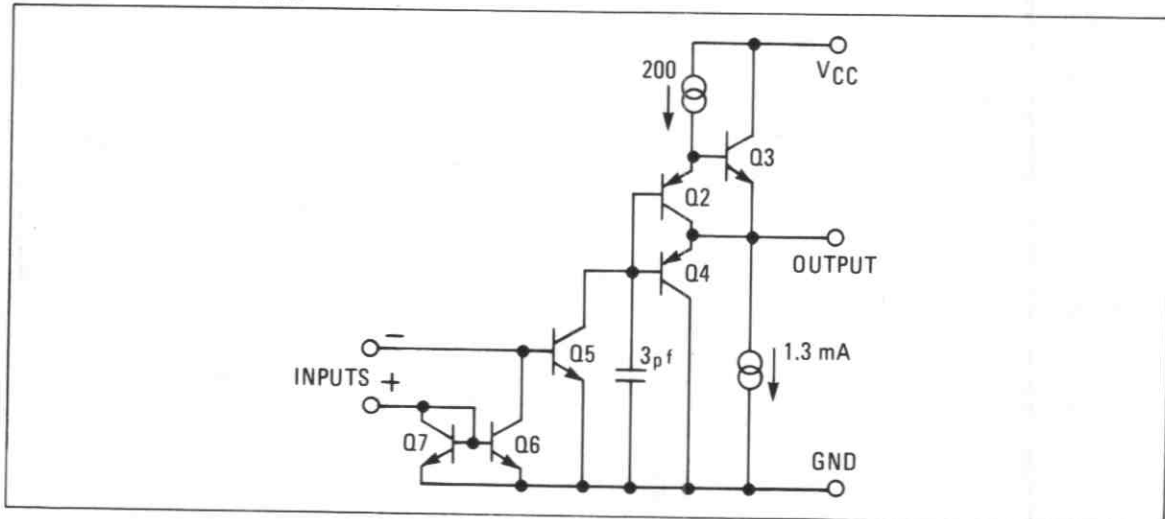
These amplifiers employ a current mirror to achieve the non-inverting inputs.

The current-differencing inputs allow a variety of applications in automotive instrumentation, industrial and consumer circuits for performing active filtering and pulse and waveform generation and processing.

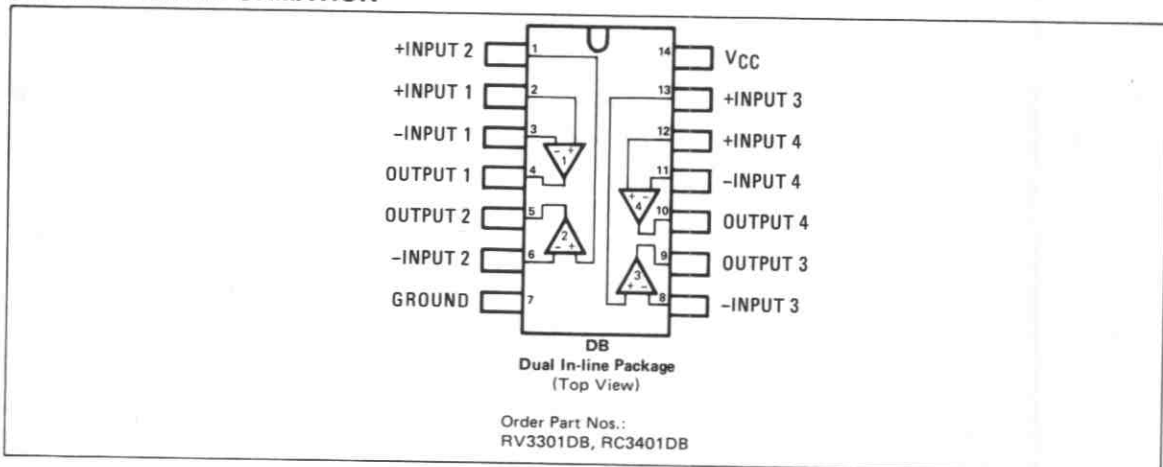
DESIGN FEATURES

- Wide Supply Voltage Range 4 to 28 V
- Wide Operating Temperature Range -40°C to $+85^{\circ}\text{C}$
- Wide Bandwidth Unity Gain 4 MHz
- Low Input Bias Current 50 nA

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



Quad Operational Amplifiers

ABSOLUTE MAXIMUM RATINGS

Power Supply Voltage		Power Dissipation (Package Limitation) 625 mW
3301	+28V	Derate above $T_A = +25^\circ\text{C}$ 5 mW/ $^\circ\text{C}$
3401	+18V	Operating Temperature Range 3301: -40°C to $+85^\circ\text{C}$
Non Inverting Input Current	5 mA	3401: 0°C to $+75^\circ\text{C}$
Sink Current	50 mA	Storage Temperature Range -65°C to $+150^\circ\text{C}$
Source Current	50 mA	Lead Temperature (Soldering, 10s) 300°C

ELECTRICAL CHARACTERISTICS ($V_{CC} = +15\text{V}$, $R_L = 5.0\text{K}\Omega$, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Conditions	NOTE	3301			3401			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
Open-Loop Voltage Gain	$T_A = +25^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq 75^\circ\text{C}$ $0^\circ\text{C} \leq T_A \leq 75^\circ\text{C}$	1	1000	2000 1600		1000 800	2000		V/V
Quiescent Power Supply Current (Total for 4 amplifiers)		2							mA
Noninverting inputs open				6.9	10		6.9	10	
Noninverting inputs grounded				7.8	14		7.8	14	
Input Bias Current	$R_L = \infty$ $T_A = +25^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $0^\circ\text{C} \leq T_A \leq +75^\circ\text{C}$	3		50 100	300		50 300		nA
Current Mirror Gain	$I_r = 200\mu\text{A}$	4	0.80	0.98	1.16				A/A
Current Mirror Gain Drift	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			± 2.5					%
Output Current		5							mA
Source Capability	($V_{OH} = 0.4\text{V}$) ($V_{OH} = 9.0\text{V}$)		3.0	10 7.0		5.0	10		
Sink Capability	($V_{OL} = 0.4\text{V}$)		0.5	0.87		0.5	1.0		
Output Voltage		6							V
High Voltage			13.5	14.2		13.5	14.2		
Low Voltage	(Inverting Input Driven) (Noninverting Input Driven)			0.03 0.6	0.1		0.03	0.1	
Undistorted Output Swing	($0^\circ\text{C} < T_A < +75^\circ\text{C}$)	7				10	13.5		V(p-p)
Input Resistance	(Inverting input only)		0.1	1.0		0.1	1.0		$M\Omega$
Slew Rate	($C_L = 100\text{ pF}$, $R_L = 5.0\text{ k}$)			0.6			0.6		V/ μs
Unity Gain Bandwidth		8		4.0			5.0		MHz
Phase Margin		8		70			70		Degrees
Power Supply Rejection	($f = 100\text{ Hz}$)	9		55			55		dB
Channel Separation	($f = 1.0\text{ kHz}$)			65			65		dB

- NOTES: 1. Open loop voltage gain is defined as the voltage gain from the inverting input to the output.
2. The quiescent current will increase approximately 0.3 mA for each noninverting input which is grounded. Leaving the noninverting input open causes the apparent input bias current to increase slightly (100 nA) at high temperatures.
3. Input bias current can be defined only for the inverting input. The noninverting input is not a true "differential input" — as with a conventional IC operational amplifier. As such this input does not have a requirement for input bias current.
4. Current mirror gain is defined as the current demanded at the inverting input divided by the current into the noninverting input.
5. Sink current is specified for linear operation. When the device is used as a gate or a comparator (non-linear operation), the sink capability of the device is approximately 5.0 milliamperes.
6. When used as a noninverting amplifier, the minimum output voltage is the V_{BE} of the inverting input transistor.
7. Peak-to-peak restrictions are due to the variations of the quiescent dc output voltage in the standard configuration.
8. Bandwidth and phase margin are defined with respect to the voltage gain from the inverting input to the output.
9. Power supply rejection is specified at closed loop unity gain, and therefore indicates the supply rejection of both the biasing circuitry and the feedback amplifier.

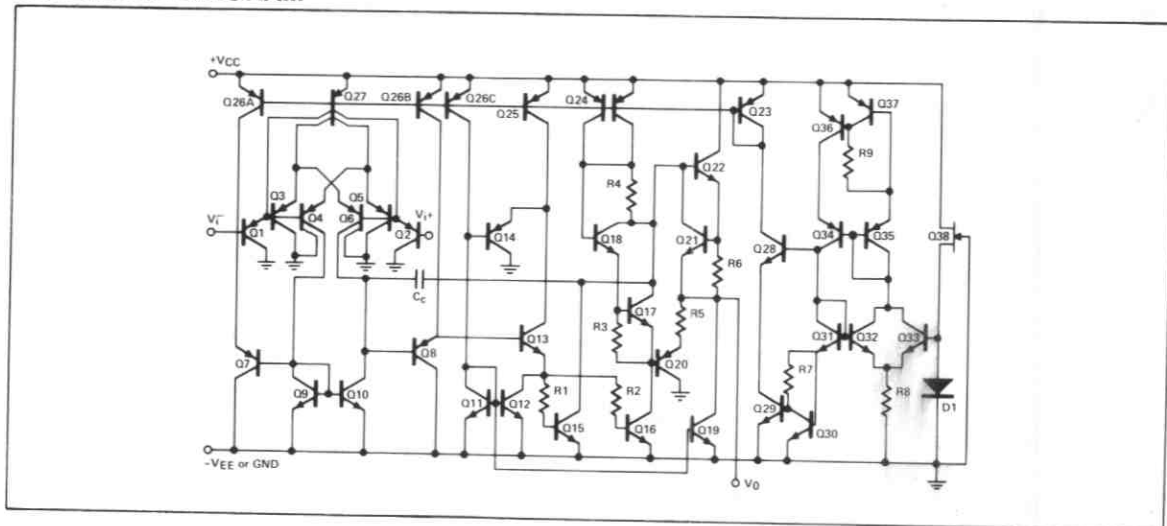
GENERAL DESCRIPTION

The 3403A high performance quad op-amp features improved large signal bandwidth and worst case DC specs equal to or better than the standard 741 type general purpose op-amp. The device uses a newly developed type of ground-sensing differential input stage which provides increased slew rate.

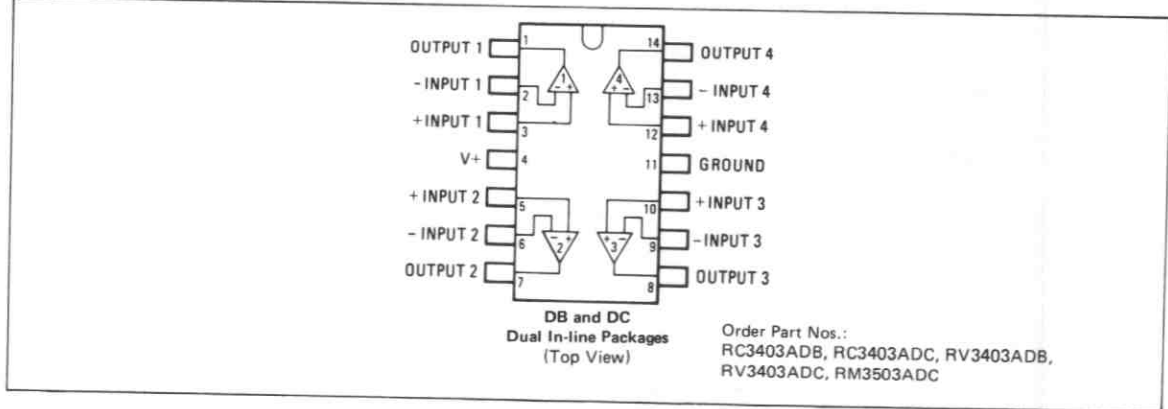
DESIGN FEATURES

- Class AB Output State; No Crossover Distortion
- Output Voltage Swings to Ground in Single Supply Operations
- High Slew Rate 1.2 V/ μ s
- Single or Split Supply Operation
- Wide Supply Operation 2.5 V to +36 V or ± 1.25 V to ± 18 V
- Pin Compatible with LM324 and 3403
- Low Power Consumption 0.8 mA/amplifier

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V^+	36 V or ± 18 V	Operating Temperature Range	
Differential Input Voltage	36 V	RM3503A	-55°C to $+125^{\circ}\text{C}$
Input Voltage	-0.3 V to $+36$ V	RC3403A	0°C to $+70^{\circ}\text{C}$
Power Dissipation		RV3403A	-40°C to $+85^{\circ}\text{C}$
"DB" package	500 mW (molded DIP epoxy "B")	Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
"DC" package	650 mW (hermetic DIP)	Lead Temperature (Soldering, 60s)	300°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$, $V_{CC} = \pm 15\text{V}$ unless otherwise noted)

PARAMETER	CONDITIONS	RM3503A			RC/RV3403A			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S = 0$		2	4*		2	6*	mV
Input Offset Current	I_{in-} or I_{in+}		± 30	± 50		± 30	± 50	nA
Input Bias Current	I_{in-} or I_{in+}		-150	-400*		-150	-500	nA
Input Common Mode Voltage Range		0		$V^+ - 2$	0		$V^+ - 2$	V
Supply Current	$R_L = \infty$ on all op-amps		3	4		3	5*	mA
Large Signal Voltage Gain	$R_L > 2\text{K}\Omega$	50	100		25*	100		V/mV
Output Voltage Swing	$R_L = 2\text{K}\Omega$	± 13	± 14		± 13	± 14		V
Common Mode Rejection Ratio	DC	70	90		70	90		dB
Channel Separation	$\pm 1\text{kHz}$ to 20kHz (in ref)		-120			-120		dB
Output Source Current	$V_{IN+} = 1\text{V}$ $V_{IN-} = 0\text{V}$	20	40		20	40		mA
Output sink current		10	20		10	20		mA
Small signal bandwidth			1			1		MHz
Slew Rate	$A_V = 1, -10 < V_i < +10$		1.2*			1.2*		V/ μs
Distortion (Crossover)	$f = 20\text{kHz}, V_O = 10\text{V}_{pp}$		1			1		%
Power Bandwidth	$V_O = 10\text{V}_{pp}$		40			40		kHz
Power Supply Rejection Ratio			20	50		20	100	$\mu\text{V}/\text{V}$

*Significantly improved performance

ELECTRICAL CHARACTERISTICS GUARANTEED OVER TEMPERATURE

Range: RM3503A: -55°C to $+125^{\circ}\text{C}$
 RC3403A: 0°C to $+70^{\circ}\text{C}$
 RV3403A: -40°C to $+85^{\circ}\text{C}$

PARAMETER	RM3503A		RC3403A		RV3403A		UNITS
	MIN	MAX	MIN	MAX	MIN	MAX	
Input Offset Voltage	-	6.0	-	10.0	-	10.0	mV
Input Offset Current	-	200	-	200	-	200	nA
Input Bias Current	-	-1500	-	-800	-	-1500	nA
Large Signal Voltage Gain	25	-	15	-	15	-	V/mV
Output Voltage Swing	± 10	-	± 10	-	± 10	-	V



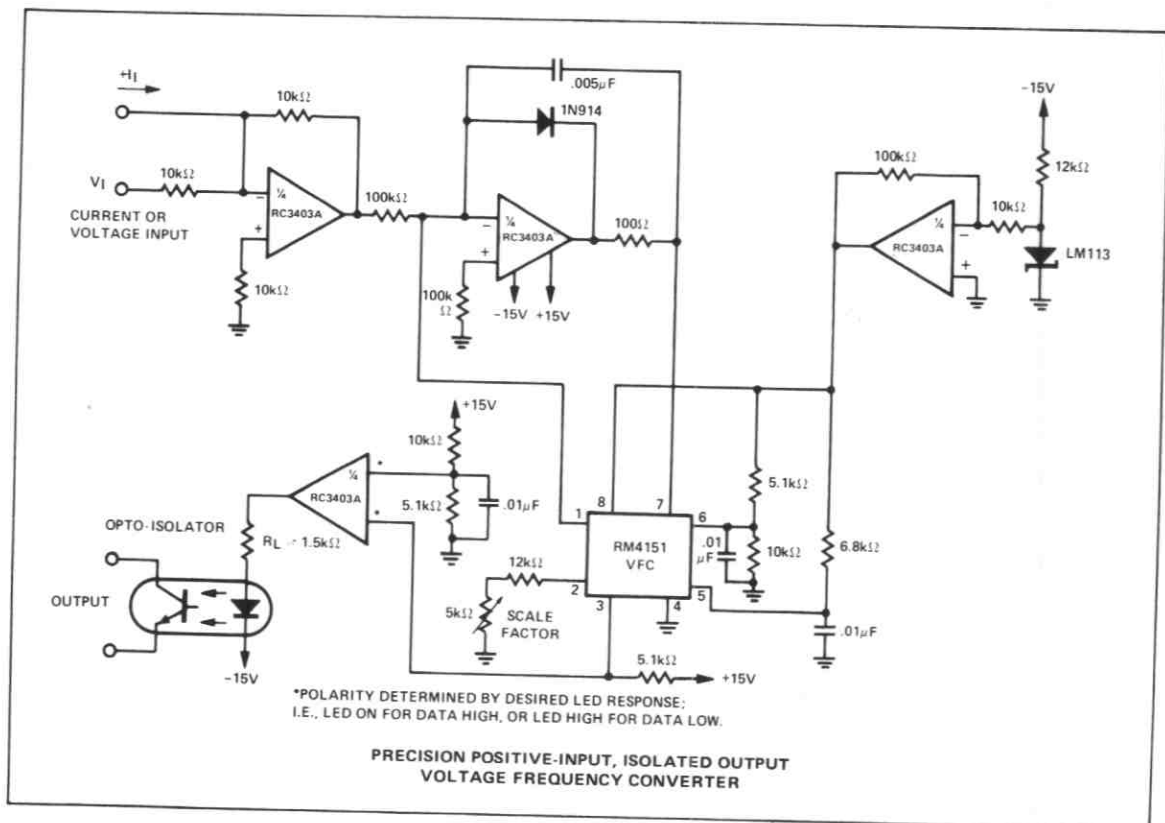
LOW VOLTAGE ELECTRICAL CHARACTERISTICS ($V_{CC} = +5V$, $V_{EE} = GND$, $T_A = +25^{\circ}C$ unless otherwise noted.)

PARAMETER	CONDITIONS	RM3503A			RC/RV3403A			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S = 0\Omega$		2.0	5.0		2.0	10	mV
Input Offset Current	$I_{in-} - I_{in+}$		30	50		30	50	nA
Input Bias Current	$I_{in-} + I_{in+}/2$		-150	-500		-150	-500	nA
Large Signal Voltage Gain	$R_L = 2K\Omega$	20	200		20	200		V/mV
Power Supply Rejection Ratio				50			150	$\mu V/V$
Output Voltage Range ¹	$R_L = 10K\Omega$	3.5			3.5			V_{p-p}
Power Supply Current	$R_L = \infty$, all amplifiers		2.5	4.0		2.5	5.0*	mA
Channel Separation	$1KHz \leq f \leq 2MHz$ (input referred)		-120			-120		dB

¹ Output will swing to ground.

*Significantly improved performance.

3403A TYPICAL APPLICATIONS



Total Quad Operational Amplifiers

ELECTRICAL CHARACTERISTICS COMPARISON
RC3403A, RC3403, LM324

	RC3403A			RC3403			LM324			Units
Maximum Ratings										
Supply Voltage	+36 or ±18			+36 or ±18			+32 or ±16			V
Differential Input Voltage	36			36			32			V
Input Voltage	36			36			32			V
Power Dissipation	DC 650 DB 500			DC 650 DB 500			N 570			mW
Electrical Characteristics	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Test Conditions		±15			±15			+5		V
Input Offset Voltage		2	6		2	8		2	7	mV
Input Offset Current		±30	±50		±30	±50		±5	±50	nA
Input Bias Current		150	500		200	500		45	500	nA
Input Common Mode Voltage Range	0		V ⁺ -2				0		V ⁺ -1.5	V
Supply Current		3	5		2.8	7.0		0.8	2	mA
Open Loop Voltage Gain	25	100		20	200			100		V/mV
Output Voltage Swing	±13	±14		±10	±13				V ⁺ -1.5	V
Common Mode Rejection Ratio	70	90		70	90			85		dB
Power Supply Rejection Ratio		20	100		30	150		100dB		μV/V
Unity Gain Bandwidth		1.0			1.0					MHz
Slew Rate		1.2			0.6					V/μs
Output Sink Current	10	20						20		mA
Output Source Current	20	40					20	40		mA
Channel Separation		120			120			120		dB
Distortion (crossover)		1.0			1.0					%

GENERAL DESCRIPTION

The RC4131/RM4131 are high performance, high gain, internally compensated operational amplifiers fabricated on a single silicon chip using the planar epitaxial process.

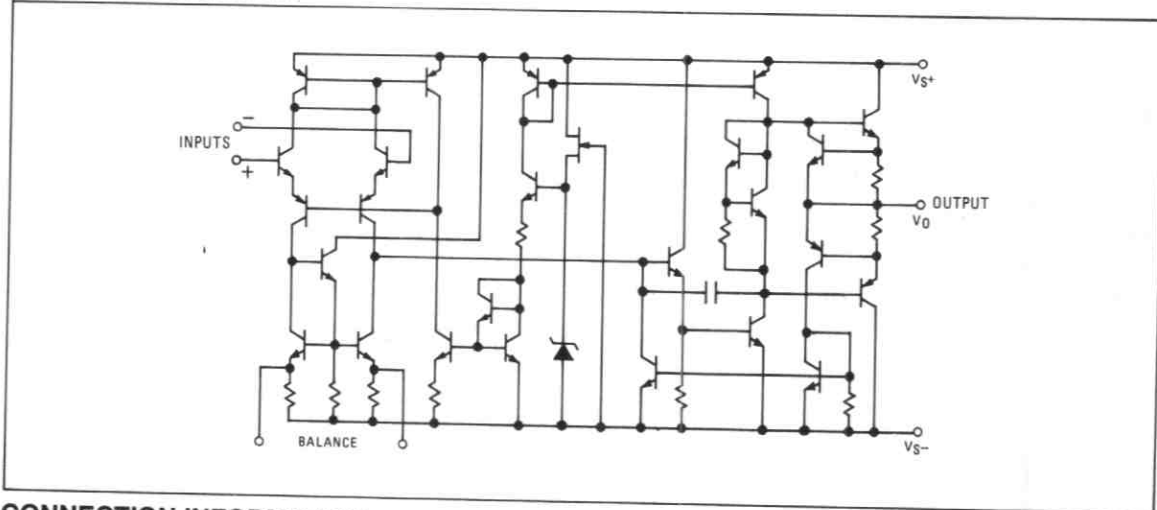
Designed as a pin for pin replacement for the RM709, they are also direct replacements for the 741 and LM107. Relative to these latter units, the RC4131/RM4131 features four times the slew rate, and $\frac{1}{2}$ the power dissipation at $\pm 20V$.

High common-mode and differential voltage range, very low input bias current, optimum performance over a very wide range of supply voltage, freedom from "latch-up," and operation over the full military temperature range from $-55^{\circ}C$ to $+125^{\circ}C$ make the RM4131 ideal for use as a voltage follower, comparator, integrator, and summing or general purpose feedback amplifier. The RC4131 operates over a temperature range of $0^{\circ}C$ to $+70^{\circ}C$.

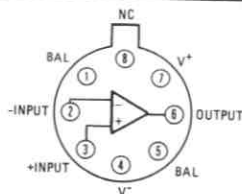
DESIGN FEATURES

- 50nA Maximum Input Bias Current
- 10nA Maximum Input Offset Current
- 2mV Maximum Input Offset Voltage
- 1.1mA Current Drain at $\pm 20V$
- Offset Voltage Nulling (10k Ω pot.)
- 2.0V/ μs Slew Rate
- 4MHz Unity Gain Bandwidth
- 3dB Gain. Variation From $\pm 3V$ to $\pm 20V$
- 88dB Minimum Gain $\pm 3V$ to $\pm 20V$, $-55^{\circ}C$ to $+125^{\circ}C$

SCHEMATIC DIAGRAM

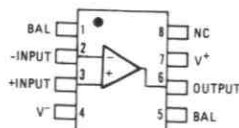


CONNECTION INFORMATION



TE Metal Can
(Top View)

Order Part Nos.:
RM4131T, RC4131T



NB Miniature
Dual In-line
(Top View)

Order Part Nos.:
RC4131NB

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM4131: $\pm 22\text{V}$ RC4131: $\pm 18\text{V}$	Operating Temperature Range	RM4131: -55°C to $+125^{\circ}\text{C}$ RC4131: 0°C to $+70^{\circ}\text{C}$
Internal Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 60s)	300°C
Differential Input Voltage	$\pm 30\text{V}$	Output Short-Circuit Duration (Note 3)	Indefinite
Input Voltage (Note 2)	$\pm 15\text{V}$		
Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$		

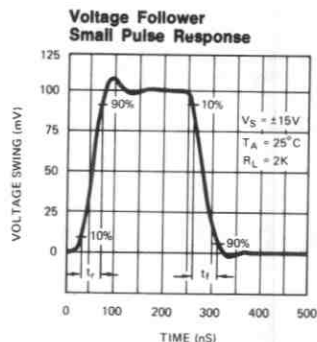
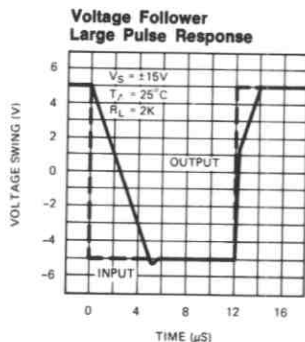
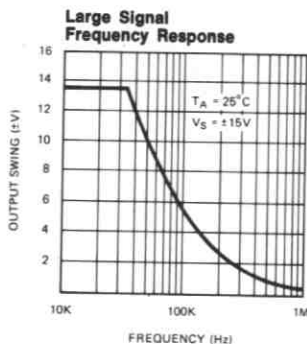
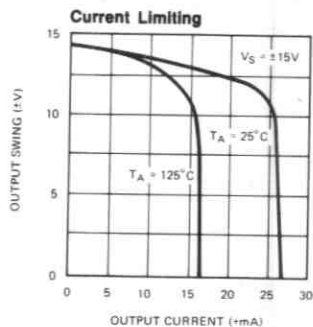
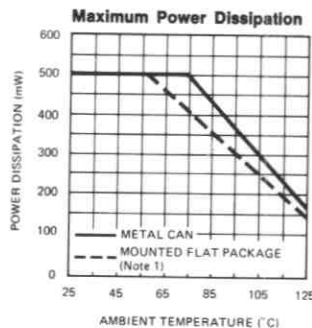
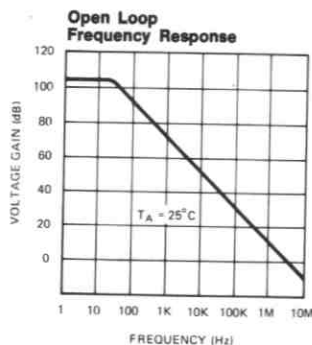
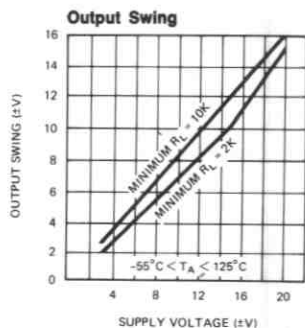
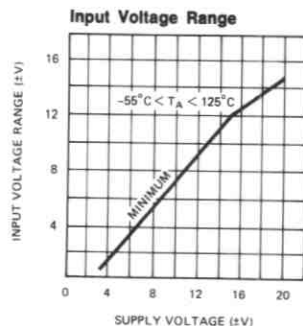
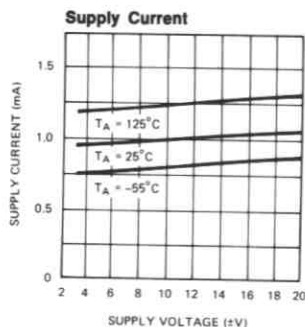
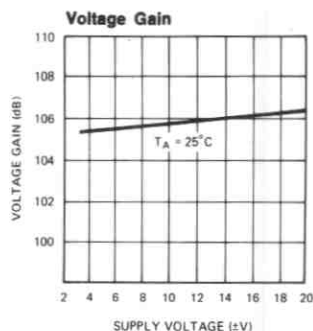
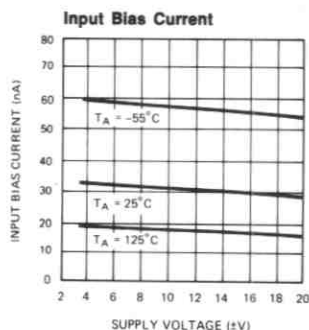
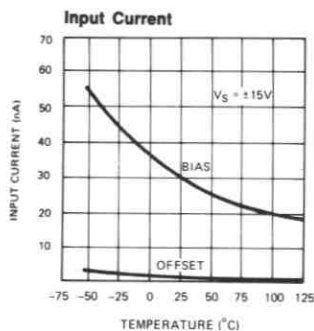
ELECTRICAL CHARACTERISTICS RM4131: $\pm 3\text{V} < V_S < \pm 20\text{V}$, $-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$, unless otherwise specified.
 RC4131: $\pm 3\text{V} < V_S < \pm 15\text{V}$, $0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$, unless otherwise specified.

PARAMETER	CONDITIONS	RM4131			RC4131			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10\text{k}\Omega$, $T_A = +25^{\circ}\text{C}$		0.7	2.0		1.5	5.0	mV
	$R_S \leq 10\text{k}\Omega$			3.0			6.0	
Input Offset Current	$T_A = +25^{\circ}\text{C}$		1.5	10		3.0	20	nA
				20			30	
Input Bias Current	$T_A = +25^{\circ}\text{C}$		30	50		70	150	nA
				100			200	
Input Resistance		2.2	3.5		0.7	3.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2\text{k}\Omega$, $T_A = +25^{\circ}\text{C}$	50			35			V/mV
	(Note 4)	25	160		25	160		
Output Voltage Swing RM4131: $V_S = \pm 20\text{V}$ RC4131: $V_S = \pm 15\text{V}$	$R_L \geq 10\text{k}\Omega$	± 16			± 12			V
	$R_L \geq 2\text{k}\Omega$	± 15			± 10			V
Input Voltage Range	RM4131: $V_S = \pm 20\text{V}$ RC4131: $V_S = \pm 15\text{V}$	± 15			± 11			V
Common-Mode Rejection Ratio	$R_S \leq 10\text{k}\Omega$	80	100		70	100		dB
Supply Voltage Rejection Ratio	$R_S \leq 10\text{k}\Omega$	80	100		70	100		dB
Supply Current	$R_L = \infty$, $T_A = +25^{\circ}\text{C}$		1.1	1.6		1.3	1.9	mA
				1.9				
Average Temperature Coefficient of Input Offset Voltage			3.0	15		5.0	20	$\mu\text{V}/^{\circ}\text{C}$
Average Temperature Coefficient of Input Offset Current	$25^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$		0.01	0.1				nA/ $^{\circ}\text{C}$
	$-55^{\circ}\text{C} \leq T_A \leq 25^{\circ}\text{C}$		0.02	0.2				
	$25^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$					0.01	0.1	
	$0^{\circ}\text{C} \leq T_A \leq 25^{\circ}\text{C}$					0.02	0.2	
Slew Rate (Unity Gain)	$R_L \geq 2\text{k}\Omega$		2.0			2.0		V/ μs
Bandwidth (Unity Gain)			4.0			4.0		MHz

NOTES:

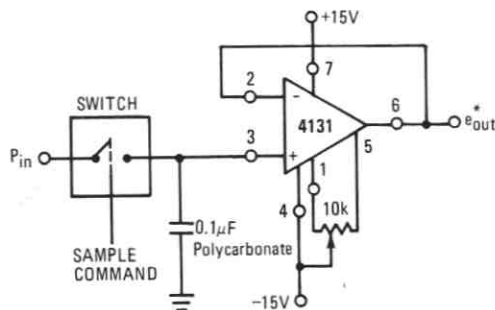
- Rating applies for case temperatures to $+125^{\circ}\text{C}$; derate linearly at $6.5\text{ mW}/^{\circ}\text{C}$ for ambient temperatures above $+75^{\circ}\text{C}$.
- For supply voltages less than $\pm 15\text{V}$, the absolute maximum input voltage is equal to the supply voltage.
- Short circuit may be to ground or either supply. Rating applies to $+125^{\circ}\text{C}$ case temperature of $+75^{\circ}\text{C}$ ambient temperature.
- RM4131: $V_S = \pm 1.3\text{V}$, $V_O = \pm 1.3\text{V}$; $V_S = \pm 20\text{V}$, $V_O = \pm 15\text{V}$. RC4131: $V_S = \pm 3\text{V}$, $V_O = \pm 1.3\text{V}$; $V_S = \pm 15\text{V}$, $V_O = \pm 10\text{V}$.

TYPICAL ELECTRICAL DATA

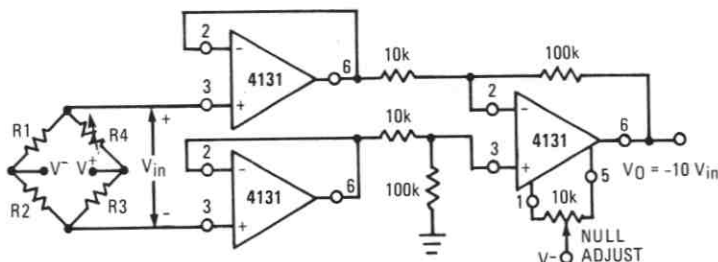


TYPICAL APPLICATIONS

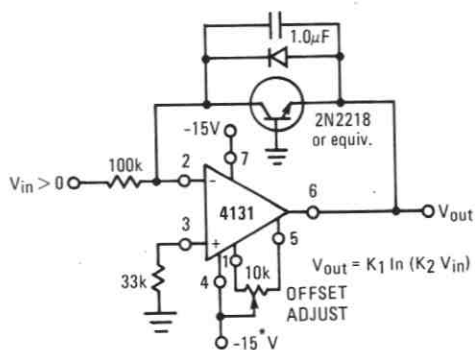
Low Drift Sample and Hold



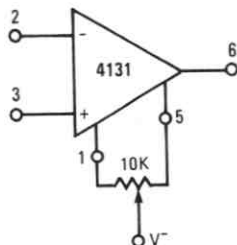
High Impedance Bridge Amplifier



Logarithmic Amplifier



Voltage Offset Null Circuit



GENERAL DESCRIPTION

The RM4136 and RC4136 include four independent high gain operational amplifiers internally compensated and constructed on a single silicon chip using the planar epitaxial processes.

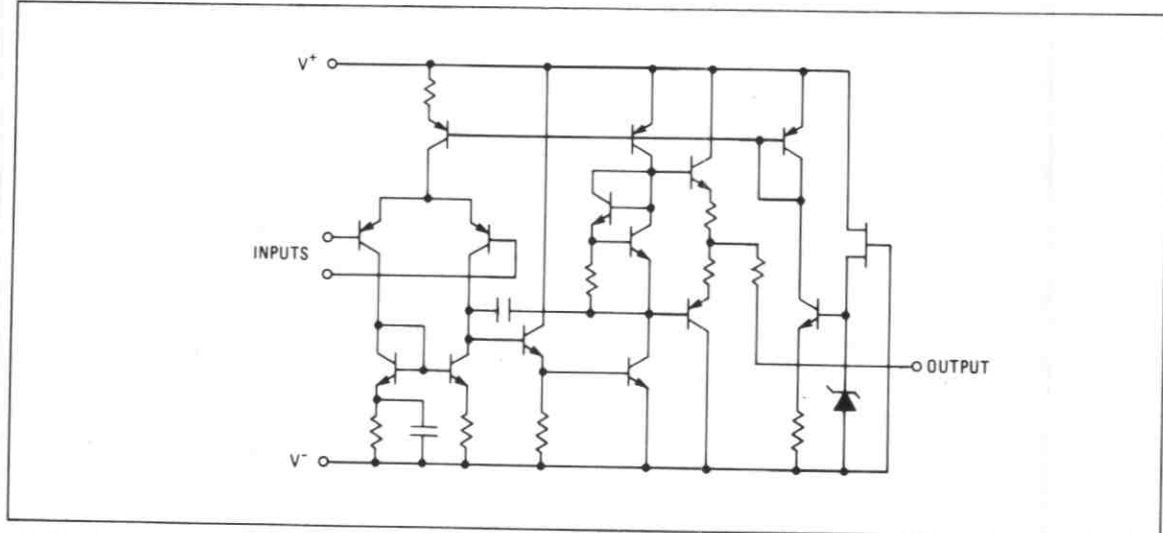
These amplifiers meet or exceed all specifications for 741 type amplifiers. Excellent channel separation allows the use of the 4136 quad amplifier in all 741 operational amplifier applications providing the highest possible packaging density.

The specially designed low noise input transistors allow the 4136 to be used in low noise signal processing applications such as audio preamplifiers and signal conditioners.

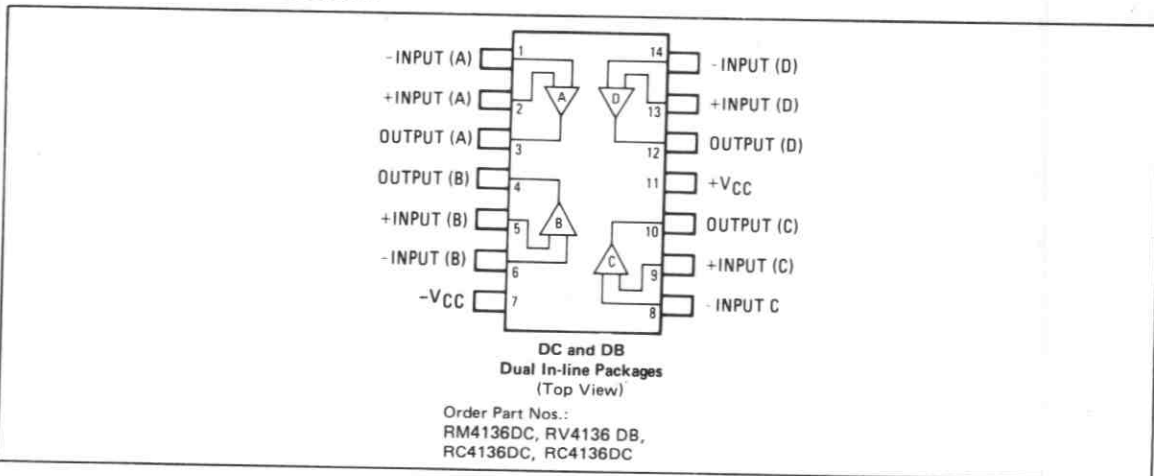
DESIGN FEATURES

- Unity Gain Bandwidth, 3MHz
- Continuous Short Circuit Protection
- No Frequency Compensation Required
- No Latch-up
- Large Common Mode and Differential Voltage Ranges
- Low Power Consumption
- Parameter Tracking Over Temperature Range
- Gain and Phase Match Between Amplifiers

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



RAYTHEON

RAYTHEON COMPANY • SEMICONDUCTOR DIVISION • 350 ELLIS STREET • MOUNTAIN VIEW, CALIFORNIA

ABSOLUTE MAXIMUM RATINGS

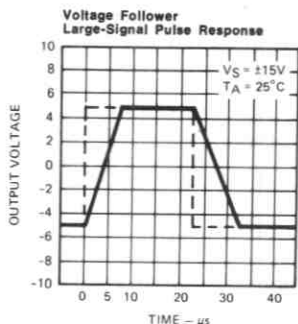
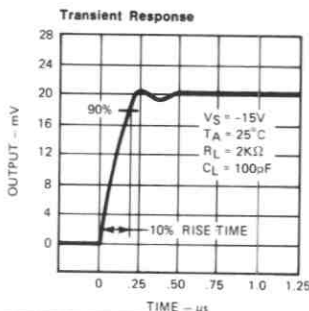
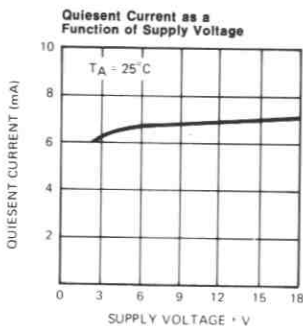
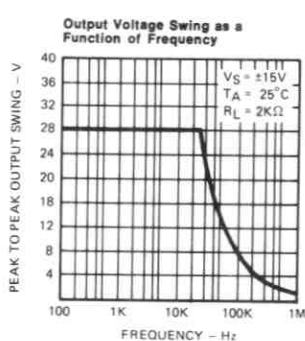
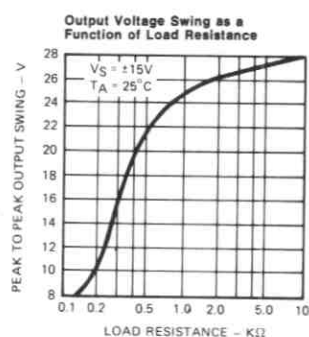
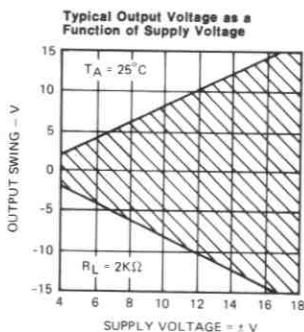
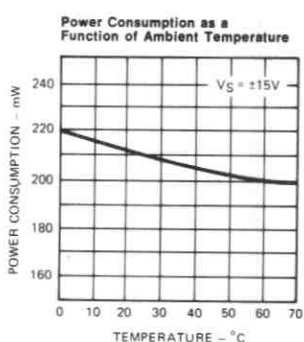
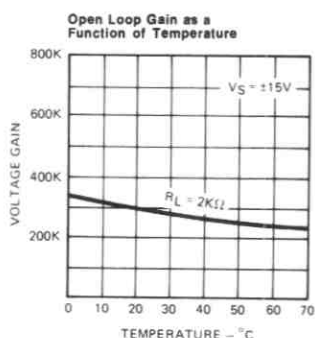
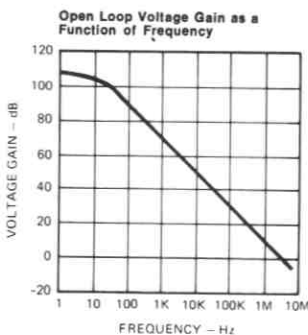
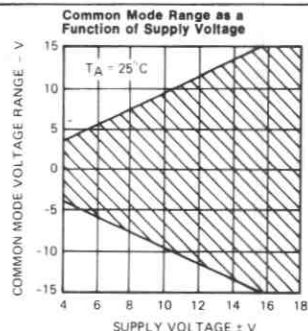
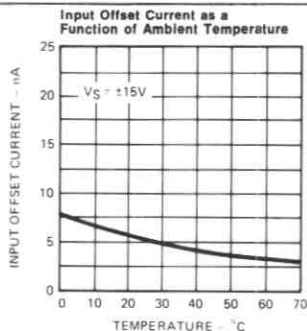
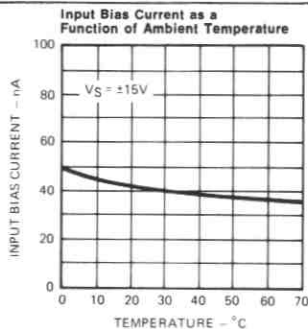
Supply Voltage	RM4136: $\pm 22V$ RV4136, RC4136: $\pm 18V$	Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$
Internal Power Dissipation (Note 1)	800mW	Operating Temperature Range	RM4136: $-55^{\circ}C$ to $+125^{\circ}C$ RC4136: $0^{\circ}C$ to $+70^{\circ}C$ RV4136: $-40^{\circ}C$ to $+85^{\circ}C$
Differential Input Voltage	$\pm 30V$	Lead Temperature (Soldering, 60s)	$300^{\circ}C$
Input Voltage (Note 2)	$\pm 15V$	Output Short-Circuit Duration (Note 3)	Indefinite

ELECTRICAL CHARACTERISTICS ($V_{CC} = \pm 15V$, $T_A = +25^{\circ}C$ unless otherwise noted.)

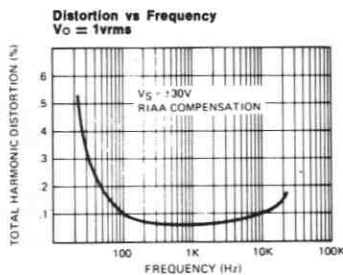
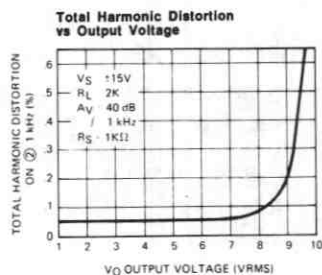
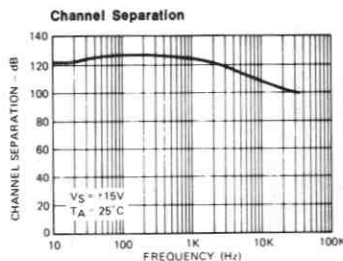
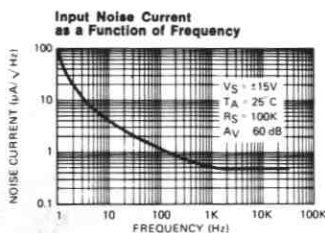
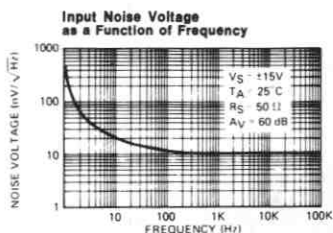
PARAMETER	CONDITIONS	RM4136			RV4136, RC4136			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10 k\Omega$		0.5	5.0		0.5	6.0	mV
Input Offset Current			5.0	200		5.0	200	nA
Input Bias Current			40	500		40	500	nA
Input Resistance		0.3	5.0		0.3	5.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2 k\Omega$ $V_{out} = \pm 10V$	50,000	300,000		20,000	300,000		V/V
Output Voltage Swing	$R_L \geq 10 k\Omega$	± 12	± 14		± 12	± 14		V
	$R_L \geq 2 k\Omega$	± 10	± 13		± 10	± 13		V
Input Voltage Range		± 12	± 14		± 12	± 14		V
Common Mode Rejection Ratio	$R_S \leq 10 k\Omega$	70	100		70	100		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 k\Omega$		10	150		10	150	$\mu V/V$
Power Consumption	$R_L = \infty$, All Outputs		210	340		210	340	mW
Transient Response (unity gain)	$V_{in} = 20 mV$ $R_L = 2 k\Omega$ $C_L \leq 100 pF$							
Risetime			0.13			0.13		μs
Overshoot			5.0			5.0		%
Unity Gain Bandwidth			3.0			3.0		MHz
Slew Rate (unity gain)	$R_L \geq 2 k\Omega$		1.5			1.0		V/ μs
Channel Separation (open loop) (Gain = 100)	$f = 10 kHz$ $R_S = 1 k\Omega$		105			105		dB
	$f = 10 kHz$ $R_S = 1 k\Omega$		105			105		dB
The following specifications apply for $-55^{\circ}C \leq T_A \leq +125^{\circ}C$ for RM4136; $0^{\circ}C \leq T_A \leq +70^{\circ}C$ for RC4136.								
Input Offset Voltage	$R_S \leq 10 k\Omega$			6.0			7.5	mV
Input Offset Current				500			300	nA
Input Bias Current				1500			800	nA
Large-Signal Voltage Gain	$R_L \geq 2 k\Omega$ $V_{out} = \pm 10V$	25,000			15,000			V/V
Output Voltage Swing	$R_L \geq 2 k\Omega$	± 10			± 10			V
Power Consumption	$T_A = High$		180	300		180	300	mW
	$T_A = Low$		240	400		240	400	mW

- NOTES:
- Rating applies for case temperature to $+25^{\circ}C$; derate linearly at 6.4 mW/ $^{\circ}C$ for ambient temperatures above $+25^{\circ}C$.
 - For supply voltages less than $\pm 15V$ the absolute maximum input voltage is equal to the supply voltage.
 - Short-circuit may be to ground or one amplifier only. $I_{CC} = 45mA$ (typical).

TYPICAL ELECTRICAL DATA



TYPICAL ELECTRICAL DATA

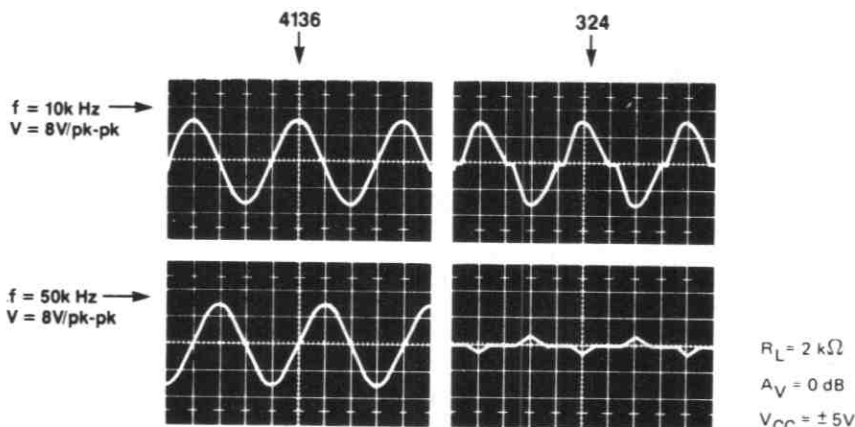
ELECTRICAL CHARACTERISTICS COMPARISON ($V_{CC} = \pm 15V$, $T_A = +25^\circ C$)

PARAMETER	RC4136 (typ)	RC741 (typ)	LM324 (typ)	UNIT
Input Offset Voltage	0.5	2.0	2	mV
Input Offset Current	5	10	5	nA
Input Bias Current	40	80	55	nA
Input Resistance	5	2		M Ω
Large-Signal Voltage Gain ($R_L = 2 k\Omega$)	300,000	200,000	100,000	V/V
Output Voltage Swing ($R_L = 2 k\Omega$)	$\pm 13V$	$\pm 13V$	$ +V_{CC} - 1.2V $ to $-V_{CC}$	\bar{V}
Input Voltage Range	$\pm 14V$	$\pm 13V$	$ +V_{CC} - 1.5V $ to $-V_{CC}$	\bar{V}
Common-Mode Rejection Ratio	100	90	85	dB
Supply Voltage Rejection Ratio	10	30	10	$\mu V/V$
Transient Response (gain = 1)	Risetime	0.13	0.3	μs
	Overshoot	5	5	%
Unity-Gain Bandwidth	3	0.8	0.8	MHz
Unity-Gain Slew Rate	1.0	0.5	0.5	V/ μs
Input Noise Voltage ($f_0 = 1 kHz$)	10	22.5		nV/ \sqrt{Hz}
Output Short-Circuit Current	± 45	± 25		mA

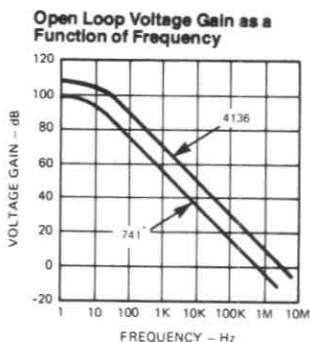
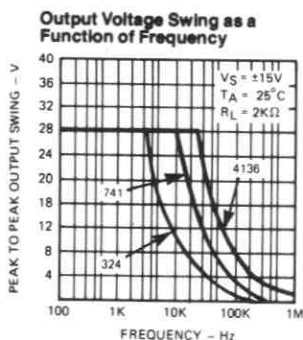
4136 vs. 741

Although the 324 is an excellent device for single-supply applications where ground-sensing is important, it is a poor substitute for four 741's in split-supply circuits.

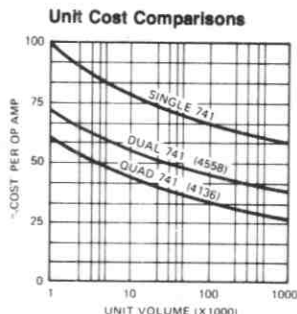
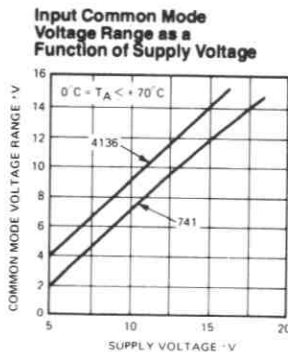
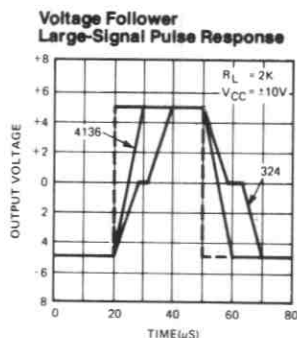
The simplified input circuit of the 4136 exhibits much lower noise than that of the 324 and exhibits no crossover distortion as compared with the 324 (see illustration). The 324 shows serious crossover distortion and pulse delay in attempting to handle a large-signal input pulse.



Comparative Cross-over Distortion

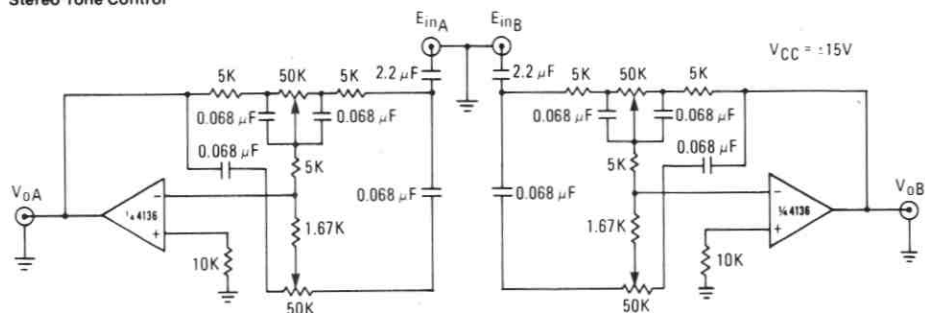


Typical Characteristics Curves Comparison

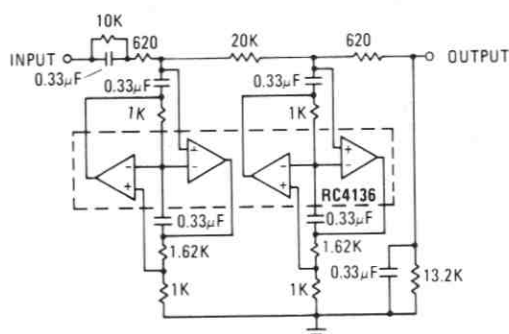


4136 TYPICAL APPLICATIONS

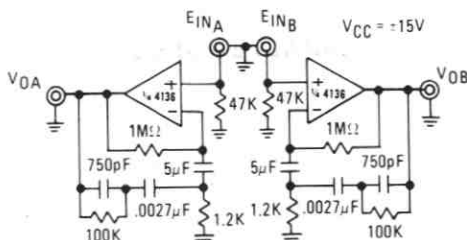
Stereo Tone Control



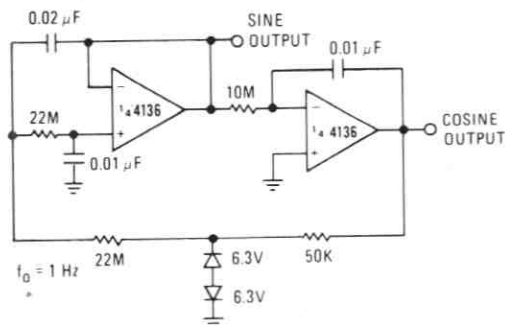
400 Hz Lowpass Butterworth Active Filter



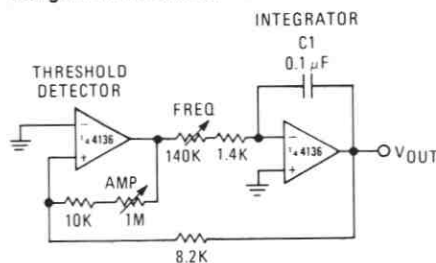
RIAA Preamplifier



Low Frequency Sine Wave Generator with Quadrature Output

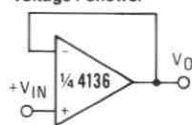


Triangular-Wave Generator

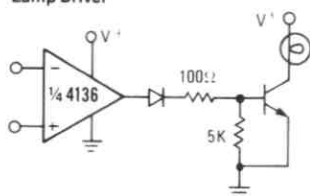


4136 TYPICAL APPLICATIONS

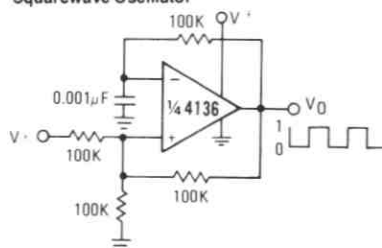
Voltage Follower



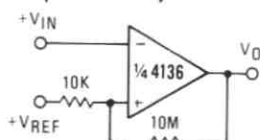
Lamp Driver



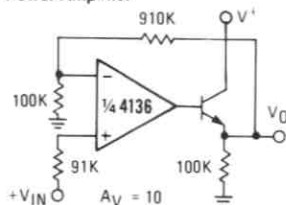
Squarewave Oscillator



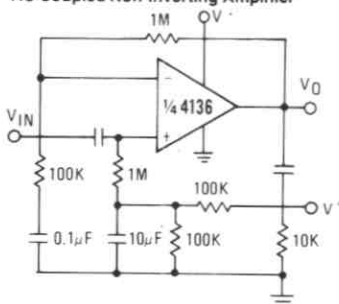
Comparator With Hysteresis



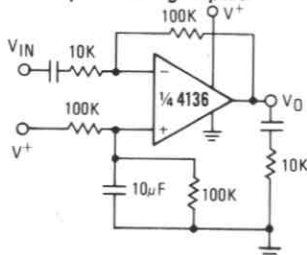
Power Amplifier



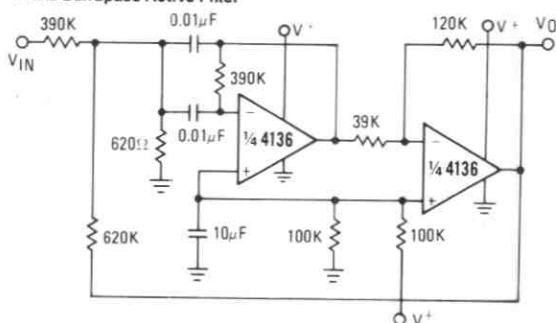
AC Coupled Non-Inverting Amplifier



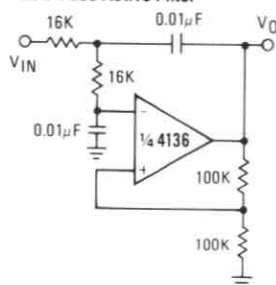
AC Coupled Inverting Amplifier



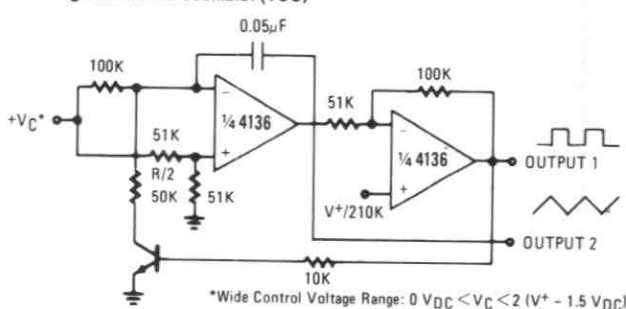
1 kHz Bandpass Active Filter



DC Coupled 1 kHz Low-Pass Active Filter



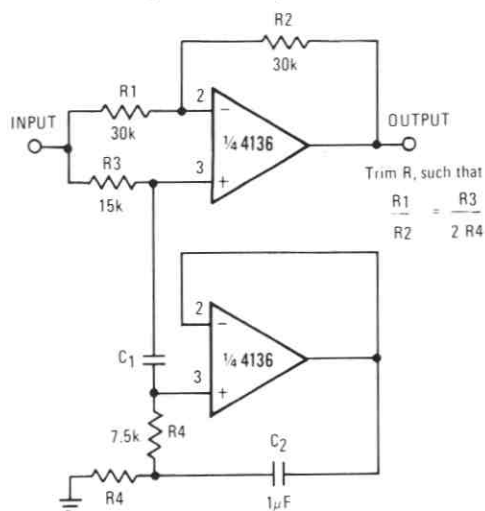
Voltage Controlled Oscillator (VCO)



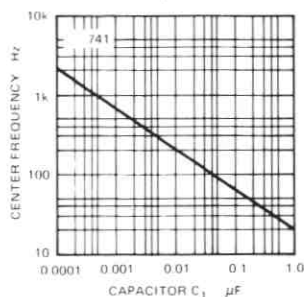
*Wide Control Voltage Range: $0 V_{DC} < V_C < 2(V^+ - 1.5 V_{DC})$

4136 TYPICAL APPLICATIONS

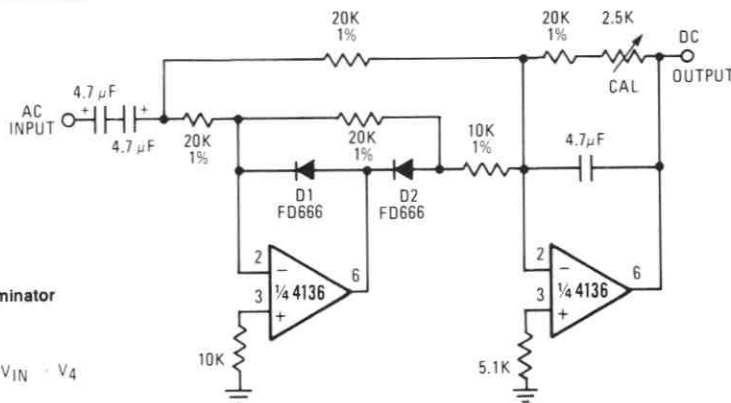
Notch Filter Using the 4136 as a Gyration



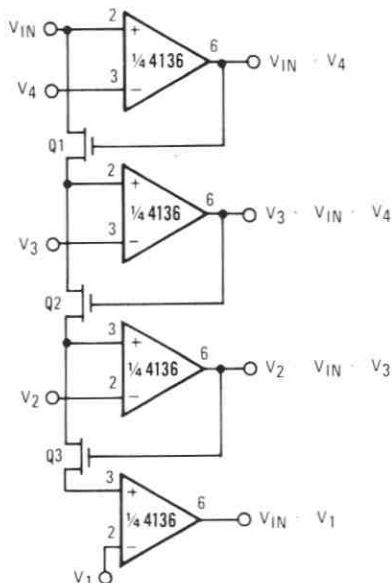
Notch Frequency as a Function of C₁



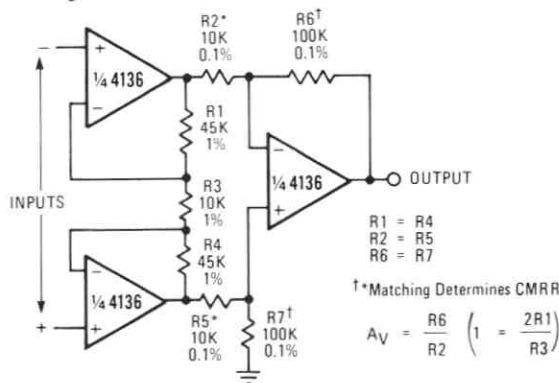
Full-Wave Rectifier and Averaging Filter



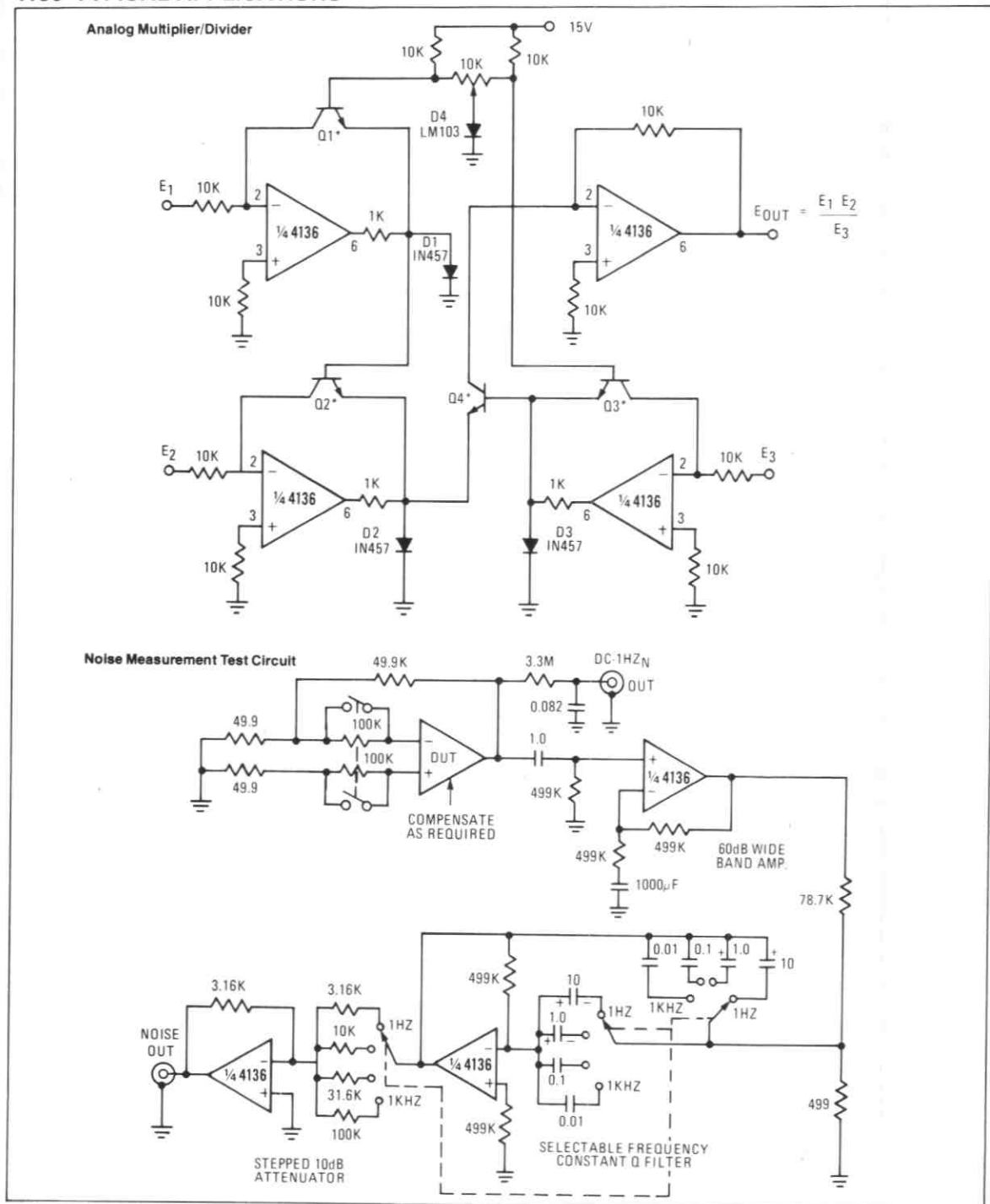
Multiple Aperture Window Discriminator



Differential Input Instrumentation Amplifier with High Common Mode Rejection



4136 TYPICAL APPLICATIONS



GENERAL DESCRIPTION

The RM4531 and RC4531 are high slew rate operational amplifiers intended for applications requiring slew rates up to 30V/ μ s while keeping the DC performance of the 741.

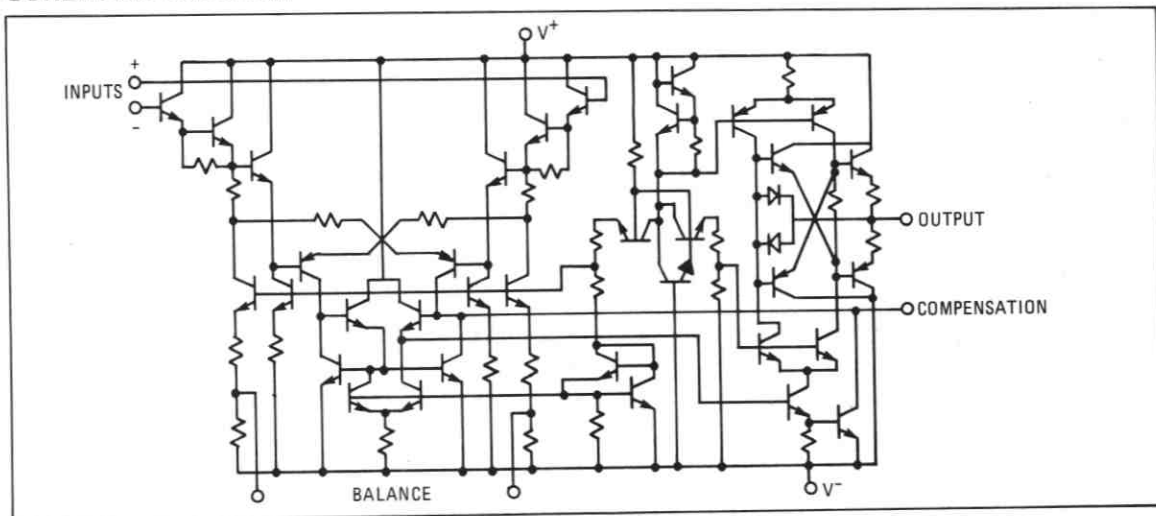
The RM4531 military version operates over a temperature range from -55°C to $+125^{\circ}\text{C}$. The RC4531 operates from 0°C to $+70^{\circ}\text{C}$.

High slew rates are achieved through use of an improved input stage which tends to retain small signal characteristics when subjected to large differential input signals. Advanced integrated circuit layout techniques are used to eliminate thermal feedback. The RM4531 and RC4531 feature offset null capability, high gain, and each can be compensated with an external 100pF capacitor connected between the output and compensation terminals.

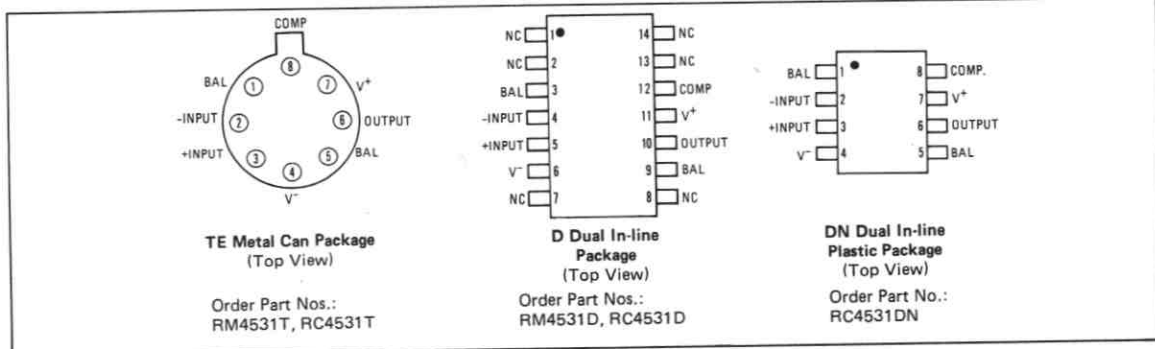
DESIGN FEATURES

- Slew Rate 35V/ μ s
- Small Signal Bandwidth 1MHz
- Large Signal Bandwidth 500kHz
- Supply Voltage $\pm 6\text{V}$ to $\pm 18\text{V}$
- Pin-for-Pin Replacement for 709, LM101A, 741
- Low Drift Offset-Null Circuitry
- Compensated with Single Capacitor

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM4531: $\pm 22V$ RC4531: $\pm 18V$	Operating Temperature Range	RM4531: $-55^{\circ}C$ to $+125^{\circ}C$ RC4531: $0^{\circ}C$ to $+70^{\circ}C$
Internal Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 60s)	$300^{\circ}C$
Differential Input Voltage	$\pm 15V$	Output Short-Circuit Duration (Note 3)	Indefinite
Input Voltage (Note 2)	$-12.5V, +15V$		
Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$		

ELECTRICAL CHARACTERISTICS ($V_S = \pm 15V$, $T_A = 25^{\circ}C$ unless otherwise specified)

PARAMETER	CONDITIONS	RM4531			RC4531			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10k\Omega$		2.0	5.0		2.0	6.0	mV
Input Offset Current			30	200		50	200	nA
Input Bias Current			300	500		400	1500	nA
Input Resistance		0.3	20		0.3	20		M Ω
Large-Signal Voltage Gain	$R_S \geq 2k\Omega$, $V_{out} = \pm 10V$	50,000	100,000		20,000	60,000		
Input Voltage Range (Note 2)		± 10			± 10			V
Common Mode Rejection Ratio	$R_S \leq 10k\Omega$				70	100		dB
Supply Voltage Rejection Ratio	$R_S \leq 10k\Omega$					10	150	$\mu V/V$
Output Resistance			75			75		Ω
Supply Current			5.5	7.0		5.5	10	mA
Power Consumption			165	210		165	300	mW
Setting Time, 1%	$A_V = +1$, $V_{IN} = \pm 10V$		1.5			1.5		μs
Setting Time, .01%	$A_V = +1$, $V_{IN} = \pm 10V$		2.5			2.5		μs
Large Signal Overshoot	$A_V = +1$, $V_{IN} = \pm 10V$		2.0			2.0		%
Small Signal Risetime	$A_V = +1$, $V_{IN} = 400mV$		300			300		ns
Small Signal Overshoot	$A_V = +1$, $V_{IN} = 400mV$		5.0			5.0		%
Slew Rate	$A_V = 100$		35			35		V/ μs
	$A_V = 10$		35			35		V/ μs
	$A_V = 1$ (non-inv.)		30			30		V/ μs
	$A_V = 1$ (inv.)		35			35		V/ μs

The following specifications apply for $-55^{\circ}C \leq T_A \leq +125^{\circ}C$ for RM4531; $0^{\circ}C \leq T_A \leq +70^{\circ}C$ for RC4531.

Input Offset Voltage	$R_S \leq 10k\Omega$			6.0			7.5	mV
Input Offset Current	$T_A = T_{min}$			500			300	nA
	$T_A = T_{max}$			200			200	nA
Input Bias Current	$T_A = T_{min}$			1.5			2.0	μA
	$T_A = T_{max}$			0.5			1.5	μA
Large-Signal Voltage Gain	$R_L > 2k\Omega$, $V_{out} = +10V$	25,000				15,000		
Output Voltage Swing	$R_L \geq 2k\Omega$	± 10	± 13		± 10	± 13		V
Common Mode Rejection Ratio	$R_S \leq 10k\Omega$	70	90					dB
Supply Voltage Rejection Ratio	$R_S \leq 10k\Omega$		10	150				$\mu V/V$
Supply Current	$T_A = T_{max}$		4.5	5.5		4.5	5.5	mA

NOTES:

- Rating applies for case temperatures to $+125^{\circ}C$; derate linearly at 6.5 mW/ $^{\circ}C$ for ambient temperatures above $+75^{\circ}C$ for RM4531.
- For supply voltages less than $\pm 15V$, the absolute maximum positive input voltage is equal to the supply voltage. The absolute maximum negative input voltage decreased by 1 volt for every 1 volt decrease in the negative supply voltage.
- Short-circuit may be to ground to either supply. Rating applies to $+125^{\circ}C$ case temperature or $+75^{\circ}C$ ambient temperature for RM4531.



GENERAL DESCRIPTION

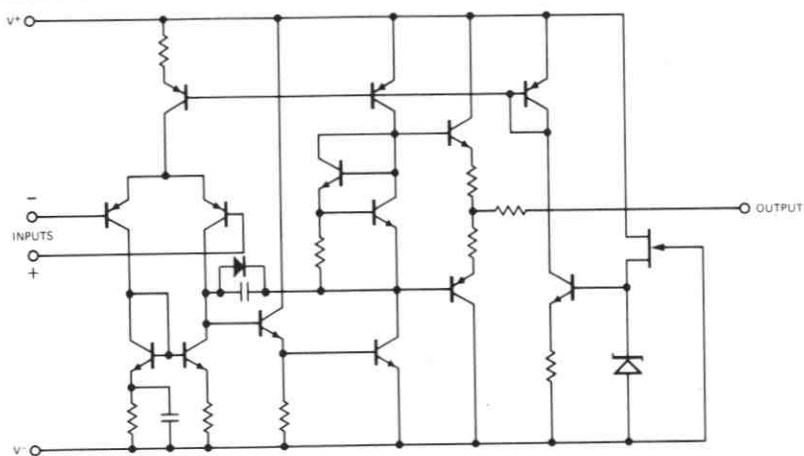
The 4558 integrated circuit is a high gain operational amplifier internally compensated and constructed on a single silicon chip using the planar epitaxial process.

Combining all of the outstanding features of the 741 with the close parameter matching and tracking of a dual device on a monolithic chip results in unique performance characteristics. Excellent channel separation allows the use of the dual device in all single 741 operational amplifier applications providing the highest possible packaging density. It is especially well suited for applications in differential-in, differential-out as well as in potentiometric amplifiers and where gain and phase matched channels are mandatory.

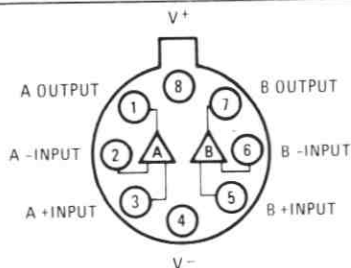
DESIGN FEATURES

- Supply Voltage ± 18 V
- Continuous Short-Circuit Protection
- No Frequency Compensation Required
- No Latch-Up
- Unity Gain Bandwidth 3 MHz
- Large Common-Mode and Differential Voltage Ranges
- Low Power Consumption
- Parameter Tracking Over Temperature Range
- Gain and Phase Match Between Amplifiers

SCHEMATIC DIAGRAM

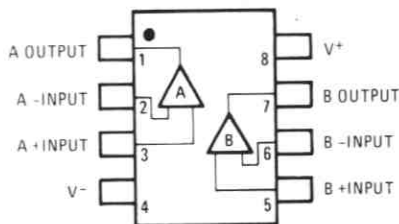


CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
RC4558T, RM4558T



NB Dual In-line
Plastic Package
(Top View)

Order Part Nos.:
RC4558NB, RV4558T

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	RM4558: $\pm 22V$ RC4558: $\pm 18V$	Operating Temperature Range	RM4558: $-55^{\circ}C$ to $+125^{\circ}C$ RV4558: $-40^{\circ}C$ to $+85^{\circ}C$ RC4558: $0^{\circ}C$ to $+70^{\circ}C$
Internal Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 60s)	$300^{\circ}C$
Differential Input Voltage	$\pm 30V$	Output Short-Circuit Duration (Note 3)	Indefinite
Input Voltage (Note 2)	$\pm 15V$		
Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$		

ELECTRICAL CHARACTERISTICS ($V_{CC} = \pm 15V$, $T_A = 25^{\circ}C$ unless otherwise specified)

PARAMETER	CONDITIONS	RM4558			RV/RC4558			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 10k\Omega$		1.0	5.0		2.0	6.0	mV
Input Offset Current			30	200		30	200	nA
Input Bias Current			200	500		200	500	nA
Input Resistance		0.3	1.0		0.3	1.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2k\Omega$ $V_{out} = \pm 10V$	50,000	200,000		20,000	100,000		
Output Voltage Swing	$R_L \geq 10k\Omega$	± 12	± 14		± 12	± 14		V
	$R_L \geq 2k\Omega$	± 10	± 13		± 10	± 13		V
Input Voltage Range		± 12	± 13		± 12	± 13		V
Common Mode Rejection Ratio	$R_S \leq 10k\Omega$	70	90		70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10k\Omega$		30	150		30	150	$\mu V/V$
Power Consumption			100	170		100	170	mW
Transient Response (unity gain)	$V_{IN} = 20mV$ $R_L = 2k\Omega$ $C_L \leq 100pF$							
Risetime			0.3			0.3		μs
Overshoot			5.0			5.0		%
Slew Rate (unity gain)	$R_L \geq 2k\Omega$		0.5			0.5		V/ μs
Channel Separation (open loop)	$f = 10kHz$ $R_S = 1k\Omega$		70			70		dB
(Gain = 100)	$f = 10kHz$ $R_S = 1k\Omega$		83			83		dB

The following specifications apply for $-55^{\circ}C \leq T_A \leq +125^{\circ}C$ for RM4558; $0^{\circ}C \leq T_A \leq +70^{\circ}C$ for RC4558; $-40^{\circ}C \leq T_A \leq +85^{\circ}C$ for RV4558

Input Offset Voltage	$R_S \leq 10k\Omega$			6.0			7.5	mV
Input Offset Current				500			300/500*	nA
Input Bias Current				1.5			.8/1.5*	nA
Large-Signal Voltage Gain	$R_L \geq 2k\Omega$ $V_{out} = \pm 10V$	25,000				15,000		
Output Voltage Swing	$R_L \geq 2k\Omega$	± 10				± 10		V
Power Consumption	$V_S = \pm 15V$ $T_A = +125^{\circ}C$ $T_A = -55^{\circ}C$		90 120	150 200		90 120	150 200	mW

MATCHING CHARACTERISTICS ($V_{CC} = \pm 15V$, $T_A = 25^{\circ}C$ unless otherwise specified)

*RV4558

PARAMETER	CONDITIONS	RM4558 TYP	RC4558 TYP	UNITS
Voltage Gain	$R_L \geq 2k\Omega$	± 5	± 1.0	dB
Input Bias Current		± 15	± 15	nA
Input Offset Current		± 7.5	± 7.5	nA
Input Offset Voltage	$R_S \geq 10k\Omega$	± 1	± 2	mV

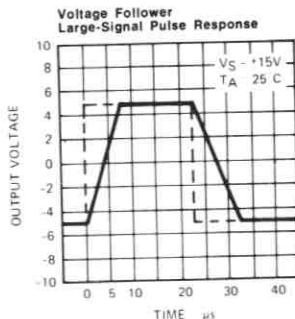
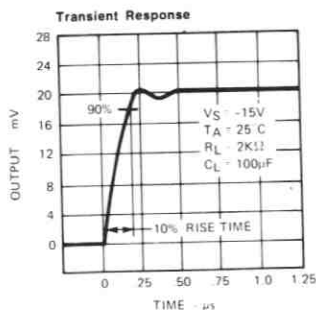
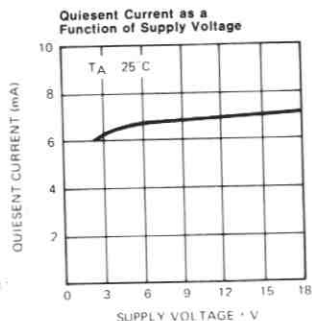
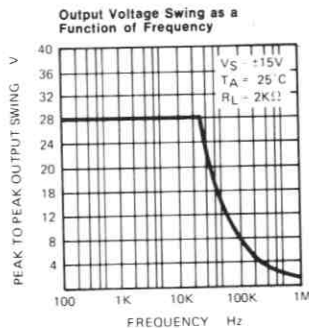
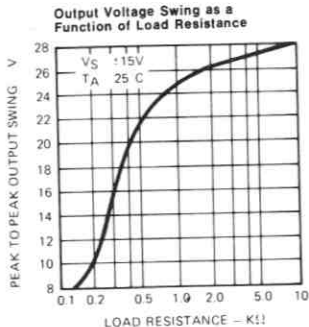
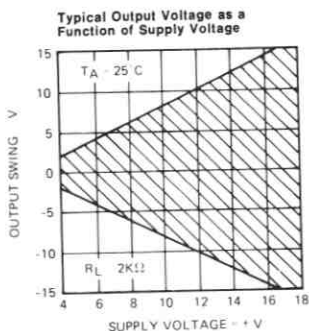
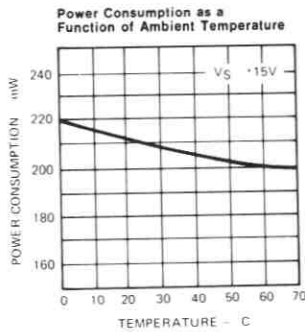
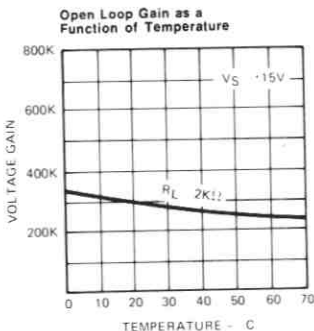
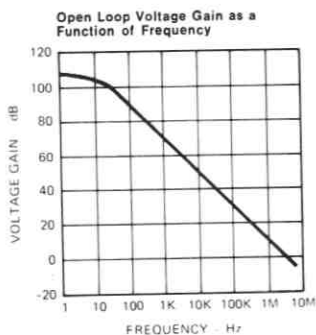
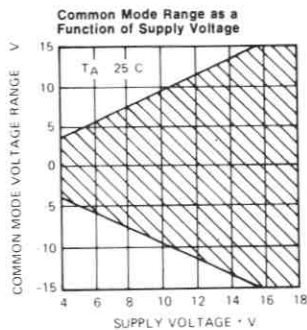
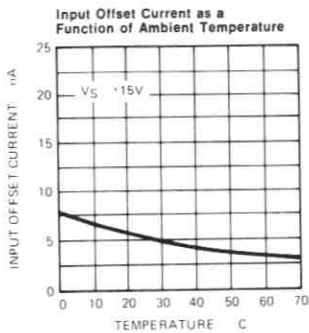
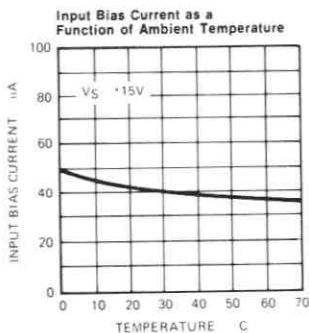
NOTE 1: Rating applies for case temperatures to $125^{\circ}C$; derate linearly at $6.5mW/^{\circ}C$ for ambient temperatures above $+75^{\circ}C$ for RM4558.

NOTE 2: For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.

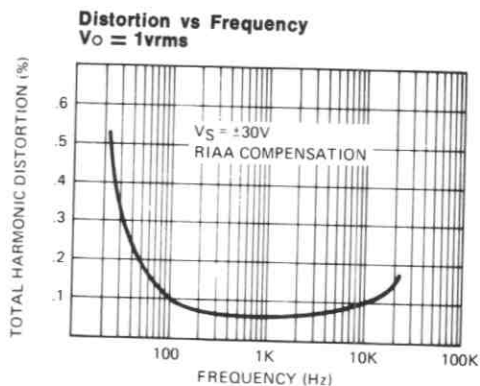
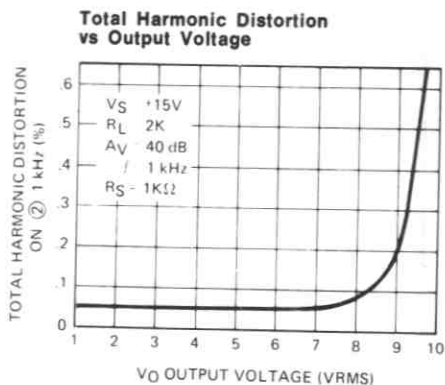
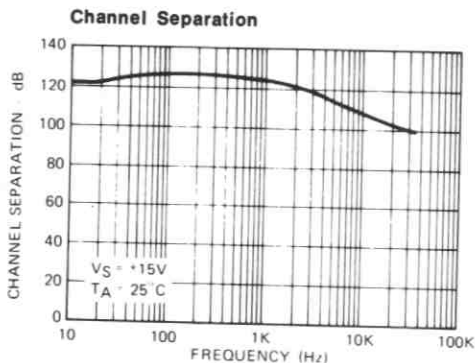
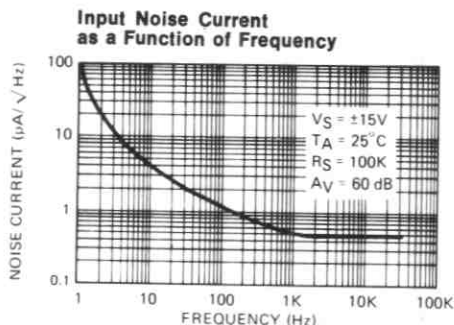
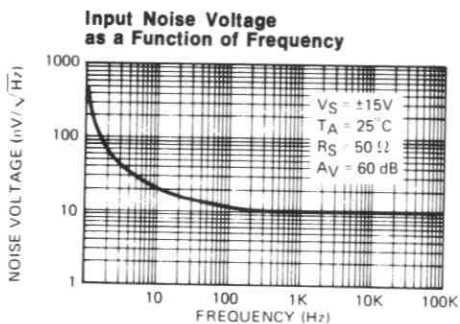
NOTE 3: Short circuit may be to ground or either supply. Rating applies to $+125^{\circ}C$ case temperature or $+75^{\circ}C$ ambient temperature for RC4558 and to $+85^{\circ}C$ ambient temperature for RV4558.



TYPICAL ELECTRICAL DATA



TYPICAL ELECTRICAL DATA



GENERAL DESCRIPTION

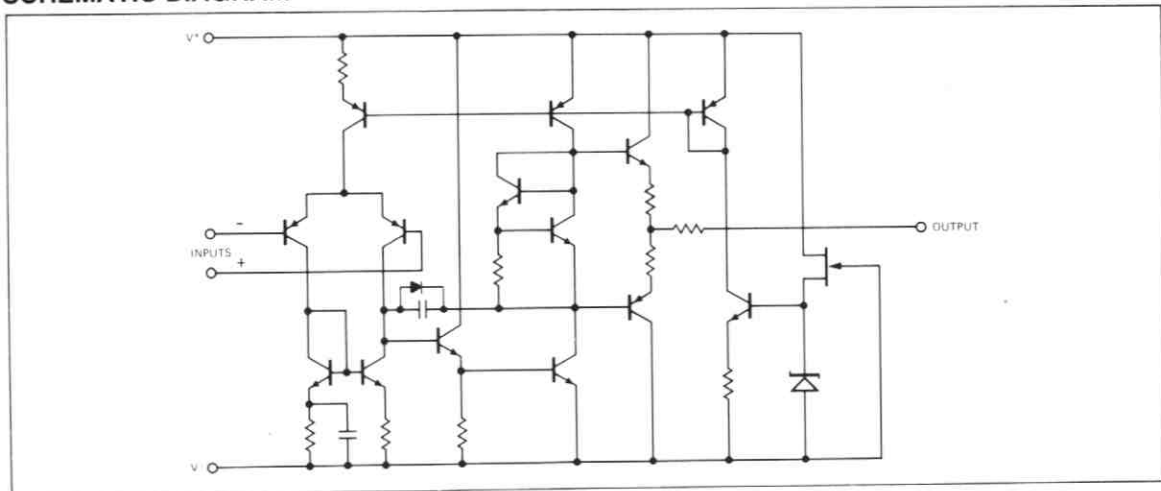
The RC4739 dual low-noise operational amplifier is fabricated on a single silicon chip using the planar epitaxial process. It was designed primarily for preamplifiers in consumer and industrial signal processing equipment. The device is pin compatible with the μ A739 and MC1303, however, compensation is internal. This permits a lowered external parts count and simplified application.

The RC4739 is available in molded dual in-line 14-pin package and operated over the commercial temperature range from 0°C to +70°C.

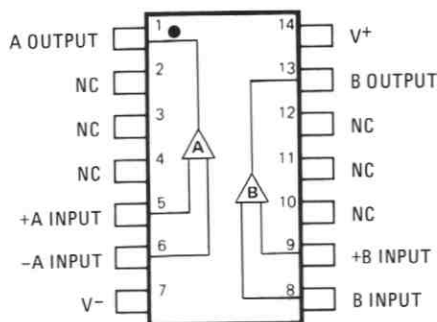
DESIGN FEATURES

- Internally Compensated Replacement for μ A739 and MC1303
- Signal-to-Noise Ratio 76 dB (RIAA 10 mV ref.)
- Channel Separation 125 dB
- Unity Gain Bandwidth 3MHz
- Output Short-Circuit Protected
- 0.1% Distortion at 8.5 V RMS Output into 2 k Ω Load

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



DB Dual In-line
Plastic Package
(Top View)

Order Part No.:
RC4739DB

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±18 V	Storage Temperature Range	-65°C to +150°C
Internal Power Dissipation (Note 1)	500 mW	Operating Temperature Range	0°C to +70°C
Differential Input Voltage	±30 V	Lead Temperature (Soldering, 60s)	300°C
Input Voltage (Note 2)	±15 V	Output Short-Circuit Duration (Note 3)	Indefinite

ELECTRICAL CHARACTERISTICS ($V_{CC} = \pm 15V$, $T_A = +25^\circ C$ unless otherwise noted.)

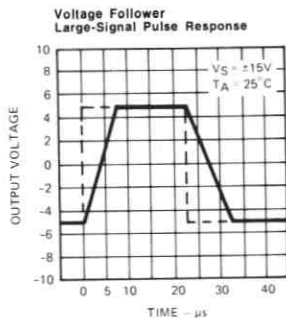
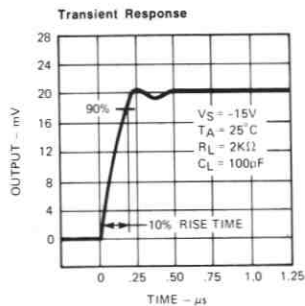
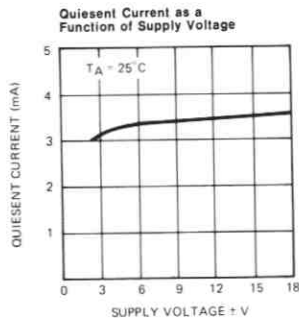
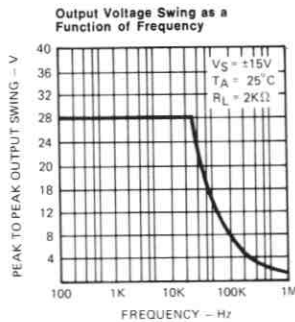
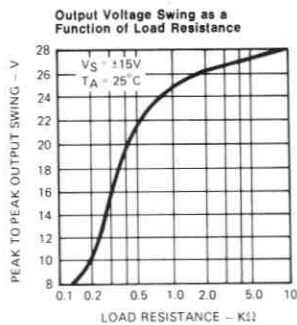
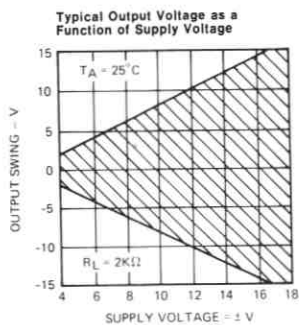
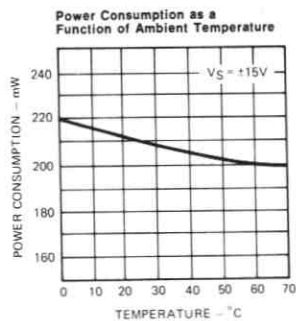
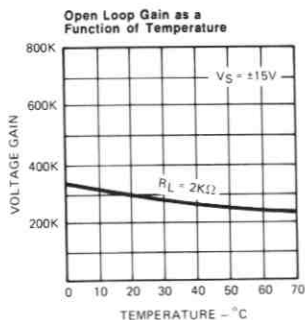
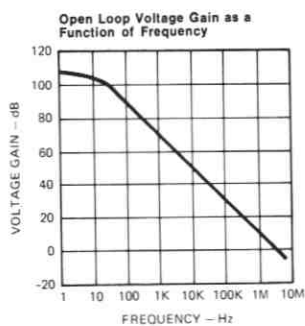
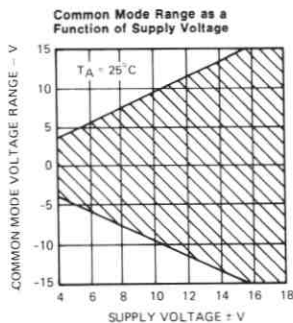
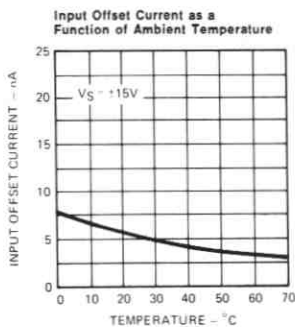
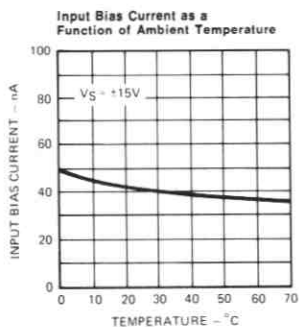
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		2.0	6.0	mV
Input Offset Current			5.0	200	nA
Input Bias Current			40	500	nA
Input Resistance		0.3	5.0		M Ω
Large-Signal Voltage Gain	$R_L \geq 2 \text{ k}\Omega$ $V_{out} = \pm 10V$	20,000	300,000		V/V
Output Voltage Swing	$R_L \geq 10 \text{ k}\Omega$	±12	±14		V
	$R_L \geq 2 \text{ k}\Omega$	±10	±13		V
Input Voltage Range		±12	±14		V
Common Mode Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	70	100		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		10	150	$\mu V/V$
Power Consumption			105	170	mW
Transient Response (unity gain) Risetime	$V_{in} = 20 \text{ mV}$ $R_L = 2 \text{ k}\Omega$ $C_L \leq 100 \text{ pF}$		0.15		μs
Transient Response (unity gain) Overshoot	$V_{in} = 20 \text{ mV}$ $R_L = 2 \text{ k}\Omega$ $C_L \leq 100 \text{ pF}$		10		%
Slew Rate (unity gain)	$R_L \geq 2 \text{ k}\Omega$		1.0		V/ μs
Broadband Noise Voltage	$BW = 10\text{-}30 \text{ KHz}$ $R_S = 1 \text{ k}\Omega$		2.5		μV_{RMS}
Channel Separation	$f = 1.0 \text{ kHz}$ $A_V = 40 \text{ dB}$ $R_S = 1 \text{ k}\Omega$		125		dB
The following specification apply for $0^\circ C \leq T_A \leq 70^\circ C$ unless otherwise specified.					
Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		3.0	7.5	mV
Input Offset Current			7.0	300	nA
Input Bias Current			50	800	nA
Large-Signal Voltage Gain	$R_L \geq 2 \text{ k}\Omega$ $V_{out} = \pm 10V$	15,000	200,000		
Output Voltage Swing	$R_L \geq 2 \text{ k}\Omega$	±10	±13		V
Power Consumption	$V_S = \pm 15V$				
	$T_A = 70^\circ C$		100	150	mW
	$T_A = 0^\circ C$		110	220	mW

NOTES:

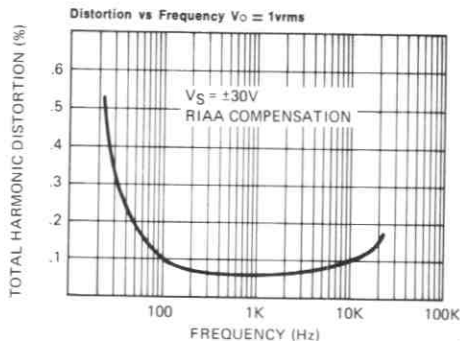
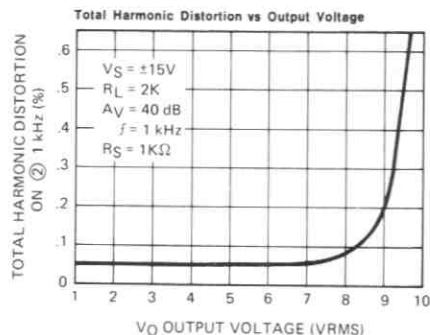
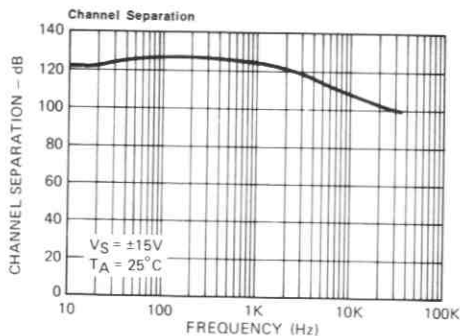
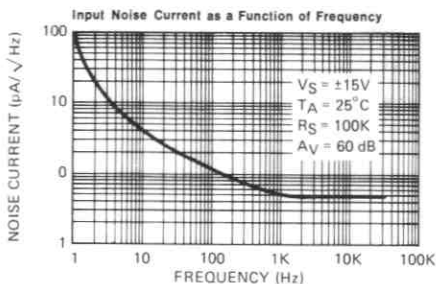
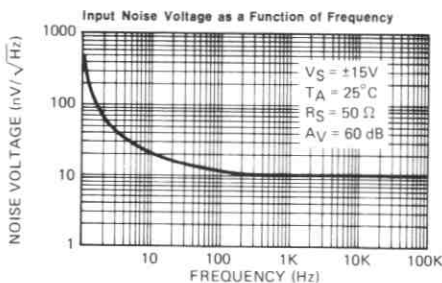
- Rating applies for ambient temperatures below +70°C.
- For supply voltages less than ±15V, the absolute maximum input voltage is equal to the supply voltage.
- Short-circuit may be to ground, typically 45 mA. Rating applies to +125°C case temperature or +75°C ambient temperature.
- Refer to RC 4558 data sheet for RC 4739 typical characteristic curves.



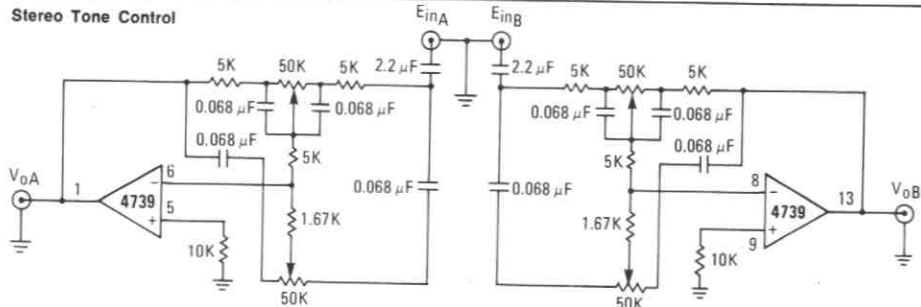
TYPICAL ELECTRICAL DATA



TYPICAL ELECTRICAL DATA



TYPICAL APPLICATIONS



SECTION 2

Wideband Amplifiers

2

CONTENTS

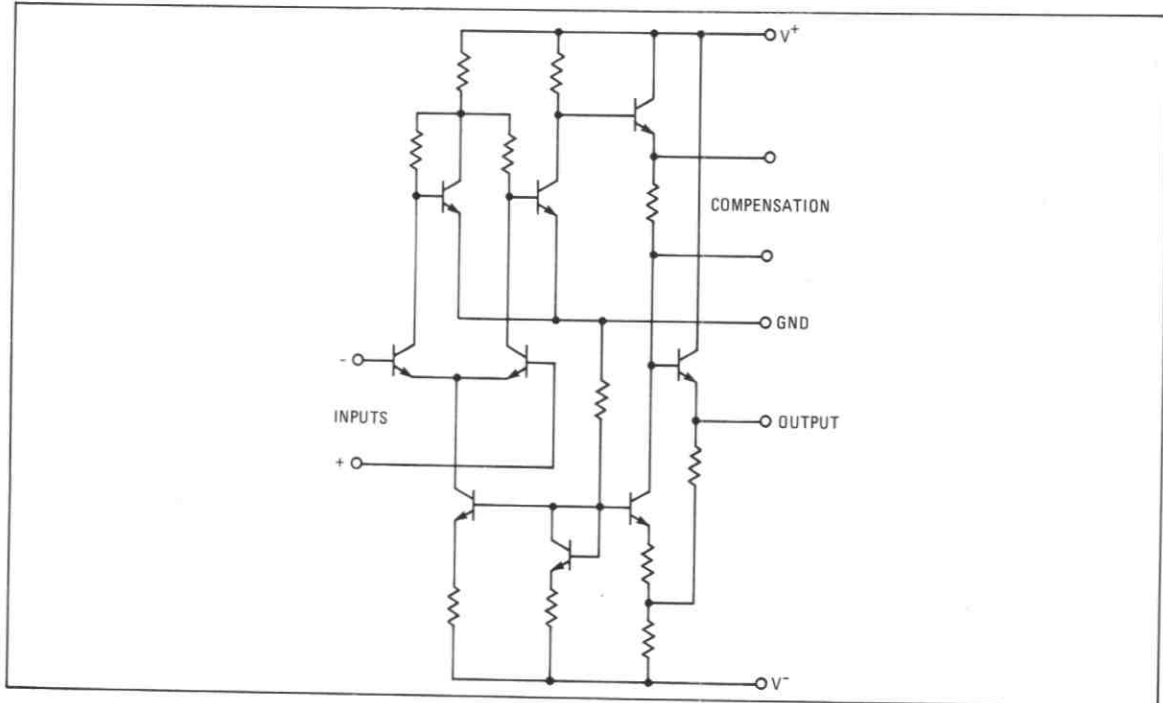
702 Wideband DC Amplifiers	2-2
733 Differential Video Amplifiers	2-5

GENERAL DESCRIPTION

The RM702 and RC702 are complete DC amplifiers constructed on a single silicon chip, using the planar epitaxial process. They are intended for use as operational amplifiers in miniaturized analog computers, as precision instrumentation amplifiers, or in other applications requiring a feedback amplifier useful from DC to 30MHz.

The RM702 operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC702 operates over a range of 0°C to $+70^{\circ}\text{C}$.

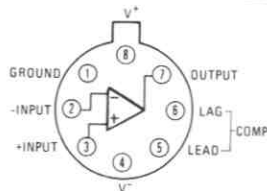
SCHEMATIC DIAGRAM



DESIGN FEATURES

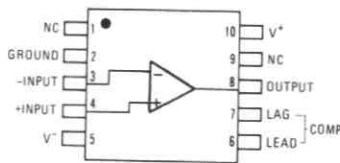
- Low Offset Voltage
- Low Offset Voltage Drift
- Wide Bandwidth 30MHz Typical
- High Slew Rate $5.0\text{V}/\mu\text{s}$ Typical

CONNECTION INFORMATION



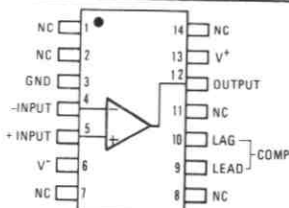
TE Metal Can Package
(Top View)

Order Part Nos.:
RM702T, RC702T



Q
Flat Package
(Top View)

Order Part No.:
RM702Q



DC Dual In-line
Package
(Top View)

Order Part Nos.:
RM702DC, RC702DC

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±8.0V	Operating Temperature Range	
Differential Input Voltage	±5.0V	RM733	-55°C to +125°C
Common Mode Input Voltage	±6.0V	RC733	0°C to +70°C
Output Current	10mA	Storage Temperature Range	-65°C to +150°C
Internal Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 60s)	300°C

ELECTRICAL CHARACTERISTICS RC702 (T_A = 25°C unless otherwise specified)

PARAMETER	CONDITIONS	V ⁺ = 12.0V, V ⁻ = -6.0V			V ⁺ = 6.0V, V ⁻ = -3.0V			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	R _S ≤ 2kΩ		1.5	5.0		1.7	6.0	mV
Input Offset Current			0.5	2.0		0.3	2.0	μA
Input Bias Current			2.5	7.5		1.5	5.0	μA
Input Resistance		10	32		16	55		kΩ
Input Voltage Range		-4.0		+0.5	-1.5		+0.5	V
Common Mode Rejection Ratio	R _S ≤ 2kΩ, f ≤ 1kHz	70	92		70	92		dB
Large Signal Voltage Gain	R _L ≥ 100kΩ, V _{OUT} = ±5.0V	2000	3400	6000				
	R _L ≥ 100kΩ, V _{OUT} = ±2.5V				500	800	1500	
Output Resistance			200	500		300	800	Ω
Supply Current	V _{OUT} = 0		5.0	6.7		2.1	3.3	mA
Power Consumption	V _{OUT} = 0		90	120		19	30	mW
Transient Response (unity-gain)	C ₁ = 0.01μF, R ₁ = 20Ω, R _L ≤ 100kΩ, V _{IN} = 10mV	Risetime		25	120			ns
		Overshoot		10	50			%
Transient Response (x100 gain)	C ₃ = 50pF, R _L ≥ 100kΩ, V _{IN} = 1mV	Risetime		10	30			ns
		Overshoot		20	40			%
The following specifications apply for 0°C ≤ T _A ≤ +70°C.								
Input Offset Voltage	R _S ≤ 2kΩ			6.5		7.5		mV
Average Temperature Coefficient of Input Offset Voltage	R _S = 50Ω, T _A = +70°C to 0°C		5.0	20		7.5	25	μV/°C
Input Offset Current				2.5		2.5		μA
Average Temperature Coefficient of Input Offset Current	T _A = 25°C to +70°C		4.0	10		3.0	8.0	nA/°C
	T _A = 25°C to 0°C		6.0	20		5.5	18	nA/°C
Input Bias Current	T _A = 0°C		4.0	12		2.7	8	μA
Input Resistance		6.0	18		9.0	27		kΩ
Common Mode Rejection Ratio	R _S ≤ 2kΩ, f ≤ 1kHz	65	86		65	86		dB
Supply Voltage Rejection Ratio	V ⁺ = 12V, V ⁻ = 6V to V ⁺ = 6V, V ⁻ = 3V, R _S ≤ 2kΩ		90	300		90	300	μV/V
Large Signal Voltage Gain	R _L ≥ 100kΩ, V _{OUT} = ±5.0V	1500		7000				
	R _L ≥ 100kΩ, V _{OUT} = ±2.5V				400		1750	
Output Voltage Swing	R _L ≥ 100kΩ	±5.0	±5.3		±2.5	±2.7		V
	R _L ≥ 10kΩ	±3.5	±4.0		±1.5	±2.0		V
Supply Current	V _{OUT} = 0		5.0	7.0		2.1	3.9	mA
Power Consumption	V _{OUT} = 0		90	125		19	35	mW

ELECTRICAL CHARACTERISTICS RM702 ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	CONDITIONS	$V^+ = 12.0\text{V}, V^- = -6.0\text{V}$			$V^+ = 6.0\text{V}, V^- = -3.0\text{V}$			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	$R_S \leq 2\text{k}\Omega$		0.5	2.0		0.7	3.0	mV
Input Offset Current			180	500		120	500	nA
Input Bias Current			2.0	5.0		1.2	3.5	μA
Input Resistance		16	40		22	67		$\text{k}\Omega$
Input Voltage Range		-4.0		+0.5	-1.5		+0.5	V
Common Mode Rejection Ratio	$R_S \leq 2\text{k}\Omega, f \leq 1\text{kHz}$	80	100		80	100		dB
Large Signal Voltage Gain	$R_L \geq 100\text{k}\Omega, V_{\text{OUT}} = \pm 5.0\text{V}$ $R_L \geq 100\text{k}\Omega, V_{\text{OUT}} = \pm 2.5\text{V}$	2500	3600	6000	600	900	1500	
Output Resistance			200	500		300	700	Ω
Supply Current	$V_{\text{OUT}} = 0$		5.0	6.7		2.1	3.3	mA
Power Consumption	$V_{\text{OUT}} = 0$		90	120		19	30	mW
Transient Response (unity-gain)	Risetime	$C_1 = 0.01\mu\text{F}, R_1 = 20\Omega,$ $R_L \geq 100\text{k}\Omega, V_{\text{IN}} = 10\text{mV}$	25	120				ns
	Overshoot		10	50				%
Transient Response (x100 gain)	Risetime	$C_3 = 50\text{pF},$ $R_L \geq 100\text{k}\Omega,$ $V_{\text{IN}} = 1\text{mV}$	10	30				ns
	Overshoot		20	40				%

The following specifications apply for $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$.

Input Offset Voltage	$R_S \leq 2\text{k}\Omega$			3.0		4.0		mV
Average Temperature Coefficient of Input Offset Voltage	$R_S = 50\Omega, T_A = 25^\circ\text{C}$ to $+125^\circ\text{C}$		2.5	10		3.5	15	$\mu\text{V}/^\circ\text{C}$
	$R_S = 50\Omega, T_A = 25^\circ\text{C}$ to -55°C		2.0	10		3.0	15	$\mu\text{V}/^\circ\text{C}$
Input Offset Current	$T_A = +125^\circ\text{C}$		80	500		50	500	nA
	$T_A = -55^\circ\text{C}$		400	1500		280	1500	nA
Average Temperature Coefficient of Input Offset Current	$T_A = 25^\circ\text{C}$ to $+125^\circ\text{C}$		1.0	5.0		0.7	4.0	$\text{nA}/^\circ\text{C}$
	$T_A = 25^\circ\text{C}$ to -55°C		3.0	16		2.0	13	$\text{nA}/^\circ\text{C}$
Input Bias Current	$T_A = -55^\circ\text{C}$		4.3	10		2.6	7.5	μA
Input Resistance		6.0			8.0			$\text{k}\Omega$
Common Mode Rejection Ratio	$R_S \leq 2\text{k}\Omega, f \leq 1\text{kHz}$	70	95		70	95		dB
Supply Voltage Rejection Ratio	$V^+ = 12\text{V}, V^- = -6\text{V}$ to $V^+ = 6\text{V}, V^- = -3\text{V}$ $R_S \leq 2\text{k}\Omega$		75	200		75	200	$\mu\text{V}/\text{V}$
Large Signal Voltage Gain	$R_L \geq 100\text{k}\Omega, V_{\text{OUT}} = \pm 5.0\text{V}$	2000		7000				
	$R_L \geq 100\text{k}\Omega, V_{\text{OUT}} = \pm 2.5\text{V}$				500		1750	
Output Voltage Swing	$R_L \geq 100\text{k}\Omega$	± 5.0	± 5.3		± 2.5	± 2.7		V
	$R_L \geq 10\text{k}\Omega$	± 3.5	± 4.0		± 1.5	± 2.0		V
Supply Current	$T_A = +125^\circ\text{C}, V_{\text{OUT}} = 0$		4.4	6.7		1.7	3.3	mA
	$T_A = -55^\circ\text{C}, V_{\text{OUT}} = 0$		5.0	7.5		2.1	3.9	mA
Power Consumption	$T_A = +125^\circ\text{C}, V_{\text{OUT}} = 0$		80	120		15	30	mW
	$T_A = -55^\circ\text{C}, V_{\text{OUT}} = 0$		90	135		19	35	mW



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GENERAL DESCRIPTION

The RM733/RC733 integrated circuit is a monolithic video amplifier with differential inputs and differential outputs. It offers three selectable voltage gains of 10, 100, or 400 and adjustable gain of 10 to 400 using a single resistor. No external frequency compensation is necessary for any gain option. The circuit and process designs are optimized to give a stable gain ($\pm 10\%$), wide bandwidth (DC to 120MHz), high input resistance ($250k\Omega$), and low phase shift that is linear up to 10MHz (2° per MHz).

The RM733/RC733 is designed for use as a read head amplifier for magnetic tape, drum, or disc memories using phase of NRZ encoding. It will also function as a preamplifier for high speed film or plated wire memory systems; as a video or pulse amplifier, pulse height detector, peak detector.

Applications for the RM733/RC733 include bulk computer

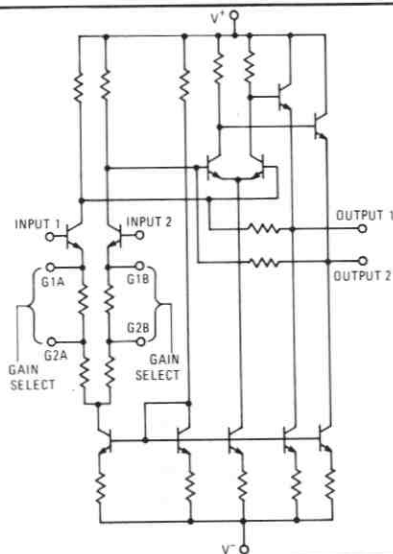
memory systems, very high speed random access memory systems, communications systems, nuclear event instrumentation, frequency counters, and other systems where the specific design features of the RM733/RC733 are required.

The RM733 video amplifier will operate over the complete military temperature range from -55°C to $+125^\circ\text{C}$ while the commercial version, the RC733, operates from 0°C to $+70^\circ\text{C}$.

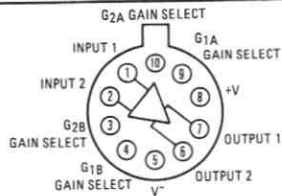
DESIGN FEATURES

- Wide Bandwidth DC to 120MHz
- Low Linear Phase Shift $2\tau/\text{MHz}$ to 10MHz
- Selectable Voltage Gains 10, 100, or 400
- Excellent Pulse Characteristics
- High Input Resistance $250k\Omega$

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



NOTE: Pin 5 connected to case.

**TF Metal Can
Package
(Top View)**

Order Part Nos.:
RM733T
RC733T

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±8.0V	Operating Temperature Range	
Differential Input Voltage	±5.0V	RM733	-55°C to +125°C
Common Mode Input Voltage	±6.0V	RC733	0°C to +70°C
Input Current	10mA	Storage Temperature Range	-65°C to +150°C
Internal Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 60s)	300°C

ELECTRICAL CHARACTERISTICS (Note 2)

PARAMETER	(Note 3)	CONDITIONS	RM733			RC733			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
Differential Voltage Gain	Gain 1		300	400	500	250	400	600	
	Gain 2		90	100	110	80	100	120	
	Gain 3		9.0	10	11	8.0	10	12	
Bandwidth	Gain 1	$R_S = 50\Omega$		40			40		MHz
	Gain 2			90		90			
	Gain 3			120		120			
Risetime	Gain 1	$R_S = 50\Omega, V_{OUT} = 1V_{PP}$		10.5			10.5		ns
	Gain 2			4.5	10	4.5	12		
	Gain 3			2.5		2.5			
Propagation Delay	Gain 1	$R_S = 50\Omega, V_{OUT} = 1V_{PP}$		7.5			7.5		ns
	Gain 2			6.0	10	6.0	10		
	Gain 3			3.6		3.6			
Input Resistance	Gain 1			4.0		4.0		k Ω	
	Gain 2		20	30	10	30			
	Gain 3			250		250			
Input Capacitance		Gain 2		2.0		2.0		pF	
Input Offset Current				0.4	3.0	0.4	5.0	μ A	
Input Bias Current				9.0	20	9.0	30	μ A	
Input Noise Voltage		$R_S = 50\Omega, BW = 1kHz \text{ to } 10MHz$		12		12		μ Vrms	
Input Voltage Range			±1.0			±1.0		V	
Common Mode Rejection Ratio	Gain 2	$V_{CM} = \pm 1V, R \leq 100kHz$	60	86		60	86		dB
		$V_{CM} = \pm 1V, f = 5MHz$		60		60			
Supply Voltage Rejection Ratio	Gain 2	$\Delta V_S = \pm 0.5V$	50	70		50	70		dB
Output Offset Voltage	Gain 1			0.6	1.5		0.6	1.5	V
	Gain 2			0.35	1.0		0.35	1.5	
	Gain 3								
Output Common Mode Voltage			2.4	2.9	3.4	2.4	2.9	3.4	V
Output Voltage Swing			3.0	4.0		3.0	4.0		V _{PP}
Output Sink Current			2.5	3.6		2.5	3.6		mA
Output Resistance				20		20			Ω
Power Supply Current				18	24		18	24	mA

NOTES:

- For RM733 the rating applies for case temperature to +125°C; derate linearly at 6.5 mW/°C for ambient temperature above 75°C. For RC733, the rating applies for ambient temperatures to 70°C.
- $V_S = \pm 6.0V$; $T_A = 25^\circ C$ unless otherwise noted.
- Gain 1: G1A and G1B connected together; Gain 2: G2A and G2B connected together; Gain 3: Gain select pins open.



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ELECTRICAL CHARACTERISTICS(The following specifications apply for $-55^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$ for the RM733 and $0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$ for the RC733, $V_S = \pm 6.0\text{V}$)

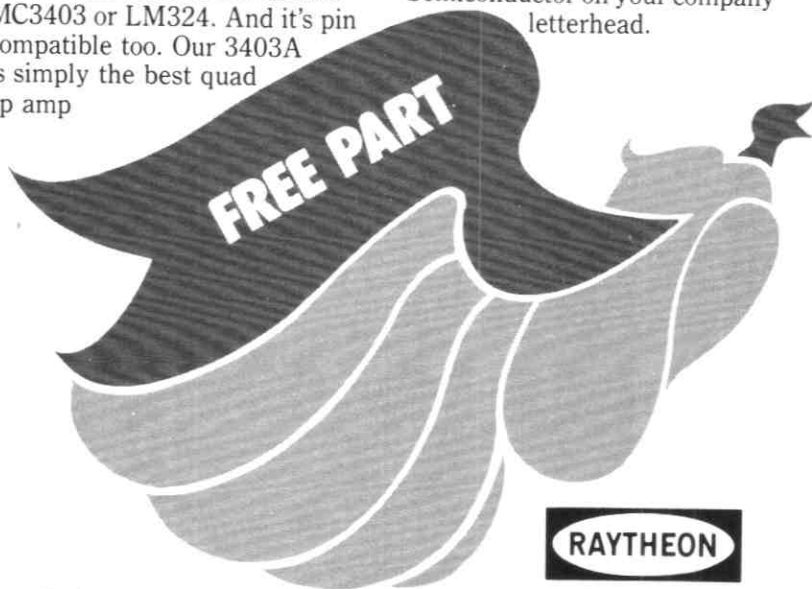
PARAMETER	CONDITIONS	LM733			LM733C			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Differential Voltage Gain								
Gain 1		200		600	250		600	
Gain 2		80		120	80		120	
Gain 3		8.0		12.0	8.0		12.0	
Input Resistance Gain 2		8			8			k Ω
Input Offset Current				5			6	μA
Input Bias Current				40			40	μA
Input Voltage Range		± 1			± 1			V
Common-Mode Rejection Ratio Gain 2		50			50			dB
Supply Voltage Rejection Ratio Gain 2		50			50			db
Output Offset Voltage								
Gain 1				1.5			1.5	V
Gain 2 and 3				1.2			1.5	V
Output Voltage Swing		2.5			2.8			V p-p
Output Sink Current		2.2			2.5			mA
Power Supply Current				27			27	mA

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RAYTHEON SEMICONDUCTOR

SECTION 3

Voltage Regulators

CONTENTS

104, 204, 304 Precision Negative Voltage Regulators	3-2
105, 205, 305/305A Positive Voltage Regulators	3-4
109, 209, 309 Monolithic 5-Volt Regulators	3-7
723 Precision Voltage Regulators	3-9
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4195 Fixed ± 15 -Volt Dual-Tracking Voltage Regulators	3-14

GENERAL DESCRIPTION

The LM104, LM204, and LM304 are precision voltage regulators which provide programmable output voltage levels. With an external resistor the voltage levels can be programmed from 40V down to 0V.

These devices are primarily designed for systems requiring regulated negative voltages which have a common ground with the unregulated supply. They are complements of the LM105/LM305 positive regulators.

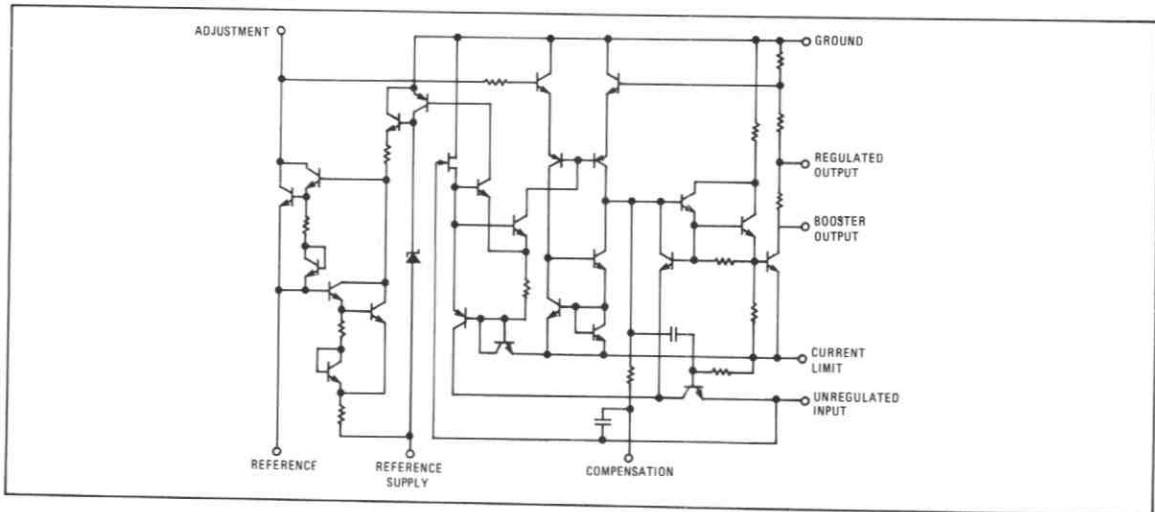
The LM104 series can also be used as switching or current regulators, or in a variety of control applications. Both constant and foldback current limiting are available.

The LM104 operates over the military temperature range of -55°C to $+125^{\circ}\text{C}$. The LM304 is the commercial version which operates from 0°C to $+70^{\circ}\text{C}$. The LM204 is the same as the LM104 except its performance is guaranteed from -25°C to $+85^{\circ}\text{C}$.

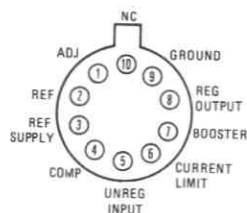
DESIGN FEATURES

- No-Load to Full-Load Regulation 1mV
- Line Regulation 0.01%/V
- Ripple Rejection 0.2mV/V
- Temperature Stability 0.3% from -55°C to $+125^{\circ}\text{C}$

SCHEMATIC DIAGRAM



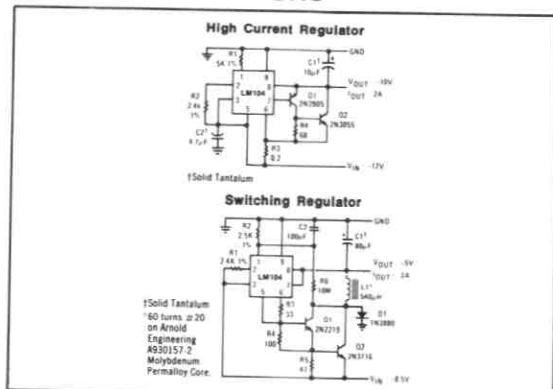
CONNECTION INFORMATION



TF Package
(Top View)

Order Part Nos.:
LM104H, LM204H,
LM304H

TYPICAL APPLICATIONS



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ABSOLUTE MAXIMUM RATINGS

Input Voltage	LM104/LM204: 50V LM304: 40V	Operating Temperature Range	LM104: -55°C to +125°C LM204: -25°C to +85°C LM304: 0°C to +70°C
Input-Output Voltage Differential	LM104/LM204: 50V LM304: 40V	Storage Temperature Range	-65°C to +150°C
Power Dissipation (Note 1)	500mW	Lead Temperature (Soldering, 10s)	300°C

ELECTRICAL CHARACTERISTICS (Note 2)

PARAMETER	CONDITIONS	LM104/LM204			LM304			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Voltage Range		-50		-8	-40		-8	V
Output Voltage Range		-40		-0.015	-30		-0.035	V
Output-Input Voltage Differential (Note 3)	$I_O = 20\text{mA}$	2.0		50	2.0		40	V
	$I_O = 5\text{mA}$	0.5		50	0.5		40	V
Load Regulation (Note 4)	$0 \leq I_O \leq 20\text{mA}$ $R_{SC} = 15\Omega$		1	5		1	5	mV
Line Regulation (Note 5)	$V_{OUT} \leq -5\text{V}$ $\Delta V_{IN} = 0.1 V_{IN}$		0.056	0.1		0.056	0.1	%
Ripple Rejection	$C_{19} = 10\mu\text{F}$, $f = 120\text{Hz}$ $V_{IN} < -15\text{V}$		0.2	0.5		0.2	0.5	mV/V
	$-7\text{V} \geq V_{IN} \geq -15\text{V}$		0.5	1.0		0.5	1.0	mV/V
Output Voltage Scale Factor	$R_{23} = 2.4\text{k}$	1.8	2.0	2.2	1.8	2.0	2.2	V/k Ω
Temperature Stability	$V_O \leq -1\text{V}$		0.3	1.0				%
	$V_O \leq -1\text{V}$, $0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$					0.3	1.0	
Output Noise Voltage	$10\text{Hz} \leq f \leq 10\text{kHz}$ $V_O \leq -5\text{V}$, $C_{19} = 0$		0.007			0.007		%
	$C_{19} = 10\mu\text{F}$		15			15		μV
Standby Current Drain	$I_L = 5\text{mA}$, $V_O = 0$		1.7	2.5		1.7	2.5	mA
	$V_O = -40\text{V}$		3.6	5.0				
	$V_O = -30\text{V}$					3.6	5.0	
Long Term Stability	$V_O \leq -1\text{V}$		0.1	1.0		0.1	1.0	%

NOTES:

- The maximum junction temperature of the LM104 is 150°C and the LM304 +85°C. For operating at elevated temperatures, devices in the TO-5 package must be derated based on a thermal resistance of +150°C/W, junction to ambient, or +45°C, junction to case. For the flat package, the derating is based on a thermal resistance of +185°C/W when mounted on a 1/16-inch-thick epoxy glass board with ten, 0.03-inch-wide, 2-ounce copper conductors.
- These specifications apply for junction temperatures between -55°C and +150°C (between 0°C and +85°C for the LM304) and for input and output voltages within the ranges given, unless otherwise specified. The load and line regulation specifications are for constant junction temperature. Temperature drift effects must be taken into

account separately when the unit is operating under conditions of high dissipation.

- When external booster transistors are used, the minimum output-input voltage differential is increased, in the worst case, by approximately 1V.
- The output currents given, as well as the load regulation, can be increased by the addition of external transistors. The improvement factor will be roughly equal to the composite current gain of the added transistors.
- With zero output, the dc line regulation is determined from the ripple rejection. Hence, with output voltages between 0V and -5V, a dc output variation, determined from the ripple rejection, must be added to find the worst case line regulation.

GENERAL DESCRIPTION

The LM105 series are positive voltage regulators, each constructed on a silicon chip by the planar epitaxial process.

They are similar to the LM100, except for an extra gain stage to improve regulation. In both linear and switching regulator circuits with outputs greater than 4.5V, these devices are direct plug-in replacements for the LM100.

The LM105 military version operates from -55°C to $+125^{\circ}\text{C}$. The LM305/LM305A are commercial versions which operate from 0°C to $+70^{\circ}\text{C}$.

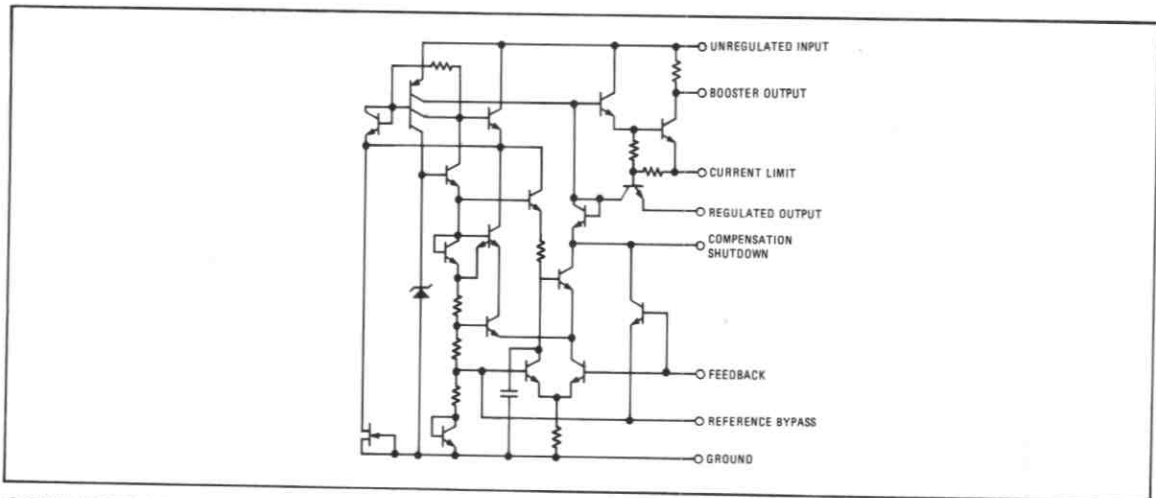
These regulators feature fast response to load and line transients, freedom from oscillations with varying resistive and reactive loads, and reliable starts on any load within ratings.

The LM205 is the same as the LM105 except its performance is guaranteed from -25°C to $+85^{\circ}\text{C}$.

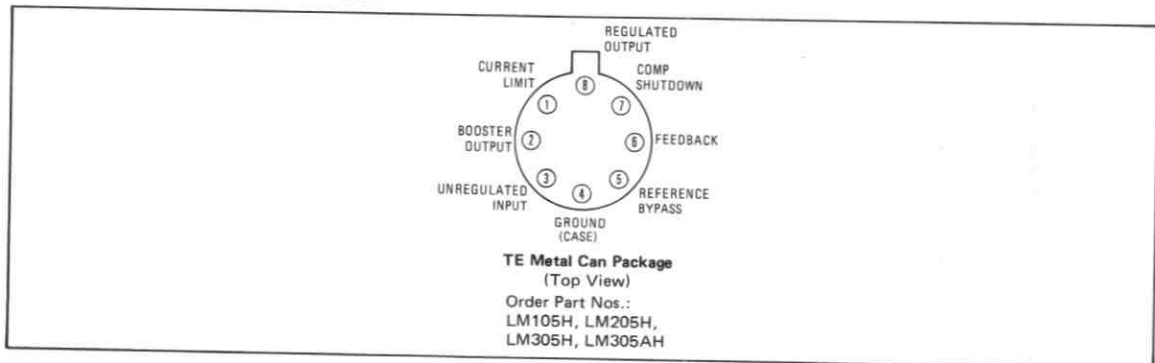
DESIGN FEATURES

- Output Voltage Adjustable from 4.5V to 40V
- Output Currents in Excess of 10A by Adding External Transistors
- Load Regulation Better Than 0.1%, Full Load With Current Limiting
- DC Line Regulation Guaranteed at 0.03%/V
- Ripple Rejection of 0.01%/V
- 45mA Output Current Without External Pass Transistor

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



Positive Voltage Regulators

ABSOLUTE MAXIMUM RATINGS

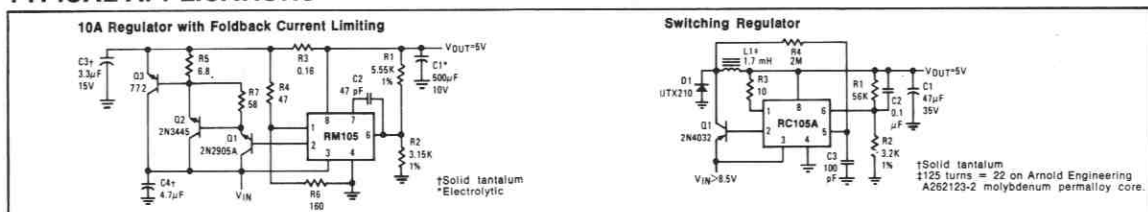
Input Voltage	LM105, LM205, LM305A: 50V LM305: 40V	Operating Temperature Range	LM105: -55°C to +150°C LM205: -25°C to +85°C LM305/305A: 0°C to +70°C
Input-Output Voltage Differential	40V	Storage Temperature Range	-65°C to +150°C
Power Dissipation (Note 1)	LM105, LM205, LM305A: 800mW LM305: 500mW	Lead Temperature (Soldering, 10s)	300°C

ELECTRICAL CHARACTERISTICS (Note 2)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
Input Voltage Range	LM105/205/305A	8.5		50	V	
	LM305	8.5		40		
Output Voltage Range	LM105/205/305A	4.5		40	V	
	LM305	4.5		30		
Output-Input Voltage Differential		3.0		30	V	
Load Regulation (Note 3)	LM105	$0 \leq I_O \leq 12\text{mA}$			%	
		$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}$		0.02		0.05
		$R_{SC} = 10\Omega, T_A = 125^\circ\text{C}$		0.03		0.1
		$R_{SC} = 10\Omega, T_A = -55^\circ\text{C}$		0.03		0.1
	LM205	$0 \leq I_O \leq 12\text{mA}$				%
		$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}$		0.02	0.05	
		$R_{SC} = 10\Omega, T_A = 85^\circ\text{C}$		0.03	0.1	
		$R_{SC} = 10\Omega, T_A = -25^\circ\text{C}$		0.03	0.1	
	LM305A	$0 \leq I_O \leq 45\text{mA}$				%
		$R_{SC} = 0\Omega, T_A = 25^\circ\text{C}$		0.02	0.2	
		$R_{SC} = 0\Omega, T_A = 70^\circ\text{C}$		0.03	0.4	
		$R_{SC} = 0\Omega, T_A = 0^\circ\text{C}$		0.03	0.4	
LM305	$0 \leq I_O \leq 12\text{mA}$				%	
	$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}$		0.02	0.05		
	$R_{SC} = 15\Omega, T_A = 70^\circ\text{C}$		0.03	0.1		
	$R_{SC} = 10\Omega, T_A = 0^\circ\text{C}$		0.03	0.1		
Line Regulation	$V_{IN} - V_{OUT} \leq 5\text{V}$		0.025	0.06	% / V	
	$V_{IN} - V_{OUT} > 5\text{V}$		0.015	0.03		
Ripple Rejection	$C_{REF} = 10\mu\text{F}, F = 120\text{Hz}$		0.003	0.01	% / V	
Temperature Stability	LM105	$-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$	0.3	1.0	%	
	LM205	$-25^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$	0.3	1.0		
	LM305/LM305A	$0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$	0.3	1.0		
Current Limit Sense Voltage (Note 4)	$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}, V_{OUT} = 0\text{V}$	225	300	375	mV	
Feedback Sense Voltage	LM105/205/305	1.63	1.7	1.81	V	
	LM305A	1.55	1.7	1.85		
Output Noise Voltage	$10\text{Hz} \leq f \leq 10\text{kHz}$				% / V	
	$C_{REF} = 0$		0.005			
	$C_{REF} > 0.1\mu\text{F}$		0.002			
Standby Current Drain	LM305	$V_{IN} = 40\text{V}$	0.8	2.0	mA	
	LM105/205/305A	$V_{IN} = 50\text{V}$	0.8	2.0		
Long Term Stability			0.1	1.0	%	

See Notes on following page.

TYPICAL APPLICATIONS



ELECTRICAL CHARACTERISTICS (Note 2)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
Input Voltage Range	LM105/205/305A		8.5		50	V
	LM305		8.5		40	
Output Voltage Range	LM105/205/305A		4.5		40	V
	LM305		4.5		30	
Output-Input Voltage Differential			3.0		30	V
Load Regulation (Note 3)	LM105	$0 \leq I_O \leq 12\text{mA}$				%
		$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}$		0.02	0.05	
		$R_{SC} = 10\Omega, T_A = 125^\circ\text{C}$		0.03	0.1	
		$R_{SC} = 10\Omega, T_A = -55^\circ\text{C}$		0.03	0.1	
	LM205	$0 \leq I_O \leq 12\text{mA}$				%
		$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}$		0.02	0.05	
		$R_{SC} = 10\Omega, T_A = 85^\circ\text{C}$		0.03	0.1	
		$R_{SC} = 10\Omega, T_A = -25^\circ\text{C}$		0.03	0.1	
	LM305A	$0 \leq I_O \leq 45\text{mA}$				%
		$R_{SC} = 0\Omega, T_A = 25^\circ\text{C}$		0.02	0.2	
		$R_{SC} = 0\Omega, T_A = 70^\circ\text{C}$		0.03	0.4	
	LM305	$0 \leq I_O \leq 12\text{mA}$				%
		$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}$		0.02	0.05	
		$R_{SC} = 15\Omega, T_A = 70^\circ\text{C}$		0.03	0.1	
		$R_{SC} = 10\Omega, T_A = 0^\circ\text{C}$		0.03	0.1	
	Line Regulation	$V_{IN} - V_{OUT} \leq 5\text{V}$			0.025	0.06
$V_{IN} - V_{OUT} > 5\text{V}$			0.015	0.03		
Ripple Rejection		$C_{REF} = 10\mu\text{F}, F = 120\text{Hz}$		0.003	0.01	% / V
Temperature Stability	LM105	$-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$		0.3	1.0	%
	LM205	$-25^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$		0.3	1.0	
	LM305/LM305A	$0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$		0.3	1.0	
Current Limit Sense Voltage (Note 4)		$R_{SC} = 10\Omega, T_A = 25^\circ\text{C}$ $V_{OUT} = 0\text{V}$	225	300	375	mV
Feedback Sense Voltage	LM105/205/305		1.63	1.7	1.81	V
	LM305A		1.55	1.7	1.85	
Output Noise Voltage	$10\text{Hz} \leq f \leq 10\text{kHz}$					%
	$C_{REF} = 0$			0.005		
	$C_{REF} > 0.1\mu\text{F}$			0.002		
Standby Current Drain	LM305	$V_{IN} = 40\text{V}$		0.8	2.0	mA
	LM105/205/305A	$V_{IN} = 50\text{V}$		0.8	2.0	
Long Term Stability				0.1	1.0	%

NOTES:

- The maximum junction temperature of the LM105 is 150°C and 85°C for the LM305. For operating at elevated temperatures, devices in the TO-5 package must be derated based on a thermal resistance of $150^\circ\text{C}/\text{W}$ junction to ambient, or $45^\circ\text{C}/\text{W}$ junction to case. For the flat package, the derating is based on a thermal resistance of $185^\circ\text{C}/\text{W}$ when mounted on a 1/16-inch thick epoxy glass board with ten, 0.03-inch-wide, 2-ounce copper conductors. Peak dissipations to 1W are allowable providing the dissipation rating is not exceeded with the power averaged over a five second interval, for the LM105, and averaged over a two second interval for the LM305.
- These specifications apply for input and output voltages within the ranges given, and for a divider impedance seen by the feedback terminal of $2\text{k}\Omega$, unless otherwise specified. The load and line regulation specifications are for constant junction temperature. Temperature drift effects must be taken into account separately when the unit is operating under conditions of high dissipation.
- The output currents given, as well as the load regulation, can be increased by the addition of external transistors. The improvement factor will be roughly equal to the composite current gain of the added transistors.
- No external pass transistor.


RAYTHEON

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GENERAL DESCRIPTION

The LM109 and LM309 are monolithic 5V regulators each constructed on a single silicon chip. They incorporate current limiting to limit the peak output current to a safe value. Also to prevent damage from excessive internal heat, the regulators include thermal shutdown circuits.

The military version, LM109 operates from -55°C to $+150^{\circ}\text{C}$. The LM309, the commercial version, operates from 0°C to $+125^{\circ}\text{C}$. The LM209 is the same as the LM109 except its performance is guaranteed from -25°C to $+85^{\circ}\text{C}$.

These devices are designed for local regulation on digital logic cards, eliminating distribution problems associated with single-point regulation. To simplify their application, the regulators require a minimum number of external parts. Input bypassing may be required when the regulators are situated an appreciable distance away from the power supply filter capacitors.

To improve transient response, output bypassing can be incorporated.

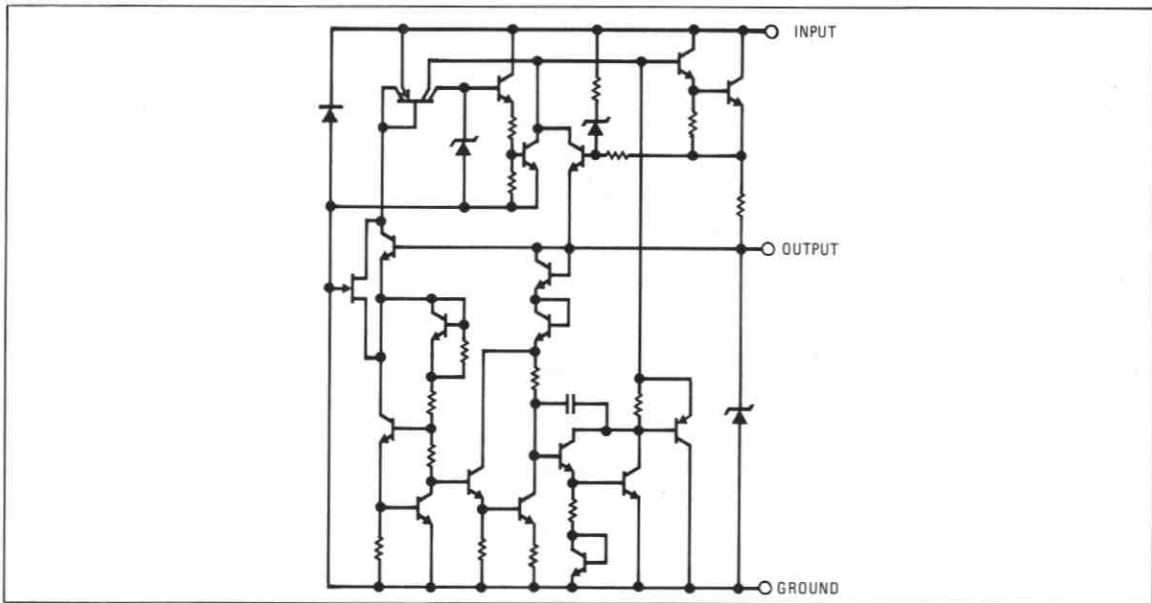
The regulators may be set to regulate voltages above 5V.

The LM109, LM209, and LM309 are available in the solid-kovar TO-5 header and the TO-3 power package. The TO-5 package can handle currents in excess of 200mA with adequate heat sinking. The TO-3 package can handle currents in excess of 1A.

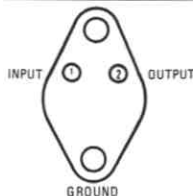
DESIGN FEATURES

- Output Current in Excess of 1A
- Internal Thermal Overload Protection
- No External Components Required
- Specified Compatible, Worst Case, with TTL and DTL

SCHEMATIC DIAGRAM

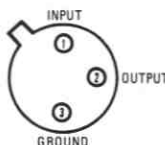


CONNECTION INFORMATION



LK (TO-3) Package
(Bottom View)

Order Part Nos.:
LM109K, LM209K,
LM309K



TH (TO-5) Package
(Top View)

Order Part Nos.:
LM109H, LM209H,
LM309H

ABSOLUTE MAXIMUM RATINGS

Input Voltage	35V	Operating Junction Temperature	
Power Dissipation	Internally Limited	LM109	-55°C to +150°C
Storage Temperature	-65°C to +150°C	LM209	-25°C to +150°C
Lead Temperature (Soldering, 10s)	+300°C	LM309	0°C to +125°C

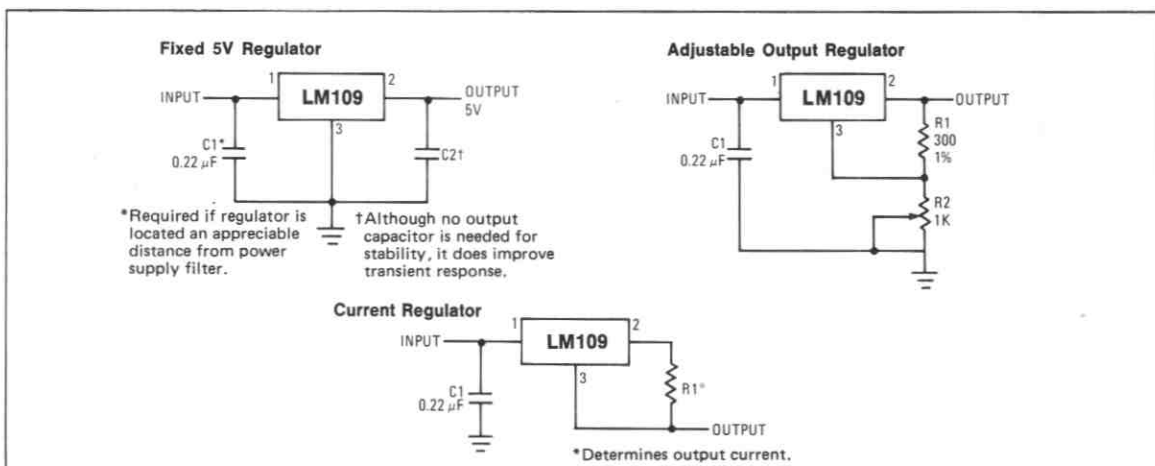
ELECTRICAL CHARACTERISTICS

PARAMETER	CONDITIONS	LM109			LM309			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Output Voltage	$T_i = 25^\circ\text{C}$	4.7	5.05	5.3	4.8	5.05	5.2	V
Line Regulation	$T_i = 25^\circ\text{C}$ $7.0\text{V} \leq V_{IN} \leq 25\text{V}$		4.0	50		4.0	50	mV
Load Regulation	$T_i = 25^\circ\text{C}$ $5\text{mA} \leq I_{OUT} \leq 0.5\text{A}$	LM109H	20	50		20	50	mV
		LM109K	50	100		50	100	
Output Voltage	$7.0\text{V} \leq V_{IN} \leq 25\text{V}$ $5\text{mA} \leq I_{OUT} \leq I_{MAX}$ $P < P_{MAX}$	4.6		5.4	4.75		5.25	V
Quiescent Current	$7.0\text{V} \leq V_{IN} \leq 25\text{V}$		5.2	10		5.2	10	mA
Quiescent Current Change	$7.0\text{V} \leq V_{IN} \leq 25\text{V}$			0.5			0.5	mA
	$5\text{mA} \leq I_{OUT} \leq I_{MAX}$			0.8			0.8	
Output Noise Voltage	$T_A = 25^\circ\text{C}$ $10\text{Hz} \leq f \leq 100\text{kHz}$		40			40		μV
Long Term Stability				10			20	mV

NOTES:

- Unless otherwise specified, these specifications apply for $-55^\circ\text{C} \leq T_i \leq 150^\circ\text{C}$ ($0^\circ\text{C} \leq T_i \leq 125^\circ\text{C}$, for the LM309), $V_{IN} = 10\text{V}$ and $I_{OUT} = 0.1\text{A}$ for the TO-5 package, or $I_{OUT} = 0.5\text{A}$ for the TO-3 package. For the TO-5 package, $I_{MAX} = 0.2\text{A}$ and $P_{MAX} = 2.0\text{W}$. For the TO-3 package, $I_{MAX} = 1.0\text{A}$ and $P_{MAX} = 20\text{W}$.
- Without a heat sink, the thermal resistance of the TO-5 package is about $150^\circ\text{C}/\text{W}$, while that of the TO-3 package is approximately $35^\circ\text{C}/\text{W}$.

TYPICAL APPLICATIONS



GENERAL DESCRIPTION

The RM723/RC723 integrated circuits are monolithic voltage regulators constructed on a single silicon chip. They consist of a temperature compensated reference amplifier, error amplifier, a power series pass transistor capable of 150mA, and current limiting circuitry.

They feature low standby current drain, low temperature drift and high ripple rejection.

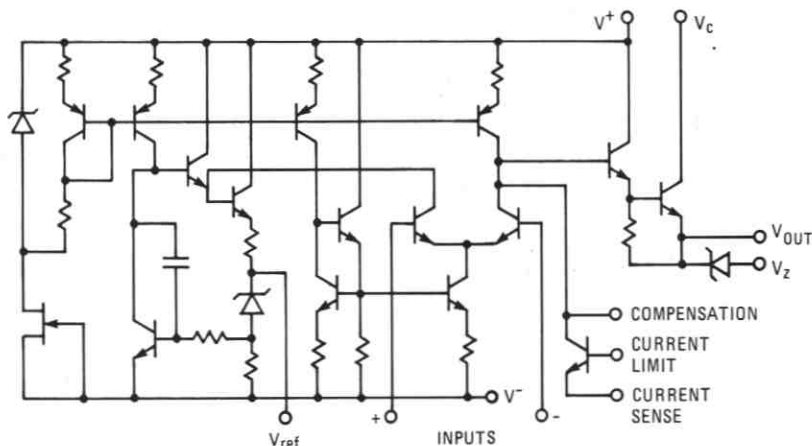
These devices are designed for use as a logic card regulator, small instrument power supply, or, by use of an external pass transistor, as a negative or floating regulator. They may also be used where local voltage supply regulation is required for linear and digital circuits. Provision is made for adjustable current limiting and remote shutdown.

The RM723 operates over the full military temperature range from -55°C to $+125^{\circ}\text{C}$. The RC723 operates from 0°C to $+70^{\circ}\text{C}$.

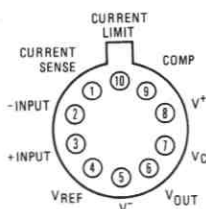
DESIGN FEATURES

- Positive or Negative Supply Operation
- Series, Shunt, Switching or Floating Operation
- 0.01% Line and Load Regulation
- Output Voltage Adjustable from 2V to 37V
- Output Current to 150mA Without External Pass Transistor

SCHEMATIC DIAGRAM



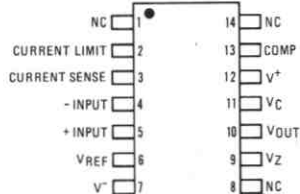
CONNECTION INFORMATION



TF Metal Can Package

(Top View)

Order Part Nos.:
RM723T, RC723T

DC and DB
Dual In-line Package
(Top View)

Order Part Nos.:
RM723DC, RC723DC,
RC723DB

ABSOLUTE MAXIMUM RATINGS

Pulse Voltage from V^+ to V^- (50 ms)	RM723: 50V	Internal Power Dissipation—DIP (Note 1)	900mW
Continuous Voltage from V^+ to V^-	40V	Operating Temperature Range	
Input-Output Voltage Differential	40V	RC723	0°C to $+70^{\circ}\text{C}$
Maximum Output Current	150mA	RM723	-55°C to $+125^{\circ}\text{C}$
Current from V_Z	25mA	Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
Current from V_{REF}	15mA	Lead Temperature (Soldering, 60s)	300°C
Internal Power Dissipation—Metal Can (Note 1) . . .	900mW		

ELECTRICAL CHARACTERISTICS (Note 2)

PARAMETER	CONDITIONS	RM723			RC723			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Line Regulation	$V_{IN} = 12\text{V}$ to $V_{IN} = 15\text{V}$		0.01	0.1		0.01	0.1	% V_{OUT}
	$V_{IN} = 12\text{V}$ to $V_{IN} = 40\text{V}$		0.02	0.2		0.1	0.5	
	$-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$, $V_{IN} = 12\text{V}$ to $V_{IN} = 15\text{V}$			0.3			0.3	
Load Regulation	$I_L = 1\text{mA}$ to $I_L = 50\text{mA}$		0.03	0.15		0.03	0.2	% V_{OUT}
	$-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$, $I_L = 1\text{mA}$ to $I_L = 50\text{mA}$			0.6			0.6	
Ripple Rejection	$f = 50\text{Hz}$ to 10kHz , $C_{REF} = 0$		74			74		dB
	$f = 50\text{Hz}$ to 10kHz , $C_{REF} = 5\mu\text{F}$		86			86		
Average Temperature Coefficient of Output Voltage	$-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$ (RM) $0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$ (RC)		0.002	0.015		0.003	0.015	%/ $^{\circ}\text{C}$
Short Circuit Current Limit	$R_{SC} = 10\Omega$, $V_{OUT} = 0$		65			65		mA
Reference Voltage		6.95	7.15	7.35	6.80	7.15	7.50	V
Output Noise Voltage	$BW = 100\text{Hz}$ to 10kHz , $C_{REF} = 0$		20			20		μV_{rms}
	$BW = 100\text{Hz}$ to 10kHz , $C_{REF} = 5\mu\text{F}$		2.5			2.5		
Long Term Stability			0.1			0.1		%/1000 hr
Standby Current Drain	$I_L = 0$, $V_{IN} = 30\text{V}$, $V_O = V_{REF}$		2.3	3.5		2.3	4.0	mA
Input Voltage Range		9.5		40	9.5		40	V
Output Voltage Range		2.0		37	2.0		37	V
Input-Output Voltage Differential		3.0		38	3.0		38	V

NOTES:

- Derate metal can package at $6.8\text{mW}/^{\circ}\text{C}$ and dual in-line package at $7.8\text{mW}/^{\circ}\text{C}$ for operation at ambient temperatures above $+25^{\circ}\text{C}$.
- Unless otherwise specified, $T_A = 25^{\circ}\text{C}$, $V_{IN} = V^+ = V_C = 12\text{V}$, $V^- = 0$, $V_{OUT} = 5\text{V}$, $I_L = 1\text{mA}$, $R_{SC} = 0$, $C_i = 100\text{pF}$, $C_{REF} = 0$, divider impedance as seen by error amplifier $\leq 10\text{k}\Omega$.
- For metal can applications where V_Z is required, an external 6.2 zener should be connected in series with V_{OUT} .



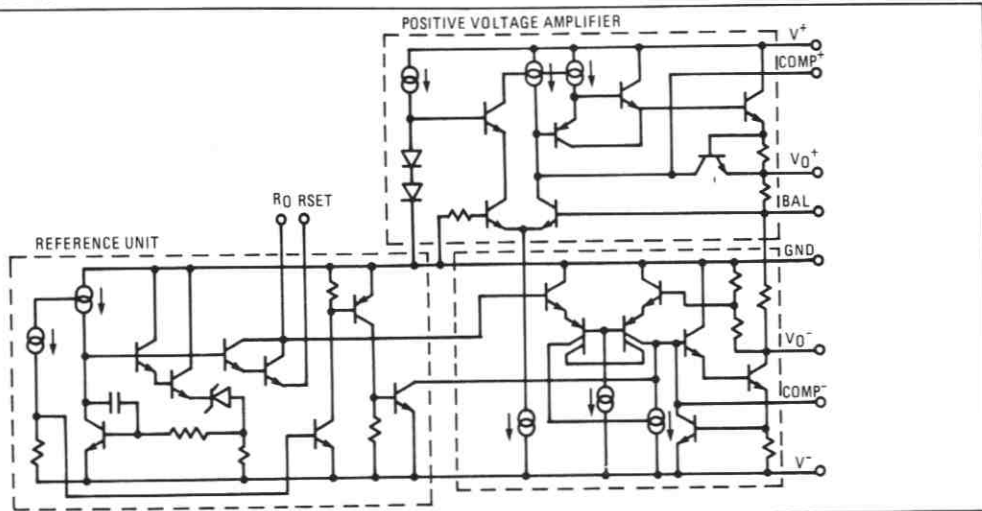
GENERAL DESCRIPTION

The RM4194 and RC4194 are dual polarity tracking regulators designed to provide balanced or unbalanced positive and negative output voltages at currents to 200mA. A single external resistor adjustment can be used to change both outputs between the limits of $\pm 50\text{mV}$ and $\pm 42\text{V}$.

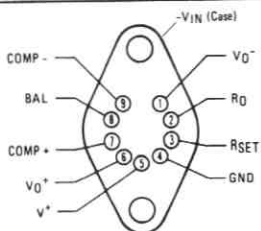
These devices are designed for local "on-card" regulation, eliminating distribution problems associated with single-point regulation. To simplify application the regulators require a minimum number of external parts.

The device is available in two package types to accommodate various power requirements. The TK (TO-66) power package can dissipate up to 3W at $T_A = 25^\circ\text{C}$. The D 14-pin dual in-line will dissipate up to 900mW.

SCHEMATIC DIAGRAM

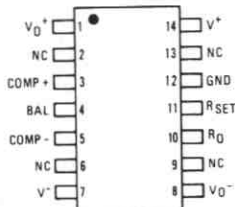


CONNECTION INFORMATION



TK (TO-66) Package
(Bottom View)

Order Part Nos.:
RC4194TK, RM4194TK



D Dual In-line Package
(Top View)

Order Part Nos.:
RC4194D, RM4194D

DESIGN FEATURES

- Simultaneously Adjustable Outputs With One Resistor to $\pm 42\text{V}$
- Load Current $\pm 200\text{mA}$ with 0.2% Load Regulation
- Internal Thermal Shutdown at $T_i = 175^\circ\text{C}$
- External Balance for $\pm V_0$ Unbalancing
- 3W Power Dissipation

ABSOLUTE MAXIMUM RATINGS

Input Voltage $\pm V$ to Ground	RM4194: $\pm 45V$ RC4194: $\pm 35V$	Load Current	
Input-Output Voltage Differential	RM4194: $\pm 45V$ RC4194: $\pm 35V$	D Package	150mA
Power Dissipation at $T_A = 25^\circ C$		TK Package	250mA
D Package	900mW	Operation Junction Temperature Range	
TK Package	3.0W	RM4194	$-55^\circ C$ to $+150^\circ C$
		RC4194	$0^\circ C$ to $+125^\circ C$
		Storage Temperature Range	$-65^\circ C$ to $+150^\circ C$
		Lead Temperature (Soldering, 10s)	$+300^\circ C$

ELECTRICAL CHARACTERISTICS ($\pm 5 \leq V_{OUT} \leq V_{MAX}$; RM4194: $-55^\circ C \leq T_i \leq +125^\circ C$; RC4194: $0^\circ C \leq T_i \leq +70^\circ C$)

PARAMETER	CONDITIONS	RM4194			RC4194			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Line Regulation	$\Delta V_{IN} = 0.1V_{IN}$		0.02	0.1		0.02	0.1	% V_{OUT}
Load Regulation	4194TK: $I_L = 1$ to $200mA$ 4194D: $I_L = 1$ to $100mA$		0.001	0.002		0.001	0.004	% V_{O}/mA
TC of Output Voltage			0.002	0.015		0.003	0.015	%/ $^\circ C$
Stand-By Current Drain (Note 1)	$V_{IN} = V_{MAX}$, $V_O = 0V$		+0.3	+1.0		+0.3	+1.5	mA
	$V_{IN} = V_{MAX}$, $V_O = 0V$		-1.2	-2.0		-1.2	-3.0	
Input Voltage Range		± 9.5		± 45	± 9.5		± 35	V
Output Voltage Scale Factor	$R_{set} = 71.5K$, $T_i = 25^\circ C$	2.45	2.5	2.55	2.38	2.5	2.62	$K\Omega/V$
Output Voltage Range	$R_{set} = 71.5K$	0.05		± 42	0.05		± 32	V
Output Voltage Tracking				1.0			2.0	%
Ripple Rejection	$f = 120Hz$, $T_i = 25^\circ C$		70			70		dB
Input-Output Voltage Differential	$I_L = 50mA$	3.0			3.0			V
Output Short Circuit Current	$V_{IN} = \pm 30V$ Max.		300			300		mA
Output Noise Voltage	$C_L = 4.7\mu F$, $V_O = \pm 15V$ $f = 10Hz$ to $100KHz$		250			250		μV RMS
Internal Thermal Shutdown			175			175		$^\circ C$

THERMAL CHARACTERISTICS

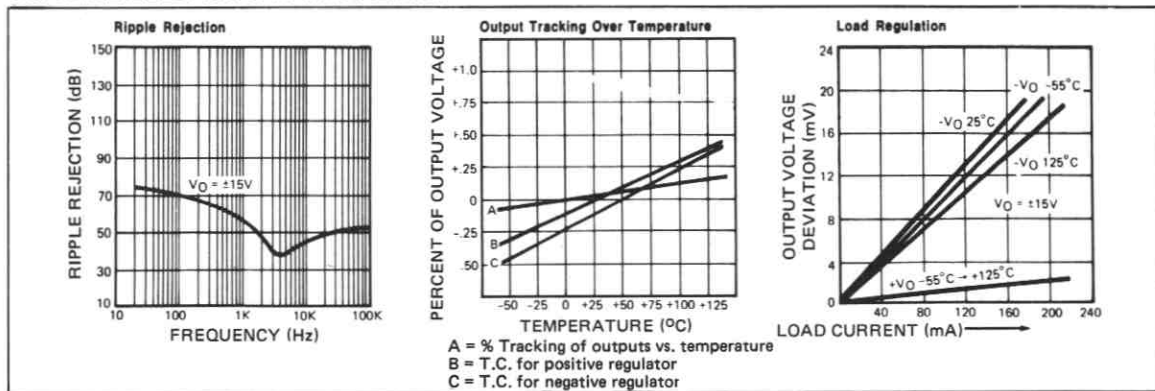
PARAMETER	CONDITIONS	PACKAGE	
		D	TK (TO-66)
Power Dissipation	$T_A = 25^\circ C$	900mW	3W
	$T_C = 25^\circ C$	2.2W	17.5W
Thermal Resistance	Junction to Ambient, θ_{J-A}	128 $^\circ C/W$	41.6 $^\circ C/W$
	Junction to Case, θ_{J-C}	55 $^\circ C/W$	7.15 $^\circ C/W$

NOTE:

$\pm I_{Quiescent}$ will increase by $50\mu A/V_{OUT}$ on positive side and $100\mu A/V_{OUT}$ on negative side.

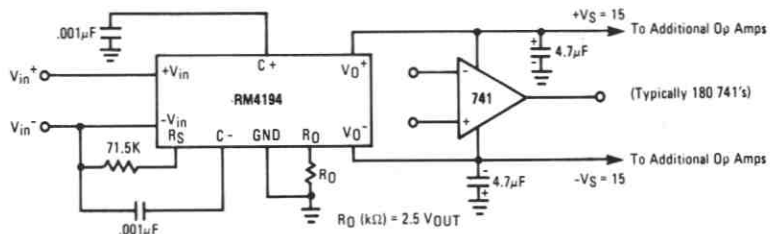


TYPICAL ELECTRICAL TEST DATA

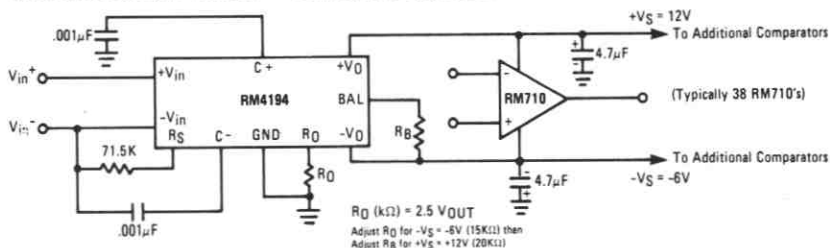


TYPICAL APPLICATIONS

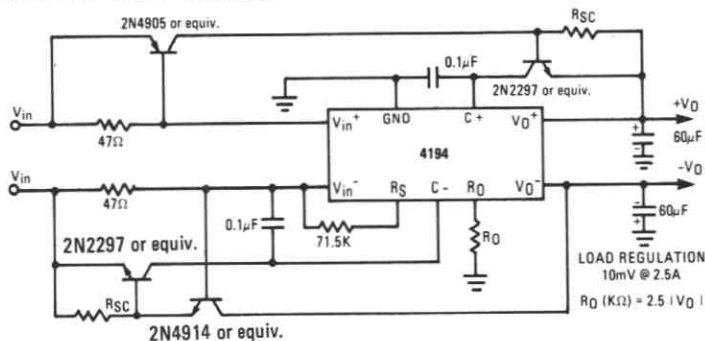
Balanced Output Voltage — Op Amp Application



Unbalanced Output Voltage — Comparator Application



High Output Current Application



GENERAL DESCRIPTION

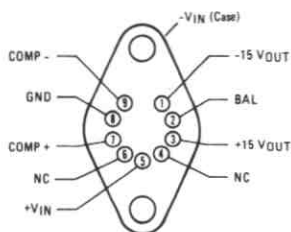
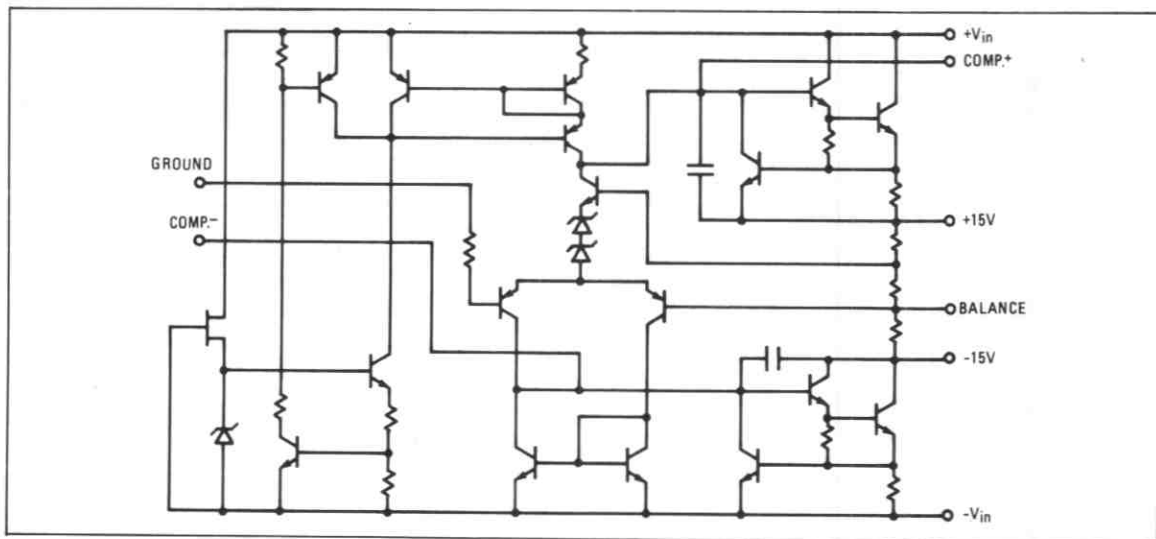
The RM4195 and RC4195 are dual polarity tracking regulators designed to provide balanced positive and negative 15V output voltages at currents to 100mA. These devices are designed for local "on-card" regulation eliminating distribution problems associated with single point regulation. The regulator is intended for ease of application. Only two external components are required for operation (two 10 μ F bypass capacitors).

The device is available in three package types to accommodate various applications requiring economy, high power dissipation, and reduced component density.

DESIGN FEATURES

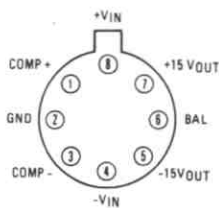
- $\pm 15V$ Operational Amplifier Power at Reduced Cost and Component Density
- Thermal Shutdown at $T_i = +175^\circ C$ in Addition to Short-Circuit Protection
- Output Currents to 100mA
- May be Used as Single Output Regulator with up to +50V Output
- Available in TO-66, TO-99, and 8-Pin Plastic Mini-DIP

SCHEMATIC DIAGRAM



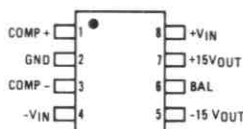
TK (TO-66) Power Package
(Bottom View)

Order Part Nos.:
RC4195TK, RM4195TK



TE Metal Can Package
(Top View)

Order Part Nos.:
RC4195T, RM4195T



NB Dual In-line
(Top View)

Order Part No.:
RC4195NB

ABSOLUTE MAXIMUM RATINGS

Input Voltage $\pm V$ to Ground	$\pm 30V$	Operating Junction Temperature Range	
Power Dissipation @ $T_A = +25^\circ C$		RM4195	$-55^\circ C$ to $+150^\circ C$
TK Package	2.4W	RC4195	$0^\circ C$ to $+125^\circ C$
T Package	800mW	Storage Junction Temperature Range	
NB Package	600mW	RM4195	$-65^\circ C$ to $+150^\circ C$
Load Current		RC4195	$-65^\circ C$ to $+125^\circ C$
TK Package	150mA	Lead Temperature (Soldering, 10s)	$+300^\circ C$
T, and NB Package	100mA		

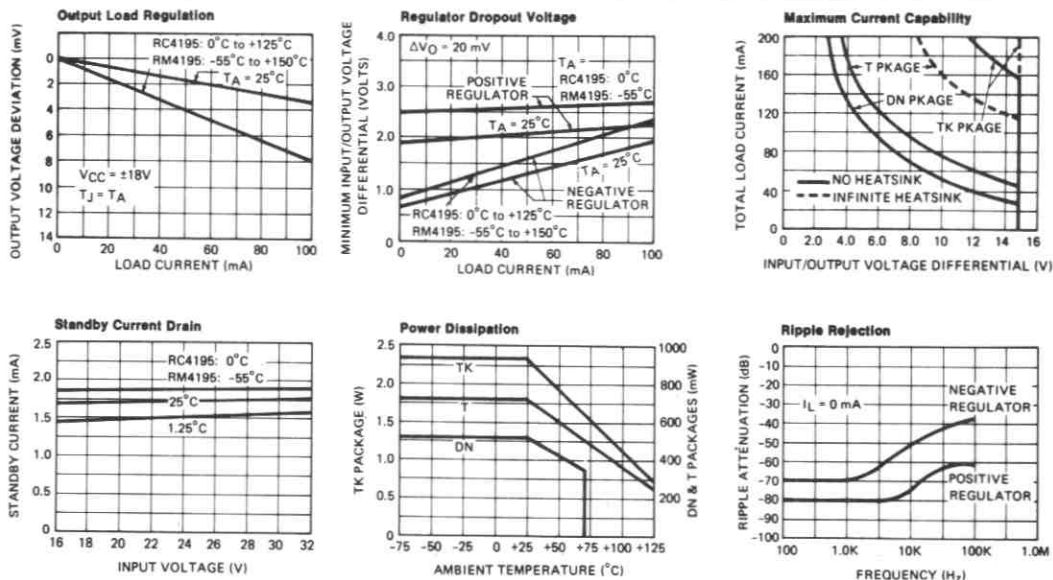
ELECTRICAL CHARACTERISTICS ($I_L = 1mA$, $V_{CC} = \pm 20V$, $C_L = 10\mu F$ unless otherwise specified)

PARAMETER	CONDITIONS	RM4195			RC4195			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Line Regulation	$V_{IN} = \pm 18$ to $\pm 30V$		2	20		2	20	mV
Load Regulation	$I_L = 1$ to $100mA$		5	30		5	30	mV
Output Voltage Temperature Stability			0.005	0.015		0.005	0.015	$\%/^\circ C$
Standby Current Drain	$V_{IN} = \pm 30V$, $I_L = 0mA$		± 1.5	± 2.5		± 1.5	± 3.0	mA
Input Voltage Range		18		30	18		30	V
Output Voltage	$T_i = +25^\circ C$	14.8	15	15.2	14.5	15	15.5	V
Output Voltage Tracking			± 50	± 150		± 50	± 300	mV
Ripple Rejection	$f = 120Hz$, $T_i = +25^\circ C$		75			75		dB
Input-Output Voltage Differential	$I_L = 50mA$	3			3			V
Short-Circuit Current	$T_i = +25^\circ C$		220			220		mA
Output Noise Voltage	$T_i = +25^\circ C$, $f = 100Hz$ to $10kHz$		60			60		μV RMS
Internal Thermal Shutdown			175			175		$^\circ C$

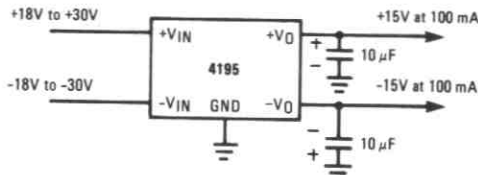
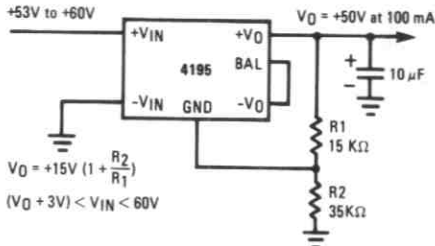
THERMAL CHARACTERISTICS

PARAMETER	CONDITIONS	PACKAGE			UNITS
		NB	T (TO-99)	TK (TO-66)	
Power Dissipation	$T_A = 25^\circ C$	0.6	0.8	2.4	W
	$T_C = 25^\circ C$		2.1	9	
Thermal Resistance	θ_{J-C}	210	70	17	$^\circ C/W$
	θ_{J-A}		185	62	

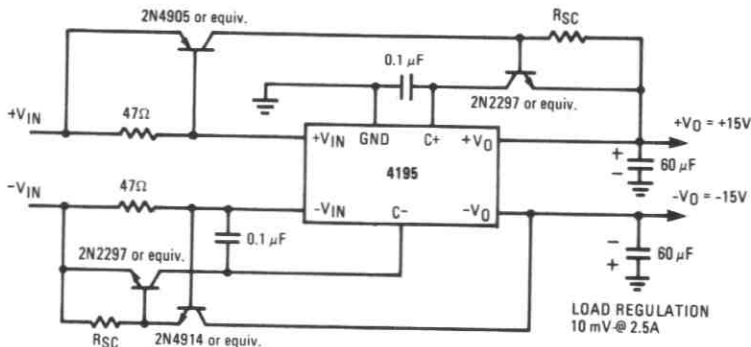
TYPICAL ELECTRICAL TEST DATA



TYPICAL APPLICATIONS

Balanced Output ($V_O = \pm 15V$)Positive Single Supply ($+15V < V_O < +50V$)

High Output Current



SECTION 4

Comparators

CONTENTS

106, 206, 306	Voltage Comparators	4-2
111, 211, 311	Precision Voltage Comparators	4-4
139, 239, 339, 2901, 3302	Quad Single-Supply Comparator	4-6
710/710A	High-Speed Differential Voltage Comparators	4-10
711/711A	Dual Differential Voltage Comparators	4-12
1414, 1514	Monolithic Dual Differential Voltage Comparators	4-14

GENERAL DESCRIPTION

The LM106, LM206, and LM306 are high-speed voltage comparators designed to accurately detect low-level analog signals and drive a digital load. They are equivalent to an RC710, combined with a two input NAND gate and an output buffer. The circuits can drive RTL, DTL or TTL integrated circuits directly. Furthermore, their outputs can switch voltages up to 24V at currents as high as 100mA.

The devices have short-circuit protection which limits the inrush current when it is used to drive loads such as incandescent lamps, in addition to preventing damage if it is accidentally short-circuited. The speed is equivalent to that of an RC710. However, it is even faster where buffers and additional logic circuitry can be eliminated by the increased flexibility of the LM106, LM206, and LM306. They can also be operated from any negative supply voltage between $-3V$ and $-12V$ with little effect on performance.

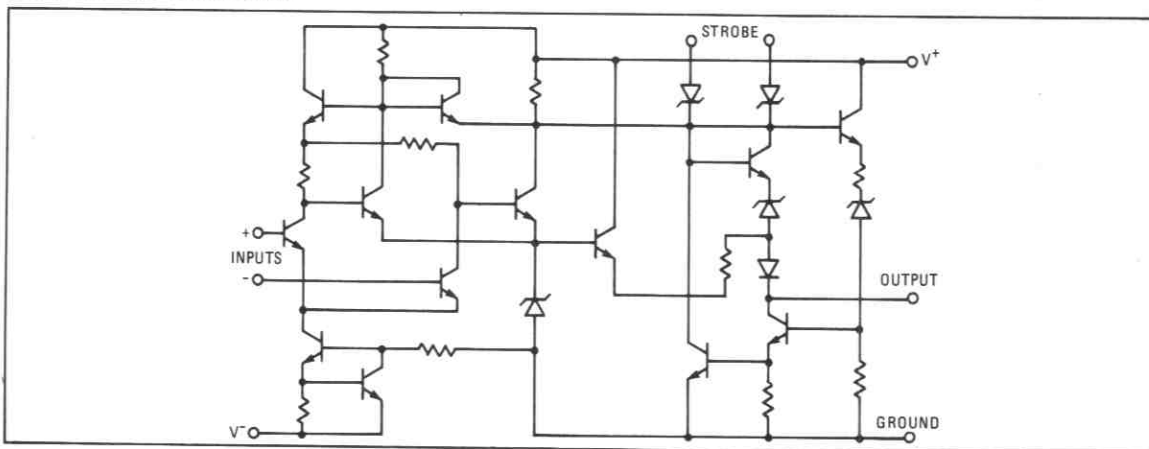
Operating temperature ranges are: LM106, $-55^{\circ}C$ to $+125^{\circ}C$; LM206, $-25^{\circ}C$ to $+85^{\circ}C$; LM306, $0^{\circ}C$ to $+70^{\circ}C$.

The LM206 is the same as the LM106 except its performance is guaranteed from $-25^{\circ}C$ to $+85^{\circ}C$.

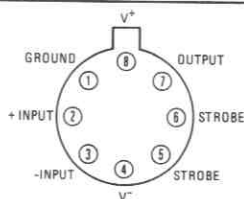
DESIGN FEATURES

- Improved Accuracy 2mV (Max) Offset, 40,000 Gain
- Fan-Out of 10 with DTL or TTL
- Useful as Relay or Lamp Driver
- Plug-in Replacement for RC710

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
LM106H, LM206H,
LM306H

RAYTHEON

RAYTHEON COMPANY • SEMICONDUCTOR DIVISION • 350 ELLIS STREET • MOUNTAIN VIEW, CALIFORNIA

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±15V	Operating Temperature Range	
Output Voltage	24V	LM106	-55°C to +125°C
Output to Negative Supply Voltage	30V	LM206	-25°C to +85°C
Differential Input Voltage	±5.0V	LM306	0°C to +70°C
Input Voltage	±7.0V	Storage Temperature Range	-65°C to +150°C
Power Dissipation (Note 1)	600mW	Lead Temperature (Soldering, 60s)	300°C
Output Short-Circuit Duration	10s		

ELECTRICAL CHARACTERISTICS (Notes 2,5)

PARAMETER	CONDITIONS	LM106, LM206			LM306			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	Notes 2 and 3		0.5	2.0		1.6	5.0	mV
Input Offset Current	Notes 2 and 3		0.7	3.0		1.8	5.0	μA
Input Bias Current	Note 2		10	20		16	25	μA
Voltage Gain	Note 2		40			40		V/mV
Response Time	Notes 2 and 4, $R_L = 390\Omega$, $C_L = 15pF$		28	40		28	40	ns
Saturation Voltage	Note 2, $V_{IN} \leq -5mV$, $I_{sink} = 100mA$		1.0	1.5		0.8	2.0	V
Output Leakage Current	Note 2, $V_{IN} \geq 5mV$, $8V \leq V_{OUT} \leq 24V$		0.02	1.0		0.02	2.0	μA
Input Offset Voltage	Note 3			3.0			6.5	mV
Average Temperature Coefficient of Input Offset Voltage			3.0	10		5.0	20	μV/°C
Input Offset Current	Note 3 $T_L \leq T_A \leq +25^\circ C$		1.8	7.0		2.4	7.5	pA
	Note 5 $+25^\circ C \leq T_A \leq T_H$		0.25	3.0			5.0	
Average Temperature Coefficient of Input Offset Current	Note 5 $T_L \leq T_A \leq +25^\circ C$ $+25^\circ C \leq T_A \leq T_H$		15	75		24	100	nA/°C
			5.0	25		15	50	
Input Bias Current	Note 5 $T_L \leq T_A \leq +25^\circ C$ $+25^\circ C \leq T_A \leq T_H$			45		25	40	pA
				20			25	
Input Voltage Range	$-7V \geq V^- \geq -12V$	±5.0			±5.0			V
Differential Input Voltage Range		±5.0			±5.0			V
Saturation Voltage	$V_{IN} \leq -5mV$, $I_{sink} = 50mA$			1.0			1.0	V
Saturation Voltage	$V_{IN} \leq -5mV$, $I_{sink} \leq 16mA$			0.4			0.4	V
Positive Output Level	$V_{IN} \geq 5mV$, $I_{OUT} = 400\mu A$	2.5		5.5	2.5		5.5	V
Output Leakage Current	$V_{IN} \geq 5mV$, $8V \leq V_O \leq 24V$, Note 5			100			100	μA
Strobe Current	$V_{strobe} = 0.4V$		-1.7	-3.2		-1.7	-3.2	mA
Strobe ON Voltage		0.9	1.4		0.9	1.4		V
Strobe OFF Voltage	$I_{sink} \leq 16mA$		1.4	2.2		1.4	2.2	V
Positive Supply Current	$V_{IN} = -5mV$		5.5	10		5.5	10	mA
Negative Supply Current			-1.5	-3.6		-1.5	-3.6	mA

NOTES:

- The maximum junction temperatures are as follows: LM106 +150°C, LM206 +110°C, LM306 +85°C. For operating at elevated temperatures, devices in the TE package must be derated based on a thermal resistance of 150°C/W, junction to ambient, or 45°C/W, junction to case. For the flat package, the derating is based on a thermal resistance of 185°C/W when mounted on a 1/16-inch-thick epoxy glass board with ten, 0.03-inch-wide, 2-ounce copper conductors.
- These specifications apply for $-3V \geq V^- \geq -12V$, $V^+ = 12V$ and $T_A = 25^\circ C$ unless otherwise specified.
- The offset voltages and offset currents given are the maximum values

required to drive the output down to 0.5V or up to 5.0V. Thus, these parameters actually define an error band and take into account the worst-case effects of voltage gain and input impedance.

- The response time specified (see definitions) is for a 100mV input step with 5mV overdrive.

	T_L	T_H
LM106	-55°C	+125°C
LM206	-25°C	+85°C
LM306	0°C	+70°C

GENERAL DESCRIPTION

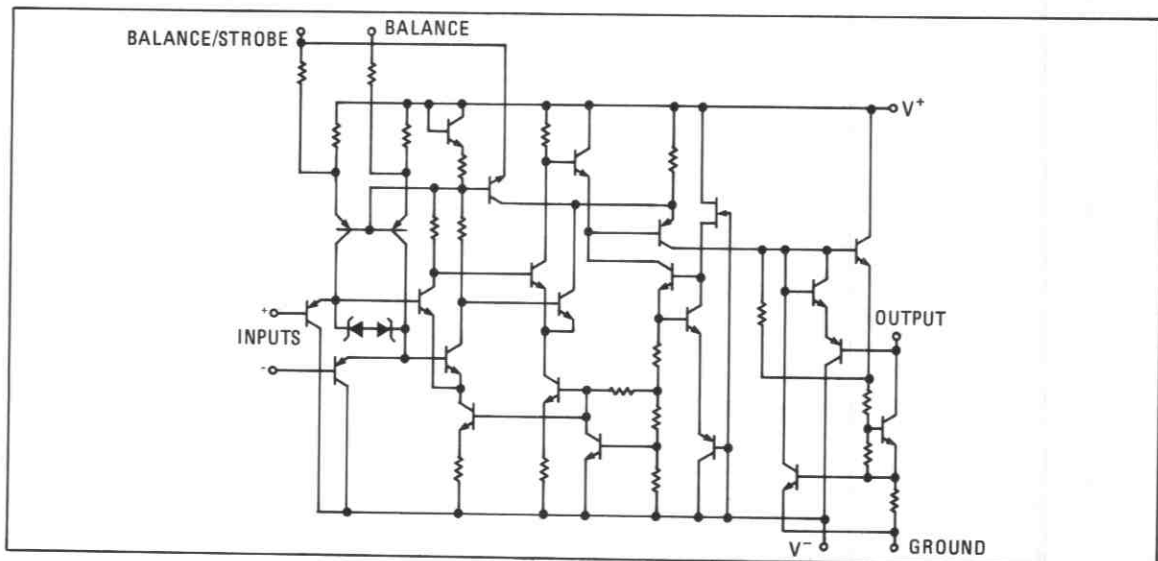
The LM111, LM211, and LM311 are voltage comparators with about one-thousandth the input current of the LM106 and LM107. These comparators are designed to operate from standard $\pm 15V$ operational amplifier supplies to a single +5V supply used for IC logic. Their outputs are compatible with DTL, RTL, TTL, and MOS devices. Offset balancing is provided, and the outputs can be OR wired.

The LM111 operates over the full military temperature range of $-55^{\circ}C$ to $+125^{\circ}C$. The LM211 is the same as the LM111 except its performance is guaranteed from $-25^{\circ}C$ to $+85^{\circ}C$. The LM311 is the commercial version which operates from $0^{\circ}C$ to $+70^{\circ}C$.

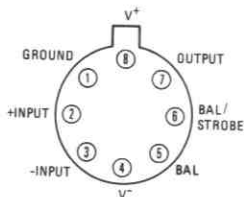
DESIGN FEATURES

- Input Current 150nA Maximum
- Operates from +5V Supply
- Offset Current 20nA Maximum

SCHEMATIC DIAGRAM



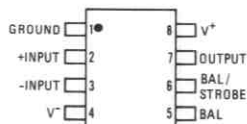
CONNECTION INFORMATION



NOTE: Pin 4 connected to case.

TE Metal Can Package
(Top View)

Order Part Nos.:
LM111H, LM211H,
LM311H



NB Dual In-line Package
(Top View)

Order Part No.:
LM311NB

ABSOLUTE MAXIMUM RATINGS

Total Supply Voltage (V_{84})	36V	Output Short-Circuit Duration	10s
Output to Negative Supply (V_{74})	LM111/LM211: 50V LM311: 40V	Operating Temperature Range	
Ground to Negative Supply Voltage (V_{14})	30V	LM111	-55°C to +125°C
Differential Input Voltage	±30V	LM221	-25°C to +85°C
Input Voltage (Note 1)	±15V	LM311	0°C to +70°C
Power Dissipation (Note 2)	500mW	Storage Temperature Range	-65°C to +150°C
		Lead Temperature (Soldering, 10s)	300°C

ELECTRICAL CHARACTERISTICS (Note 3)

PARAMETER	CONDITIONS	LM111/211		LM311		UNITS
		TYP	MAX	TYP	MAX	
Input Offset Voltage (Note 4)	$T_A = 25^\circ\text{C}$, $R_S \leq 50\text{k}$	0.7	3.0	2.0	7.5	mV
Input Offset Current (Note 4)	$T_A = 25^\circ\text{C}$	4.0	10	6.0	50	nA
Input Bias Current	$T_A = 25^\circ\text{C}$	60	100	100	250	nA
Voltage Gain	$T_A = 25^\circ\text{C}$		200	200		V/mV
Response Time (Note 5)	$T_A = 25^\circ\text{C}$		200	200		ns
Saturation Voltage	$V_{IN} \leq -5\text{mV}$, $I_{OUT} = 50\text{mA}$, $T_A = 25^\circ\text{C}$	0.75	1.5	0.75	1.5	V
Strobe On Current	$T_A = 25^\circ\text{C}$	3.0		3.0		mA
Output Leakage Current	$V_{IN} \geq 5\text{mV}$, $V_{OUT} = 35\text{V}$, $T_A = 25^\circ\text{C}$	0.2	10	0.2	50	nA
Input Offset Voltage (Note 4)	$R_S \leq 50\text{k}$		4.0		10	mV
Input Offset Current (Note 4)			20		70	nA
Input Bias Current			150		300	nA
Input Voltage Range		±14		±14		V
Saturation Voltage	$V^+ \geq 4.5\text{V}$, $V^- = 0$, $V_{IN} \leq -6\text{mV}$, $I_{SINK} \leq 8\text{mA}$	0.23	0.4	0.23	0.4	V
Output Leakage Current	$V_{IN} \geq 5\text{mV}$, $V_{OUT} = 35\text{V}$	0.1	0.5			μA
Positive Supply Current	$T_A = 25^\circ\text{C}$	5.1	6.0	5.1	7.5	mA
Negative Supply Current	$T_A = 25^\circ\text{C}$	4.1	5.0	4.1	5.0	mA

NOTES:

- This rating applies for ±15V supplies. The positive input voltage limit is 30V above the negative supply. The negative input voltage limit is equal to the negative supply voltage of 30V below the positive supply, whichever is less.
- The maximum junction temperature of the LM111 is 150°C, while that of the LM311 is +85°C. For operating at elevated temperatures, devices in the TO-5 package must be derated based on a thermal resistance of 150°C/W, junction to ambient, or 45°C/W, junction to case.
- These specifications apply for $V_S = \pm 15\text{V}$ and $-55^\circ\text{C} < T_A < +125^\circ\text{C}$, unless otherwise stated. With the LM311, however, all temperature specifications are limited to $0^\circ\text{C} < T_A < +70^\circ\text{C}$. The offset voltage, offset current and bias current specifications apply for any supply voltage from a single 5V supply up to ±15V supplies.
- The offset voltages and offset currents given are the maximum values required to drive the output within a volt of either supply with a 1mA load. Thus, these parameters define an error band and take into account the worst case effects of voltage gain and input impedance.
- The response time specified (see definitions) is for a 100mV input step with 5mV overdrive.

GENERAL DESCRIPTION

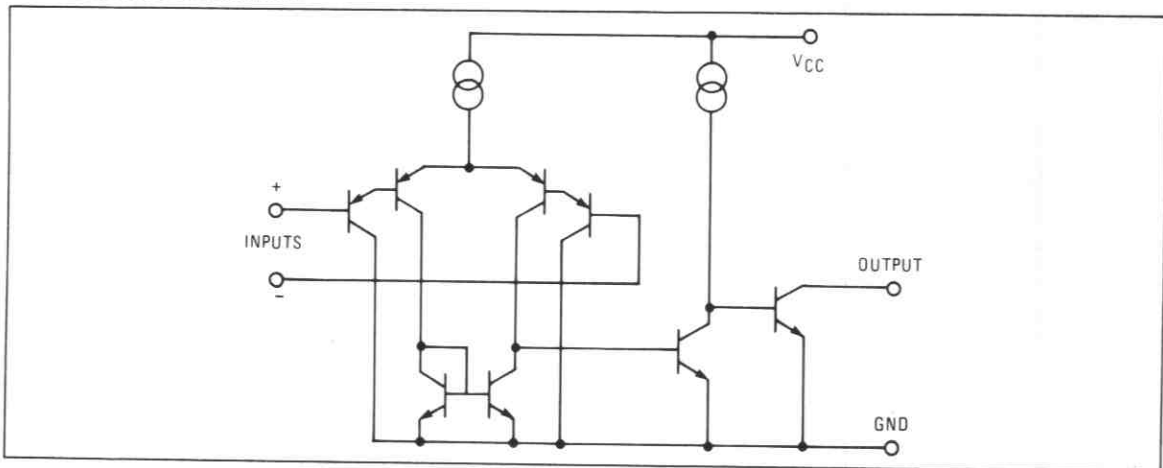
These devices offer higher frequency operation and faster switching than can be had from internally compensated quad op amps. Intended for single-supply applications, the Darlington PNP input stage allows them to compare voltages that include ground. The two-stage common-emitter output circuit provides gain and output sink capacity of 3 μ A at an output level of 400 mV. The output collector is left open, permitting the designer to drive devices in the range of 2 V to 36 V.

They are intended for commercial and industrial applications not needing response time less than 20 ns, but demanding excellent op amp input parameters of offset voltage and current, and bias current, to insure accurate comparison with reference voltage.

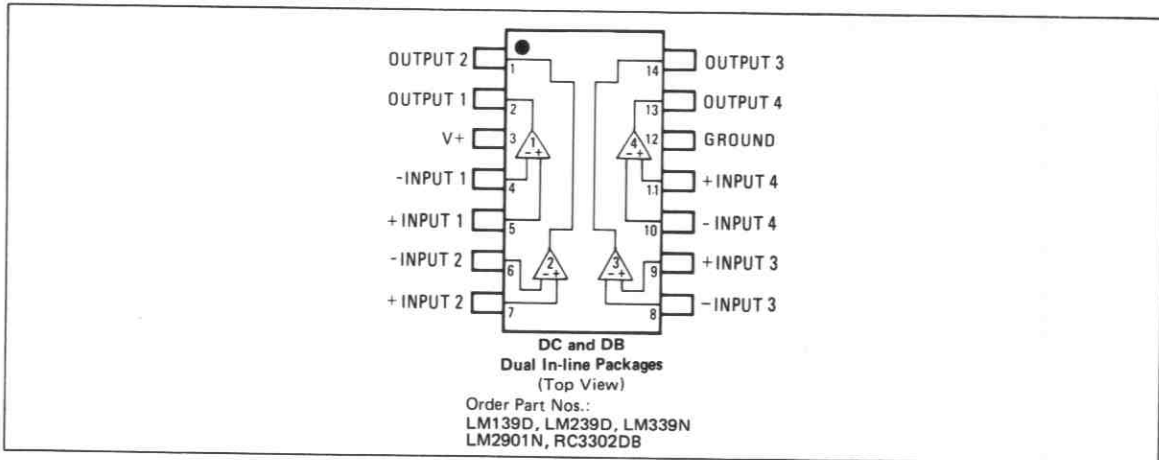
DESIGN FEATURES

- Input Common Mode Voltage Range Includes Ground
- Wide Single Supply Voltage Range, 2 to 36V
- Output Compatible with TTL, DTL, ECL, MOS and CMOS Logic Systems
- Very Low Supply Current Drain (.8mA) Independent of Supply Voltage

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V^+	36 V or ± 18 V	Operating Temperature Range . LM2901:	0°C to +70°C
Differential Input Voltage	36 V	LM239:	-25°C to +85°C
Input Voltage	-0.3 V to +36 V	LM2901:	-40°C to +85°C
Power Dissipation (Note 1)		LM139:	-55°C to +125°C
Molded DIP . . . LM339N, LM2901N:	570 mW	Storage Temperature Range	-65°C to +150°C
Cavity DIP . . . LM139D, LM239D & LM339D:	900 mW	Lead Temperature (Soldering, 10s)	300°C
Output Short-Circuit to GND (Note 2)	Continuous		

ELECTRICAL CHARACTERISTICS (139, 239, 339, 2901) ($V^+ = +5V$ and $T_A = +25^\circ C$ unless otherwise noted.)

PARAMETER	CONDITIONS	LM139			LM2901, LM239, LM339			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	At Output Switch Point, $V_O \cong 1.4V$ $V_{REF} = +1.4V, R_S = 0\Omega$ LM 2901		2	5		2	5	mV
						2	7	mV
Input Bias Current (Note 3)	$I_{IN(+)}$ or $I_{IN(-)}$ With Output in Linear Range		25	100		25	250	nA
Input Offset Current	$I_{IN(+)} - I_{IN(-)}$		3	25		5	50	nA
Input Common-Mode Voltage Range (Note 4)		0		$V^+ - 1.5$	0		$V^+ - 1.5$	V
Supply Current	$R_L = \infty$ On All Comparators		0.8	2		0.8	2	mA
Voltage Gain	$R_L = 15 k\Omega$		200			200		V/mV
Response Time (Note 5)	$V_{RL} = 5.0V$ and $R_L = 5.1 k\Omega$		1.3			1.3		μs
Output Sink Current	$V_{IN(-)} = +1V, V_{IN(+)} = 0,$ $V_O \leq +1.5V$	6	16		6	16		mA
Saturation Voltage	$V_{IN(-)} = +1V, V_{IN(+)} = 0,$ $I_{SINK} = 3 mA$		200	400		200	400	mV
Output Leakage Current	$V_{IN(+)} = +1V, V_{IN(-)} = 0,$ $V_{OUT} = 5V$		0.1			0.1		nA

NOTES:

- For operating at high temperatures, the LM339 and the LM2901 must be derated based on a +125°C maximum junction temperature and a thermal resistance of 175°C/W which applies for the device soldered in a printed circuit board operating in a still air ambient. The LM239 and LM139 must be derated based on a +150°C maximum junction temperature. The low bias dissipation and the ON-OFF characteristic of the outputs keeps the chip dissipation very small ($P_d \leq 100mW$), provided the transistors are allowed to saturate.
- Short circuits from the output to V^+ can cause excessive heating and eventual destruction. The maximum output current is approximately 20mA independent of the magnitude of V^+ .
- The direction of the input current is out of the IC due to the PNP input stage. This current is essentially constant, independent of the state of the output so no loading change exists on the reference or input lines.
- The input common-mode voltage or either input signal voltage should not be allowed to go negative by more than 0.3V. The upper end of the common-mode voltage range is $V^+ - 1.5V$, but either or both inputs can go to +30V_{DC} without damage.
- The response time specified is for a 100mV input step with 5mV overdrive. For larger overdrive signals 300 ns can be obtained, see typical performance characteristics section.



ABSOLUTE MAXIMUM RATINGS

Supply Voltage	+2.0 V to +28 V	Storage Temperature Range	-65°C to +150°C
Output Sink Current (Note 1)	20 mA	Operating Temperature Range	-40°C to +85°C
Internal Power Dissipation (Note 1)	625 mW	Lead Temperature (Soldering, 60s)	300°C
Differential Input Voltage	±2.0 V to ±28 V	Output Short-Circuit Duration (Note 2)	Continuous
Input Voltage (Note 2)	-0.3 V ±V _{CC}		

ELECTRICAL CHARACTERISTICS (V⁺ = +15V and T_A = +25°C unless otherwise noted.)

Characteristic	Conditions	Symbol	3302			Unit
			Min	Typ	Max	
Input Offset Voltage	(V _{ref} = 1.2V) (T _A = +25°C) (T _A = -40° to +85°C)	V _{IO}	-	3.0	20	mV
Input Offset Current		I _{IO}	-	3.0	40	nA
Input Bias Current	(T _A = +25°C) (T _A = -40°C to +85°C)	I _{IB}	-	30	500	nA
Voltage Gain	(R _L = 15 kΩ)	A _{vol}	2,000	30,000	-	V/V
Transconductance		g _m	-	2.0	-	mhos
Differential Input Voltage Range		V _{IDR}	±V _{CC}	-	-	V
Output Leakage Current (Output Voltage High)		I _{off}	-	-	1.0	μA
Negative Output Voltage	(I _S = 2.0mA, V _{CC} = +5.0 to +28V)	V _{OL}	-	150	400	mV
Output Sink Current	(V _{CC} = +5.0V) (T _A = +25°C, V _{OL} = 400mV) (T _A = -40°C to +85°C, V _{OL} = 800mV)	I _S	-	6.0	-	mA
Input Common-Mode Range	(V _{CC} = +28V)	V _{ICR}	0.26	-	-	Volts
Common Mode Rejection Ratio		CMRR	-	60	-	dB
Propagation Delay Time For Positive and Negative Going Input Pulse		t _{PHL/LH}	-	2.0	-	μs
Slew Rate	(R _L = 15kΩ)	t _{SR-} t _{SR+}	-	200	-	V/μs
Power Supply Current (Total of four comparators)	(I _S = 0, V _{CC} = +5.0 to +28V)	I _D	-	0.7	1.5	mA

NOTES:

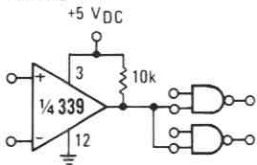
- Requires an external resistor, R_L, to limit current below maximum rating.
- If either (+) or (-) inputs of any comparator go more than several tenths of a volt below ground, a parasitic transistor turns "on," causing high input current and possible faulty outputs.



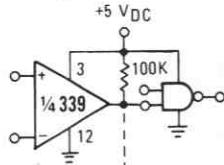
339 TYPICAL APPLICATIONS

Single Supply ($V^+ = 15V_{DC}$)

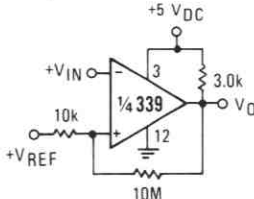
Driving TTL



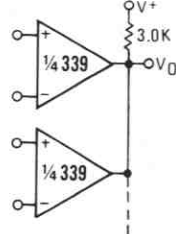
Driving CMOS



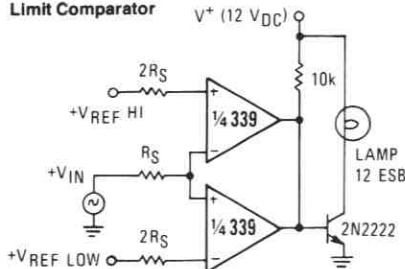
Comparator with Hysteresis



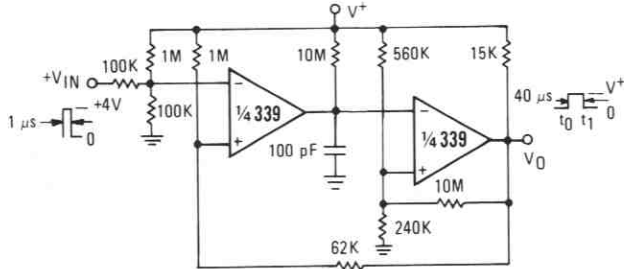
ORing the Outputs



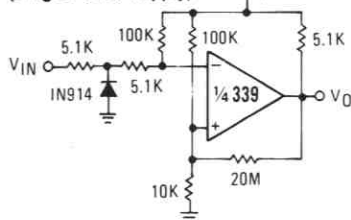
Limit Comparator



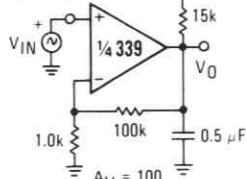
One-Shot Multivibrator with Input Lock Out



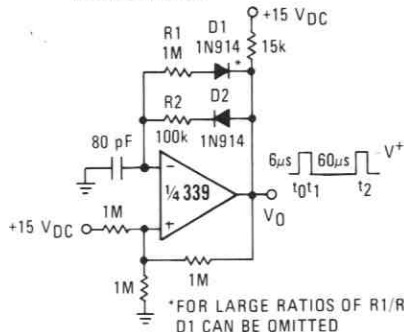
Zero Crossing Detector (Single Power Supply)



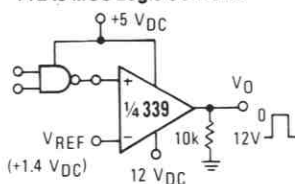
Low Frequency Op Amp



Pulse Generator

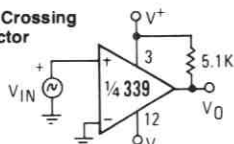


TTL to MOS Logic Converter

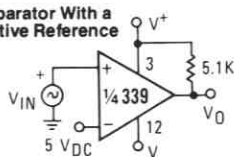


Split Supply ($V^+ = +15V_{DC}$ & $V^- = -15V_{DC}$)

Zero Crossing Detector



Comparator With a Negative Reference



GENERAL DESCRIPTION

The RM710/RM710A and RC710 integrated circuits are monolithic, high speed, differential voltage comparators. Manufactured by the planar process, component matching is inherent. Characteristic of the devices is low offset voltage and low drift parameters as well as high accuracy and fast response.

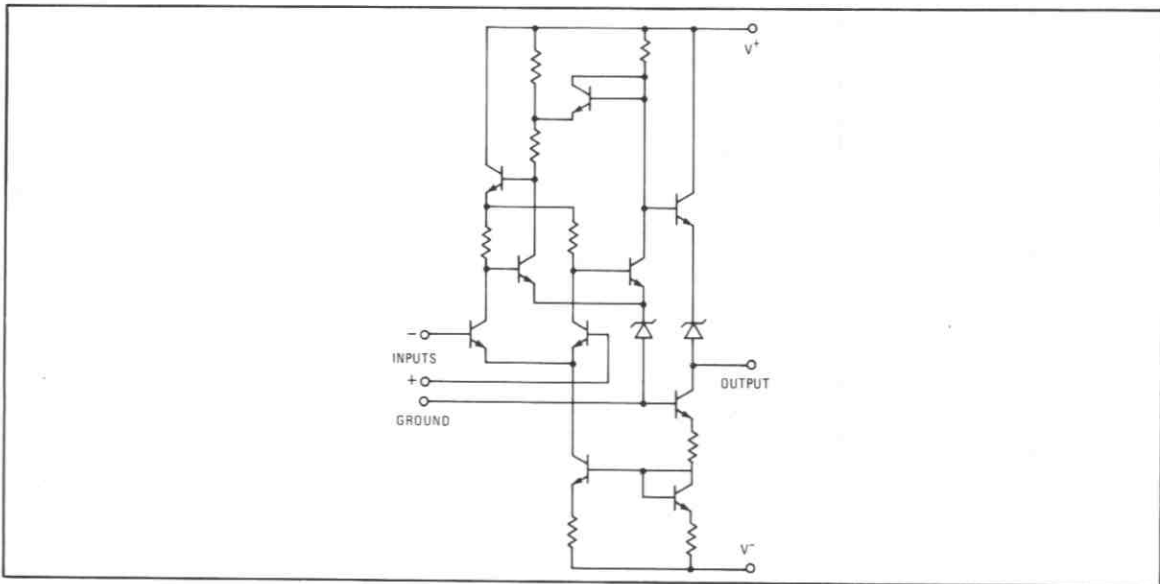
These voltage comparators are specially designed for a variety of applications such as high speed A/D converter, memory sense amplifier, zero crossing detector, amplitude discriminator and variable threshold Schmitt trigger.

The RM710/RM710A operate over the full military temperature range from -55°C to $+125^{\circ}\text{C}$. The RC710, commercial equivalent of the RM710, operates over a temperature from 0°C to $+70^{\circ}\text{C}$.

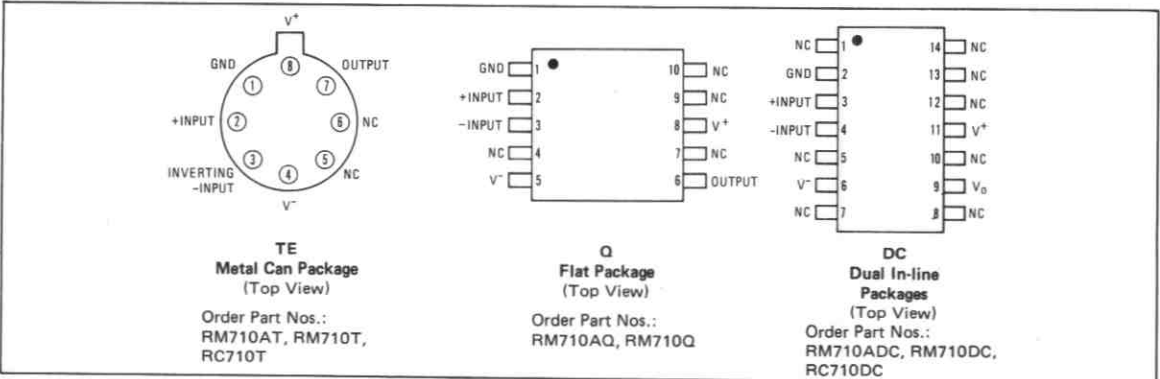
DESIGN FEATURES

- Low Offset Voltage and Drift Over Entire Temperature Range
- Fast Response Time
- Output Logic Compatible With All Existing Integrated Logic Forms
- Meets or Exceeds All Environmental Requirements of MIL-S-19500, MIL-STD-202, and MIL-STD-750

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



High-Speed Differential Voltage Comparators

ABSOLUTE MAXIMUM RATINGS

Positive Supply Voltage	+14V	Operating Temperature Range	
Negative Supply Voltage	-7.0V	RM710, RM710A	-55°C to +125°C
Peak Output Current	10.0mA	RC710	0°C to +70°C
Differential Input Voltage	±5.0V	Internal Power Dissipation (Note 1)	
Input Voltage	±7.0V	TO-5	300mW
Storage Temperature Range	-65°C to +150°C	Flat Package	200mW
Lead Temperature (Soldering, 60s)	300°C		

ELECTRICAL CHARACTERISTICS (V⁺ = 12.0V, V⁻ = -6.0V, T_A = +25°C unless otherwise specified)

PARAMETER	CONDITIONS	RM710A			RM710			RC710			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage (Note 3)	R _S ≤ 200Ω		0.3	1.0		0.6	2.0		1.6	5.0	mV
Input Offset Current (Note 3)			0.3	1.0		0.75	3.0		1.8	5.0	μA
Input Bias Current			10	15		13	20		16	25	μA
Voltage Gain		1400	1700		1250	1700		1000	1500		V/V
Output Resistance			200			200			200		Ω
Output Sink Current	ΔV _{in} ≥ 5mV, V _{out} = 0	2.0	2.5		2.0	2.5		1.6	2.5		mA
Response Time (Note 2)			40	60		40	60		40		ns
The following specifications apply for -55°C ≤ T _A ≤ +125°C.								The following specifications apply for 0°C ≤ T _A ≤ +70°C.			
Input Offset Voltage (Note 3)	R _S ≤ 200Ω			1.5			3.0			6.5	mV
Average Temperature Coefficient of Input Offset Voltage	R _S = 20Ω, T _A = Low to T _A = High, R _S = 20Ω		3.5	5.0		3.5	10		5.0	20	μV/°C
	T _A = 25°C to T _A = Low		2.7	5.0		2.7	10				
Input Offset Current (Note 3)	T _A = +125°C		0.15	2.0		0.25	3.0				μA
	T _A = Low		1.0	5.0		1.8	7.0			7.5	
Average Temperature Coefficient of Input Offset Current	T _A = 25°C to T _A = High		2.0	10		5.0	25		15	50	nA/°C
	T _A = 25°C to T _A = Low		9.0	50		15	75		24	100	
Input Bias Current	T _A = Low		20	28		27	45		25	40	μA
Input Voltage Range	V ⁻ = -7.0V	±5.0			±5.0			±5.0			V
Common Mode Rejection Ratio	R _S ≤ 200Ω	90	100		80	100		70	98		dB
Differential Input Voltage Range		±5.0			±5.0			±5.0			V
Voltage Gain		1100			1000			800			
Positive Output Level	ΔV _{in} ≥ 5mV, 0 ≤ I _{out} ≤ 5.0mA	2.5	3.2	4.0	2.5	3.2	4.0	2.5	3.2	4.0	V
Negative Output Level	ΔV _{in} ≥ 5mV	-1.0	-0.5	0	-1.0	-0.5	0	-1.0	-0.5	0	V
Output Sink Current	T _A = Low, ΔV _{in} ≥ 5mV, V _{out} = 0	0.5	2.3		0.5	2.3		0.5			mA
	T _A = High, ΔV _{in} ≥ 5mV, V _{out} = 0	1.0	1.7		0.5	1.7		0.5			
Positive Supply Current	V _{out} ≤ 0		5.2	9.0		5.2	9.0		5.2	9.0	mA
Negative Supply Current			4.6	7.0		4.6	7.0		4.6	7.0	mA
Power Consumption			90	150		90	150		90	150	mW

NOTES:

- The thermal characteristics are based on a maximum chip temperature of 160°C. Derate maximum power dissipation of TO-5 Can by 6.7mW/°C for T_A ≥ 114°C, of Flat Pak by 5.3mW/°C for T_A ≥ 103°C, and of Dip Pak by 9.6mW/°C for T_A ≥ 118°C. The ratings apply for -55°C ≤ T_A ≤ +125°C.
- The response time specified (see definitions) is for a 100mV input step with 5mV overdrive.
- The input offset voltage and input offset current are specified for a logic threshold voltage as follows: For RM710/710A grade 1.8V at -55°C, 1.4V at +25°C and 1.0V at +125°C. For RC710 grade 1.5V at +25°C and 1.2V at +70°C.

RAYTHEON

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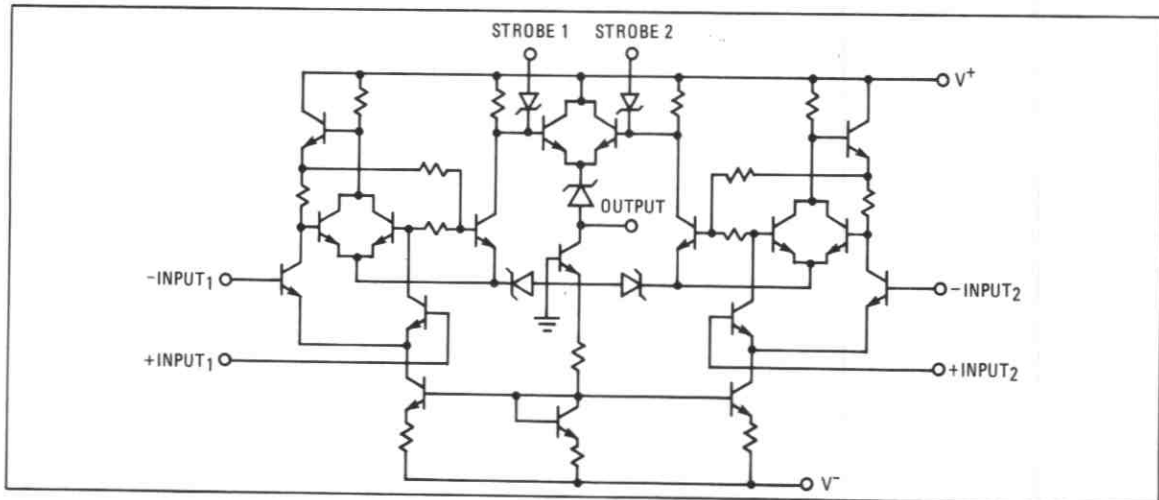
GENERAL DESCRIPTION

The Raytheon RM711A, RM711, and RC711 integrated circuit is a monolithic dual differential voltage comparator fabricated on a single silicon chip. Component matching inherent with the planar process yields a comparator of high performance and characteristics.

It is ideally suited for a number of applications such as: core-memory sense amplifier, high speed voltage comparator in A/D converters, zero crossing detector, and double ended limit detector for automatic Go/No-Go test equipment.

The RM711 and RM711A operate over the full military temperature range from -55°C to $+125^{\circ}\text{C}$. The RC711 operates over a temperature range from 0°C to $+70^{\circ}\text{C}$.

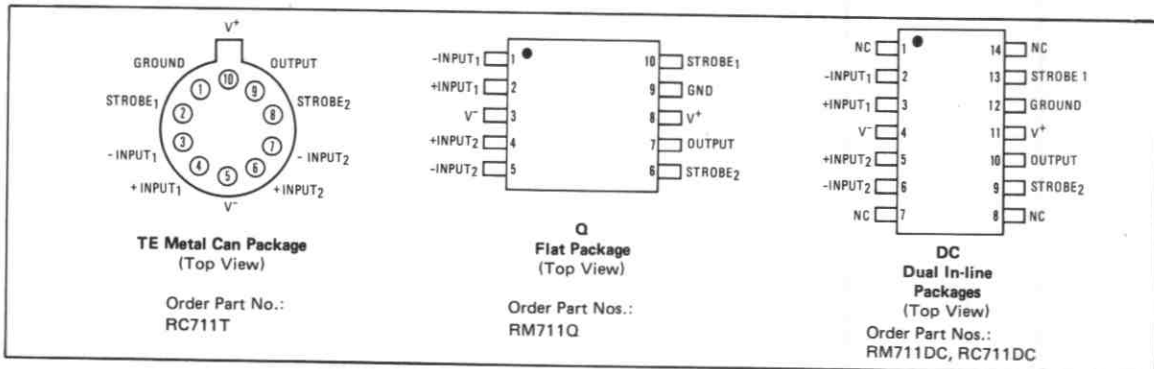
SCHEMATIC DIAGRAM



DESIGN FEATURES

- High Accuracy, Fast Response Time and Wide Threshold Range
- Inherently OR'd Outputs
- Independent Strobing of Either Side of the Device
- Low Power Dissipation
- Low Offsets and Thermal Drift
- Compatible With All Forms of Logic
- Meets or Exceeds All Environmental Requirements of MIL-S-19500, MIL-STD-202, MIL-STD-883

CONNECTION INFORMATION



Dual Differential Voltage Comparators

ABSOLUTE MAXIMUM RATINGS

Power Supply Voltage	+14V	Operating Temperature Range	
Negative Supply Voltage	-7.0V	RM711	-55°C to +125°C
Peak Output Current	50mA	RC711	0°C to +70°C
Differential Input Voltage	±5.0V	Internal Power Dissipation (Note 1)	
Input Voltage	±7.0V	TO-5 Package	300mW
Strobe Voltage	0 to +6.0V	Flat Package	300mW
Storage Temperature Range	-65°C to +150°C	Dual In-line Package	400mW
Lead Temperature (Soldering, 60s)	300°C		

ELECTRICAL CHARACTERISTICS ($V^+ = 12V$, $V^- = -6.0V$, $T_A = 25°C$ unless otherwise specified)

PARAMETER	CONDITIONS	RM711			RC711			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	(Note 3) $R_S \leq 200\Omega$, $V_{CM} = 0$		1.0	3.5		1.0	5.0	mV
			1.0	5.0		1.0	7.5	
Input Offset Current	(Note 3)		0.5	10		0.5	15	μA
Input Bias Current			25	75		25	100	μA
Voltage Gain		750	1500		750	1500		V/V
Output Sink Current	$\Delta V_{IN} \geq 10mV$, $V_{OUT} \leq 0V$	0.68			0.68			mA
Strobe Current	$V_{strobe} = 100mV$		1.15	2.5		1.15	2.5	mA
Response Time	(Note 2)		40			40		ns
Output Resistance			200			200		Ω
Strobe Release Time			12			12		ns
Positive Output Level	$\Delta V_{IN} \geq 10mV$, $I_O = 5.0mA$	2.5	3.5		2.5	3.5		V
The following specifications apply for $T_L \leq T_A \leq T_H$ (Note 5)								
Input Offset Voltage	(Note 3) $R_S \leq 200\Omega$, $V_{CM} = 0V$			4.5			6.0	mV
				6			10	
Input Bias Current				150			150	μA
Input Offset Current	(Note 3)			20			25	μA
Voltage Gain		500			500			
Loaded Positive Output Level	$\Delta V_{IN} \geq 10mV$	2.5	4.5	5.0	2.5	4.5	5.0	V
Negative Output Level (Note 4)	$\Delta V_{IN} \geq 10mV$, $I_O = 0$	-1.0	-0.5	0	-1.0	-0.5	0	V
Input Voltage Range	$V^- = -7.0V$	±5.0			±5.0			V
Differential Input Voltage Range		±5.0			±5.0			V
Average Temperature Coefficient of Input Offset Voltage	$R_S = 20\Omega$, T_L to T_H		5.0	20		5.0	20	$\mu V/^\circ C$
Average Temperature Coefficient of Input Offset Current	+25°C to T_H		15	50		15	50	nA/°C
	+25°C to T_L		24	100		24	100	
Strobed Output Level	$V_{strobe} \leq 0.3V$	-1.0	-0.3		-1.0	-0.3	0	V
Positive Supply Current	$V_{out} \leq 0$		7.2	12		7.2	12	mA
Negative Supply Current			3.7	6.0		3.7	6.0	mA
Common Mode Rejection Ratio		70	90		70	90		dB
Power Consumption			130	180		130	180	mW

NOTES:

- Thermal characteristics based on maximum chip temperature of +160°C. Derate maximum power dissipation for TO-5 by 6.7mW/°C for $T_A \geq +114^\circ C$, Flat Pack by 5.3mW/°C for $T_A \geq +103^\circ C$, Dip Pack by 9.6mW/°C for $T_A \geq +118^\circ C$. Ratings apply for $-55^\circ C \leq T_A \leq +125^\circ C$.
- The response time specified (see definitions) is for a 100mV input step with 5mV overdrive.
- Input offset voltage and input offset current are specified for a logic threshold voltage as follows: For RM711, 1.8V at -55°C, 1.4V at

+25°C, and 1.0V at +125°C; RC711, 1.5V at +25°C and 1.2V at +70°C.

- Negative output level is measured at $\Delta V_{IN} = 5V$.
-

	T_L	T_H
RM711	-55°C	+125°C
RC711	0°C	+70°C

GENERAL DESCRIPTION

The RM1514 and RC1414 are monolithic high-speed, differential voltage comparators manufactured by the planar process. Component matching is inherent.

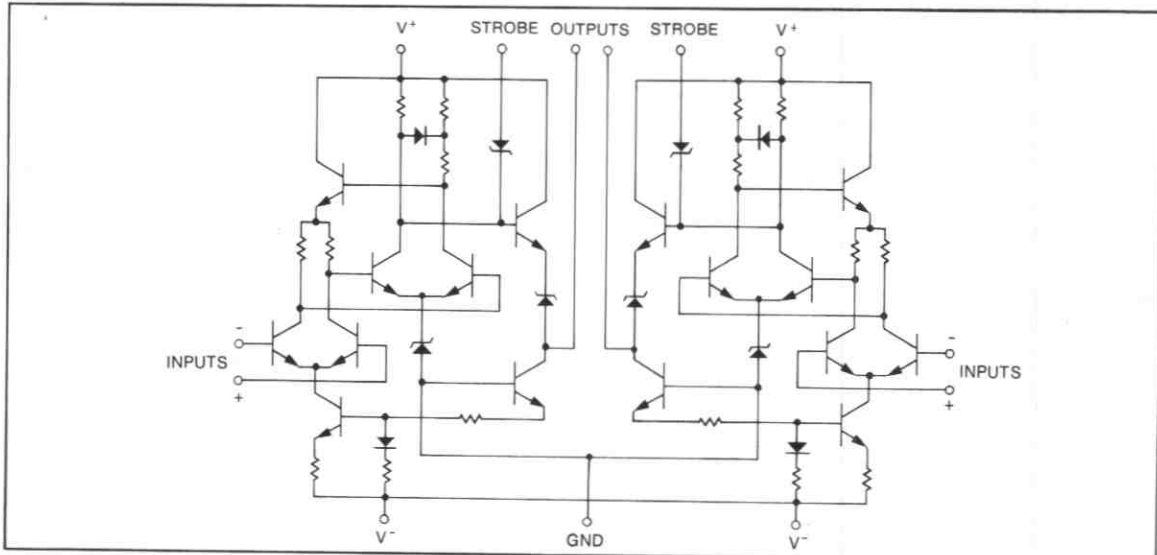
They were designed for low-level sensing and memory sense amplifier applications, as well as A/D converters, Schmitt triggers, and zero crossing detectors.

The RM1514 military version operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC1414 is the commercial type which operates from 0°C to $+70^{\circ}\text{C}$.

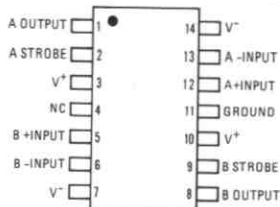
DESIGN FEATURES

- Two Separate Outputs
- Strobe Capability
- High Output Sink Current 2.8mA Minimum Each Comparator
- Input Offset Voltage 1.0mV
- Offset Voltage $3.0\mu\text{V}/^{\circ}\text{C}$
- Short Propagation Delay Time 40ns
- Output Compatible With All Saturating Logic Forms:
 V_{OUT} is +3.2V to -0.5V Typical

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



DC Dual In-line Packages
(Top View)

Order Part Nos.:
RM1514DC, RC1414DC

ABSOLUTE MAXIMUM RATINGS

Power Supply Voltage	+14V, -7.0V
Differential Input Signal	±5.0V
Common-Mode Input Swing	±7.0V
Peak Load Current	10mA
Internal Power Dissipation (Note)	RM1514: 1000mW RM1414: 625mW

Operating Temperature Range	
RM1514	-55°C to +125°C
RC1414	0°C to +75°C
Storage Temperature Range	-65°C to +150°C

ELECTRICAL CHARACTERISTICS (V⁺ = +12Vdc, V⁻ = -6Vdc, T_A = 25°C unless otherwise noted; each comparator.)

PARAMETER	CONDITIONS	RM1514			RC1414			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage (R _S ≤ 200Ω)	V _{OUT} = 1.4Vdc, T _A = 25°C		1.0	2.0		1.5	5.0	mV
	V _{OUT} = 1.8Vdc, T _A = Min.			3.0			6.5	
	V _{OUT} = 1.0Vdc, T _A = Max.			3.0			6.5	
Temperature Coefficient of Input Offset Voltage			3.0			5.0		μV/°C
Input Offset Current	V _{OUT} = 1.4Vdc, T _A = 25°C		1.0	3.0		1.0	5.0	μA
	V _{OUT} = 1.8Vdc, T _A = Min.			7.0			7.5	
	V _{OUT} = 1.0Vdc, T _A = Max.			3.0			7.5	
Input Bias Current	V _{OUT} = 1.4Vdc, T _A = 25°C		12	20		15	25	μA
	V _{OUT} = 1.8Vdc, T _A = Min.			45		18	40	
	V _{OUT} = 1.0Vdc, T _A = Max.			20			40	
Open Loop Voltage Gain	T _A = 25°C	1250	1700		1000	1500		V/V
	T _A = Min. to Max.	1000			800			
Output Resistance			200			200		ohms
Differential Voltage Range		±5.0			±5.0			V
Positive Output Voltage	V _{IN} ≥ 5.0mV, 0 ≤ I _O ≤ 5.0mA	2.5	3.2	4.0	2.5	3.2	4.0	V
Negative Output Voltage	V _{IN} ≥ -5.0mV	-1.0	-0.5	0	-1.0	-0.5	0	V
Output Sink Current	V _{IN} ≥ -5.0mV, V _{OUT} ≥ 0, T _A = Min. to Max.	2.8	3.4		1.6	2.5		mA
Input Common Mode Range	V ⁻ = -7.0Vdc	±5.0			±5.0			V
Common Mode Rejection Ratio	V ⁻ = -7.0Vdc, R _S ≤ 200Ω	80	100		70	100		dB
Propagation Delay Time For Positive and Negative Going Input Pulse	V overdrive = 5mV		40			40		ns
Total Power Supply Current	V _{OUT} ≤ 0Vdc		12.8	18		12.8	18	mA
			11	14		11	14	
Total Power Consumption			230	300		230	300	mW

NOTE:

Derate above T_A = 25°C.
DC Package: 6.0mW/°C. DB Package: 5.0mW/°C.



THE NEW 4151. WORLD'S FIRST MONOLITHIC IC VFC.

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RAYTHEON SEMICONDUCTOR

SECTION 5

Line Drivers and Receivers

CONTENTS

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1489/1489A Quad Line Receivers	5-4
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DESCRIPTION

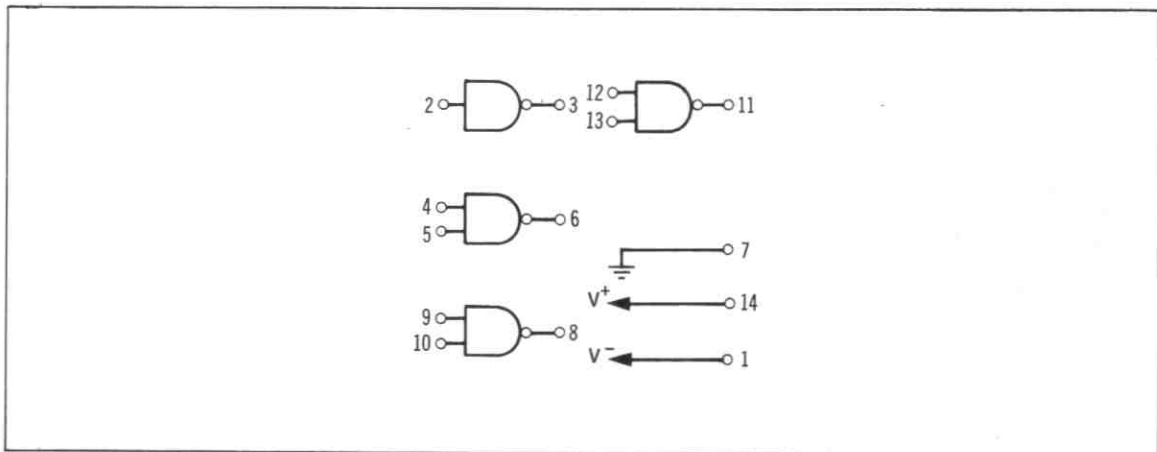
The RC1488 is a monolithic quad line driver designed to interface data terminal equipment with data communications equipment in conformance with the specifications of EIA standard number RS-232-C. This standard specifies not only the number and type of interface leads, but also the voltage levels to be used.

The RC1488 and its companion circuit, the RC1489/RC1489A quad line receiver, provide a complete interface system between DTL and TTL logic levels and the RS-232-C defined levels.

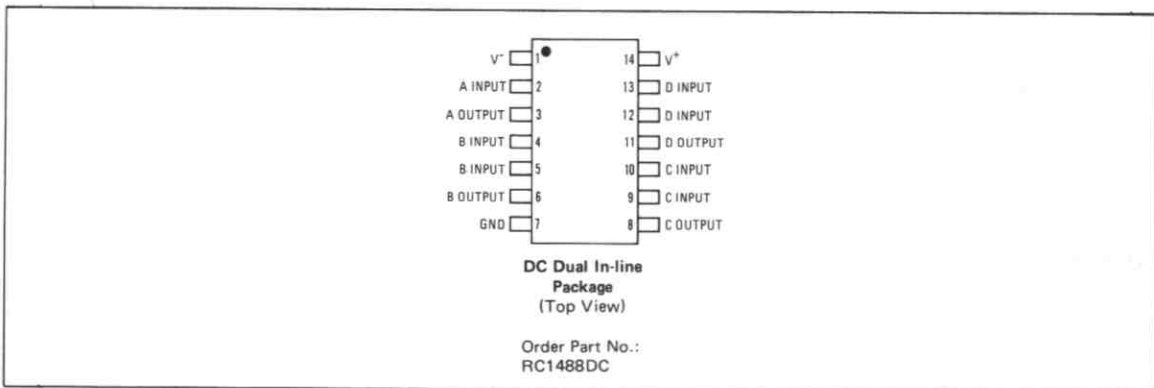
DESIGN FEATURES

- Current Limited Output 10mA Typical
- Power-off Source Impedance 300 Ohms Minimum
- Simple Slew Rate Control With External Capacitor
- Flexible Operating Supply Range
- Compatible With All DTL and TTL Logic

LOGIC DIAGRAM



CONNECTION INFORMATION



ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$ unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Power Supply Voltage	V ⁺	+15	V
	V ⁻	-15	
Input Signal Voltage	V _{in}	$-15 \leq V_{in} \leq 7.0$	V
Output Signal Voltage	V _O	±15	V
Power Derating (Package Limitation, Ceramic Dual In-Line Package) Derate above $T_A = +25^\circ\text{C}$	P _D	1000	mW
	1/θ _{JA}	6.7	mW/°C
Operating Temperature Range	T _A	0 to +75	°C
Storage Temperature Range	T _{stg}	-65 to +175	°C

ELECTRICAL CHARACTERISTICS ($V^+ = +9.0 \pm 1\% \text{Vdc}$, $V^- = -9.0 \pm 1\% \text{Vdc}$, $T_A = 0^\circ\text{C}$ to $+75^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Input Current	I _F	V _{in} = 0V		1.0	1.3	mA
Reverse Input Current	I _R	V _{in} = +5.0V			10	μA
Output Voltage High	V _{OH}	V _{in} = 0.8V, R _L = 3.0kΩ, V ⁺ = +9.0V, V ⁻ = -9.0V	+6.0	+7.0		V
		V _{in} = 0.8V, R _L = 3.0kΩ, V ⁺ = +13.2V, V ⁻ = -13.2V	+9.0	+10.5		
Output Voltage Low	V _{OL}	V _{in} = 1.9Vdc, R _L = 3.0kΩ, V ⁺ = +9.0V, V ⁻ = -9.0V	-6.0	-7.0		V
		V _{in} = 1.9Vdc, R _L = 3.0kΩ, V ⁺ = +13.2V, V ⁻ = -13.2V	-9.0	-10.5		
Positive Output Short-Circuit Current	I _{SC+}		+6.0	+10	+12	mA
Negative Output Short-Circuit Current	I _{SC-}		-6.0	-10	-12	mA
Output Resistance	R _O	V ⁺ = V ⁻ = 0, V _O = ±2.0V	300			Ω
Positive Supply Current (R _I = ∞)	I ⁺	V _{in} = 1.9Vdc, V ⁺ = +9.0V		+15	+20	mA
		V _{in} = 0.8Vdc, V ⁺ = +9.0V		+4.5	+6.0	
		V _{in} = 1.9Vdc, V ⁺ = +12V		+19	+25	
		V _{in} = 0.8Vdc, V ⁺ = +12V		+5.5	+7.0	
		V _{in} = 1.9Vdc, V ⁺ = +15V			+34	
		V _{in} = 0.8Vdc, V ⁺ = +15V			+12	
Negative Supply Current (R _L = ∞)	I ⁻	V _{in} = 1.9Vdc, V ⁻ = -9.0V		-13	-17	mA
		V _{in} = 0.8Vdc, V ⁻ = -9.0V		0	0	
		V _{in} = 1.9Vdc, V ⁻ = -12V		-18	-23	
		V _{in} = 0.8Vdc, V ⁻ = -12V		0	0	
		V _{in} = 1.9Vdc, V ⁻ = -15V			-34	
		V _{in} = 0.8Vdc, V ⁻ = -15V			-2.5	
Power Dissipation	P _D	V ⁺ = 9.0Vdc, V ⁻ = -9.0V			333	mW
		V ⁺ = 12Vdc, V ⁻ = -12V			576	

SWITCHING CHARACTERISTICS ($V^+ = +9.0 \pm 1\% \text{Vdc}$, $V^- = -9.0 \pm 1\% \text{Vdc}$, $T_A = 25^\circ\text{C}$)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Propagation Delay Time	t _{pd+}	Z _L = 3.0k and 15pF		150	200	ns
Fall Time	t _f	Z _L = 3.0k and 15pF		45	75	ns
Propagation Delay Time	t _{pd-}	Z _L = 3.0k and 15pF		65	120	ns
Rise Time	t _r	Z _L = 3.0k and 15pF		55	100	ns

GENERAL DESCRIPTION

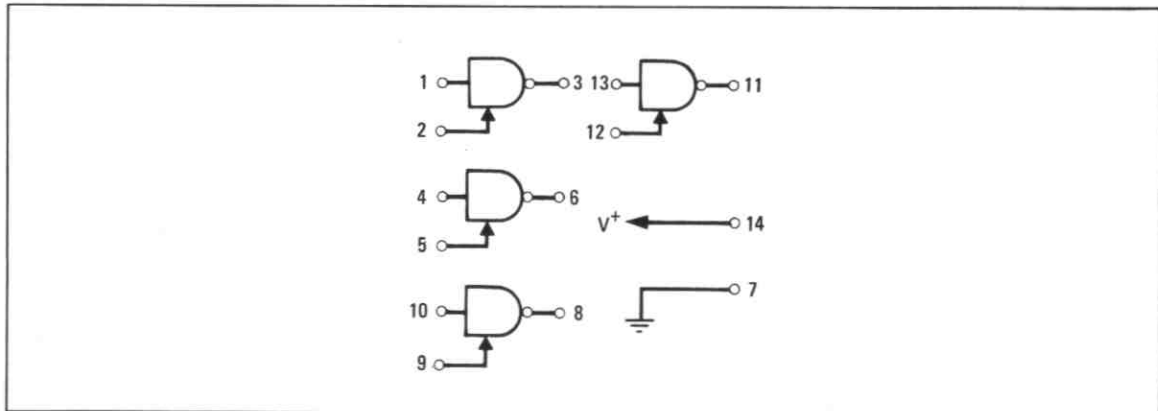
The RC1489 and RC1489A are monolithic quad line receivers designed to interface data terminal equipment in conformance with the specifications of EIA standard number RS-232-C. This standard specifies not only the number and type of interface leads, but also the voltage levels to be used.

The RC1488 quad driver and its companion circuit, the RC1489/RC1489A quad receiver, provide a complete interface system between DTL or TTL logic levels and the RS-232-C defined levels.

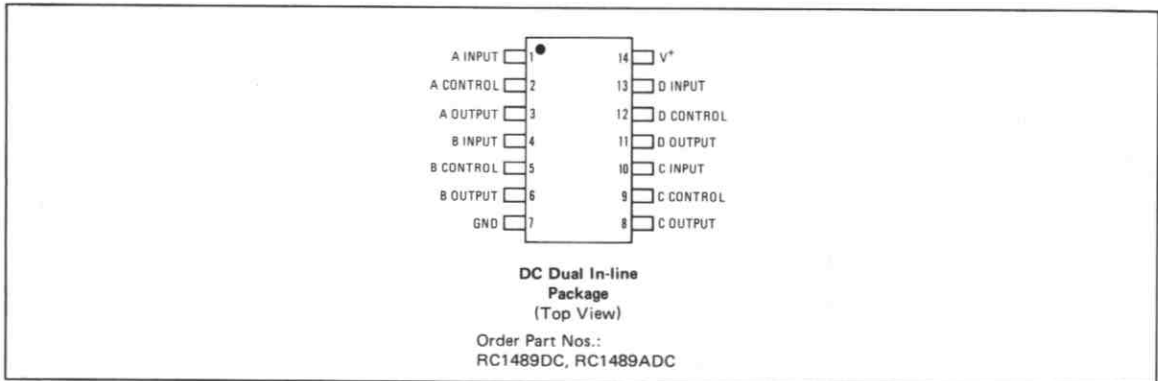
DESIGN FEATURES

- Input Resistance 3k to 7k
- Input Signal Range $\pm 30V$
- Built-in Input Threshold Hysteresis
- Response Control: Logic Threshold Shifting and Input Noise Filtering

LOGIC DIAGRAM



CONNECTION INFORMATION



ABSOLUTE MAXIMUM RATINGS (T_A = +25°C unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Power Supply Voltage	V ⁺	+10	V
Input Signal Range	V _{in}	±30	V
Output Load Current	I _L	20	mA
Power Dissipation (Package Limitation, Ceramic Dual In-Line Package) Derate above T _A = +25°C	P _D	1000	mW
	1/θ _{JA}	6.7	mW/°C
Operating Temperature Range	T _A	0 to +75	°C
Storage Temperature Range	T _{stg}	-65 to +175	°C

ELECTRICAL CHARACTERISTICS

(Response control pin is open. V⁺ = +5.0Vdc ±1%, T_A = 0°C to +75°C unless otherwise noted)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Positive Input Current	I _{IH}	V _{in} = +25V	3.6		8.3	mA
		V _{in} = +3.0V	0.43			
Negative Input Current	I _{IL}	V _{in} = -25V	-3.6		-8.3	mA
		V _{in} = -3.0V	-0.43			
Input Turn-On Threshold Voltage	V _{IH}	T _A = +25°C, V _{OL} ≤ 0.45V RC1489	1.0		1.5	V
		RC1489A	1.75	1.95	2.25	
Input Turn-Off Threshold Voltage	V _{IL}	T _A = +25°C, V _{OH} ≥ 2.5V, I _L = -0.5mA RC1489	0.75		1.25	V
		RC1489A	0.75	0.8	1.25	
Output Voltage High	V _{OH}	V _{in} = 0.75V, I _L = -0.5mA	2.6	4.0	5.0	V
		Input Open Circuit, I _L = -0.5mA	2.6	4.0	5.0	
Output Voltage Low	V _{OL}	V _{in} = 3.0V, I _L = 10mA		0.2	0.45	V
Output Short-Circuit Current	I _{SC}			3.0		mA
Power Supply Current	I ⁺	V _{in} = +5.0V		20	26	mA
Power Dissipation	P _D	V _{in} = +5.0V		100	130	mW

SWITCHING CHARACTERISTICS (V⁺ = +5.0 Vdc ±1%, T_A = +25°C)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Propagation Delay Time	t _{pd+}	R _L = 3.9Ω		25	85	ns
Rise Time	t _r	R _L = 3.9Ω		120	175	ns
Propagation Delay Time	t _{pd-}	R _L = 390Ω		25	50	ns
Fall Time	t _f	R _L = 390Ω		10	20	ns

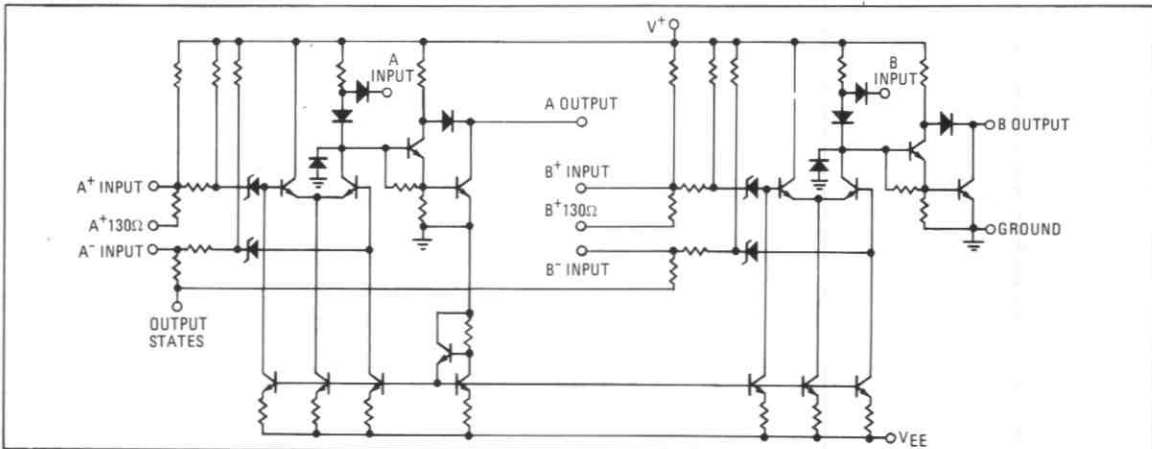
GENERAL DESCRIPTION

The RM9622 and RC9622 are dual line receivers designed to discriminate a worst-case logic swing of 2V from a $\pm 10V$ common-mode noise signal or ground shift. To provide a CCSL-compatible threshold voltage and maximum noise immunity, the differential amplifier has a built-in threshold of 1.5V. The offset is obtained by use of current sources and matched resistors, and varies only $\pm 5\%$ (75mV) over the military and commercial temperature ranges.

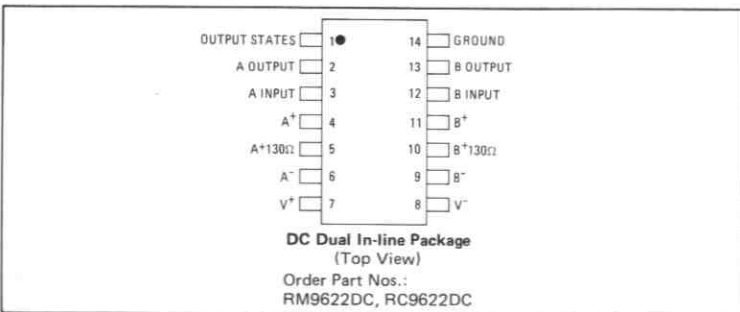
The RM9622 military version operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC9622 is the commercial type which operates from 0°C to $+70^{\circ}\text{C}$.

These dual line receivers offer a choice of output states with the inputs open, without affecting circuit performance by use of S3. At the input of each line receiver a 130-ohm terminating resistor is provided. The output is CCSL-compatible. And the output high level can be increased to +12V by connecting to a positive supply through a resistor. The outputs can be wired OR.

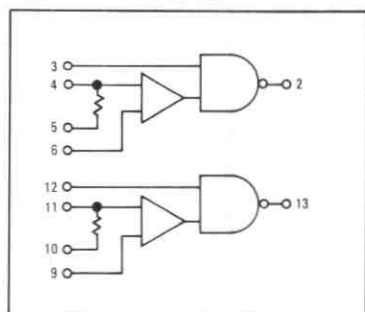
SCHEMATIC DIAGRAM



CONNECTION INFORMATION



LOGIC DIAGRAM



DESIGN FEATURES

- CCSL-Compatible Threshold Voltage
- Input Terminating Resistors
- Choice of Output State With Inputs Open
- CCSL-Compatible Output
- High Common-Mode
- Wire-OR Capability
- Enable Inputs
- Full Military Temperature Range
- Logic Compatible Supply Voltages



ABSOLUTE MAXIMUM RATINGS

V _{CC} , Pin Potential to Ground Pin	-0.5V to +7V	Enable Pin Potential to Ground Pin	-0.5V to -15V
Input Voltage	±15V	Storage Temperature Range	-65°C to +150°C
Voltage Applied to Outputs for High Output State	-0.5V to +13.2V	Operating Temperature Range	
V _{EE} Pin Potential to Ground Pin	-0.5V to -12V	RM9622	-55°C to +125°C
		RC9622	0°C to +70°C

ELECTRICAL CHARACTERISTICS (-55°C to +125°C, V_{CC} = 5.0V ±10%, V_{EE} = -10V ±10%)

SYMBOL	CHARACTERISTICS	CONDITIONS & COMMENTS	LIMITS						UNITS	
			-55°C		+25°C		+125°C			
			MIN	MAX	MIN	TYP	MAX	MIN		MAX
V _{OL}	Output Low Voltage	V _{CC} = 4.5V *V _D DIFF = 2.0V V _{EE} = -11V I _{OL} = 12.4mA		0.40		0.25	0.40		0.40	V
V _{OH}	Output High Voltage	V _{CC} = 4.5V *V _D DIFF = 1.0V V _{EE} = -9.0V I _{OH} = -0.2mA	2.8		3.0	3.3		2.9		V
I _{CEX}	Output Leakage Current	V _{CC} = 4.5V *V _D DIFF = 1.0V V _{EE} = -11V V _C EX = 12V		50			100		200	μA
I _{SC}	Output Shorted Current	V _{CC} = 5.0V *V _D DIFF = 1.0V V _{EE} = -10V V _S C = 0V	-1.3	-3.1	-1.4	-2.15	-3.1	-1.3	-3.1	mA
I _{R(ENABLE)}	Enable Input Leakage Current	V _{CC} = 4.5V S ₃ = 4.5V V _{EE} = -11V V _R = 4.0V					2.0		5.0	μA
I _{F(ENABLE)}	Enable Input Forward Current	V _{CC} = 5.5V S ₃ = 0V V _{EE} = -9.0V V _F = 0V		-1.5		-0.96	-1.5		-1.5	mA
I _{F(+ INPUT)}	+ Input Forward Current	V _{CC} = 5.0V -Input = Gnd V _{EE} = -10V V _F = 0V		-2.3		-1.67	-2.1		-2.0	mA
I _{F(- INPUT)}	- Input Forward Current	V _{CC} , S ₃ = 5.0V + Input = Gnd V _{EE} = -10V V _F = 0V		-2.6		-1.87	-2.4		-2.3	mA
V _{IL(ENABLE)}	Input Low Voltage	V _{CC} = 5.0V ±10% V _{EE} = -10V ±10%		1.3		1.4	1.0		0.7	V
V _{th}	Differential Input Threshold Voltage	V _{CC} = 5.0V ±10% V _{EE} = -10V ±10%	1.0	2.0	1.0	1.5	2.0	1.0	2.0	V
V _{CM}	Common Mode Voltage	V _{CC} = 5.0V *V _D DIFF = 1.0V or 2.0V V _{EE} = -10V			-10	±12	+10			V
R _{130Ω}	Terminating Resistance	V _{CC} = 5.5V V _{EE} = -11V			100	130	175			Ω
I _{CC}	5V Supply Current	S ₃ , + Inputs = 5.5V, -Inputs = 0V				13.7	22.9			mA
I _{EE}	-10V Supply Current	V _{CC} = 5.5V S ₃ , + Inputs = 5.5V, -Inputs = 0V V _{EE} = -11V				-6.5	-11.1			mA
t _{pd+}	Turn-off Time	V _{CC} = 5.0V V _{IN0} → 3.0V, R _L = 3.9kΩ, C _L = 30pF V _{EE} = -10V				38	50			ns
t _{pd-}	Turn-on Time	V _{CC} = 5.0V V _{IN0} → 3.0V, R _L = 0.39kΩ, C _L = 30pF V _{EE} = -10V				35	50			ns

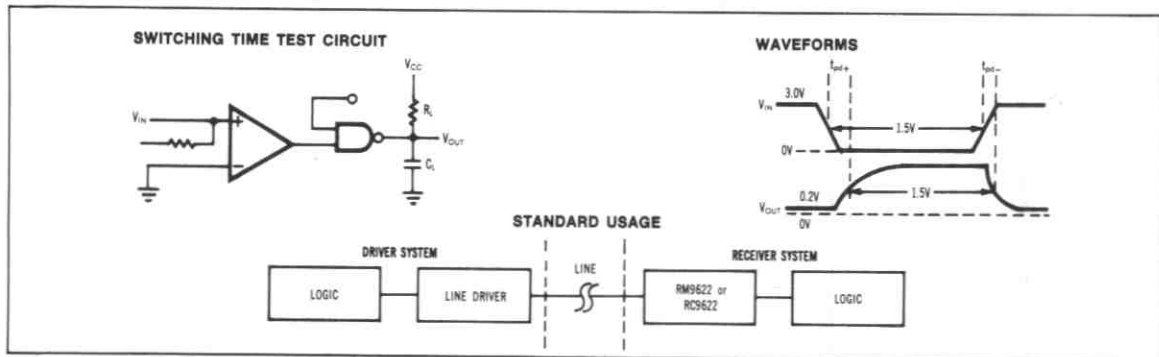
*V_DDIFF is a differential input voltage referred from A+ to A- and from B+ to B-.

ELECTRICAL CHARACTERISTICS (0°C to +75°C, $V_{CC} = 5.0V \pm 5\%$, $V_{EE} = -10V \pm 5\%$)

SYMBOL	CHARACTERISTICS	CONDITIONS & COMMENTS	LIMITS						UNITS	
			0°C		+25°C		+75°C			
			MIN	MAX	MIN	TYP	MAX	MIN		MAX
V_{OL}	Output Low Voltage	$V_{CC} = 4.75V$ $*V_{DIFF} = 2.0V$ $V_{EE} = -10.5V$ $I_{OL} = 14.1mA$		0.45		0.25	0.45		0.45	V
V_{OH}	Output High Voltage	$V_{CC} = 4.75V$ $*V_{DIFF} = 1.0V$ $V_{EE} = -9.5V$ $I_{OH} = -0.2mA$	2.9		3.0	3.3		2.9		V
I_{CEX}	Output Leakage Current	$V_{CC} = 4.75V$ $*V_{DIFF} = 1.0V$ $V_{EE} = -10.5V$ $V_{CEX} = 5.25V$		80			100		200	μA
I_{SC}	Output Shorted Current	$V_{CC} = 5.0V$ $*V_{DIFF} = 1.0V$ $V_{EE} = -10V$ $V_{SC} = 0V$	-1.3	-3.1	-1.4	-2.15	-3.1	-1.3	-3.1	mA
$I_{R(ENABLE)}$	Enable Input Leakage Current	$V_{CC} = 4.75V$ $S_3 = 4.75V$ $V_{EE} = -10.5V$ $V_R = 4.0V$					5.0		10	μA
$I_{F(ENABLE)}$	Enable Input Forward Current	$V_{CC} = 5.25V$ $S_3 = 0V$ $V_{EE} = -9.5V$ $V_F = 0V$		-1.5		-0.96	-1.5		-1.5	mA
$I_{F(+ INPUT)}$	+ Input Forward Current	$V_{CC} = 5.0V$ -Input = Gnd $V_{EE} = -10V$ $V_F = 0V$		-2.6		-1.67	-2.4		-2.3	mA
$I_{F(- INPUT)}$	- Input Forward Current	$V_{CC}, S_3 = 5.0V$ + Input = Gnd $V_{EE} = -10V$ $V_F = 0V$		-2.9		-1.87	-2.7		-2.6	mA
$V_{IL(ENABLE)}$	Input Low Voltage	$V_{CC} = 5.0V \pm 5\%$ $V_{EE} = -10V \pm 5\%$		1.2		1.4	1.0		0.85	V
V_{th}	Differential Input Threshold Voltage	$V_{CC} = 5.0V \pm 5\%$ $V_{EE} = -10V \pm 5\%$	1.0	2.0	1.0	1.5	2.0	1.0	2.0	V
V_{CM}	Common Mode Voltage	$V_{CC} = 5.0V$ $*V_{DIFF} = 1.0V$ or $2.0V$ $V_{EE} = -10V$			-7.5	± 12	+7.5			V
$R_{130\Omega}$	Terminating Resistance	$V_{CC} = 5.25V$ $V_{EE} = -10.5V$			91	130	185			Ω
I_{CC}	5V Supply Current	$S_3, +$ Inputs = 5.25V, -Inputs = 0V				13.7	22.9			mA
I_{EE}	-10V Supply Current	$V_{CC} = 5.25V$ $S_3, +$ Inputs = 5.25V, -Inputs = 0V				-6.5	-11.1			mA
t_{pd+}	Turn-off Time	$V_{CC} = 5.0V$ $V_{EE} = -10V$ $V_{IN0} = 3.0V, R_L = 3.9k\Omega, C_L = 30pF$				38	100			ns
t_{pd-}	Turn-on Time	$V_{CC} = 5.0V$ $V_{EE} = -10V$ $V_{IN0} = 3.0V, R_L = 0.39k\Omega, C_L = 30pF$				35	100			ns

* V_{DIFF} is a differential input voltage referred from A+ to A- and from B+ to B-.

TYPICAL APPLICATIONS

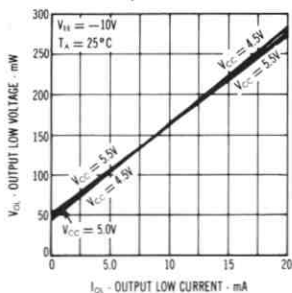


RAYTHEON

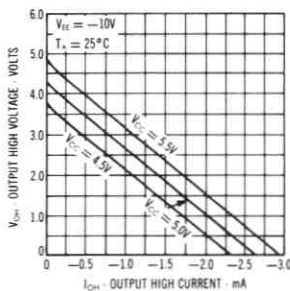
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TYPICAL ELECTRICAL DATA

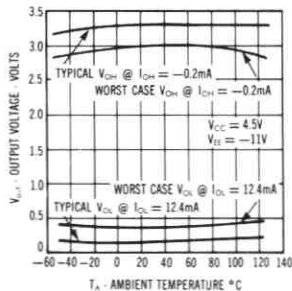
Output Low Voltage versus Output Low Current



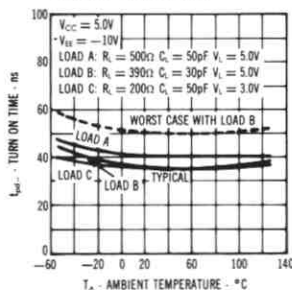
Output High Voltage versus Output High Current



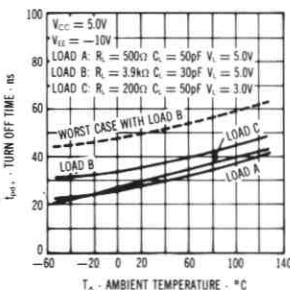
Logic Levels versus Ambient Temperature



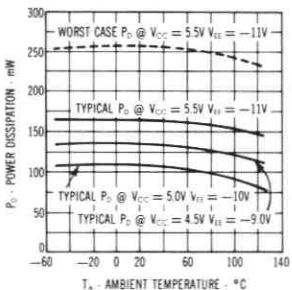
Turn On Time versus Ambient Temperature



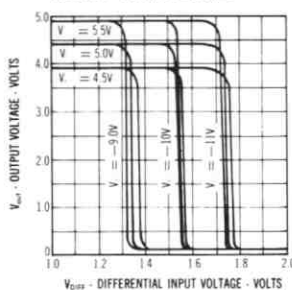
Turn Off Time versus Ambient Temperature



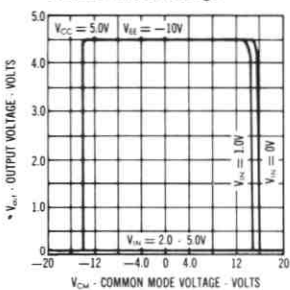
Power Dissipation versus Ambient Temperature



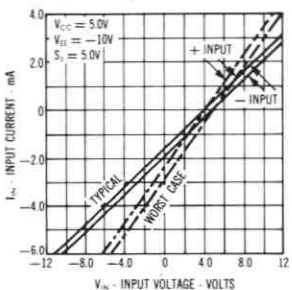
V_{out} - V_{DIFF} Transfer Characteristics



Output Voltage versus Common Mode Voltage



Input Current versus Input Voltage



5



GENERAL DESCRIPTION

The RM8T13/RC8T13 is a monolithic dual line driver designed to drive 50-ohm or 75-ohm coaxial transmission lines. TTL multiple emitter inputs allow this line driver to interface with standard TTL or DTL systems. The outputs are designed to drive long lengths of coaxial cable, strip line, or twisted pair transmission lines with impedances of 50 to 500 ohms.

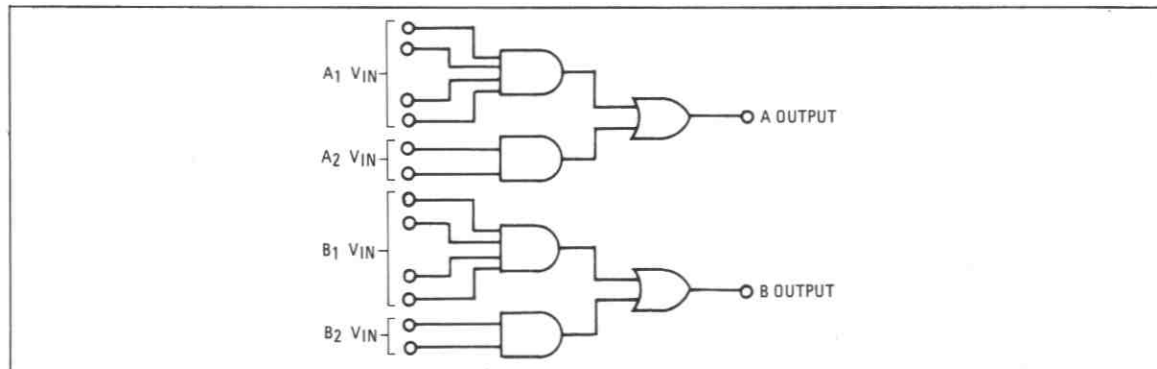
The device incorporates a latch-back short-circuit protection feature which protects the device by limiting the current it may source when operating under conditions of zero load resistance.

The RM8T13 operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC8T13 operates from 0°C to $+75^{\circ}\text{C}$.

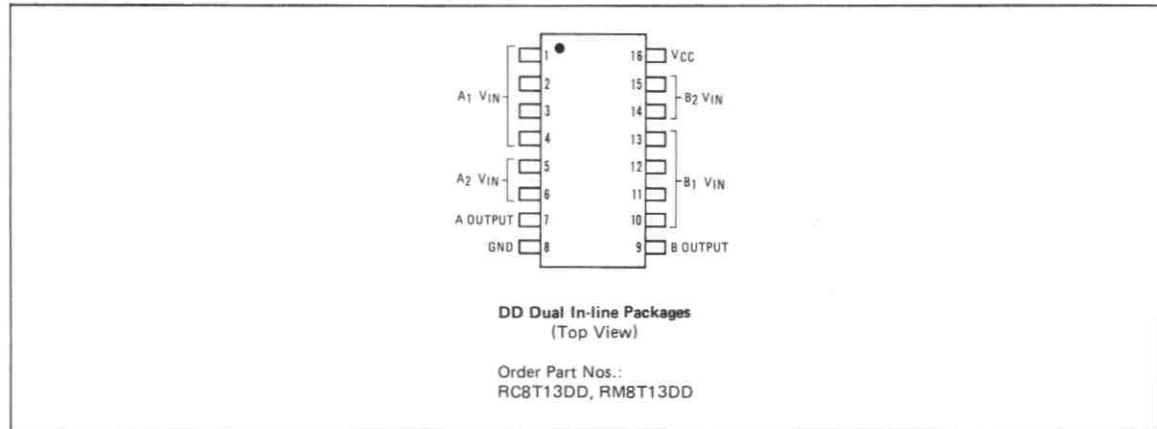
DESIGN FEATURES

- High-Power Drive Specified at -75mA Sink Current Rating at 2.4V (V_{OH}) at 25°C
- Party-Line Operation
- Input Gating Structure Allows Use of "OR" and "AND" Function
- High Speed $t_{\text{ON}} = t_{\text{OFF}} = 20\text{ns}$ Maximum
- Input Clamp Diodes Protect Inputs from Line Ringing
- Single 5V Power Supply

LOGIC DIAGRAM



CONNECTION INFORMATION



ABSOLUTE MAXIMUM RATINGS

Input and Output Voltage, V _{CC}	+6.0V	Storage Temperature	
Input Current	±30mA	MP Package	-65°C to +150°C
Operating Temperature		L and DD Package	-65°C to +200°C
RM8T13	-55°C to +125°C	Thermal Resistance (θ_{J-A} , Junction to Ambient for Each Package)	
RC8T13	0°C to +75°C	MP Package	0.16°C/mW
		L Package	0.12°C/mW
		DD Package	0.10°C/mW

ELECTRICAL CHARACTERISTICS (Recommended Operating Voltage 5V ±5%. Notes 1-5.)

CHARACTERISTICS	LIMITS				TEMP °C		TEST CONDITIONS					NOTES
							V _{CC} (Volts)	AND GATE #1		INPUTS OF #2	OUTPUTS	
								INPUT UNDER TEST	OTHER INPUTS			
MIN	TYP	MAX	UNIT	S	N							
"1" Output Voltage	2.4			V	-55		4.75	2.0V	2.0V	0.8V	-75mA	6
	2.8			V	+25	+25	5.0	2.0V	2.0V	0.8V	-75mA	
	2.6			V		+75.0	4.75	2.0V	2.0V	0.8V	-75mA	
	2.5			V	+125		4.75	2.0V	2.0V	0.8V	-75mA	
"1" Output Leakage Current			500	μA	+25	+25	0.0	0V	0V	0V	3.0V	8
		-700		μA	+125	+75	5.25	0.8V	4.5V	0V	0V	
"0" Output Leakage Current			-10	μA	+25	+25	5.25	0.8V	4.5V	0V	0V	
				μA	+25	+25	5.25	0.8V	4.5V	0V	0V	
"0" Input Current	-0.1		-1.6	mA	-55,+25, +125	0,+25, +75	5.25	0.4V	4.5V			
"1" Input Current			25	μA	+125	+75	5.0	4.5V	0V			
Turn-On Delay			20	ns	+25	+25	5.0					9, 12
		32		ns	+25	+25	5.0					10, 12
Turn-Off Delay			20	ns	+25	+25	5.0					9, 12
		22		ns	+25	+25	5.0					10, 12
Power/Current Consumption: Output at "0"			315/60	mW/mA	+25	+25	5.25	0.8V	0.8V	0.8V		11
			150/28	mW/mA	+25	+25	5.25	2.0V	2.0V	2.0V		
Input Latch Voltage	5.5			V	+25	+25	5.0	10mA	0V	0V		7
"1" Output Current	-100		-250	mA	+25	+25	5.0	4.5V	4.5V	0V	2.0V	13
Output Short Circuit			-30	mA	+25	+25	5.0	4.5V	4.5V	0V	0V	13
Input Clamp Voltage			-1.5	V	+25	+25	5.0	-12mA				

NOTES:

- All voltage measurements are referenced to the ground terminal. Terminals not specifically referenced are left electrically open.
- All measurements are taken with ground pin tied to zero volts.
- Positive current is defined as into the terminal referenced.
- Positive logic definition: "UP" Level = "1", "DOWN" Level = "0".
- Precautionary measures should be taken to ensure current limiting in accordance with Absolute Maximum Ratings should the isolation diodes become forward biased.
- Output source current is supplied through a resistor to ground.
- This test guarantees operation free of input latch-up over the specified operating supply voltage range.
- With forced output voltage of 3 Volts no more than 500μA will enter the driver when output is in "0" state.
- R_L = 37Ω to ground.
- Load is 37Ω in parallel with 1000pF.
- I_{CC} is dependent upon loading. I_{CC} limit specified is for no-load test condition.
- Reference AC Test Circuit and Pulse Requirements.
- Reference "Typical Output Current vs. Output Voltage Curve."
- Output sink current is supplied through a resistor to V_{CC}.
- One DC fan-out is defined as 0.8mA.
- Hysteresis is defined as voltage difference between R input level at which output begins to go from "0" to "1" state and level at which output begins to go from "1" to "0".
- See Hysteresis test circuit.
- Previous condition is a "1" output state.
- Previous condition is a "0" output state.
- One AC fan-out is defined at 50pF.

GENERAL DESCRIPTION

The RM8T14/RC8T14 is a triple line receiver designed for applications requiring digital information to be transmitted over long lengths of coaxial cable, strip line, or twisted pair transmission lines.

The receiver's high impedance input structure presents a minimal load to the driver circuit and allows the transmission line to be terminated in its characteristic impedance to minimize line reflections. The built-in hysteresis characteristic of the RM8T14/RC8T14 also makes it ideal for such applications as Schmitt triggers, one-shots and oscillators.

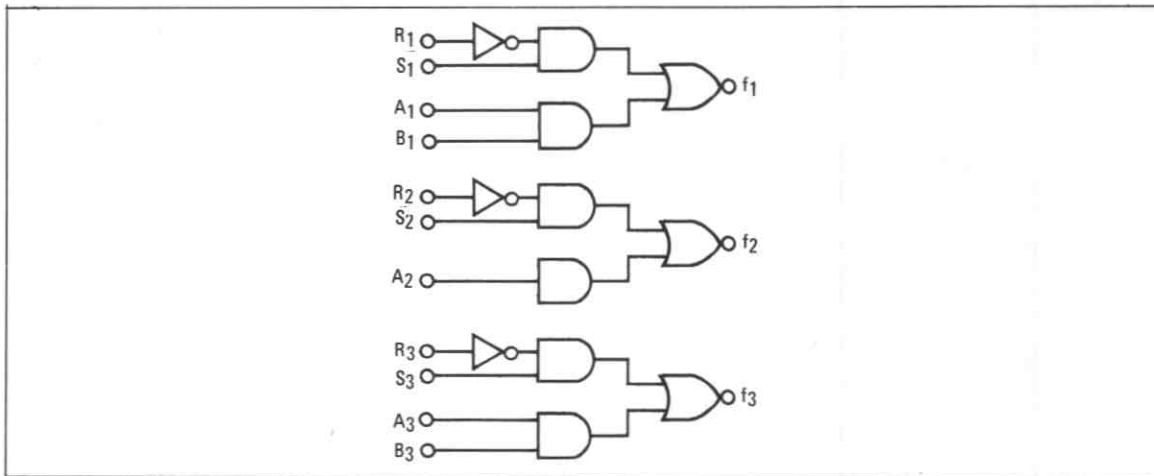
The RM8T14 operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC8T14 operates from 0°C to $+75^{\circ}\text{C}$.

DESIGN FEATURES

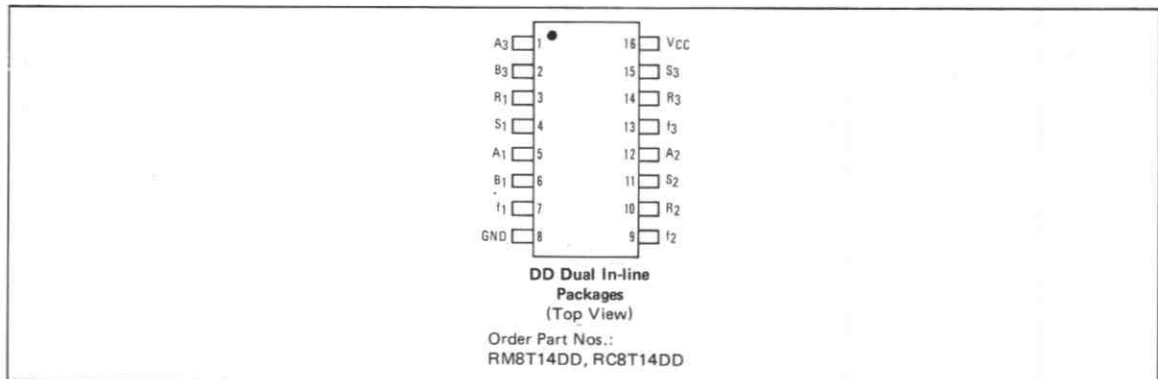
- Built-in Input Threshold Hysteresis*
- High Speed $t_{\text{ON}} = t_{\text{OFF}} = 20\text{ns}$ Typical
- Each Channel Can Be Strobed Independently
- Fanout of 10 With Standard TTL IC
- Input Gating Increases Application Flexibility
- Operates From Single 5V Logic Supply

*Hysteresis is defined as the difference between the input threshold for the "1" and "0" output states. Hysteresis is specified at 0.5V typically and 0.3V minimum over the operating temperature range.

LOGIC DIAGRAM



CONNECTION INFORMATION



ABSOLUTE MAXIMUM RATINGS

Input and Output Voltage, V_{CC}	+6.0V	Storage Temperature	
Input Current	$\pm 30\text{mA}$	MP Package	-65°C to $+150^{\circ}\text{C}$
Output Current	$\pm 100\text{mA}$	L Package	-65°C to $+200^{\circ}\text{C}$
Operating Temperature		Thermal Resistance (θ_{JA} , Junction to Ambient for Each Package)	
RM8T14	-55°C to $+125^{\circ}\text{C}$	MP Package	$0.16^{\circ}\text{C}/\text{mW}$
RC8T14	0°C to $+75^{\circ}\text{C}$	L Package	$0.12^{\circ}\text{C}/\text{mW}$

ELECTRICAL CHARACTERISTICS (Recommended Operating Voltage 5V $\pm 5\%$, Notes 1-6.)

CHARACTERISTICS	LIMITS			UNIT	TEST CONDITIONS								NOTES
	Min	Typ	Max		TEMP $^{\circ}\text{C}$		V_{CC} (Volts)	INPUTS				OUTPUTS	
					S	N		R	S	A	B		
"1" Output Voltage	2.6			V	$-55,+125$	$0,+75$	4.75	2.0V	4.5V	0V	0V	$-500\mu\text{A}$	6
	2.8			V	$+25$	$+25$	5.00	2.0V	4.5V	0V	0V	$-500\mu\text{A}$	6
	2.6			V	$-55,+125$	$0,+75$	4.75	0V	0.8V	0V	0V	$-500\mu\text{A}$	6
	2.8			V	$+25$	$+25$	5.00	0V	0.8V	0V	0V	$-500\mu\text{A}$	6
Receiver "Hold" Test Condition	2.6			V	$-55,+125$	$0,+75$	5.00	1.45V	4.5V	0V	0V	$-500\mu\text{A}$	6, 18
	2.8			V	$+25$	$+25$	5.00	1.45V	4.5V	0V	0V	$-500\mu\text{A}$	6, 18
"0" Output Voltage			0.4	V	$-55,+125$	$0,+75$	4.75	0.8V	2.0V	0V	0V	16mA	14
			0.4	V	$+25$	$+25$	5.00	0.8V	2.0V	0V	0V	16mA	14
			0.4	V	$-55,+125$	$0,+75$	4.75	0V	0V	2.0V	2.0V	16mA	14
			0.4	V	$+25$	$+25$	5.00	0V	0V	2.0V	2.0V	16mA	14
Receiver "Hold" Test Condition			0.4	V	$-55,+125$	$0,+25$	5.00	1.45V	4.5V	0V	0V	16mA	14, 19
"0" Input Current	S_n	-0.1	-1.6	mA	$-55,+25$	$0,+25$	5.25	0V	0.4V				
	A_n	-0.1	-1.6	mA	$-55,+25$	$0,+25$	5.25	0V		0.4V			
	B_n	-0.1	-1.6	mA	$-55,+25$	$0,+25$	5.25				0.4V		
"1" Input Current	R_n		0.17	mA	$+125$	$+75$	5.25	3.8V					
	S_n		40	μA	$+125$	$+75$	5.25	3.8V	4.5V				
	A_n		40	μA	$+125$	$+75$	5.25			4.5V	0V		
	B_n		40	μA	$+125$	$+75$	5.25			0V	4.5V		
Turn-on Propagation Delay		20	30	ns	$+25$	$+25$	5.00					DCFO=20	15
Turn-Off Propagation Delay		20	30	ns	$+25$	$+25$	5.00					DCFO=20	15
Hysteresis	0.30	0.50		V	$-55,+25$	$0,+25$	5.00		4.5V	0V	0V		16, 17
Power/Current Consumption		315/60	380/72	mW/mA	$+25$	$+25$	5.25						
Input Latch Voltage	S	5.5		V	$+25$	$+25$	5.00	3.8V	10mA	0V	0V		7
	A	5.5		V	$+25$	$+25$	5.00	0V	0V	10mA	0V		7
	B	5.5		V	$+25$	$+25$	5.00	0V	0V	0V	10mA		7
Output Short-Circuit Current	-50		-100	mA	$+25$	$+25$	5.00	3.8V	0V	0V	0V		
Input Clamp Voltage S, A, B			-1.5	V	$+25$	$+25$	5.00		-12mA	-12mA	-12mA		
Output Fall Time			50	ns	-55	0	4.75					ACFO=6	20

NOTES:

1. All voltage measurements are referenced to the ground terminal. Terminals not specifically referenced are left electrically open.
2. All measurements are taken with ground pin tied to zero volts.
3. Positive current is defined as into the terminal referenced.
4. Positive logic definition: "UP" Level = "1", "DOWN" Level = "0".
5. Precautionary measures should be taken to ensure current limiting in accordance with Absolute Maximum Ratings should the isolation diodes become forward biased.
6. Output source current is supplied through a resistor to ground.
7. This test guarantees operation free of input latch-up over the specified operating supply voltage range.
8. With forced output voltage of 3 Volts no more than 500 μ A will enter the driver when output is in "0" state.
9. $R_L = 37\Omega$ to ground.
10. Load is 37 Ω in parallel with 1000pF.
11. I_{CC} is dependent upon loading. I_{CC} limit specified is for no-load test condition.
12. Reference AC Test Circuit and Pulse Requirements.
13. Reference "Typical Output Current vs. Output Voltage Curve."
14. Output sink current is supplied through a resistor to V_{CC} .
15. One DC fan-out is defined as 0.8mA.
16. Hysteresis is defined as voltage difference between R input level at which output begins to go from "0" to "1" state and level at which output begins to go from "1" to "0".
17. See Hysteresis test circuit.
18. Previous condition is a "1" output state.
19. Previous condition is a "0" output state.
20. One AC fan-out is defined at 50pF.



GENERAL DESCRIPTION

The RM8T23/RC8T23 is a dual line driver designed to meet all the requirements of the IBM System 360 interface specification for interface drivers.

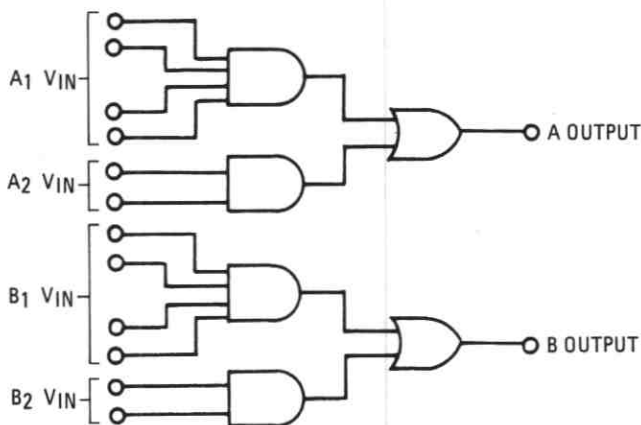
The low impedance emitter follower output will drive terminated lines such as coaxial cable or twisted pair. The output is protected against accidental shorting by an internal clamping network which turns on once the output voltage drops below approximately 1.5V. The uncommitted emitter output structure allows "Dot-OR" logic to be performed as in "party-line" operations.

The RM8T23 operates from -55°C to $+125^{\circ}\text{C}$; the RC8T23 from 0°C to $+70^{\circ}\text{C}$.

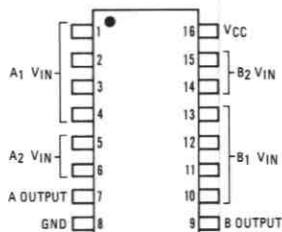
DESIGN FEATURES

- Output Current 59.3mA at 3.11V
- Uncommitted Emitter Output Structure for Party-Line Operation
- Short-Circuit Protection
- Single 5V Power Supply
- AND-OR Logic Configuration

LOGIC DIAGRAM



CONNECTION INFORMATION



DD Dual In-line
Packages
(Top View)

Order Part Nos.:
RM8T23DD, RC8T23DD

ABSOLUTE MAXIMUM RATINGS

Input Voltage	+5.5V	Operating Temperature	
Output Voltage	+7.0V	RM8T23	-55°C to +125°C
V _{CC}	+7.0V	RC8T23	0°C to +75°C
Input Current	±30mA	Storage Temperature	-65°C to +150°C

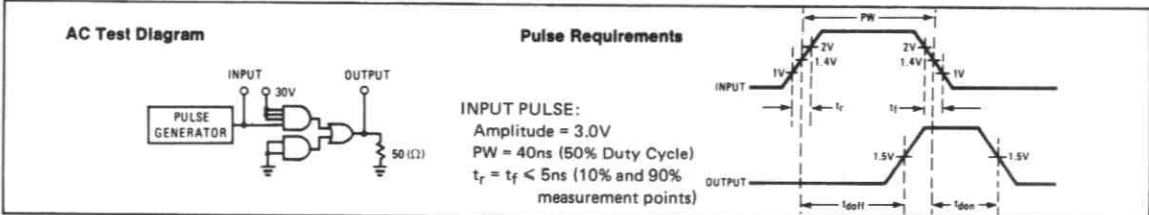
ELECTRICAL CHARACTERISTICS (Over Full Operating Temperature and Voltage Ranges)

CHARACTERISTICS	LIMITS				TEST CONDITIONS				NOTES
					AND GATE #1		INPUTS OF #2 AND GATE	OUTPUT	
					INPUT UNDER TEST	OTHER INPUT			
MIN	TYP	MAX	UNITS						
"0" Output Voltage			+0.15	V				-240μA	7
"1" Output Leakage Current			40	μA	0V	0V	0V	3.0V	1, 14
"0" Input Current	-0.1		-1.6	mA	0.4V	4.5V			
"1" Input Current			40	μA	4.5V	0V			
V_{CC} = 5.0V, T_A = 25°C									
"1" Output Voltage	3.11			V	2.0V	2.0V	0.8V	59.3mA	
Turn-on Delay		12	20	ns					8, 12
		30	50	ns					9, 12
Turn-off Delay		12	20	ns					8, 12
		20	35	ns					9, 12
Power/Current Consumption									
	Output at "0"		315/60	mW/mA	0.8V	0.8V	0.8V		11, 15
Output at "1"			150/28	mW/mA	2.0V	2.0V	2.0V		
Input Latch Voltage	5.5			V	10mA	0V	0V		10
"1" Output Current	-100		-250	mA	4.5V	4.5V	0V	2.0V	13
Input Clamp Voltage			-1.5	V	-12mA				13

NOTES:

- All voltage measurements are referenced to the ground terminal. Terminals not specifically referenced are left electrically open.
- All measurements are taken with ground pin tied to zero volts.
- Positive current is defined as into the terminal referenced.
- Positive logic definition: "UP" Level = "1", "DOWN" Level = "0".
- Precautionary measures should be taken to ensure current limiting in accordance with Absolute Maximum Ratings should the isolation diodes become forward biased.
- Output source current is supplied through a resistor to ground.
- With forced output current of 240μA the output voltage must not exceed 0.15V.
- R_L = 50 ohms to ground.
- Load is 50 ohms in parallel with 1000pF.
- This test guarantees operation free of input latch-up over the specified operating supply voltage range.
- I_{CC} is dependent upon loading. I_{CC} limit specified is for no-load test condition for both drivers.
- Reference AC Test Circuit and Pulse Requirements.
- Reference "Typical Output Current vs. Output Voltage Curve."
- V_{CC} = 0.00V.
- V_{CC} = 5.25V.
- Output sink current is supplied through a resistor to V_{CC}.
- Hysteresis is defined as voltage difference between R input level at which output begins to go from "0" to "1" state and level at which output begins to go from "1" to "0".
- See Hysteresis test circuit.

AC TEST CIRCUIT AND WAVEFORMS



GENERAL DESCRIPTION

The RM8T24/RC8T24 are triple line receivers designed specifically to meet the IBM System 360 interface specification. Each receiver incorporates hysteresis to provide high noise immunity and high input impedance to minimize loading on the driver circuit.

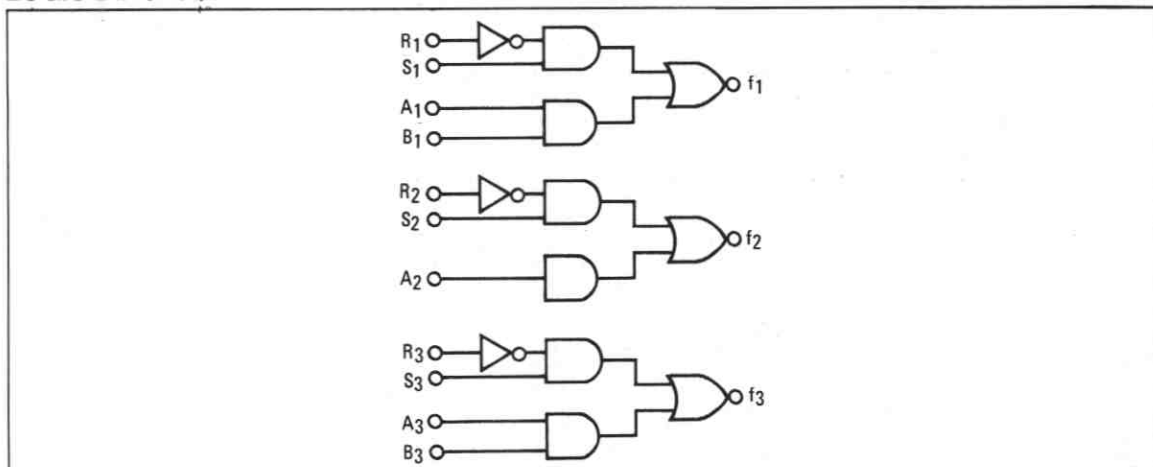
The RM8T24/RC8T24 is fully compatible with TTL and DTL systems and operates from a single 5V power supply.

The RM8T24 operates over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC8T24 operates from 0°C to $+70^{\circ}\text{C}$.

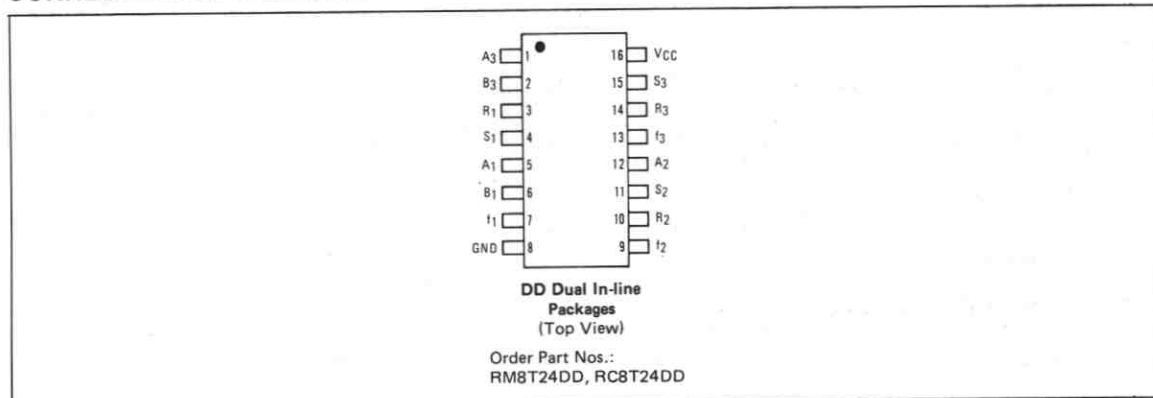
DESIGN FEATURES

- Built-in Input Threshold Hysteresis*
- High Speed $t_{\text{ON}} = t_{\text{OFF}} = 20 \text{ ns}$ Typical
- Each Channel Can Be Strobed Independently
- Fanout of 10 With Standard TTL IC
- Input Gating Increases Application Flexibility
- Operates From Single 5V Logic Supply

LOGIC DIAGRAM



CONNECTION INFORMATION



*Hysteresis is defined as the difference between the input threshold for the "1" and "0" output states. Hysteresis is specified at 0.4V typically and 0.2V minimum over the operating temperature range.

ABSOLUTE MAXIMUM RATINGS

Input and Output Voltage, V_{CC}	+7.0V	Operating Temperature	
Input Current	± 30 mA	RM8T24	-55°C to +125°C
Output Current	± 100 mA	RC8T24	0°C to +75°C
		Storage Temperature	-65°C to +150°C

ELECTRICAL CHARACTERISTICS (Over Recommended Temperature and Voltage Ranges)

CHARACTERISTIC	LIMITS				TEST CONDITIONS					NOTES
	MIN	TYP	MAX	UNITS	R	S	A	B	OUTPUTS	
"1" Output Voltage	2.6	3.4		V	1.7V	4.5V	0V	0V	-800 μ A	6
	2.6	3.4		V	0V	0.8V	0V	0V	-800 μ A	
"0" Output Voltage		0.2	0.4	V	0.7V	2.0V	0V	0V	16mA	16
		0.2	0.4	V	0V	0V	2.0V	2.0V	16mA	
"0" Input Current	S_n	-0.1		-1.6	mA	0V	0.4V			
	A_n	-0.1		-1.6	mA	0V		0.4V		
	B_n	-0.1		-1.6	mA				0.4V	
"1" Input Current	R_n			0.17	mA	3.8V				14
	R_n			5.0	mA	7.0V				
	R_n			5.0	mA	6.0V				
	S_n			40	μ A	3.8V	4.5V			
	A_n			40	μ A			4.5V	0V	
	B_n			40	μ A			0V	4.5V	
$V_{CC} = 5.0V, T_A = 25^\circ C$										
Turn-on Propagation Delay		20	30	ns						12
Turn-off Propagation Delay		20	30	ns						12
Hysteresis	0.2	0.4		V		4.5V	0V	0V		17, 18
Power/Current Consumption		315 60	380 72	mW/mA						15
Input Latch Voltage	S	5.5		V	3.8V	10mA	0V	0V		10
	A	5.5		V	0V	0V	0V	10mA		
	B	5.5		V	0V	0V	0V	10mA		
Output Short-Circuit Current	-50		-100	mA	3.8V	0V	0V	0V		
Input Clamp Voltage	S		-1.5	V		-12mA				
	A		-1.5	V			-12mA			
	B		-1.5	V				-12mA		

NOTES:

- All voltage measurements are referenced to the ground terminal. Terminals not specifically referenced are left electrically open.
- All measurements are taken with ground pin tied to zero volts.
- Positive current is defined as into the terminal referenced.
- Positive logic definition: "UP" Level = "1", "DOWN" Level = "0".
- Precautionary measures should be taken to ensure current limiting in accordance with Absolute Maximum Ratings should the isolation diodes become forward biased.
- Output source current is supplied through a resistor to ground.
- With forced output current of 240 μ A the output voltage must not exceed 0.15V.
- $R_L = 50$ ohms to ground.
- Load is 50 ohms in parallel with 1000pF.
- This test guarantees operation free on input latch-up over the specified operating supply voltage range.
- I_{CC} is dependent upon loading. I_{CC} limit specified is for no-load test condition for both drivers.
- Reference AC Test Circuit and Pulse Requirements.
- Reference "Typical Output Current vs. Output Voltage Curve."
- $V_{CC} = 0.00V$.
- $V_{CC} = 5.25V$.
- Output sink current is supplied through a resistor to V_{CC} .
- Hysteresis is defined as voltage difference between R input level at which output begins to go from "0" to "1" state and level at which output begins to go from "1" to "0".
- See Hysteresis test circuit.



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GENERAL DESCRIPTION

The RM55325/RC75325 are monolithic integrated circuit memory drivers with logic inputs designed for use with magnetic memories.

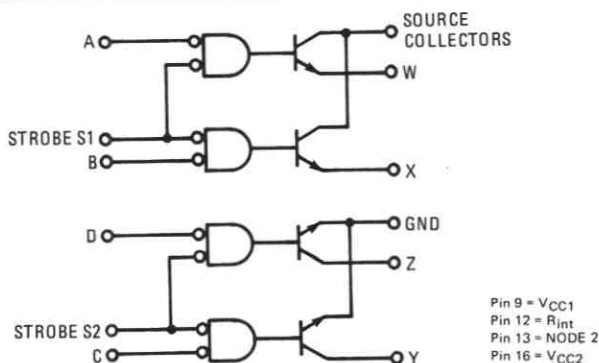
The devices contain two 600mA source switch pairs and two 600mA sink-switch pairs. Source selection is determined by one of two logic inputs, and source turn-on is determined by the source strobe. Likewise, sink selection is determined by one of two logic inputs, and sink turn-on is determined by the sink strobe. This arrangement allows selection of one of the four switches and its subsequent turn-on with minimum time skew of the output current rise.

The RM55325 will operate over a temperature range of -55°C to $+125^{\circ}\text{C}$. The RC75325 operates from 0°C to $+70^{\circ}\text{C}$.

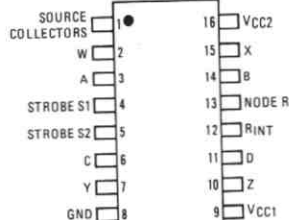
DESIGN FEATURES

- 600mA Output Capability
- Fast Switching Times
- Output Short-Circuit Protection
- Dual Sink and Dual Source Outputs
- Minimum Time Skew Between Address and Output Current Rise
- 24V Output Capability
- Source Base Drive Externally Adjustable
- TTL or DTL Compatibility
- Input Clamping Diodes
- Transformer Coupling Eliminated
- Reliability Increased
- Drive Line Lengths Reduced
- Use of External Components Minimized

LOGIC DIAGRAM



CONNECTION INFORMATION



DD Dual In-line Packages
(Top View)

Order Part Nos.:
RM55325DD, RC75325DD

TRUTH TABLE

Address Inputs				Strobe Inputs		Outputs			
Source		Sink		Source	Sink	Source	Sink	Source	Sink
A	B	C	D	S1	S2	W	X	Y	Z
L	H	X	X	L	H	ON	OFF	OFF	OFF
H	L	X	X	L	H	OFF	ON	OFF	OFF
X	X	L	H	H	L	OFF	OFF	ON	OFF
X	X	H	L	H	L	OFF	OFF	OFF	ON
X	X	X	X	H	H	OFF	OFF	OFF	OFF
H	H	H	H	X	X	OFF	OFF	OFF	OFF

H = high level, L = low level, X = irrelevant
NOTE: Not more than one output is to be on at any one time.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage		Operating Temperature	
V _{CC1} (Note 1)	7.0V	RM55325	-55°C to +125°C
V _{CC2} (Note 1)	25V	RC75325	0°C to +70°C
Input Voltage (any address or strobe input)	5.5V	Storage Temperature	-65°C to +150°C
Continuous Total Dissipation (at or below +70°C)	800mW	Lead Temperature (Soldering, 10s)	+300°C

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	55325			75325			UNITS
			MIN	TYP (Note 3)	MAX	MIN	TYP (Note 3)	MAX	
V _{IH}	High Level Input Voltage		2.0			2.0			V
V _{IL}	Low Level Input Voltage				0.8			0.8	V
V _I	Input Clamp Voltage	V _{CC1} =4.5V, I _I =-10mA		-1.3	-1.7		-1.3	-1.7	V
I _(off)	Source-collectors Terminal Off-state Current	V _{CC1} =4.5V, V _{CC2} =24V		3.0	150		3.0	200	μA
V _{OH}	High Level Sink Output Voltage	V _{CC1} =4.5V, I _O =0	19	23		19	23		V
V _(sat)	Saturation Voltage (Note 5)	source outputs	Full range		0.9			0.9	V
			T _A =25°C	0.43	0.7	0.43	0.75		
		sink outputs	Full range		0.9		0.9		
			T _A =25°C	0.43	0.7	0.43	0.75		
I _I	Input Current at maximum Input Voltage	address inputs	V _{CC1} =5.5V,	V _{CC2} =24V,		1.0	1.0	mA	
		strobe inputs	V _I =5.5V			2.0	2.0		
I _{IH}	High Level Input Current	address inputs	V _{CC1} =5.5V,	V _{CC2} =24V,	3.0	40	3.0	40	μA
		strobe inputs	V _I =2.4V		6.0	80	6.0	80	
I _{IL}	Low Level Input Current	address inputs	V _{CC1} =5.5V,	V _{CC2} =24V,	-1.0	-1.6	-1.0	-1.6	mA
		strobe inputs	V _I =0.4V		-2.0	-3.2	-2.0	-3.2	
I _{CC(off)}	Supply Current, All Sources and Sinks Off	from V _{CC1}	V _{CC1} =5.5V,	V _{CC2} =24V,	14	22	14	22	mA
		from V _{CC2}	T _A =25°C			7.5	20	7.5	
I _{CC1}	Supply Current from V _{CC1} , Either Sink On	V _{CC1} =5.5V, I _(sink) =50mA,	V _{CC2} =24V, T _A =25°C		55	70	55	70	mA
I _{CC2}	Supply Current from V _{CC2} , Either Source On	V _{CC1} =5.5V, I _(source) =-50mA,	V _{CC2} =24V, T _A =25°C		32	50	32	50	mA

SWITCHING CHARACTERISTICS (V_{CC1} = 5V, T_A = 25°C)

PARAMETER	TO (OUTPUT)	CONDITIONS	MIN	TYP	MAX	UNITS
t _{PLH}	Source Collectors	V _{CC2} = 15V, R _L = 24Ω, C _L = 25pF		25	50	ns
t _{PHL}				25	50	
t _{TLH}	Source Outputs	V _{CC2} = 20V, R _L = 1kΩ, C _L = 25pF		55		ns
t _{THL}				7.0		
t _{PLH}	Sink Outputs	V _{CC2} = 15V, R _L = 24Ω, C _L = 25pF		20	45	ns
t _{PHL}				20	45	
t _{TLH}	Sink Outputs	V _{CC2} = 15V, R _L = 24Ω, C _L = 25pF		7.0	15	ns
t _{THL}				9.0	20	
t _S	Sink Outputs	V _{CC2} = 15V, R _L = 24Ω, C _L = 25pF		15	30	ns

NOTES:

1. Voltage values are with respect to network ground terminal.
2. These parameters must be measured using pulse techniques t_w = 200μs, duty cycle < 2%.
3. All typical values are at T_A = 25°C.
4. Not more than one output is to be on at any one time.

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SECTION 6

Special Functions

CONTENTS

555 Timer	6-2
556 Dual Timer	6-6
4151 Voltage-to-Frequency Converter	6-10
4444 4x4x2 Balanced Switching	6-17
Crosspoint Array	

GENERAL DESCRIPTION

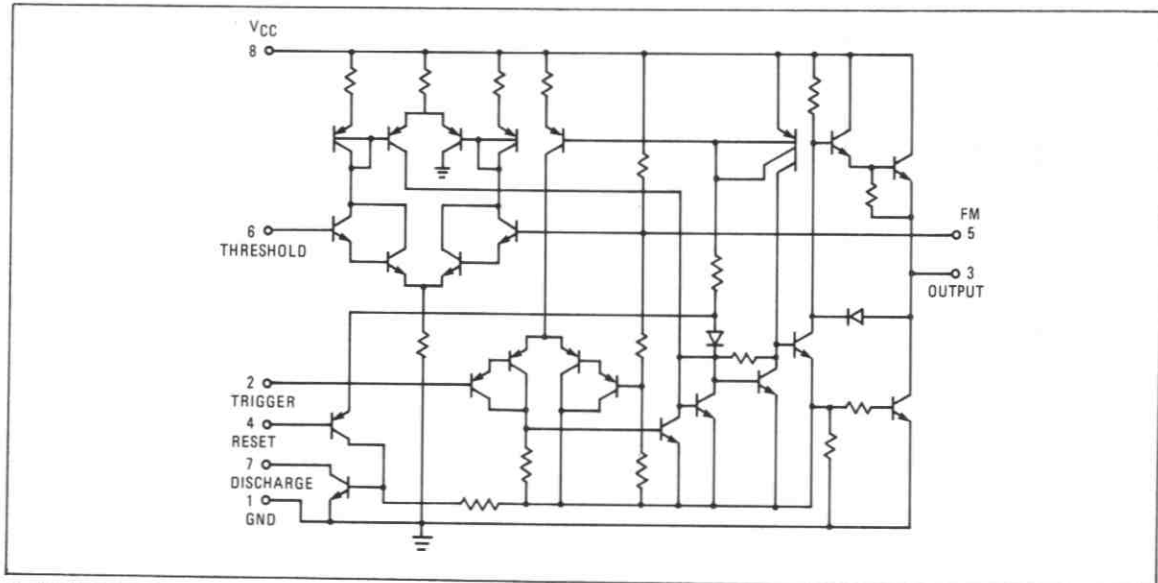
The RC555 and RM555 monolithic timing circuits are highly stable controllers capable of producing accurate time delays or oscillation. In the time delay mode, delay time is precisely controlled by only two external parts: a resistor and a capacitor. For operation as an oscillator, both the free running frequency and the duty cycle are accurately controlled by two external resistors and a capacitor.

Terminals are provided for triggering and resetting. The circuit will trigger and reset on falling waveforms. The output can source or sink up to 200mA or drive TTL circuits.

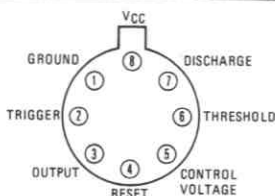
DESIGN FEATURES

- Timing From Microseconds Through Hours
- Operates in Both Astable and Monostable Modes
- Adjustable Duty Cycle
- Output Drives TTL
- High Current Output Can Source or Sink 200mA
- Temperature Stability of 0.005%/°C
- Normally On and Normally Off Output

SCHEMATIC DIAGRAM

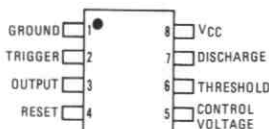


CONNECTION INFORMATION



TE Metal Can Package
(Top View)

Order Part Nos.:
RC555T, RM555T



NB Dual In-line
(Top View)

Order Part Nos.
RC555NB, RV555NB

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	+18V	Operating Temperature Range	
Power Dissipation	600mW	RC555	0°C to +70°C
Storage Temperature Range	-65°C to +150°C	RM555	-55°C to +125°C
Lead Temperature (Soldering, 60s)	+300°C		

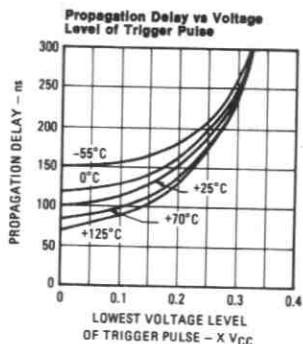
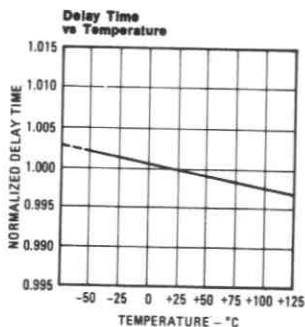
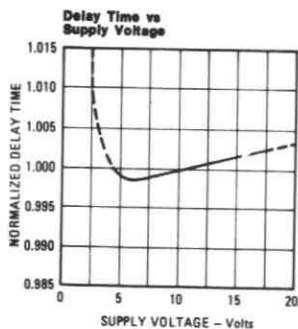
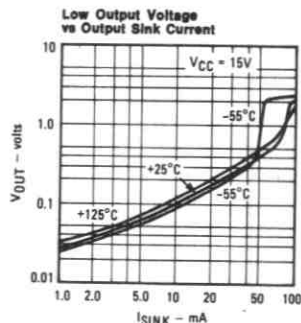
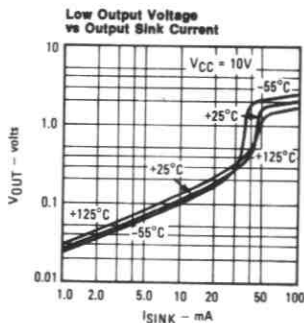
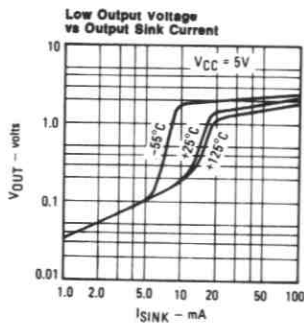
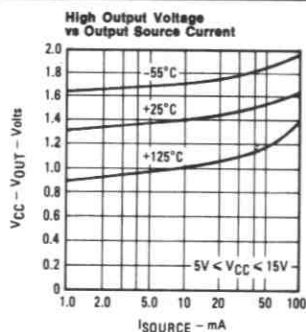
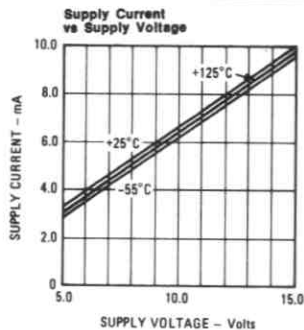
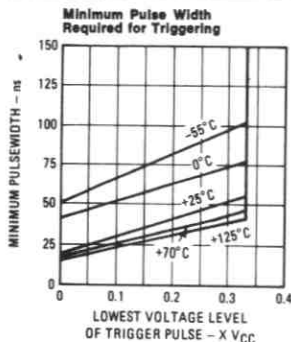
ELECTRICAL CHARACTERISTICS ($V_{CC} = +5V$ to $+15V$, $T_A = 25^\circ C$ unless otherwise specified)

PARAMETER	CONDITIONS	RM555			RC555			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Supply Voltage		4.5		18	4.5		16	V
Supply Current	$V_{CC} = 5V, R_L = \infty$ $V_{CC} = 15V, R_L = \infty$ Low State, (Note 1)		3 10	5 12		3 10	6 15	mA mA
Timing Error	$R_A, R_B = 1k\Omega$ to $100k\Omega$ $C = 0.1\mu F$ (Note 2)							
Initial Accuracy			0.5	2		1		%
Drift with Temperature			30	100		50		ppm/ $^\circ C$
Drift with Supply Voltage			0.005	0.02		0.01		%/Volt
Threshold Voltage			2/3			2/3		$\times V_{CC}$
Trigger Voltage	$V_{CC} = 15V$ $V_{CC} = 5V$	4.8 1.45	5 1.67	5.2 1.9		5 1.67		V V
Trigger Current			0.5			0.5		μA
Reset Voltage		0.4	0.7	1.0	0.4	0.7	1.0	V
Reset Current			0.1			0.1		mA
Threshold Current	(Note 3)		0.1	0.25		0.1	0.25	μA
Control Voltage Level	$V_{CC} = 15V$ $V_{CC} = 5V$	9.6 2.9	10 3.33	10.4 3.8	9.0 2.6	10 3.33	11 4	V V
Output Voltage Drop (low)	$V_{CC} = 15V$ $I_{SINK} = 10mA$ $I_{SINK} = 50mA$ $I_{SINK} = 100mA$ $I_{SINK} = 200mA$ $V_{CC} = 5V$ $I_{SINK} = 8mA$ $I_{SINK} = 5mA$		0.1 0.4 2 2.5	0.15 0.5 2.2		0.1 0.4 2 2.5	0.25 0.75 2.5	V V V V V
Output Voltage Drop (high)	$I_{SOURCE} = 200mA$ $V_{CC} = 15V$ $I_{SOURCE} = 100mA$ $V_{CC} = 15V$ $V_{CC} = 5V$		12.5			12.5		V
		13 3	13.3 3.3		12.75 2.75	13.3 3.3		V V
Rise Time of Output			100			100		ns
Fall Time of Output			100			100		ns

NOTES:

- Supply current when output high typically 1mA less.
- Tested at $V_{CC} = 5V$ and $V_{CC} = 15V$.
- This will determine the maximum value of $R_A + R_B$. For 15V operation, the max total $R = 20$ megohm.

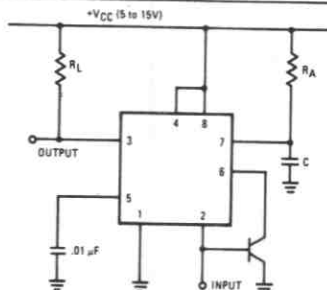
TYPICAL ELECTRICAL DATA



TYPICAL APPLICATIONS

Missing Pulse Detector

With the RC555/RM555 connected as shown, the timing cycle will be continuously reset by the input pulse train. A change in frequency, or a missing pulse, allows the timing cycle to go to completion and change the output level. For proper operation the time delay should be set slightly longer than the normal time between pulses.



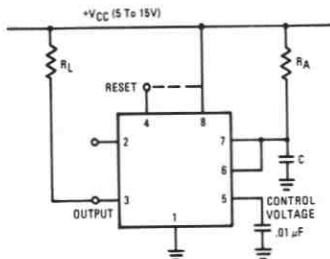
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TYPICAL APPLICATIONS (Cont.)

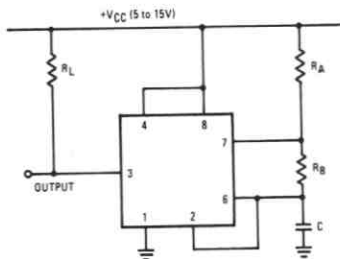
Monostable Operation

In this mode, the timer functions as a one-shot. The external capacitor is initially held discharged by a transistor internal to the timer. Applying a negative trigger pulse to Pin 2 sets the flip-flop, driving the output high and releasing the short-circuit across the external capacitor. The voltage across the capacitor increases with time constant $\tau = R_A C$ to $2/3 V_{CC}$, where the comparator resets the flip-flop and discharges the external capacitor. The output is now in the low state.

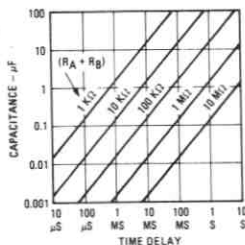


Free Running Operation

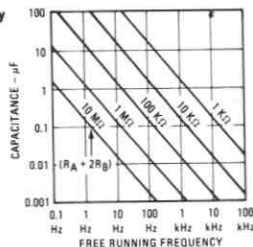
With the circuit connected as shown, it will trigger itself and free run as a multivibrator. The external capacitor charges through R_A and R_B and discharges through R_B only. Thus the duty cycle is set by the ratio of these two resistors, and the capacitor charges and discharges between



Circuit triggering takes place when the negative-going trigger pulse reaches $1/3V_{CC}$ and the circuit stays in the output high state until the set time elapses. The time the output remains in the high state is $1.1R_A C$ and can be determined by the graph. A negative pulse applied to Pin 4 (reset) during the timing cycle will discharge the external capacitor and start the cycle over again beginning on the positive-going edge of the reset pulse. If reset function is not used, Pin 4 should be connected to V_{CC} to avoid false resetting.

Time Delay vs R_A , R_s and C 

$1/3V_{CC}$ and $2/3V_{CC}$. Charge and discharge times, and therefore frequency, are independent of supply voltage. The free running frequency versus R_A , R_B , and C is shown in the graph.

Free Running Frequency vs R_A , R_s and C 

GENERAL DESCRIPTION

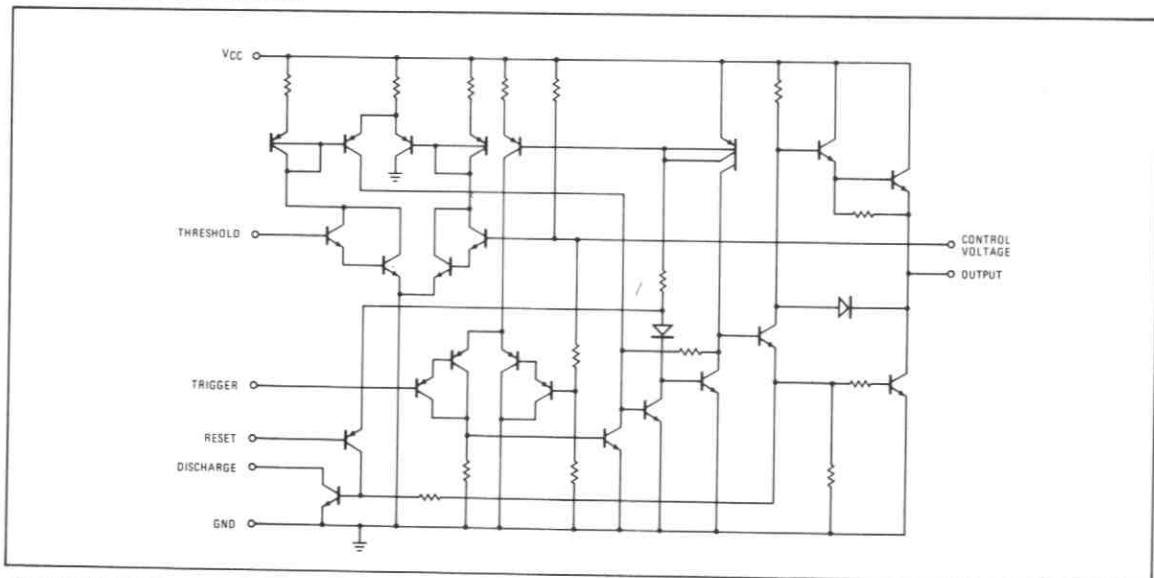
The RC556 and RM556 monolithic timing circuits are highly stable controllers capable of producing accurate time delays or oscillation. In the time delay mode, delay time is precisely controlled by only two external parts: a resistor and a capacitor. For operation as an oscillator, both the free running frequency and the duty cycle are accurately controlled by two external resistors and a capacitor.

Terminals are provided for triggering and resetting. The circuit will trigger and reset on falling waveforms. The output can source or sink up to 200mA or drive TTL circuits.

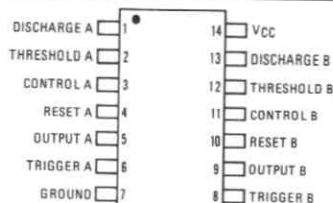
DESIGN FEATURES

- Timing From Microseconds Through Hours
- Operates in Both Astable and Monostable Modes
- Adjustable Duty Cycle
- Output Drives TTL
- High Current Output Can Source or Sink 200mA
- Temperature Stability of 0.005%/°C
- Normally On and Normally Off Output

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



D and DP
Dual In-line Package
(Top View)

Order Part Nos.;
RC556DB, RC556DC,
RM556DC



ABSOLUTE MAXIMUM RATINGS

Supply Voltage	+18V	Operating Temperature Range	
Power Dissipation	600mW	RC556	0°C to +70°C
Storage Temperature Range	-65°C to +150°C	RM556	-55°C to +125°C
Lead Temperature (Soldering, 60s)	+300°C	RV556	-40°C to +85°C

ELECTRICAL CHARACTERISTICS (V_{CC} = +5V to +15V, T_A = 25°C unless otherwise specified)

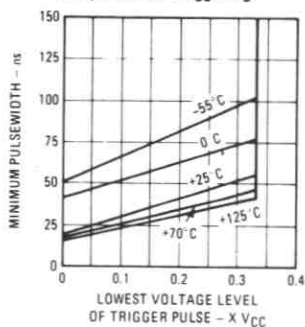
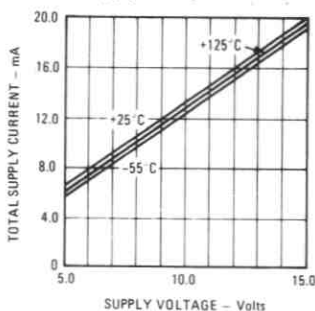
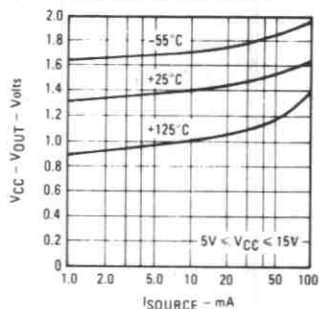
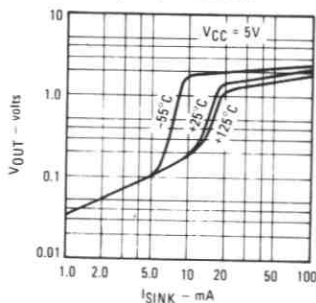
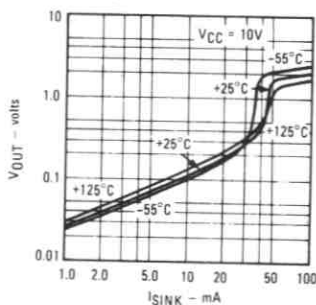
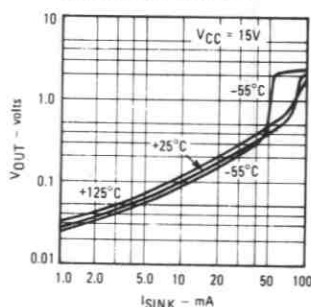
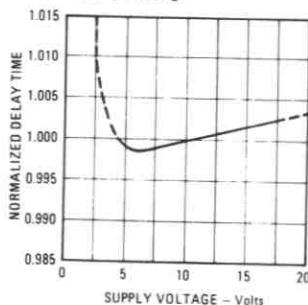
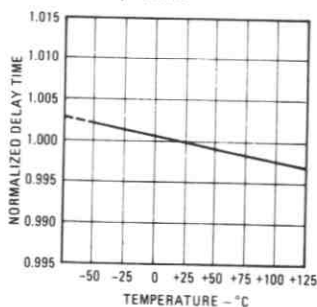
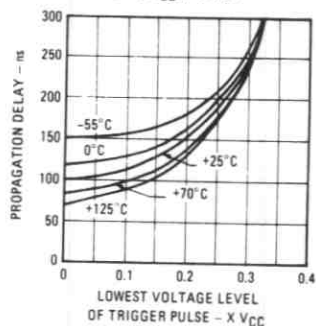
PARAMETER	CONDITIONS	RM556			RC556, RV556			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Supply Voltage		4.5		18	4.5		16	V
Supply Current (Each Side)	V _{CC} = 5V, R _L = ∞ V _{CC} = 15V, R _L = ∞ Low State, (Note 1)		3 10	5 11		3 10	6 14	mA mA
Timing Error (Free Running)	R _A , R _B = 2kΩ to 100kΩ C = 0.1μF (Note 2)							
Initial Accuracy			1.5			2.25		%
Drift with Temperature			90			150		ppm/°C
Drift with Supply Voltage			0.15			0.3		%/Volt
Timing Error (Monostable)	R _A , R _B = 2kΩ to 100kΩ C = 0.1μF (Note 2)							
Initial Accuracy			0.5	1.5		0.75		%
Drift with Temperature			30	100		50		ppm/°C
Drift with Supply Voltage			0.05	0.2		0.1		%/Volt
Threshold Voltage			2/3			2/3		x V _{CC}
Trigger Voltage	V _{CC} = 15V V _{CC} = 5V	4.8 1.45	5 1.67	5.2 1.9		5 1.67		V V
Trigger Current			0.5			0.5		μA
Reset Voltage		0.4	0.7	1.0	0.4	0.7	1.0	V
Reset Current			0.1			0.1		mA
Threshold Current	(Note 3)		0.03	0.1		0.03	0.1	μA
Control Voltage Level	V _{CC} = 15V V _{CC} = 5V	9.6 2.9	10 3.33	10.4 3.8	9.0 2.6	10 3.33	11 4	V V
Output Voltage Drop (low)	V _{CC} = 15V I _{SINK} = 10mA I _{SINK} = 50mA I _{SINK} = 100mA I _{SINK} = 200mA V _{CC} = 5V I _{SINK} = 8mA I _{SINK} = 5mA		0.1 0.4 2 2.5	0.15 0.5 2.25		0.1 0.4 2 2.5	0.25 0.75 2.75	V V V V V
Output Voltage Drop (high)	I _{SOURCE} = 200mA V _{CC} = 15V I _{SOURCE} = 100mA V _{CC} = 15V V _{CC} = 5V			12.5		12.5		V V V
Rise Time of Output			100			100		ns
Fall Time of Output			100			100		ns
Matching Characteristics Between Each Section								
Initial Timing Accuracy			.05	0.1		0.1	0.2	%
Timing Drift with Temperature			±10			±10		ppm/°C
Drift with Supply Voltage			0.1	0.2		0.2	0.5	%/Volt

Notes on following page.



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TYPICAL ELECTRICAL DATA

Minimum Pulse Width
Required for TriggeringSupply Current
vs Supply VoltageHigh Output Voltage
vs Output Source CurrentLow Output Voltage
vs Output Sink CurrentLow Output Voltage
vs Output Sink CurrentLow Output Voltage
vs Output Sink CurrentDelay Time vs
Supply VoltageDelay Time
vs TemperaturePropagation Delay vs Voltage
Level of Trigger Pulse

NOTES

1. Supply current when output high typically 2mA less.
2. Tested at $V_{CC} = 5V$ and $V_{CC} = 15V$.
3. This will determine the maximum value of $R_A + R_B$. For 15V operation, the maximum total $R = 20M\Omega$.

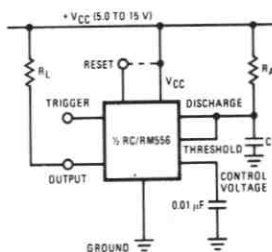
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BASIC OPERATIONAL MODES

Monostable Operation

In this mode, the timer functions as a one-shot. The external capacitor is initially held discharged by a transistor internal to the timer. Applying a negative trigger pulse to Pin 2 sets the flip-flop, driving the output high and releasing the short-circuit across the external capacitor. The voltage across the capacitor increases with time constant $\tau = R_A C$ to $2/3 V_{CC}$, where the comparator resets the flip-flop and discharges the external capacitor. The output is now in the low state.

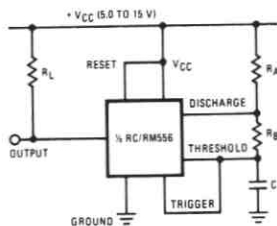
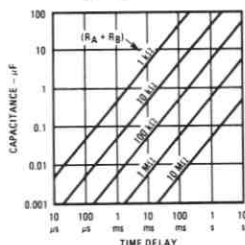
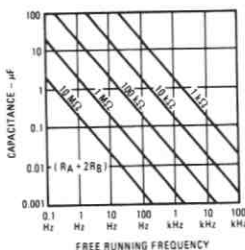


Circuit triggering takes place when the negative-going trigger pulse reaches $1/3V_{CC}$ and the circuit stays in the output high state until the set time elapses. The time the output remains in the high state is $1.1R_A C$ and can be determined by the graph. A negative pulse applied to Pin 4 (reset) during the timing cycle will discharge the external capacitor and start the cycle over again beginning on the positive-going edge of the reset pulse. If reset function is not used, Pin 4 should be connected to V_{CC} to avoid false resetting.

Free Running Operation (Astable)

With the circuit connected as shown, it will trigger itself and free run as a multivibrator. The external capacitor charges through R_A and R_B and discharges through R_B only. Thus the duty cycle is set by the ratio of these two resistors, and the capacitor charges and discharges between

$1/3V_{CC}$ and $2/3V_{CC}$. Charge and discharge times, and therefore frequency, are independent of supply voltage. The free running frequency versus R_A , R_B , and C is shown in the graph.

Time Delay vs R_A , R_B and C Free Running Frequency vs R_A , R_B and C 

GENERAL DESCRIPTION

The RC4151 and RM4151 provide a simple low-cost method of A/D conversion. They have all the inherent advantages of the voltage-to-frequency conversion technique. The output of RC4151/RM4151 is a series of pulses of constant duration. The frequency of the pulses is proportional to the applied input voltage. These converters are designed for use in a wide range of data conversion and remote sensing applications.

DESIGN FEATURES

- Single Supply Operation (+8V to +22V)
- Pulse Output Compatible With All Logic Forms
- Programmable Scale Factor (K)
- Linearity $\pm 0.05\%$ typical—precision mode
- Temperature stability $\pm 100\%$ ppm/ $^{\circ}\text{C}$ typical
- High Noise Rejection
- Inherent Monotonicity
- Easily Transmittable Output
- Simple Full Scale Trim
- Single-Ended Input, Referenced to Ground
- Also Provides Frequency-to-Voltage Conversion

SCHEMATIC DIAGRAM

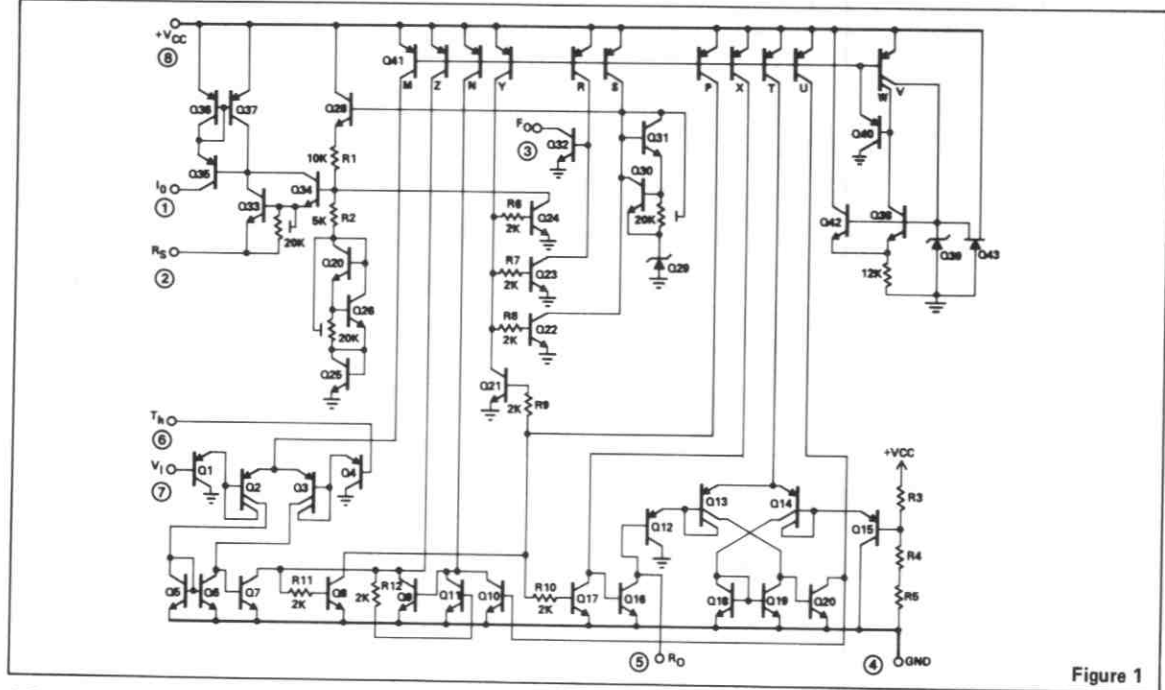
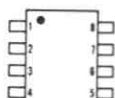


Figure 1

CONNECTION INFORMATION

TE (TO-99) METAL CAN
(Top View)Order Part Nos.: RC4151T, RM4151T
NOTE: PIN 4 CONNECTED TO CASENB MINIATURE
DUAL-IN-LINE
(Top View)

Order Part Nos.: RC4151NB, RV4151NB

PIN	FUNCTION
1	CURRENT SOURCE
2	SCALE FACTOR
3	LOGIC OUTPUT
4	GROUND
5	ONE-SHOT R, C
6	THRESHOLD
7	INPUT VOLTAGE
8	V _{CC}

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ABSOLUTE MAXIMUM RATINGS

Supply Voltages	+8.0 to +22V	Storage Temperature Range	
Output Sink Current	20mA	RM4151	-65°C to +150°C
Internal Power Dissipation	500mW	RV4151	-55°C to +125°C
Input Voltage	-0.2V to +V _{CC}	RC4151	-55°C to +125°C
Output Short Circuit to Ground	Continuous	Operating Temperature Range	
		RM4151	-55°C to +125°C
		RV4151	-40°C to +85°C
		RC4151	0°C to +70°C

ELECTRICAL CHARACTERISTICS (V_{CC} = +15V, T_A = +25°C, unless otherwise specified)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Current	8V < V _{CC} < 15V	2.0	3.5	6.0	mA
	15V < V _{CC} < 22V	2.0	4.5	7.5	mA
Conversion Accuracy Scale Factor	Circuit Figure 3, V _I = 10V R _S = 14.0k	0.90	1.00	1.10	kHz/V
Drift with Temperature	Circuit Figure 3, V _I = 10V	-	±100	-	ppM/°C
Drift with V _{CC}	Circuit Figure 3, V _I = 1.0V 8V < V _{CC} < 18V	-	0.2	1.0	%/V
Input Comparator Offset Voltage		-	5	10	mV
Offset Current		-	±50	±100	nA
Input Bias Current		-	-100	-300	nA
Common Mode Range (Note 1)		0	0 to V _{CC} - 2	V _{CC} - 3.0	V
One-Shot Threshold Voltage, Pin 5		0.63	.667	0.70	x V _{CC}
Input Bias Current, Pin 5		-	-100	-500	nA
Reset VSAT	Pin 5, I = 2.2mA	-	0.15	0.50	V
Current Source Output Current (R _S = 14.0kΩ)	Pin 1, Figure 2, V = 0	-	138.7	-	μA
Change with Voltage	Pin 1, V = 0V to V = 10V	-	1.0	2.5	μA
Off Leakage	Pin 1, V = 0V	-	1	50.0	nA
Reference Voltage	Pin 2, Figure 2	1.70	1.9	2.08	V
Logic Output VSAT	Pin 3, I = 3.0mA	-	0.15	0.50	V
VSAT	Pin 3, I = 2.0mA	-	0.10	0.30	V
Off Leakage		-	.1	1.0	μA

Note 1: Input Common Mode Range includes ground.



PRINCIPLE OF OPERATION

Single Supply Mode Voltage-to-Frequency Conversion

In this application the RC4151/RM4151 functions as a stand-alone voltage to frequency converter operating on a single positive power supply. Refer to Figure 2, the simplified block diagram. The RC/RM4151 contains a voltage comparator, a one-shot, and a precision switched current source. The voltage comparator compares a positive input voltage applied at pin 7 to the voltage at pin 6. If the input voltage is higher, the comparator will fire the one-shot. The output of the one-shot is connected to both the logic output and the precision switched current source. During the one-shot period, T , the logic output will go low and the current source will turn on with current I . At the end of the one-shot period the logic output will go high and the current source will shut off. At this time the current source has injected an amount of charge $Q = I_0 T$ into the network R_B-C_B . If this charge has not increased the voltage V_B such that $V_B > V_I$, the comparator again fires the one-shot and the current source injects another lump of charge, Q , into the R_B-C_B network. This process continues until $V_B > V_I$. When this condition is achieved the current source remains off and the voltage V_B decays until V_B is again equal to V_I . This completes one cycle. The VFC will now run in a steady state mode. The current source dumps lumps of charge into the capacitor C_B at a rate fast enough to keep $V_B \geq V_I$. Since the discharge rate of capacitor C_B is proportional to V_B/R_B , the frequency at which the system runs will be proportional to the input voltage.

The 4151 VFC is easy to use and apply if you understand the operation of it through the block diagram, Figure 2. Many users, though, have expressed the desire to understand the workings of the internal circuitry. Figure 1 shows the schematic of the 4151. The circuit can be divided into five sections: the internal biasing network, input comparator, one-shot, voltage reference, and the output current source.

The internal biasing network is composed of Q39-Q43. The N-channel FET Q43 supplies the initial current for zener diode Q39. The NPN transistor Q38 senses the zener voltage to derive the current reference for the multiple collector current source Q41. This special PNP transistor provides active pull-up for all of the other sections of the 4151.

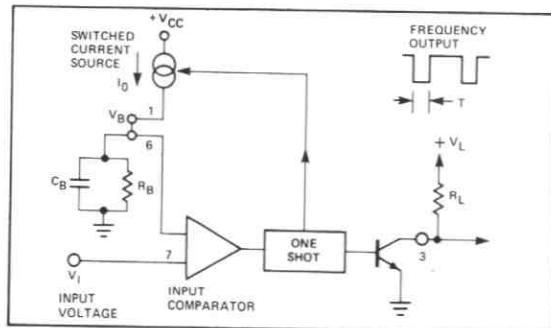


Figure 2. Simplified Block Diagram, Single Supply Mode

The input comparator section is composed of Q1-Q7. Lateral PNP transistors Q1-Q4 form the special ground-sensing input which is necessary for VFC operation at low input voltages. NPN transistors Q5 and Q6 convert the differential signal to drive the second gain stage Q7. If the voltage on input pin 7 is less than that on threshold pin 6, the comparator will be off and the collector of Q7 will be in the high state. As soon as the voltage on pin 7 exceeds the voltage on pin 6, the collector of Q7 will go low and trigger the one-shot.

The one-shot is made from a voltage comparator and an R-S latch. Transistors Q12-Q15 and Q18-Q20 form the comparator, while Q8-Q11 and Q16-Q17 make up the R-S latch. One latch output, open-collector reset transistor Q16, is connected to a comparator input and to the terminal, pin 5. Timing resistor R_0 is tied externally from pin 5 to $+V_{CC}$ and timing capacitor C_0 is tied from pin 5 to ground. The other comparator input is tied to a voltage divider R_3-R_5 which sets the comparator threshold voltage at $0.667 V_{CC}$. One-shot operation is initiated when the collector of Q7 goes low and sets the latch. This causes Q16 to turn off, releasing the voltage at pin 5 to charge exponentially towards $+V_{CC}$ through R_0 . As soon as this voltage reaches $0.667 V_{CC}$, comparator output Q20 will go high causing Q10 to reset the latch. When the latch is reset, Q16 will discharge C_0 to ground. The one-shot has now completed its function of creating a pulse of period $T = 1.1 R_0 C_0$ at the latch output, Q21. This pulse is buffered through Q23 to drive the open-collector logic circuit transistor Q32. During the one-shot period the logic output will be in the low state. The one-shot output is also used to switch the reference voltage by Q22 and Q24. The low T.C. reference voltage is derived from the combination of a 5.5V zener diode with resistor and diode level shift networks. A stable 1.89 volts is developed at pin 2, the emitter of Q33.

Connecting the external current-setting resistor $R_S = 14.0\Omega$ from pin 2 to ground gives $135\mu A$ from the collectors of Q33 and Q34. This current is reflected in the precision current mirror Q35-Q37 and produces the output current I_0 at pin 1. When the R-S latch is reset, Q22 and Q24 will hold the reference voltage off, pin 2 will be at 0V, and the current will be off. During the one-shot period T , the latch will be set, the voltage of pin 2 will go to 1.89V, and the output current will be switched on.

TYPICAL APPLICATIONS

Single Supply Voltage-to-Frequency Converter

Figure 3 shows the simplest type of VFC that can be made with the 4151. Input voltage range is from 0 to +10V, and output frequency is from 0 to 10kHz. Full scale frequency can be tuned by adjusting R_S , the output current set resistor. This circuit has the advantage of being simple and low in cost, but it suffers from inaccuracy due to a number of error sources. Linearity error is typically 1%. A frequency offset will also be introduced by the input comparator offset voltage. Also, response time for this circuit is limited by the passive integration network R_B C_B . For the component values shown in Figure 3, response time for a step change input from 0 to +10V will be 135msec. For applications which require fast response time and high accuracy, use the circuits of Figure 4 and 5.

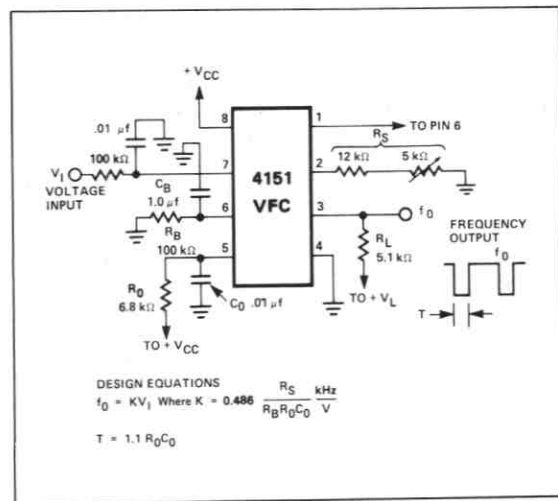


Figure 3. Single Supply Voltage-to-Frequency Converter

Precision VFC with Single Supply Voltage

For applications which require a VFC which will operate from a single positive supply with positive input voltage, the circuit of Figure 4 will give greatly improved linearity, frequency offset, and response time. Here, an active integrator using one section of the RC3403A quad ground-sensing op-amp has replaced the R_B - C_B network in Figure 3. Linearity error for this circuit is due only to the 4151 current source output conductance. Frequency offset is due only to the op-amp input offset and can be nulled to zero by adjusting R_B . This technique uses the op-amp bias current to develop the null voltage, so an op-amp with stable bias current, like the RC3403A, is required.

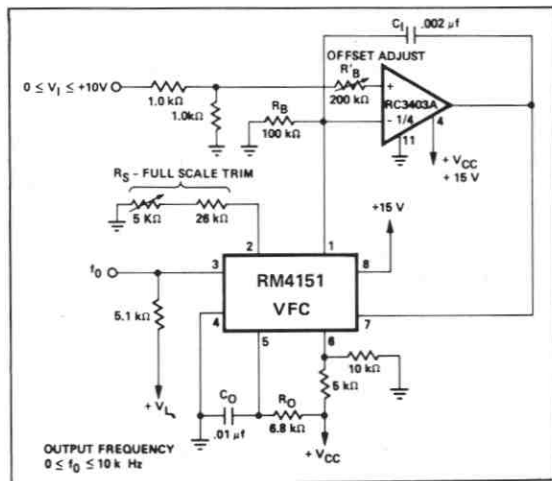


Figure 4. Precision Voltage-to-Frequency Converter Single Supply

Precision Voltage-to-Frequency Converter

In this application (Figure 5) the 4151 VFC is used with an operational amplifier integrator to provide typical linearity of 0.05% over the range of 0 to -10V. Offset is adjustable to zero. Unlike many VFC designs which lose linearity below 10mV, this circuit retains linearity over the full range of input voltage, all the way to 0V.

Trim the full scale adjust pot at $V_1 = -10V$ for an output frequency of 10kHz. The offset adjust pot should be set for 10Hz with an input voltage of -10mV.

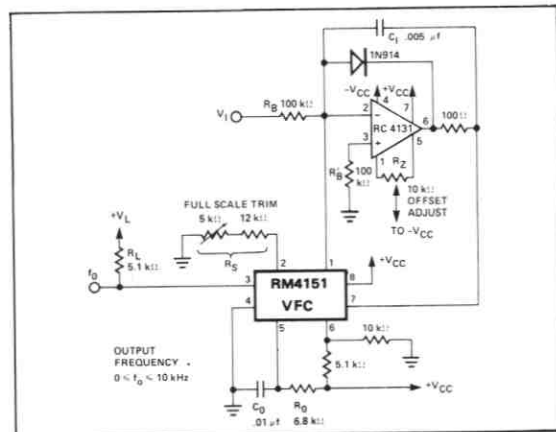


Figure 5. Precision Voltage-to-Frequency Converter

The 4151 operational amplifier integrator improves linearity of this circuit over that of Figure 3 by holding the output of the source, Pin 1, at a constant 0V. Therefore linearity error due to the current source output conductance is eliminated. The diode connected around the op-amp prevents the voltage at 4151 pin 7 from going below 0. Use a low-leakage diode here, since any leakage will degrade the accuracy. This circuit can be operated from a single positive supply if an RC3403A ground-sensing op-amp is used for the integrator. In this case, the diode can be left out. Note that even though the circuit itself will operate from a single supply, the input voltage is necessarily negative. For operation above 10kHz, bypass 4151 pin 6 with $0.01\mu\text{F}$.

Comparison of Voltage-to-Frequency Applications Circuits

Table 1 compares the VFC applications circuits for typical linearity, frequency offset, response time for a step input from 0 to 10 volts, sign of input voltage, and whether the circuit will operate from a single positive supply or split supplies.

Table 1

	Figure 3	Figure 4	Figure 5
Linearity	1%	0.2%	0.05%
Frequency Offset	+10Hz	0	0
Response Time	135msec	10 μsec	10 μsec
Input Voltage	+	+	-
Single Supply	yes	yes	yes
Split Supply	-	-	yes

Frequency-to-Voltage Conversion

The 4151 can be used as a frequency-to-voltage converter. Figure 6 shows the single-supply FVC configuration. With no signal applied, the resistor bias networks tied to pins 6 and 7 hold the input comparator in the off state. A negative going pulse applied to pin 6 (or positive pulse to pin 7) will cause the comparator to fire the one-shot. For proper operation, pulse width must be less than the period of the one-shot, $T = 1.1 R_0 C_0$. For a 5V p-p square-wave input the differentiator network formed by the input coupling capacitor and the resistor bias network will provide pulses which correctly trigger the one-shot. An external voltage comparator such as the 311 or 339 can be used to "square-up" sinusoidal input signals before they are applied to the 4151. Also, the component values for the input signal differentiator and bias network can be altered to accommodate square waves with different amplitudes and frequencies. The passive integrator network $R_B C_B$ filters the current pulses from the pin 1 output. For less output ripple, increase the value of C_B .

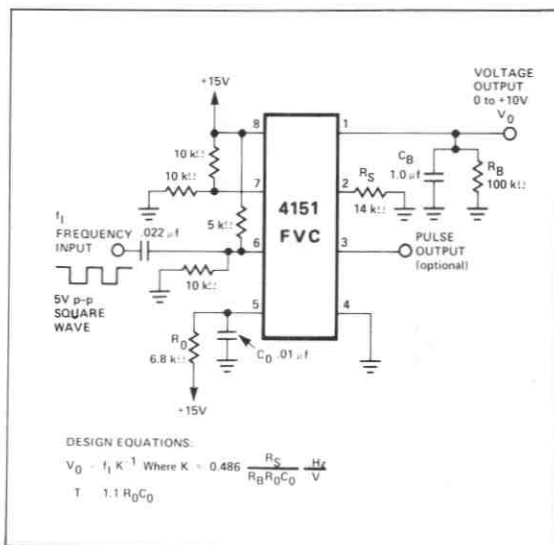


Figure 6. Single Supply Frequency-to-Voltage Converter

For increased accuracy and linearity, use an operational amplifier integrator as shown in Figure 7, the precision FVC configuration. Trim the offset to give -10mV out with 10Hz in and trim the full scale adjust for -10V out with 10kHz in. Input signal conditioning for this circuit is necessary just as for the single supply mode, and scale factor can be programmed by the choice of component values. A tradeoff exists between output ripple and response time, through the choice of integration capacitor C_1 . If $C_1 = 0.1\mu\text{F}$ the ripple will be about 100mV . Response time constant $\tau_R = R_B C_1$. For $R_B = 100\text{k}\Omega$ and $C_1 = 0.1\mu\text{F}$, $\tau_R = 10\text{msec}$.

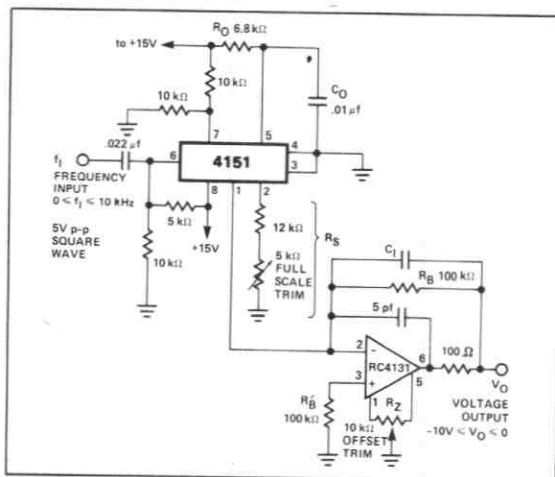


Figure 7. Precision Frequency-to-Voltage Converter



PRECAUTIONS

1. The voltage applied to comparator input pins 6 and 7 should not be allowed to go below ground by more than 0.3 volt.
2. Pins 3 and 5 are open-collector outputs. Shorts between these pins and +V_{CC} can cause overheating and eventual destruction.
3. Reference voltage terminal pin 2 is connected to the emitter of an NPN transistor and is held at approximately 1.9 volts. This terminal should be protected from accidental shorts to ground or supply voltages. Permanent damage may occur if current in pin 2 exceeds 5mA.
4. Avoid stray coupling between 4151 pins 5 and 7, which could cause false triggering. For the circuit of Figure 3, bypass pin 7 to ground with at least 0.01μf. If false triggering is experienced with the precision mode circuits, bypass pin 6 to ground with at least 0.01μf. This is necessary for operation above 10kHz.

PROGRAMMING THE 4151

The 4151 can be programmed to operate with a full scale frequency anywhere from 1.0Hz to 100kHz. In the case of the VFC configuration, nearly any full scale input voltage from 1.0V and up can be tolerated if proper scaling is employed. Here is how to determine component values for any desired full scale frequency.

1. Set $R_S = 14k\Omega$ or use a 12k resistor and 5k pot as shown in the figures. (The only exception to this is Figure 5.)
2. Set $T = 1.1 R_O C_O = 0.75 \left[\frac{1}{f_o} \right]$ where f_o is the desired full scale frequency. For optimum performance make $6.8k\Omega < R_O < 680k\Omega$ and $0.001\mu f < C_O < 1.0\mu f$.
3. a) For the circuit of Figure 3 make $C_B = 10^{-2} \left[\frac{1}{f_o} \right]$ Farads.
Smaller values of C_B will give faster response time, but will also increase frequency offset and nonlinearity.
b) For the active integrator circuits make
$$C_I = 5 \times 10^{-5} \left[\frac{1}{f_o} \right] \text{ Farads.}$$
The op-amp integrator must have a slew rate of at least $135 \times 10^{-6} \left[\frac{1}{C_I} \right]$ volts per second where the value of C_I is again give in Farads.
4. a) For the circuits of Figure 3 and 4 keep the values of R_B and R'_B as shown and use an input attenuator to give the desired full scale input voltage.
b) For the precision mode circuit of Figure 5, set $R_B = \frac{V_{IO}}{100\mu A}$ where V_{IO} is the full scale input voltage. Alternately the op-amp inverting input (summing node) can be used as a current input with full scale input current $I_{IO} = -100\mu A$.

5. For the FVCs, pick the value of C_B or C_I to give the optimum tradeoff between response time and output ripple for the particular application.

DESIGN EXAMPLE

- I. Design a precision VFC (from Figure 5) with $f_o = 100kHz$ and $V_{IO} = -10V$.
 1. Set $R_S = 14.0k\Omega$.
 2. $T = 0.75 \left[\frac{1}{10^5} \right] = 7.5\mu sec$
Let $R_O = 6.8k\Omega$ and $C_O = 0.001\mu f$.
 3. $C_I = 5 \times 10^{-5} \left[\frac{1}{10^5} \right] = 500pf$.
Op-amp slew rate must be at least
 $SR = 135 \times 10^{-6} \left[\frac{1}{500pf} \right] = 0.27\mu sec$
 4. $R_B = \frac{10V}{100\mu A} = 100k\Omega$.
- II. Design a precision VFC with $f_o = 1Hz$ and $V_{IO} = -10V$.
 1. Let $R_S = 14.0k\Omega$.
 2. $T = 0.75 \left[\frac{1}{1} \right] = 0.75 sec$.
Let $R_O = 680k\Omega$ and $C_O = 1.0\mu f$.
 3. $C_I = 5 \times 10^{-5} \left[\frac{1}{1} \right] F = 50\mu f$.
 4. $R_B = 100k\Omega$.
- III. Design a single supply FVC to operate with a supply voltage of 9V and full scale input frequency $f_o = 83.3Hz$. The output voltage must reach at least 0.63 of its final value in 200msec. Determine the output ripple.
 1. Set $R_S = 14.0k\Omega$.
 2. $T = 0.75 \left[\frac{1}{83.3} \right] = 9msec$
Let $R_O = 82k\Omega$ and $C_O = 0.1\mu f$.
 3. Since this FVC must operate from .8.0V, we shall make the full scale output voltage at pin 6 equal to 5.0V.
 4. $R_B = \frac{5V}{100\mu A} = 50k\Omega$.
 5. Output response time constant is $\tau_R \leq 200msec$
Therefore $C_B \leq \frac{\tau_R}{R_B} = \frac{200 \times 10^{-3}}{50 \times 10^3} = 4\mu f$.
Worst case ripple voltage is:
$$V_R = \frac{9mS \times 135\mu A}{4\mu f} = 304mV.$$

GENERAL DESCRIPTION

The RC4444 is a monolithic dielectrically isolated crosspoint array arranged into a 4x4x2 matrix. The primary applications are for balanced switching of 600 ohm transmission lines. The ring and tip are selected by selective biasing of the P+ and P- gate.

Designed to replace reed-relays in telephone switchboards, it does not require a constant gate drive to keep the SCR in the "on" condition. It is several orders faster, with no bouncing, and has a much longer operating life than its mechanical counterpart.

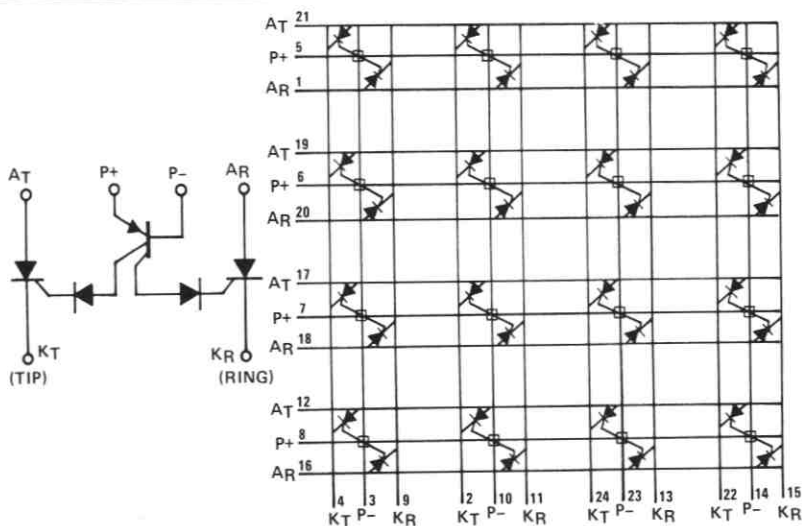
The 16 SCR pairs with the gating system are packaged in a 24 pin dual-in-line package.

The RC4444 is a monolithic pin-for-pin replacement for the MC3416 and MCBH7601.

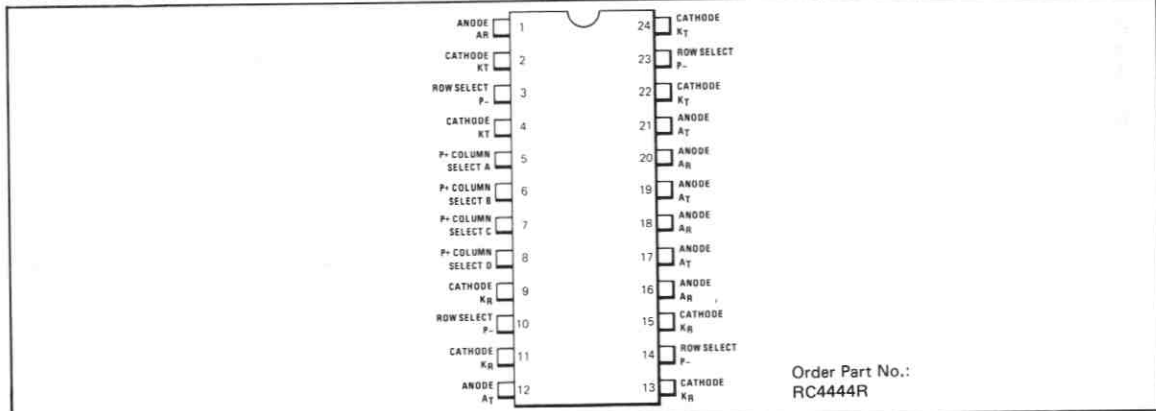
DESIGN FEATURES

- Low Bi-Directional R_{on}
- High R_{off}
- Excellent Matching of Gates
- Low Capacitance
- High Rate Firing
- Predictable Holding Current

SCHEMATIC DIAGRAM



CONNECTION INFORMATION



6



ABSOLUTE MAXIMUM RATINGS

Operating Voltage (Note 1)	25V	Storage Temperature Range	-65°C to +150°C
Internal Power Dissipation (Note 2)	900mW	Operating Temperature Range	0°C to +70°C
Operating Current per Crosspoint (Note 2)	100mA	Lead Temperature (Soldering, 60s)	300°C

ELECTRICAL CHARACTERISTICS (0°C ≤ T_A ≤ 70°C unless otherwise noted)

CHARACTERISTIC	SYMBOL	MIN	MAX	UNIT
Anode-Cathode Breakdown Voltage (I _{AK} = 25μA)	BV _{AK}	25	—	Vdc
Cathode-Anode Breakdown Voltage (I _{KA} = 25μA)	BV _{KA}	25	—	Vdc
Base-Cathode Breakdown Voltage (I _{BK} = 25μA)	BV _{BK}	25	—	Vdc
Cathode-Base Breakdown Voltage (I _{KB} = 25μA)	BV _{KB}	25	—	Vdc
Base-Emitter Breakdown Voltage (I _{BE} = 25μA)	BV _{BE}	25	—	Vdc
Emitter-Cathode Breakdown Voltage (I _{EK} = 25μA)	BV _{EK}	25	—	Vdc
OFF State Resistance (V _{AK} = 10V)	r _{off}	100	—	MΩ
Dynamic ON Resistance (Center Current = 10mA)	r _{on}	4.0	12	Ω
(Center Current = 20mA)		2.0	10	
Holding Current (See Figure 10)	I _H	0.9	3.8	mA
Enable Current (V _{BE} = 1.5V)	I _{En}	4.0	—	mA
Anode-Cathode ON Voltage (I _{AK} = 10mA)	V _{AK}	—	1.0	V
(I _{AK} = 20mA)		—	1.1	
Gate Sharing Current Ratio @ Cathodes (Under Select Conditions with Anodes Open)	GSh	0.8	1.25	mA/mA
Inhibit Voltage (V _B = 3.0V)	V _{inh}	—	0.3	V
Inhibit Current (V _B = 3.0V)	I _{inh}	—	0.1	mA
OFF State Capacitance (V _{AK} = 0V)	C _{off}	—	2.0	pF
Turn-ON Time	t _{on}	—	1.0	μs
Minimum Voltage Ramp (Which Could Fire the SCR Under Transient Conditions)	dv/dt	800	—	V/μs

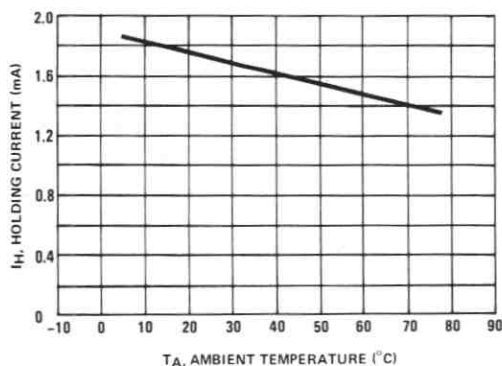
NOTES:

- Maximum voltage from anode to cathode.
- Package thermal resistance θ_{JA} typically .055°C/mW. Package power dissipation limited to 900mW.

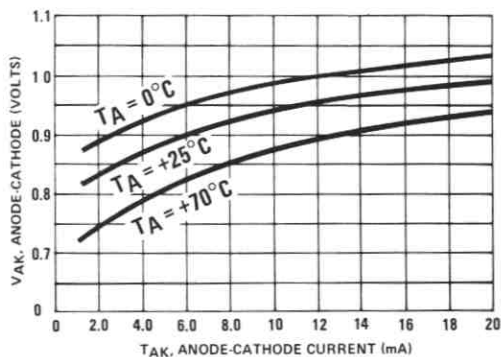


TYPICAL APPLICATIONS

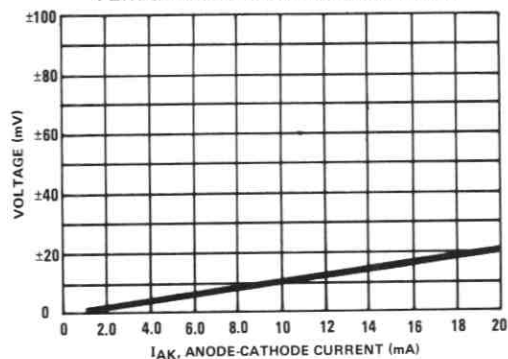
HOLDING CURRENT VERSUS AMBIENT TEMPERATURE



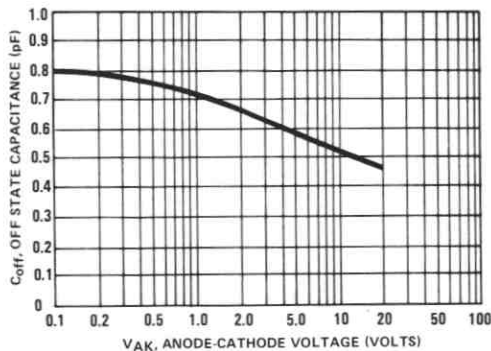
ANODE-CATHODE ON VOLTAGE VERSUS CURRENT AND TEMPERATURE



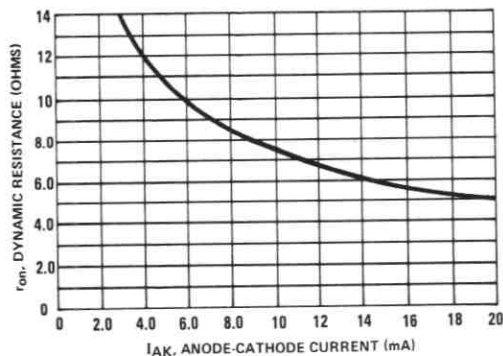
DIFFERENCE IN ANODE-CATHODE ON VOLTAGE (Between Associate Pairs of SCR's) VERSUS ANODE-CATHODE CURRENT



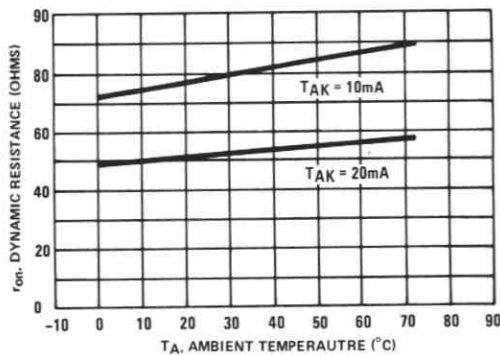
OFF-STATE CAPACITANCE VERSUS ANODE CATHODE VOLTAGE



DYNAMIC ON RESISTANCE VERSUS ANODE-CATHODE CURRENT

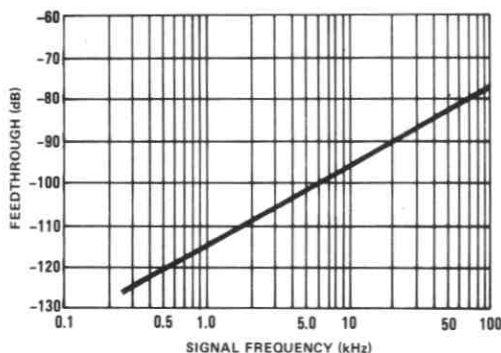


DYNAMIC ON RESISTANCE VERSUS AMBIENT TEMPERATURE

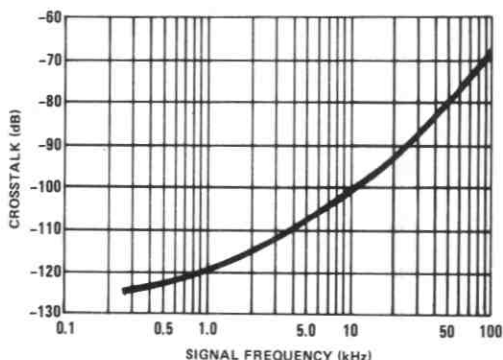


TYPICAL APPLICATIONS

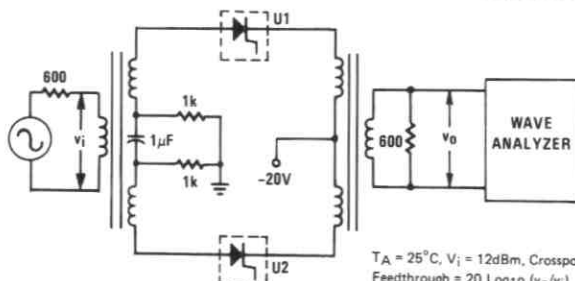
FEEDTHROUGH VERSUS SIGNAL FREQUENCY



CROSSTALK VERSUS SIGNAL FREQUENCY

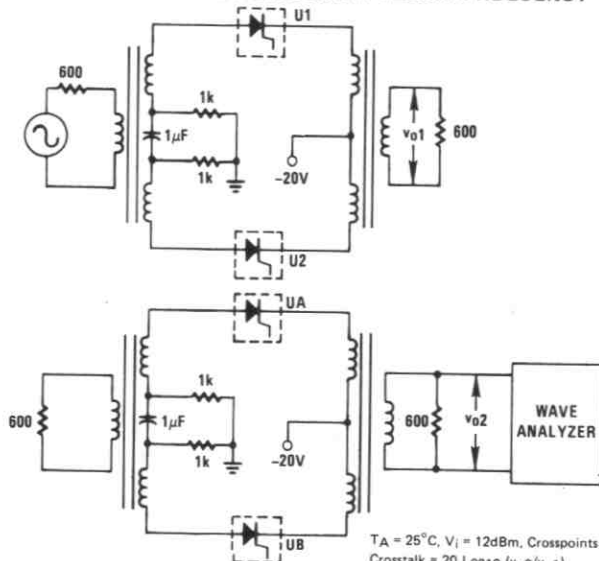


TEST CIRCUIT FOR FEEDTHROUGH VERSUS FREQUENCY



$T_A = 25^\circ\text{C}$, $V_i = 12\text{dBm}$, Crosspoints Off
 Feedthrough = $20 \text{ Log}_{10} (v_o/v_i)$

TEST CIRCUIT FOR CROSSTALK VERSUS FREQUENCY



$T_A = 25^\circ\text{C}$, $V_i = 12\text{dBm}$, Crosspoints On
 Crosstalk = $20 \text{ Log}_{10} (v_{o2}/v_{o1})$

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SECTION 7

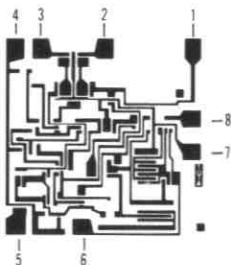
Chips and Beam Lead Products

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Linear IC Chips	7-2
Beam Lead Linear IC's	7-10
Mechanical Outline Information	7-13

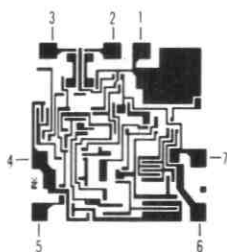
Linear IC Chips

101A GENERAL PURPOSE OPERATIONAL AMPLIFIER
Die Size: 55 x 55 mils.



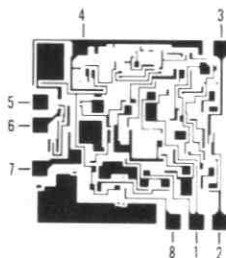
- | | |
|-------------|-----------|
| 1. COMP/BAL | 5. BAL |
| 2. - INPUT | 6. OUTPUT |
| 3. + INPUT | 7. V^+ |
| 4. V^- | 8. COMP |

107 GENERAL PURPOSE OPERATIONAL AMPLIFIER
Die Size: 55 x 55 mils.



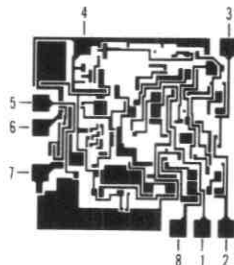
- | | |
|------------|-----------|
| 1. NC | 5. NC |
| 2. - INPUT | 6. OUTPUT |
| 3. + INPUT | 7. V^+ |
| 4. V^- | |

108 SUPER BETA OPERATIONAL AMPLIFIER
Die Size: 63 x 65 mils.



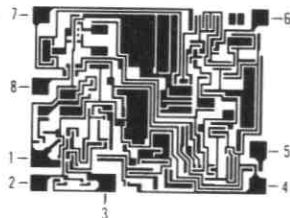
- | | |
|------------|-----------|
| 1. COMP | 5. NC |
| 2. - INPUT | 6. OUTPUT |
| 3. + INPUT | 7. V^+ |
| 4. V^- | 8. COMP |

112 SUPER BETA OPERATIONAL AMPLIFIER
Die Size: 63 x 65 mils.



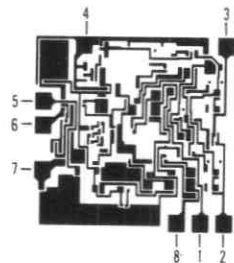
- | | |
|------------|-----------|
| 1. BAL | 5. COMP |
| 2. - INPUT | 6. OUTPUT |
| 3. + INPUT | 7. V^+ |
| 4. V^- | 8. BAL |

118 HIGH SLEW RATE OPERATIONAL AMPLIFIER
Die Size: 59 x 74 mils.



- | | |
|---------------|---------------|
| 1. BAL/COMP 1 | 5. BAL/COMP 3 |
| 2. - INPUT | 6. OUTPUT |
| 3. + INPUT | 7. V^+ |
| 4. V^- | 8. COMP 2 |

216 HIGH INPUT IMPEDANCE OPERATIONAL AMPLIFIER
Die Size: 63 x 65 mils.



- | | |
|------------|----------|
| 1. BAL | 5. COMP |
| 2. - INPUT | 6. COMP |
| 3. + INPUT | 7. V^+ |
| 4. V^- | 8. BAL |

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709 GENERAL PURPOSE OPERATIONAL AMPLIFIER

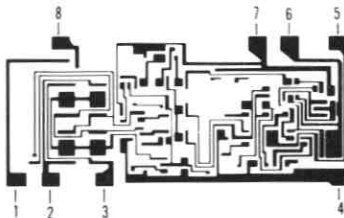
Die Size: 55 x 55 mils.



- | | |
|-------------------|-------------------|
| 1. INPUT COMP (A) | 5. OUTPUT COMP |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V' |
| 4. V^- | 8. INPUT COMP (B) |

725 INSTRUMENTATION OPERATIONAL AMPLIFIER

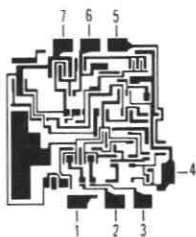
Die Size: 46 x 98 mils.



- | | |
|-----------|-----------|
| 1. BAL | 5. COMP |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V' |
| 4. V^- | 8. BAL |

741 GENERAL PURPOSE OPERATIONAL AMPLIFIER

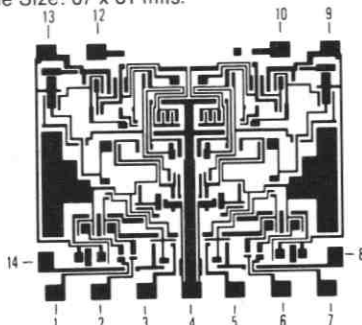
Die Size: 55 x 55 mils.



- | | |
|-----------|-----------|
| 1. BAL | 5. BAL |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V' |
| 4. V^- | |

747 DUAL 741 OPERATIONAL AMPLIFIER

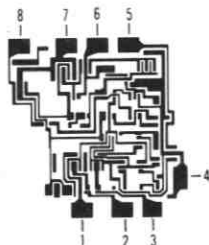
Die Size: 67 x 81 mils.



- | | | |
|---------------|----------------|----------------|
| 1. -INPUT (A) | 6. +INPUT (B) | 11. NC |
| 2. +INPUT (A) | 7. -INPUT (B) | 12. OUTPUT (A) |
| 3. BAL (A) | 8. BAL (B) | 13. V^+ (A) |
| 4. V^- | 9. V^+ (B) | 14. BAL (A) |
| 5. BAL (B) | 10. OUTPUT (B) | |

748 GENERAL PURPOSE OPERATIONAL AMPLIFIER

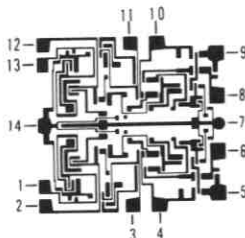
Die Size: 55 x 55 mils



- | | |
|-----------|-----------|
| 1. BAL | 5. BAL |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V' |
| 4. V^- | 8. COMP |

1437/1537 (4709) DUAL 709 OPERATIONAL AMPLIFIERS

Die Size: 75 x 80 mils.

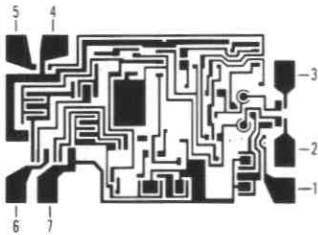


- | | | |
|-----------------|-----------------|------------------|
| 1. OUTPUT LAG 2 | 6. +INPUT 2 | 11. INPUT LAG 1 |
| 2. OUTPUT 2 | 7. V^- | 12. OUTPUT 1 |
| 3. INPUT LAG 2 | 8. +INPUT 1 | 13. OUTPUT LAG 2 |
| 4. INPUT LAG 2 | 9. -INPUT 1 | 14. V^+ |
| 5. -INPUT 2 | 10. INPUT LAG 1 | |

Linear IC Chips

1556A SUPER BETA OPERATIONAL AMPLIFIER

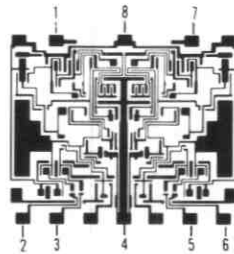
Die Size: 38 x 61 mils.



- | | |
|-------------------|-------------------|
| 1. BAL | 5. BAL |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V ⁺ |
| 4. V ⁻ | |

1458/1558 DUAL 741 OPERATIONAL AMPLIFIER

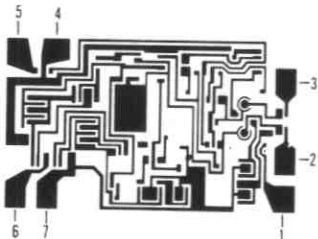
Die Size: 68 x 81 mils.



- | | |
|-------------------|-------------------|
| 1. OUTPUT (A) | 5. +INPUT (B) |
| 2. -INPUT (A) | 6. -INPUT (B) |
| 3. +INPUT (A) | 7. OUTPUT (B) |
| 4. V ⁻ | 8. V ⁺ |

4131 HIGH-GAIN OPERATIONAL AMPLIFIER

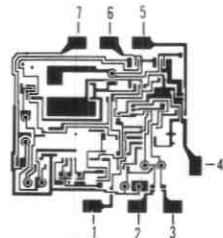
Die Size: 38 x 61 mils.



- | | |
|-------------------|-------------------|
| 1. BAL | 5. BAL |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V ⁺ |
| 4. V ⁻ | |

4132 MICROPOWER OPERATIONAL AMPLIFIER

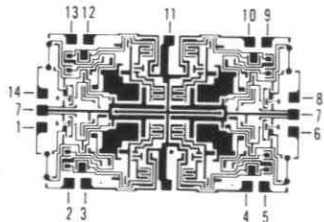
Die Size: 60 x 70 mils.



- | | |
|-------------------|-------------------|
| 1. BAL | 5. BAL |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V ⁺ |
| 4. V ⁻ | |

4136 QUAD 741 OPERATIONAL AMPLIFIER

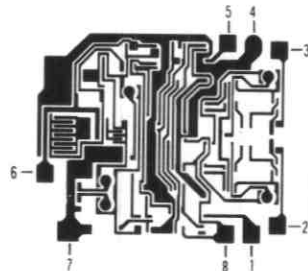
Die Size: 61 x 99 mils.



- | | | |
|---------------|----------------|----------------|
| 1. -INPUT (A) | 6. -INPUT (B) | 11. +V |
| 2. +INPUT (A) | 7. -V | 12. OUTPUT (D) |
| 3. OUTPUT (A) | 8. -INPUT (C) | 13. +INPUT (D) |
| 4. OUTPUT (B) | 9. +INPUT (C) | 14. -INPUT (D) |
| 5. +INPUT (B) | 10. OUTPUT (C) | |

4531 HIGH SLEW RATE OPERATIONAL AMPLIFIER

Die Size: 53 x 63 mils.



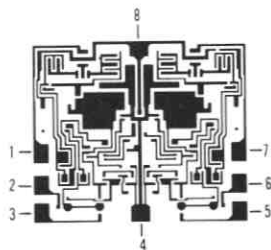
- | | |
|-------------------|-------------------|
| 1. BAL | 5. BAL |
| 2. -INPUT | 6. OUTPUT |
| 3. +INPUT | 7. V ⁺ |
| 4. V ⁻ | 8. COMP |

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4558 DUAL 741 OPERATIONAL AMPLIFIER

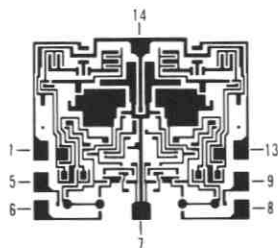
Die Size: 52 x 61 mils.



- | | |
|-------------------|-------------------|
| 1. OUTPUT (A) | 5. +INPUT (B) |
| 2. -INPUT (A) | 6. -INPUT (B) |
| 3. +INPUT (A) | 7. OUTPUT (B) |
| 4. V ⁻ | 8. V ⁺ |

4739 LOW NOISE DUAL OPERATIONAL AMPLIFIER

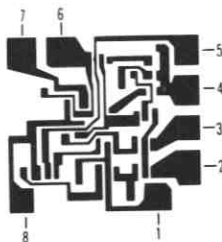
Die Size: 52 x 61 mils.



- | | | |
|---------------|-------------------|--------------------|
| 1. OUTPUT (A) | 6. -INPUT (A) | 11. NC |
| 2. NC | 7. V ⁻ | 12. NC |
| 3. NC | 8. -INPUT (B) | 13. B OUTPUT |
| 4. NC | 9. +INPUT (B) | 14. V ⁺ |
| 5. +INPUT (A) | 10. NC | |

702 WIDEBAND AMPLIFIER

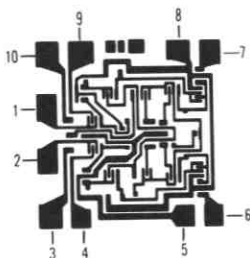
Die Size: 40 x 44 mils.



- | | |
|-------------------|-------------------|
| 1. GROUND | 5. LEAD/COMP |
| 2. -INPUT | 6. LAG/COMP |
| 3. +INPUT | 7. OUTPUT |
| 4. V ⁻ | 8. V ⁺ |

733 VIDEO WIDEBAND AMPLIFIER

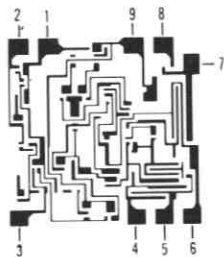
Die Size: 47 x 47 mils.



- | | |
|--------------------------------|---------------------------------|
| 1. INPUT 1 | 6. OUTPUT 2 |
| 2. INPUT 2 | 7. OUTPUT 1 |
| 3. G _{2B} GAIN SELECT | 8. V ⁺ |
| 4. G _{1B} GAIN SELECT | 9. G _{1A} GAIN SELECT |
| 5. V ⁻ | 10. G _{2A} GAIN SELECT |

104 NEGATIVE VOLTAGE REGULATOR

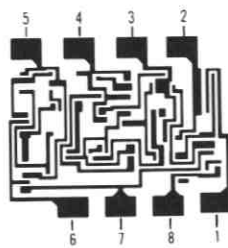
Die Size: 50 x 51 mils.



- | | |
|----------------|------------------|
| 1. ADJ | 6. CURRENT LIMIT |
| 2. REF | 7. BOOSTER |
| 3. REF SUPPLY | 8. REG OUTPUT |
| 4. COMP | 9. GROUND |
| 5. UNREG INPUT | |

105 POSITIVE VOLTAGE REGULATOR

Die Size: 40 x 48 mils.

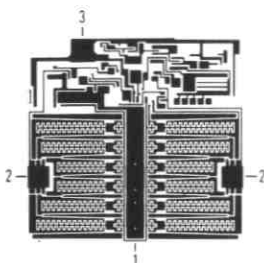


- | | |
|----------------------|---------------------|
| 1. CURRENT LIMIT | 5. REFERENCE BYPASS |
| 2. BOOSTER OUTPUT | 6. FEEDBACK |
| 3. UNREGULATED INPUT | 7. COMP SHUTDOWN |
| 4. GROUND (CASE) | 8. REGULATED OUTPUT |

Linear IC Chips

109 +5 VOLT VOLTAGE REGULATOR

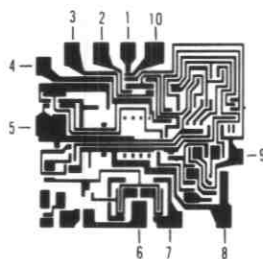
Die Size: 82 x 88 mils.



- 1. INPUT
- 2. OUTPUT
- 3. GND

723 PRECISION VOLTAGE REGULATOR

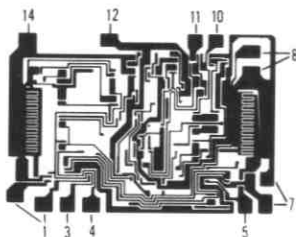
Die Size: 53 x 60 mils.



- 1. CURRENT SENSE
- 2. - INPUT
- 3. + INPUT
- 4. V_{REF}
- 5. V^-
- 6. V_{OUT}
- 7. V_C
- 8. V^+
- 9. COMP
- 10. CURRENT LIMIT

4194 ADJUSTABLE DUAL TRACKING VOLTAGE REGULATOR

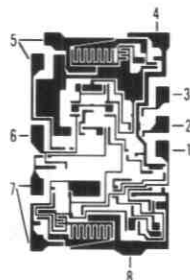
Die Size: 66 x 96 mils.



- 1. V_{O^+}
- 2. NC
- 3. COMP +
- 4. BAL
- 5. COMP -
- 6. NC
- 7. V^-
- 8. V_{O^-}
- 9. NC
- 10. R_O
- 11. R_{SET}
- 12. GND
- 13. NC
- 14. V^+

4195 ± 5 VOLT FIXED DUAL TRACKING VOLTAGE REGULATOR

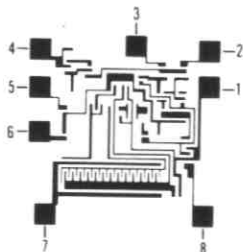
Die Size: 49 x 74 mils.



- 1. COMP +
- 2. GND
- 3. COMP -
- 4. $-V_{IN}$
- 5. $-15V_{OUT}$
- 6. BAL
- 7. $+15V_{OUT}$
- 8. $+V_{IN}$

106 HIGH SPEED COMPARATOR

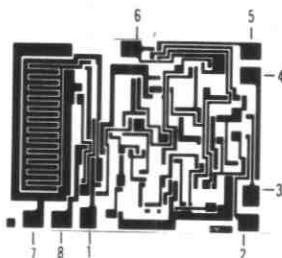
Die Size: 49 x 49 mils.



- 1. GND
- 2. + INPUT
- 3. - INPUT
- 4. V^-
- 5. STROBE
- 6. STROBE
- 7. OUTPUT
- 8. V^+

111 PRECISION COMPARATOR

Die Size: 52 x 68 mils.



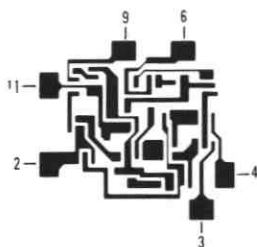
- 1. GND
- 2. + INPUT
- 3. - INPUT
- 4. V^-
- 5. BAL
- 6. BAL/STROBE
- 7. OUTPUT
- 8. V^+

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710 GENERAL PURPOSE COMPARATOR

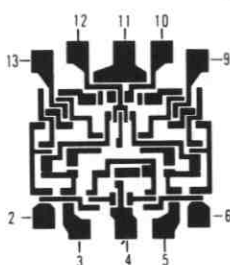
Die Size: 39 x 43 mils.



- | | |
|------------|-----------|
| 1. NC | 7. NC |
| 2. GND | 8. NC |
| 3. + INPUT | 9. V_O |
| 4. - INPUT | 10. NC |
| 5. NC | 11. V^+ |
| 6. V^- | |

711 DUAL 710 COMPARATOR

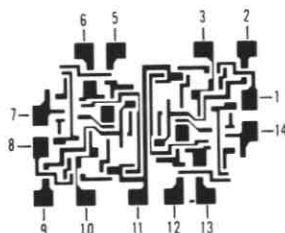
Die Size: 46 x 50 mils.



- | | | |
|-------------------------|-------------------------|--------------|
| 1. NC | 6. - INPUT ₂ | 11. V^+ |
| 2. - INPUT ₁ | 7. NC | 12. GROUND |
| 3. + INPUT ₁ | 8. NC | 13. STROBE 1 |
| 4. V^- | 9. STROBE ₂ | 14. NC |
| 5. + INPUT ₂ | 10. OUTPUT | |

1514 DUAL 710 COMPARATOR

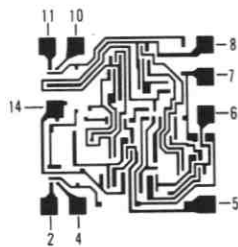
Die Size: 44 x 60 mils.



- | | | |
|---------------|---------------|----------------|
| 1. OUTPUT (A) | 6. -INPUT (B) | 11. GND |
| 2. STROBE (A) | 7. V^- | 12. +INPUT (B) |
| 3. V^+ | 8. OUTPUT (B) | 13. -INPUT (A) |
| 4. NC | 9. STROBE (B) | 14. V^- |
| 5. +INPUT (B) | 10. V^+ | |

1150 DUAL LINE DRIVER

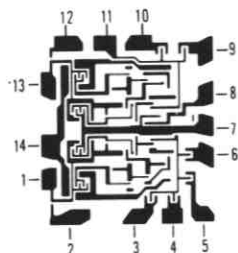
Die Size: 45 x 45 mils.



- | | | |
|-----------------------------|-----------------------------|-----------------------------|
| 1. NC | 6. OUTPUT (B) | 11. INPUT (B ₂) |
| 2. INPUT (A) | 7. GND | 12. NC |
| 3. NC | 8. -12V | 13. NC |
| 4. INPUT (A ₁) | 9. NC | 14. +12V |
| 5. OUTPUT (A ₂) | 10. INPUT (B ₁) | |

9621 DUAL LINE DRIVER

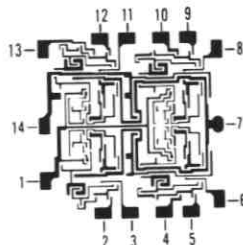
Die Size: 49 x 53 mils.



- | | | |
|--------------------|---------------|---------------------|
| 1. OUTPUT (A) | 6. INPUT (A) | 11. EXTENDER |
| 2. 105Ω OUTPUT (A) | 7. GND | 12. 105Ω OUTPUT (B) |
| 3. INPUT (A) | 8. V_{CC2} | 13. OUTPUT (B) |
| 4. INPUT (A) | 9. INPUT (B) | 14. V_{CC1} |
| 5. INPUT (A) | 10. INPUT (B) | |

1488 QUAD LINE DRIVER

Die Size: 68 x 68 mils.

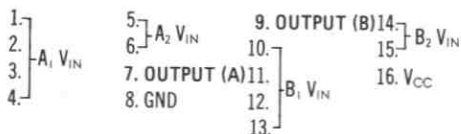
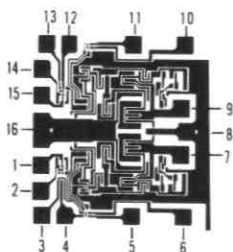


- | | | |
|---------------|---------------|----------------|
| 1. V^- | 6. OUTPUT (B) | 11. OUTPUT (D) |
| 2. INPUT (A) | 7. GND | 12. INPUT (D) |
| 3. OUTPUT (A) | 8. OUTPUT (C) | 13. INPUT (D) |
| 4. INPUT (B) | 9. INPUT (C) | 14. V^+ |
| 5. INPUT (B) | 10. INPUT (C) | |

Linear IC Chips

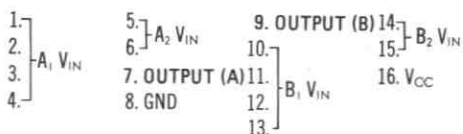
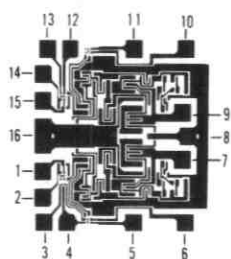
8T13 DUAL LINE DRIVER

Die Size: 64 x 71 mils.



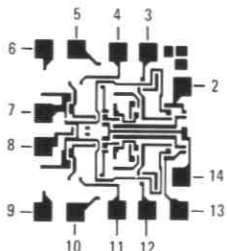
8T23 DUAL LINE DRIVER

Die Size: 64 x 71 mils.



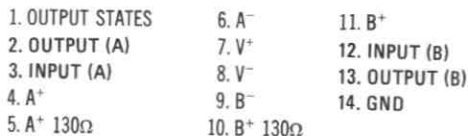
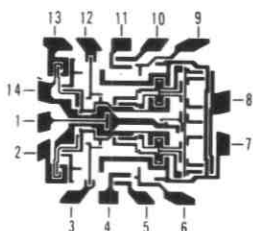
1160 DUAL LINE RECEIVER

Die Size: 44 x 45 mils.



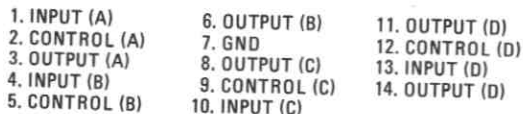
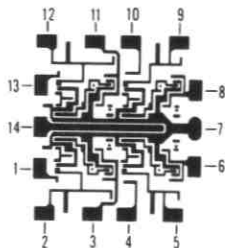
9622 DUAL LINE RECEIVER

Die Size: 55 x 64 mils.



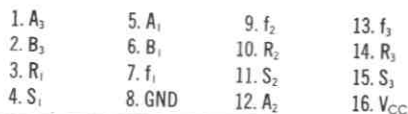
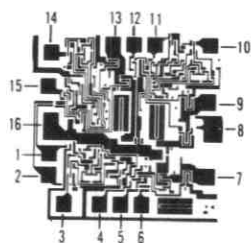
1489/1489A QUAD LINE RECEIVERS

Die Size: 55 x 66 mils.



8T14 TRIPLE LINE RECEIVER

Die Size: 78 x 78 mils.

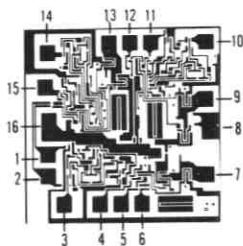


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8T24 TRIPLE LINE RECEIVER

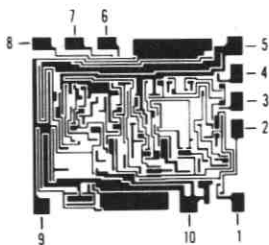
Die Size: 78 x 78 mils.



- | | | | |
|-------------------|-------------------|--------------------|---------------------|
| 1. A ₃ | 5. A ₁ | 9. f ₂ | 13. f ₃ |
| 2. B ₃ | 6. B ₁ | 10. R ₂ | 14. R ₃ |
| 3. R ₁ | 7. f ₁ | 11. S ₂ | 15. S ₃ |
| 4. S ₁ | 8. GND | 12. A ₂ | 16. V _{CC} |

8341 LOW POWER AUDIO AMPLIFIER

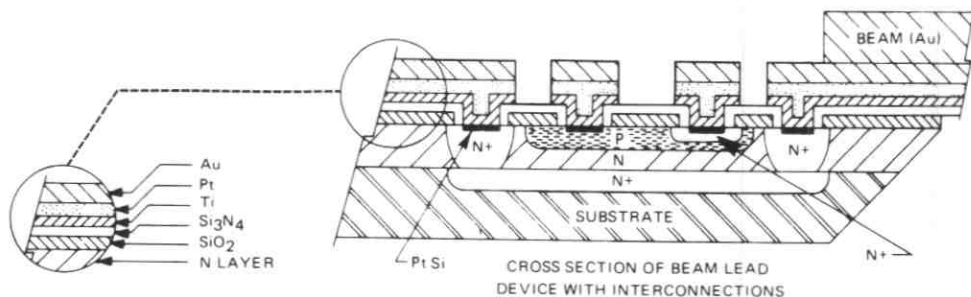
Die Size: 60 x 71 mils.



- | | |
|----------------|---------------------|
| 1. VOL CONTROL | 6. AGC LEVEL SELECT |
| 2. MIC BYPASS | 7. AGC CONTROL |
| 3. +INPUT | 8. GAIN SELECT |
| 4. -INPUT | 9. OUTPUT |
| 5. GND | 10. V _{CC} |

Beam Lead Linear IC's

Typical Beam Lead Cross Section with Interconnections



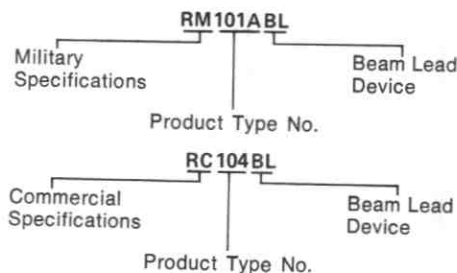
Ordering Information

Beam Lead Linear IC's may be ordered either as military or commercial grade devices:

RM = -55°C to $+125^{\circ}\text{C}$ operating temperature range, B-level visual.

RC = 0°C to $+70^{\circ}\text{C}$, C-level visual.

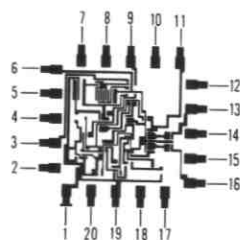
Examples



101A GENERAL PURPOSE OPERATIONAL AMPLIFIER

Order Part Nos.:
RM101ABL,
RC101ABL

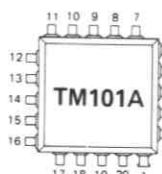
Die Size: 58 x 60 mils.



ACTIVE SIDE

- | | | | |
|-----------|---------------------|--------------|----------------------|
| 1. BAL | 6. +V _{CC} | 11. COMP/BAL | 16. +INPUT |
| 2. NC | 7. NC | 12. NC | 17. NC |
| 3. OUTPUT | 8. NC | 13. -INPUT | 18. NC |
| 4. NC | 9. COMP | 14. NC | 19. -V _{CC} |
| 5. NC | 10. NC | 15. NC | 20. NC |

Mechanical Outline 16

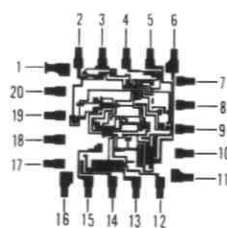


AS BONDED

104 NEGATIVE VOLTAGE REGULATOR

Order Part Nos.:
RM104BL,
RC104BL

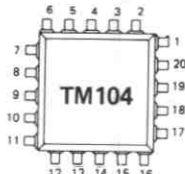
Die Size: 55 x 55 mils.



ACTIVE SIDE

- | | | | |
|---------------------------|----------------|--------------------|--------|
| 1. NC | 6. UNREG INPUT | 11. NC | 16. NC |
| 2. OUTPUT VOL-TAGE ADJUST | 7. NC | 12. CURRENT LIMIT | 17. NC |
| 3. REF | 8. NC | 13. BOOSTER OUTPUT | 18. NC |
| 4. REF SUPPLY | 9. NC | 14. REG OUTPUT | 19. NC |
| 5. COMP | 10. NC | 15. GND | 20. NC |

Mechanical Outline 15
EIA STANDARD



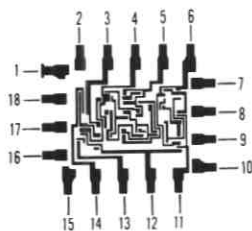
AS BONDED

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105 POSITIVE VOLTAGE REGULATOR

Die Size: 53 x 63 mils.

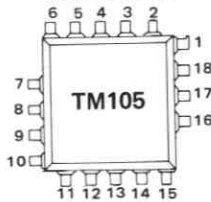


ACTIVE SIDE

- | | | | |
|-------------------|-----------|-------------------|--------|
| 1. NC | 5. GND | 10. NC | 15. NC |
| 2. NC | 6. BYPASS | 11. FEEDBACK | 16. NC |
| 3. BOOSTER OUTPUT | 7. NC | 12. COMP | 17. NC |
| 4. UNREG INPUT | 8. NC | 13. REG OUTPUT | 18. NC |
| | 9. NC | 14. CURRENT LIMIT | |

Order Part Nos.:
RM105BL,
RC105BL

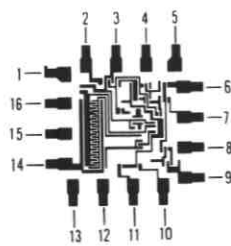
Mechanical Outline 22
EIA STANDARD



AS BONDED

106 HIGH SPEED COMPARATOR

Die Size: 45 x 45 mils.

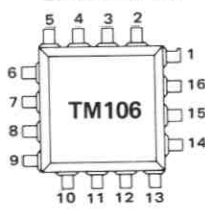


ACTIVE SIDE

- | | | | |
|---------------------|-----------|---------------------|------------|
| 1. NC | 5. NC | 9. -V _{CC} | 13. NC |
| 2. +V _{CC} | 6. +INPUT | 10. STROBE 1 | 14. OUTPUT |
| 3. GND | 7. -INPUT | 11. STROBE 2 | 15. NC |
| 4. NC | 8. NC | 12. NC | 16. NC |

Order Part Nos.:
RM106BL,
RC106BL

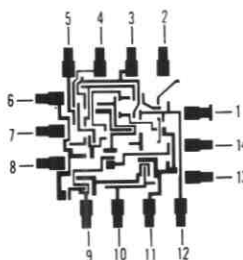
Mechanical Outline 10
EIA STANDARD



AS BONDED

709 GENERAL PURPOSE OPERATIONAL AMPLIFIER

Die Size: 48 x 48

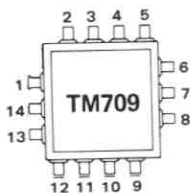


ACTIVE SIDE

- | | | | |
|---------------|---------------------|----------------------|----------------|
| 1. NC | 5. +INPUT | 9. OUTPUT COMP | 12. INPUT COMP |
| 2. NC | 6. -V _{CC} | 10. OUTPUT | 13. NC |
| 3. INPUT COMP | 7. NC | 11. +V _{CC} | 14. NC |
| 4. -INPUT | 8. NC | | |

Order Part Nos.:
RM709BL,
RM709ABL,
RC709BL

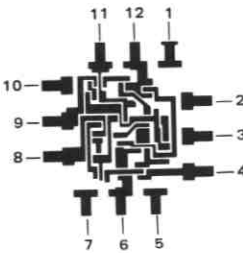
Mechanical Outline 8



AS BONDED

710 GENERAL PURPOSE COMPARATOR

Die Size: 41 x 41 mils.

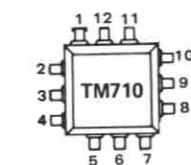


ACTIVE SIDE

- | | | | |
|-------|-----------|---------------------|----------------------|
| 1. NC | 4. +INPUT | 7. NC | 10. NC |
| 2. NC | 5. NC | 8. -V _{CC} | 11. +V _{CC} |
| 3. NC | 6. -INPUT | 9. OUTPUT | 12. GND |

Order Part Nos.:
RM710BL,
RM710ABL,
RC710BL

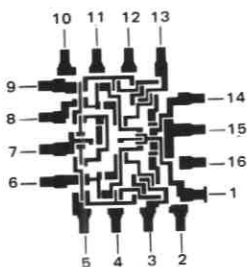
Mechanical Outline 5



AS BONDED

711 DUAL COMPARATOR

Die Size: 44 x 49 mils.

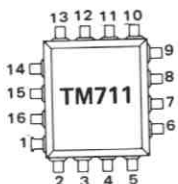


ACTIVE SIDE

- | | | | |
|-------------|---------------------|---------------|----------------------|
| 1. GND | 5. -INPUT (A) | 9. -INPUT (B) | 13. STROBE 2 |
| 2. NC | 6. +INPUT (A) | 10. NC | 14. OUTPUT |
| 3. STROBE 1 | 7. -V _{CC} | 11. NC | 15. +V _{CC} |
| 4. NC | 8. +INPUT (B) | 12. NC | 16. NC |

Order Part Nos.:
RM711BL,
RC711BL

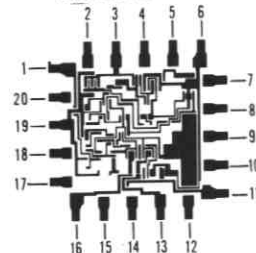
Mechanical Outline 9



AS BONDED

7141 GENERAL PURPOSE OPERATIONAL AMPLIFIER

Die Size: 55 x 55 mils.

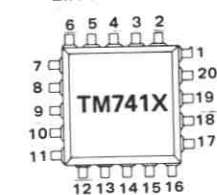


ACTIVE SIDE

- | | | | |
|------------|---------------------|-------------|----------------------|
| 1. BALANCE | 6. +V _{CC} | 11. BALANCE | 16. +INPUT |
| 2. NC | 7. NC | 12. NC | 17. NC |
| 3. OUTPUT | 8. NC | 13. -INPUT | 18. NC |
| 4. NC | 9. NC | 14. NC | 19. -V _{CC} |
| 5. NC | 10. NC | 15. NC | 20. NC |

Order Part Nos.:
RM1741BL,
RC1741BL

Mechanical Outline 15
EIA STANDARD



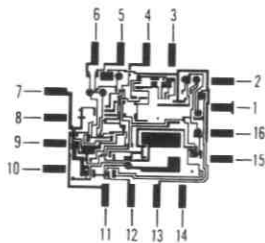
AS BONDED

Beam Lead Linear IC's

4132 MICRO POWER OPERATIONAL AMPLIFIER

Die Size: 64 x 74 mils.

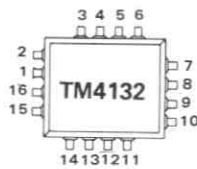
Order Part Nos.:
RM4132BL,
RC4132BL



ACTIVE SIDE

- | | |
|--------|-----------|
| 1. NC | 5. -INPUT |
| 2. NC | 6. +INPUT |
| 3. NC | 7. -VCC |
| 4. BAL | 8. NC |

Mechanical Outline 14



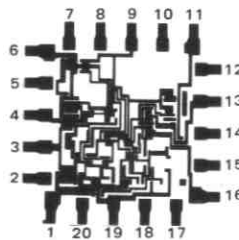
AS BONDED

- | | |
|------------|--------|
| 9. NC | 13. V+ |
| 10. NC | 14. NC |
| 11. BAL | 15. NC |
| 12. OUTPUT | 16. NC |

748 OPERATIONAL AMPLIFIER

Die Size: 55 x 55

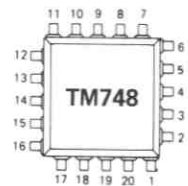
Order Part Nos.:
RM748BL,
RC748BL



ACTIVE SIDE

- | | |
|-----------|---------|
| 1. BAL | 6. +VCC |
| 2. NC | 7. NC |
| 3. OUTPUT | 8. NC |
| 4. COMP | 9. COMP |
| 5. NC | 10. NC |

Mechanical Outline 15
EIA STANDARD



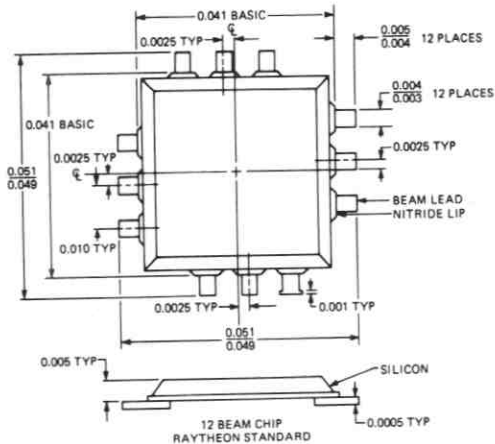
AS BONDED

- | | |
|------------|------------|
| 11. BAL | 16. +INPUT |
| 12. NC | 17. NC |
| 13. -INPUT | 18. NC |
| 14. NC | 19. -VCC |
| 15. NC | 20. NC |



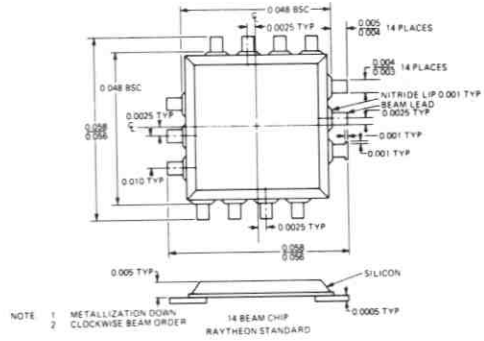
RAYTHEON COMPANY • SEMICONDUCTOR DIVISION • 350 ELLIS STREET • MOUNTAIN VIEW, CALIFORNIA

Mechanical Outline Information



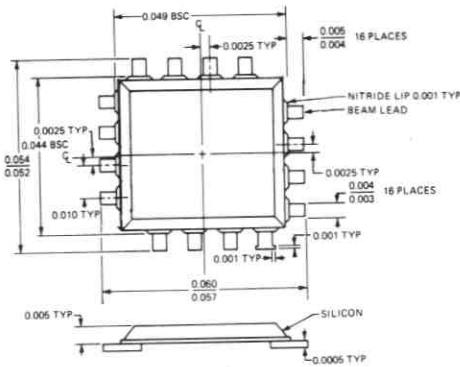
NOTE 1 METALIZATION DOWN
2 COUNTER CLOCKWISE BEAM ORDER

MECHANICAL OUTLINE 5



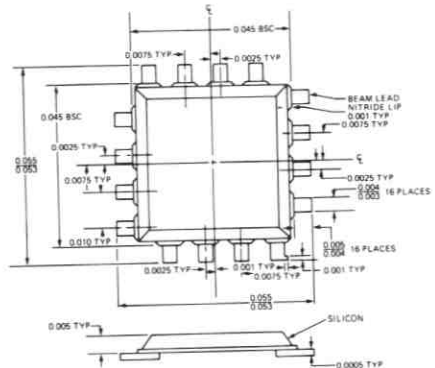
NOTE 1 METALIZATION DOWN
2 COUNTER CLOCKWISE BEAM ORDER

MECHANICAL OUTLINE 8



NOTE 1 METALIZATION DOWN
2 COUNTER CLOCKWISE BEAM ORDER

MECHANICAL OUTLINE 9

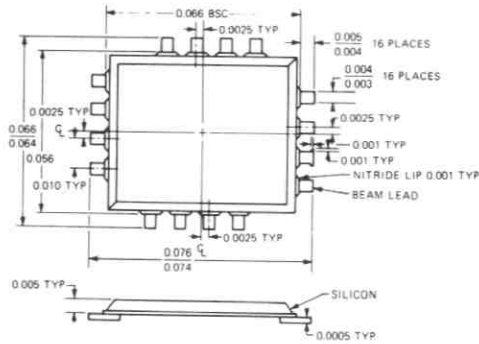


NOTE 1 METALIZATION DOWN
2 COUNTER CLOCKWISE BEAM ORDER

EIA STANDARD
MECHANICAL OUTLINE 10

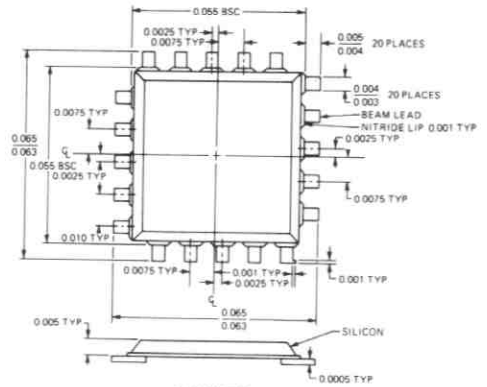


Mechanical Outline Information



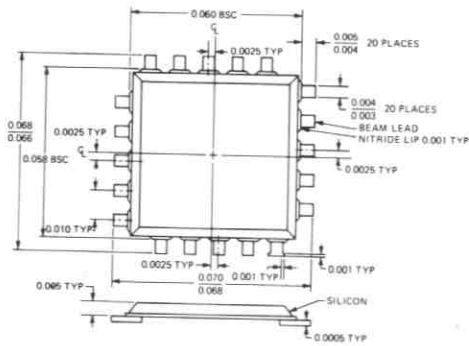
NOTE: 1. METALIZATION DOWN
2. CLOCKWISE BEAM ORDER

MECHANICAL OUTLINE 14



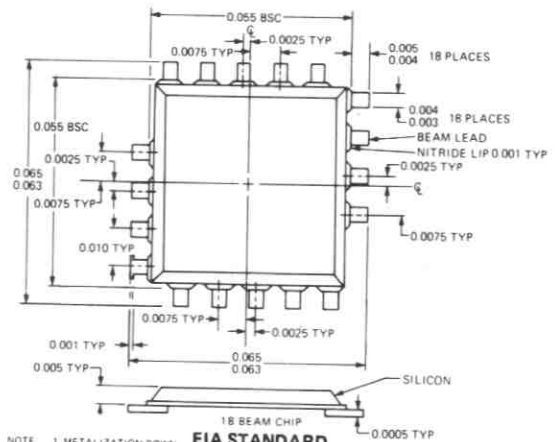
NOTE: 1. METALIZATION DOWN
2. COUNTER CLOCKWISE BEAM ORDER

MECHANICAL OUTLINE 15



NOTE: 1. METALIZATION DOWN
2. COUNTER CLOCKWISE BEAM ORDER

MECHANICAL OUTLINE 16



NOTE: 1. METALIZATION DOWN
2. COUNTER CLOCKWISE BEAM ORDER

MECHANICAL OUTLINE 22



SECTION 8

Appendices

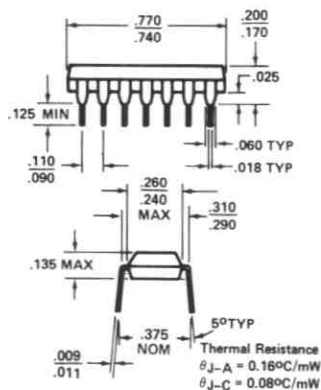
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Package Information	8-2
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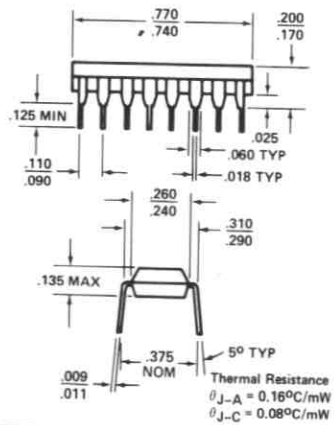
Package Information

DUAL IN-LINE CERAMIC PACKAGES

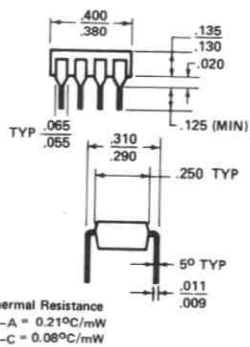
14-Pin DB Package



16-Pin MP Package

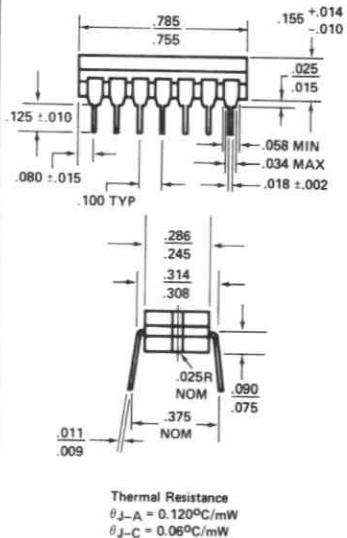


8-Pin DN Package

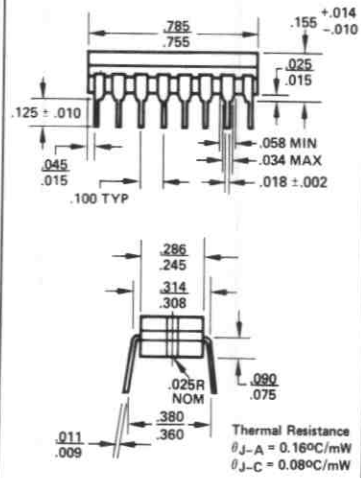


DUAL IN-LINE PLASTIC PACKAGES

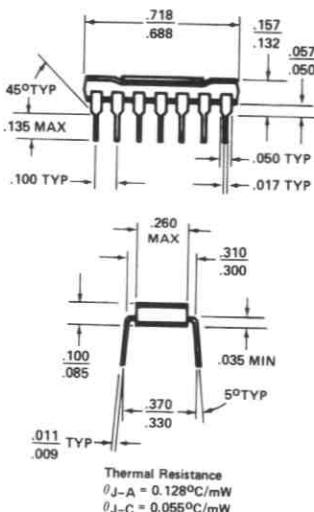
14-Pin DC Package



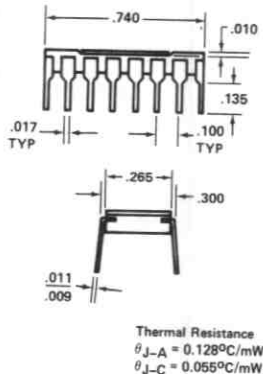
16-Pin DD Package



14-Pin D Package

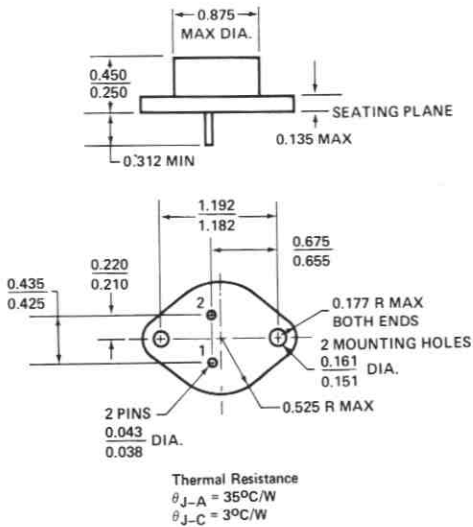


16-Pin M Package

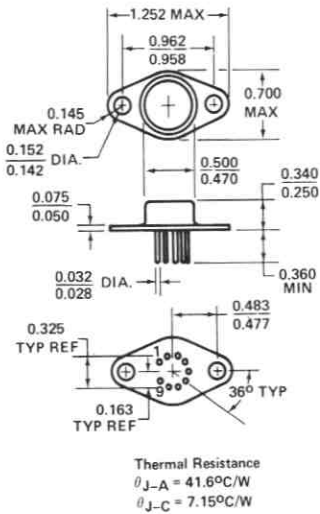


METAL CAN PACKAGES

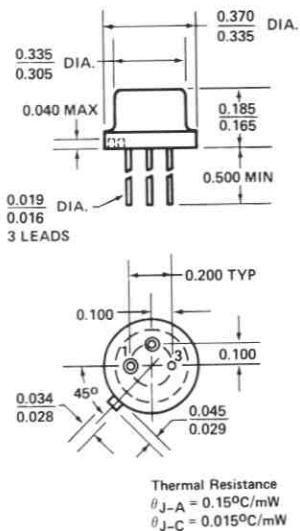
2-pin LK(TO-3) Package



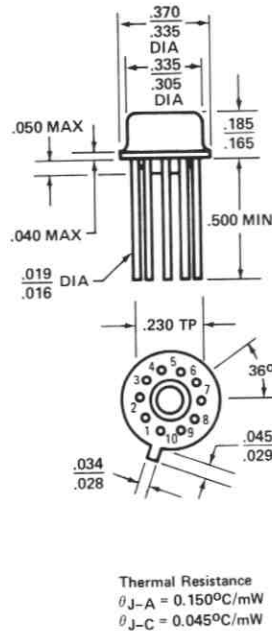
10-pin TK(TO-66) Package



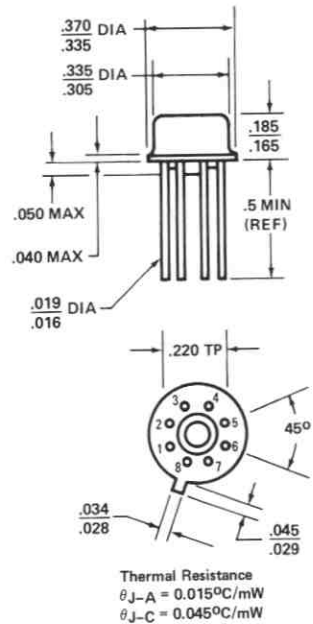
3-pin TH(TO-5) Package



10-pin TF(TO-100) Package



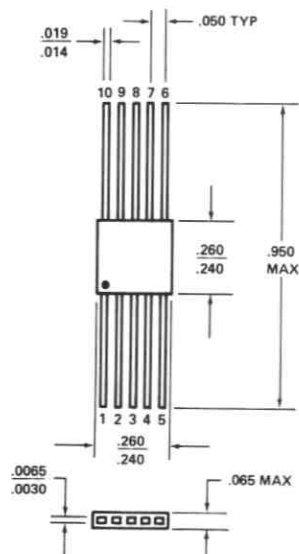
8-pin TE(TO-99) Package



Package Information

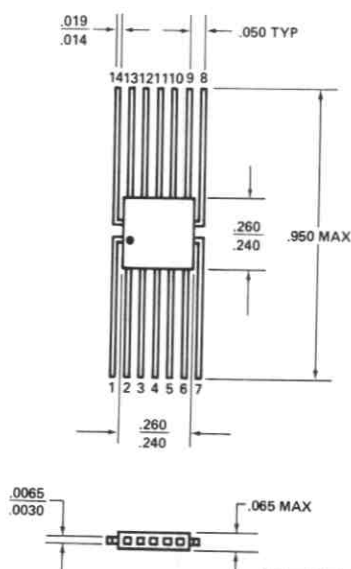
FLAT PACKAGES

10-pin Q(TO-91) Package



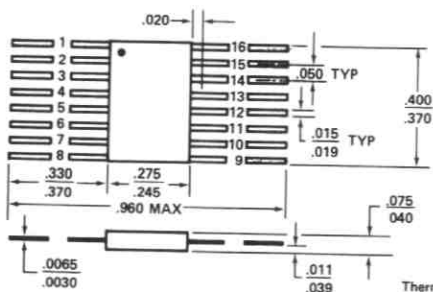
Thermal Resistance
 $\theta_{J-A} = 0.17^{\circ}\text{C}/\text{mW}$
 $\theta_{J-C} = 0.06^{\circ}\text{C}/\text{mW}$

14-pin J(TO-86) Package



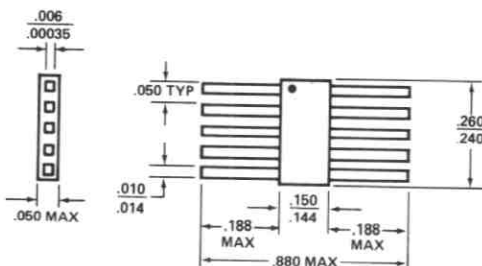
Thermal Resistance
 $\theta_{J-A} = 0.15^{\circ}\text{C}/\text{mW}$
 $\theta_{J-C} = 0.05^{\circ}\text{C}/\text{mW}$

16-pin L Package



Thermal Resistance
 $\theta_{J-A} = 0.15^{\circ}\text{C}/\text{mW}$
 $\theta_{J-C} = 0.05^{\circ}\text{C}/\text{mW}$

10-pin G Package



OP AMPS

Average Input Offset Current t° Coefficient—Change in input offset current divided by change in ambient temperature producing it.

Average Input Offset Voltage t° Coefficient—Change in input offset voltage divided by change in ambient temperature producing it.

Common-Mode Input Resistance—Resistance looking into both inputs tied together.

Common-Mode Rejection Ratio (CMRR)—Ratio of change of input offset voltage to input common-mode voltage change producing it.

Full Power Bandwidth—Maximum frequency at which full sinewave output might be obtained.

Input Bias Current—Average of the two input currents at zero output voltage. In some cases, input current for either input independently.

Input Capacitance—Capacitance looking into either input terminal with other grounded.

Input Current—Current into an input terminal.

Input Noise Voltage—Square root of mean square narrow-band noise voltage referred to input.

Input Offset Current—Difference in currents into two input terminals with output at zero volts.

Input Offset Voltage—Voltage which must be applied between input terminals to obtain zero output voltage. Input offset voltage may also be defined for case where two equal resistances are inserted in series with input leads.

Input Resistance—Resistance looking into either input terminal with other grounded.

Input Voltage Range—Range of voltages on input terminals for which amplifier operates within specifications. In some cases, input offset specifications apply over input voltage range.

Large-Signal Voltage Gain—Ratio of maximum output voltage swing to change in input voltage required to drive output to this voltage.

Output Resistance—Resistance seen looking into output terminal with output at null. This parameter is defined only under small signal conditions at frequencies above a few hundred cycles to eliminate influence of drift and thermal feedback.

Settling Time—Time between initiation of input step function and time when output voltage has settled to within specified error band of final output voltage.

Output Short-Circuit Current—Maximum output current available from amplifier with output shorted to ground or to either supply.

Output Voltage Swing—Peak output swing, referred to zero, that can be obtained.

Power Consumption—DC power required to operate amplifier with output at zero and with no load current.

Power Supply Rejection Ratio—Ratio of change in input offset voltage to change in supply voltages producing it.

Rise Time—Time required for an output voltage step to change from 10% to 90% of its final value.

Slew Rate—Maximum rate of change of output voltage under large signal condition.

Supply Current—Current required from power supply to operate amplifier with no load and output at zero.

Temperature Stability Of Voltage Gain—Maximum variation of voltage gain over specified temperature range.

Harmonic Distortion—Percentage of harmonic distortion being defined as 100 times ratio of RMS sum of harmonics to fundamental.

$$\% \text{ harmonic distortion} = \frac{(V_2^2 + V_3^2 + V_4^2 + \dots)^{1/2}}{V_1} (100\%)$$

where V_1 is RMS amplitude of fundamental and V_2, V_3, V_4, \dots are RMS amplitudes of individual harmonics.

Transient Response—Closed-loop step-function response of amplifier under small-signal conditions.

Unity Gain Bandwidth—Frequency range from DC to frequency where amplifier open-loop gain rolls off to one.

Voltage Gain—Ratio of output voltage to input voltage under stated conditions for source resistance (R_S) and load resistance (R_L).

Bandwidth—Frequency at which voltage gain is reduced to $1/\sqrt{2}$ times the low frequency value.

Output Impedance—Ratio of output voltage to output current under stated conditions for source resistance (R_S) and load resistance (R_L).

Input Impedance—Ratio of input voltage to input current under stated conditions for source resistance (R_S) and load resistance (R_L).

REGULATORS

Dropout Voltage—Input-output voltage differential at which circuit ceases to regulate against further reductions in input voltage.

Input-Output Voltage Differential—Range of voltage difference between supply voltage and regulated output voltage over which regulator will operate.

Line Regulator—Percentage change in output voltage for a specified change in input voltage.

Load Regulator—Percentage change in output voltage for specified change in load current.

Maximum Power Dissipation—Maximum total device dissipation for which regulator will operate within specifications.

Output Noise Voltage—RMS output noise voltage with constant load and no input ripple.

Glossary of Terms

Output Voltage Range—Range of output voltage over which regulator will operate.

Quiescent Current—Part of input current to regulator that is not delivered to load.

Reference Voltage—Output of reference amplifier measured with respect to negative supply.

Ripple Rejection—Ratio of peak-to-peak input ripple voltage to peak-to-peak output ripple voltage.

Sense Voltage—Voltage between current sense and current limit terminals necessary to cause current limiting.

Short-Circuit Current Limit—Output current of regulator with output shorted to negative supply.

Standby Current Drain—Supply current drawn by regulator with no output load and no reference voltage load.

Temperature Stability—Percentage change in output voltage for thermal variation from room temperature to either temperature extreme.

Long Term Stability—Output voltage stability under accelerated life-test conditions at 125°C with maximum rated voltages and power dissipation for 1000 hours.

Output Voltage Scale Factor—Output voltage obtained for unit value of resistance between adjustment terminal and ground.

Input Voltage Range—Range of DC input voltages over which regulator will operate within specifications.

Current-Limit Sense Voltage—Voltage across current limit terminals required to cause regulator to current-limit with short-circuited output. This voltage is used to determine value of external current-limit resistor when external booster transistors are used.

COMPARATORS/SENSE AMPLIFIERS

Common-Mode Firing Voltage—CM input voltage that exceeds dynamic range of inputs with strobe enabled resulting in output switching states.

Common-Mode Recovery Time—Time from turn off of CM signal to analog input threshold of earliest sense line pulse signal that can be processed normally. Processed normally refers to bi-polar signals greater than or less than input threshold with corresponding proper output.

Equivalent Input Common-Mode Noise Voltage—Change in input offset voltage due to common-mode input noise.

Logic Input High Voltage—Minimum voltage allowed at bit control gate to hold bit off.

Logic Input Low Voltage—Maximum voltage allowed at bit control gate to hold bit on.

Output Sink Current—Maximum negative current that can be delivered by comparator.

Peak Output Current—Maximum current that may flow into output load without causing damage to comparator.

Propagation Delay—Interval between application of an input voltage step and its arrival at either output, measured at 50% of final value.

Response Time—Interval between application of input step function and time when output crosses logic threshold voltage. Input step drives comparator from some initial, saturated input voltage to input level just barely in excess of that required to bring output from saturation to logic threshold voltage overdrive.

Strobe Current—Maximum current drawn by strobe terminals when it is at zero logic level.

Strobe Delay—Time delay measured from strobe to output threshold with signal present exceeding input threshold.

Strobe Release Time—Time required for output to rise to logic threshold voltage after strobe terminal has been driven from zero to one logic level. Appropriate input conditions are assumed.

Strobed Output Level—DC output voltage, independent of input voltage, with voltage on strobe terminal equal to or less than minimum specified amount.

Switching Speed—Time required to turn on least significant bit.

Threshold Uncertainty—With all sense amps sharing same input threshold less uncertainty as "0." This includes unit to unit, power supply and temperature variations.

Threshold Voltage—Typical referred to input voltage which determines whether input is "1" or "0." Signal whose magnitude is greater than threshold level is sensed as logic "1" and signal whose magnitude is less as "0."

Zero Scale Output Current—Output current for all bits turned off.

Supply Current—Current required from positive or negative supply to operate comparator with no output load. Power will vary with input voltage, but is specified as maximum for entire range of input voltage conditions.

Voltage Gain—Ratio of change in output voltage to change in voltage between input terminals producing it.

Differential Input Offset Current—Absolute difference in two input bias currents of one differential input.

Differential Input Overload Recovery Time—Time necessary for device to recover from 2V differential pulse ($t_f = t_r = 20\text{ns}$) prior to strobe enable signal.

Offset Voltage—Difference between absolute values of threshold voltage in positive- and negative-going directions.

Input Bias Current—Average of two input currents.

Input Offset Current—Absolute value of difference between two input currents for which output will be driven higher or lower than specified voltages.



Glossary of Terms

Input Offset Voltage—Absolute value of voltage between input terminals required to make output voltage greater or less than specified voltages.

Input Voltage Range—Range of voltage on input terminals (common-mode) over which offset specifications apply.

Positive Output Level—High output voltage level with given load and input drive equal to or greater than specified value.

Power Consumption—Power required to operate comparator with no output load. Power will vary with signal level, but is specified as maximum for entire range of input signal conditions.

Output Leakage Current—Current into output terminal with output voltage within given range and input drive equal to or greater than given value.

Output Resistance—Resistance seen looking into output terminal with DC output level at logic threshold voltage.

Strobed Output Level—DC output voltage, independent of input conditions, with voltage on strobe terminal equal to or less than specified low state.

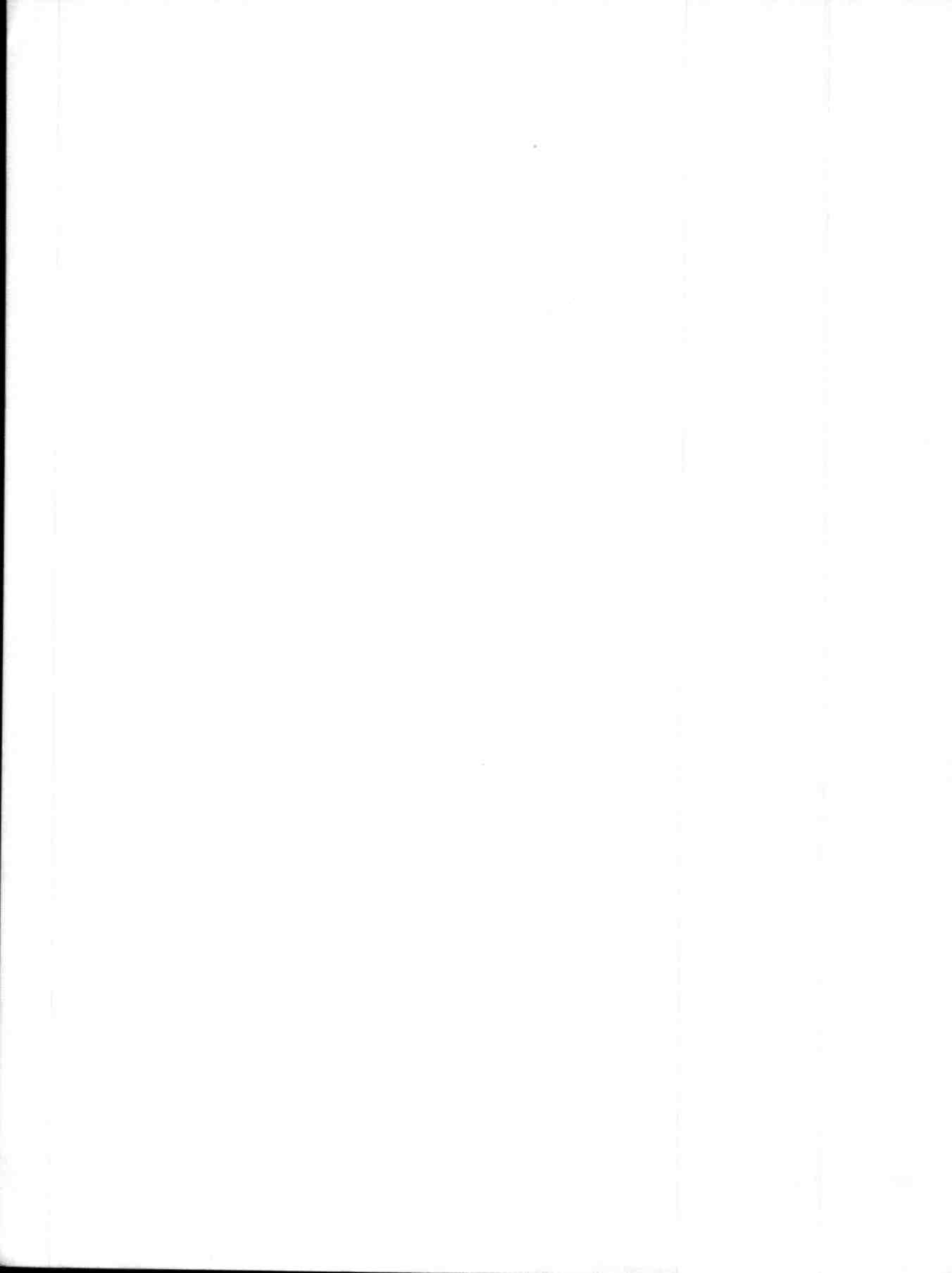
Strobe ON Voltage—Maximum voltage on either strobe terminal required to force output to specified high state independent of input voltage.

Differential Input Threshold Voltage—DC input voltage which forces logic output to logic threshold voltage ($\sim 1.5V$) level.

Input Bias Current—DC current which flows into each input pin with differential input of 0V.

Negative Output Level—Negative DC output voltage with comparator saturated by differential input equal to or greater than specified voltage.

Strobe OFF Voltage—Minimum voltage on strobe terminal that will guarantee that it does not interfere with operation of comparator.



NOTES



NOTES

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St. Louis, MO 63144
(314) 645-8550

Hall-Mark Electronics
13789 Rider Trail
Earth City, MO 63045
(314) 291-5350

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Arrow/Angus
Pleasant Valley Avenue
Moorestown, NJ 08057
(609) 235-1900

Components Plus
310 Railroad Avenue
Hanksack, NJ 07601
(201) 487-0565

Cramer/New Jersey
One Barrett Avenue
Moonachie, NJ 07074
(201) 935-5600

Cramer/Pennsylvania
12 Springdale Road
Cherry Hill, NJ 08034
(609) 424-5993

NEW MEXICO

Century Electronics
121 Elizabeth N.E.
Albuquerque, NM 87108
(505) 292-2700

Cramer/New Mexico
137 Vermont N.E.
Albuquerque, NM 87103
(505) 265-5767

Kierulff Electronics
2524 Baylor Drive, S.E.
Albuquerque, NM 87103
(505) 247-1055

NEW YORK

ACI Electronics Corp.
28 South Mall
Plainville, NY 11803
(516) 293-6630

Components Plus
40 Oser Avenue
Hauppauge, L.I., NY 11787
(516) 231-9200

Cramer/Long Island
29 Oser Avenue
Hauppauge, L.I., NY 11787
(516) 231-5600

Cramer/Syracuse
6716 Joy Road
East Syracuse, NY 13057
(315) 437-6671

Cramer/Rochester
3000 Winton Road
Rochester, NY 14623
(716) 275-0300

Diplomat Electronics Corp.
303 Crossways Park Drive
Woodbury, NY 11797
(516) 921-9373

Lafayette Industrial Electronics
1327 Second Avenue
New Hyde Park, L.I., NY 11040
(516) 488-6600

Rome Electronics
216 Erie Boulevard East
Rome, NY 13440
(315) 337-5400

Semiconductor Concepts
145 Oser Avenue
Hauppauge, L.I., NY 11787
(516) 273-1234

Zeus Components, Inc.
175 Clearbrook Road
Elmsford, NY 10523
(914) 592-4120

NORTH CAROLINA

Cramer/Winston-Salem
938 Burke Street
Winston-Salem, NC 27102
(919) 725-8711

OHIO

Cramer/Cleveland
5835 Harper Road
Cleveland, OH 44139
(216) 248-8400

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Diplomat/Ohio
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Dayton, OH 45404
(513) 228-1080

Reptron/Ohio Electronics, Inc.
715 Harmon Plaza
Columbus, OH 43223
(614) 443-0231

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Component Specialties
7920 East 40th Street
Tulsa, OK 74145
(918) 664-2820

PENNSYLVANIA

Leff Radio Parts
225 Braddock Avenue
Braddock, PA 15104
(412) 271-7100

TEXAS

Component Specialties
8330 Burnet Road, Suite 101
Austin, TX 78758
(512) 459-3307

Components Specialties
10907 Shady Trail
Dallas, TX 75220
(214) 357-4576

Component Specialties
7315 Ashcroft Street, Suite 113
Houston, TX 77036
(713) 771-7137

Cramer/Texas
13740 Midway Road
Dallas, TX 75240
(214) 661-9300
(800) 492-6940 - Toll Free

UTAH

Cramer/Utah
391 West 2500 South
Salt Lake City, UT 84115
(801) 487-4131

Diplomat/Altalind
2280 South Main Street
Salt Lake City, UT 84115
(801) 486-7227

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Bell Electronics
1900 132nd N.E.
Bellevue, WA 98005
(206) 747-1515

Cramer/Seattle
5602 6th Avenue, South
Seattle, WA 98108
(206) 762-5755

Intermark Electronics
6301 Sixth Avenue, South
Seattle, WA 98108
(206) 767-3160

WISCONSIN

Hall-Mark Electronics
237 South Curtis Road
West Allis, WI 53214
(414) 476-1270

CANADA

Cramer/Canada
920 Ainess Street, Unit 9
Downsview, Ontario
(416) 661-9222

Future Electronics
5647 Ferrier Street
Montreal, Quebec H4P 2K5
(514) 735-5775

Future Electronics
44 Fasken Drive, Unit #24
Rexdale, Ontario
M9W-1K5
(416) 677-7820

PAAR Industrial Electronics, Ltd.
4531 Manitoba Road, S.E.
Calgary T2G 4B9, Alberta
(403) 287-2840

Prelec Electronics Ltd.
480 Port Royal Street W.
Montreal 357, Quebec
(514) 389-8051

Wackid Radio & Television Labs
312 Parkdale Avenue
Ottawa, Ontario
(613) 728-1821

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2212 Dupont Drive
Irvine, CA 92664
(714) 833-9042
TWX: 910-595-1936

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351 NW 40th Avenue
Fort Lauderdale, FL 33317
(305) 792-8400

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3158 Des Plaines Avenue
Des Plaines, IL 60018
(312) 297-5540
TWX: 910-233-2780

MASSACHUSETTS

155 Middlesex Turnpike
Burlington, MA 01803
(617) 272-8500
TWX: 710-332-1869

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888 West County Rd. D.
New Brighton, MI 55112
(612) 636-7696
TWX: 910-576-3404

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Pennsauken, NJ 08109
(609) 663-4066

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275 Broadhollow Road
Melville, L.I., NY 11746
(516) 420-0700

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5th Mori Bldg., No. 25
Nishikubo-Sakuragawa-Cho
Shiba Minato-KU, Tokyo, Japan
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TWX: 781-0222-6154

SWITZERLAND

Transistor AG-Raytheon
Hohlstrasse 610/612
CH-8048 Zürich
Telephone: 01 625611

GERMANY

Raytheon HALBLEITER GmbH
Thalkirchnerstrasse 74
8000 München 2 West Germany
Telephone: 089/539693
TWX: 841-528-242

ALL OTHER OVERSEAS AREAS

CONTACT:
Raytheon Company
International Affairs
350 Ellis Street
Mountain View, CA 94042
(415) 968-9211
TWX: 910-379-6481

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ARIZONA

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13452 North Hayden Road
Scottsdale, AZ 85260
(602) 991-9197

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Mission Marketing
1080 East Duane Avenue, Suite E
Sunnyvale, CA 94086
(408) 732-9611

Relcom

10469 Marquesas Way, Suite 303
Marina Del Rey, CA 90291
(213) 822-1187
TWX: 910-343-6459

COLORADO

Barnhill Five, Inc.
7100 Broadway
Building 3-I
Watervleit Business Park
Denver, CO 80221
(303) 426-0222

FLORIDA

Perrott Associates
511 Rosery Road, N.E.
Largo, FL 33540
(813) 585-3327

Perrott Associates

1607 Forsyth Road
Orlando, FL 32807
(305) 275-1132

Perrott Associates

P. O. Box 15067
Fort Lauderdale, FL 33318
(305) 792-2211
TWX: 510-955-9831

GEORGIA

Macro Marketing Associates
3320 Holcomb Bridge Road
Norcross, GA 30071
(404) 449-7440

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Carlson Electronic Sales
7448 North Harlem Avenue
Chicago, IL 60648
(312) 774-9022
(312) 774-4812

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Electri-Rep
P. O. Box 4805
Overland Park, KA 66204
(913) 649-2168

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MASSACHUSETTS

Circuit Sales Company
One Militia Drive
Lexington, MA 02173
(617) 861-0567
TWX: 710-326-6307

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Miltimore Sales, Inc.
23995 Freeway Park Drive
Farmington, MI 48024
(313) 476-2446

MINNESOTA

Electronic Sales Agency
8053 Bloomington Freeway
Bloomington, MN 55420
(612) 884-8291

MISSOURI

Kebco
11722 Studt Lane
St. Louis, MO 63141
(314) 569-2660

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(See Overland Park, Kansas)

NEW YORK

Precision Sales
223 Taft Road
North Syracuse, NY 13212
(315) 458-2223

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4180 Abbott Road
Orchard Park, NY 14127
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Precision Sales

29 Page Street
Owego, NY 13827
(607) 687-2893

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Baldwin, NY 11510
(516) 623-3344

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(513) 296-1010

J. C. Hofstetter Co.

5168 Valley View Drive
Medina, OH 44256
(216) 241-4880

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10300 North Central Expressway
Dallas, TX 75231
(214) 691-4592
TWX: 910-861-9016

Kruvand Associates

112 Meyerland Plaza, Suite 27
Houston, TX 77035
(713) 661-3007

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Cantec Representatives, Inc.
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Ottawa, Ontario K2G 0B6
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TWX: 610-562-8967

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624 Elliot Crescent
Milton, Ontario L9T 3G4
(416) 475-4455

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